

FIG. 2

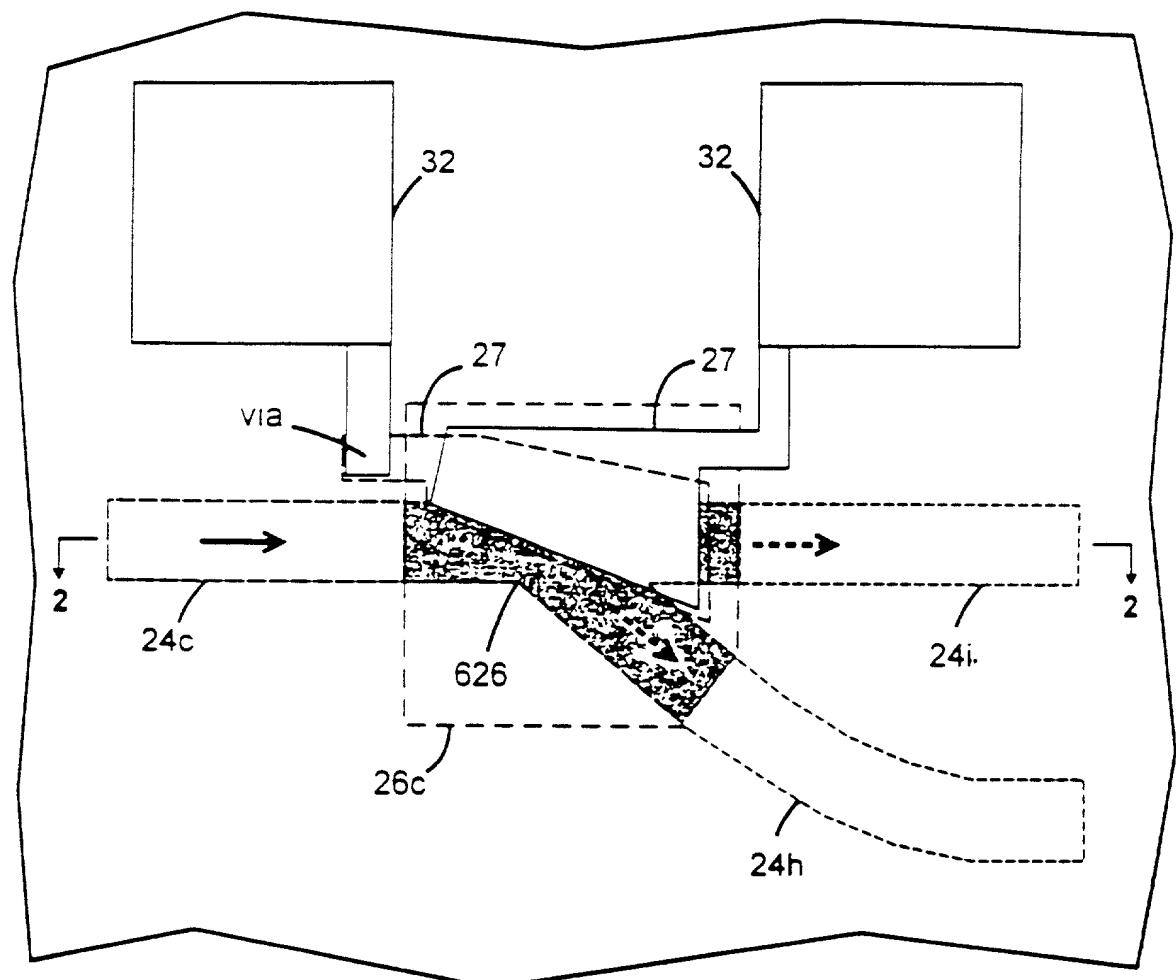


FIG. 3

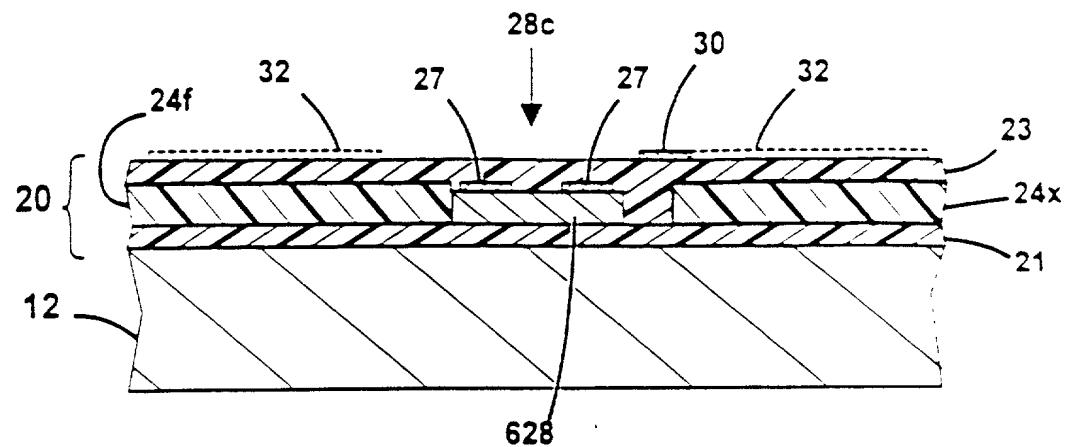


FIG._4-1

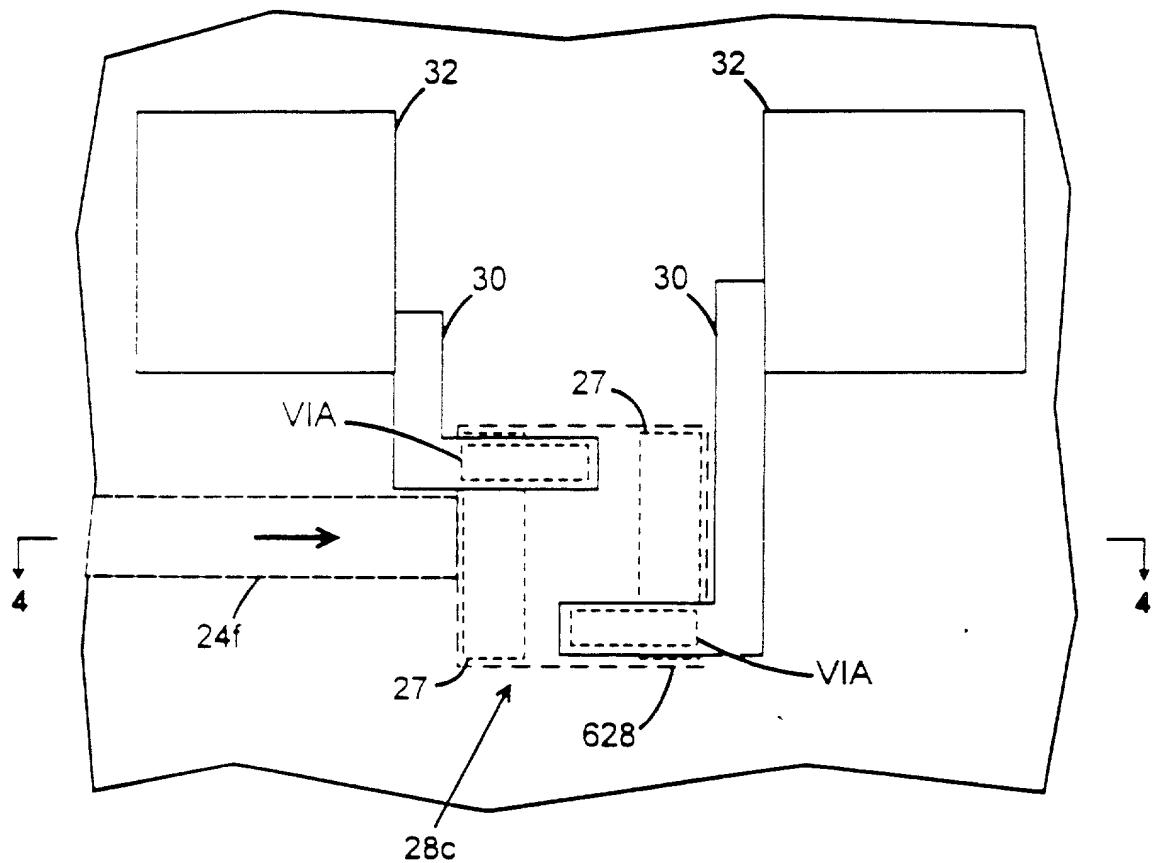


FIG._5-1

图 2.8.2 光电二极管

2.8.2'

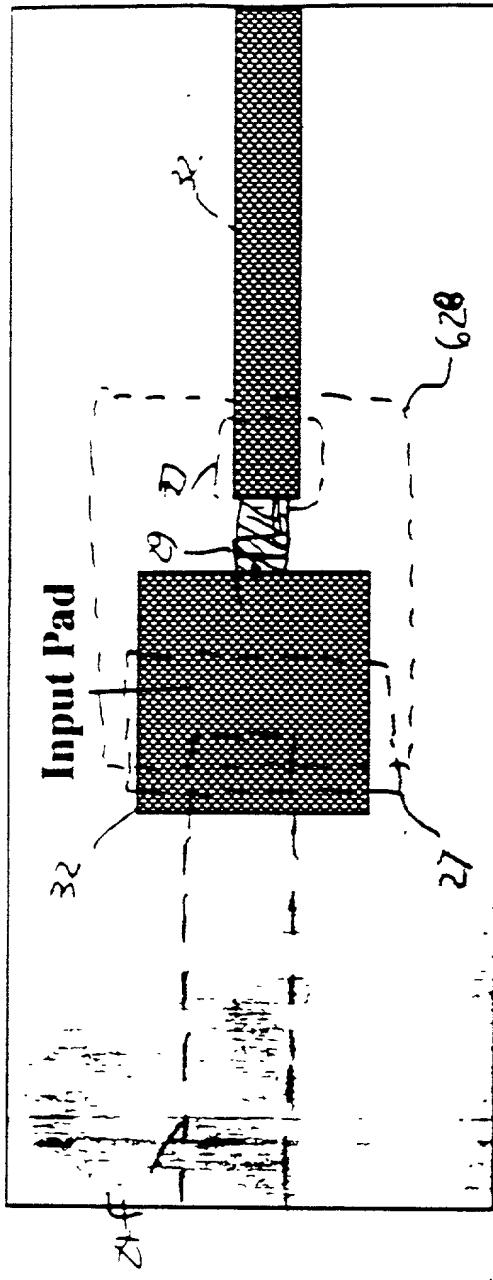


Fig. 2.8.2

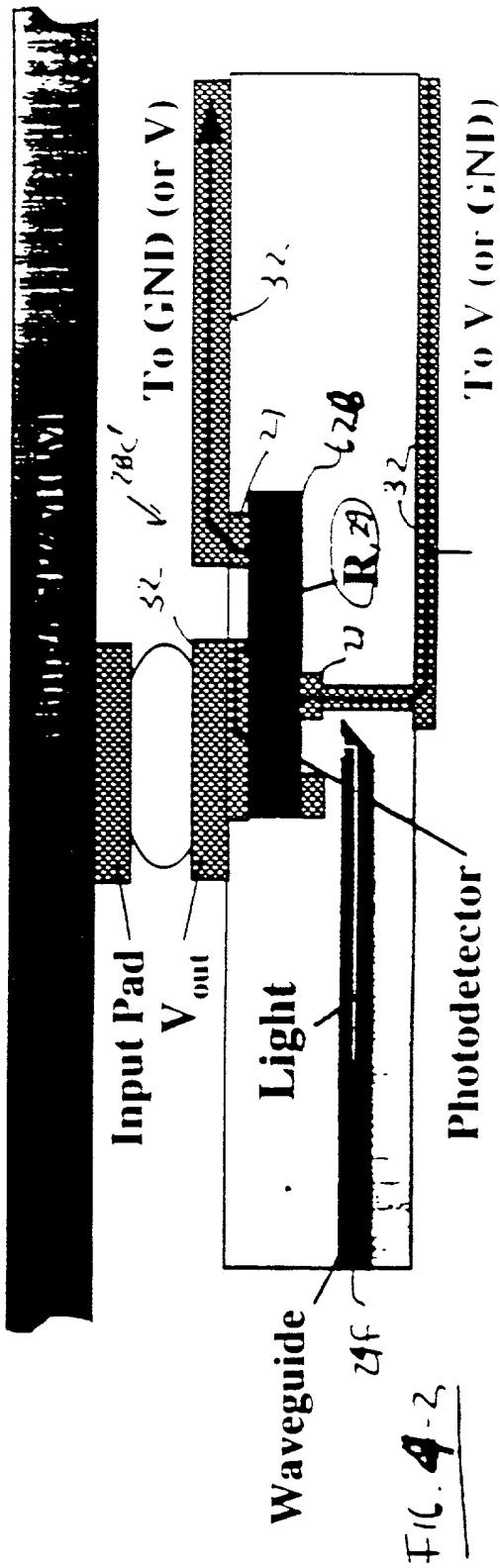


Fig. 2.8.2

Figure 5-3

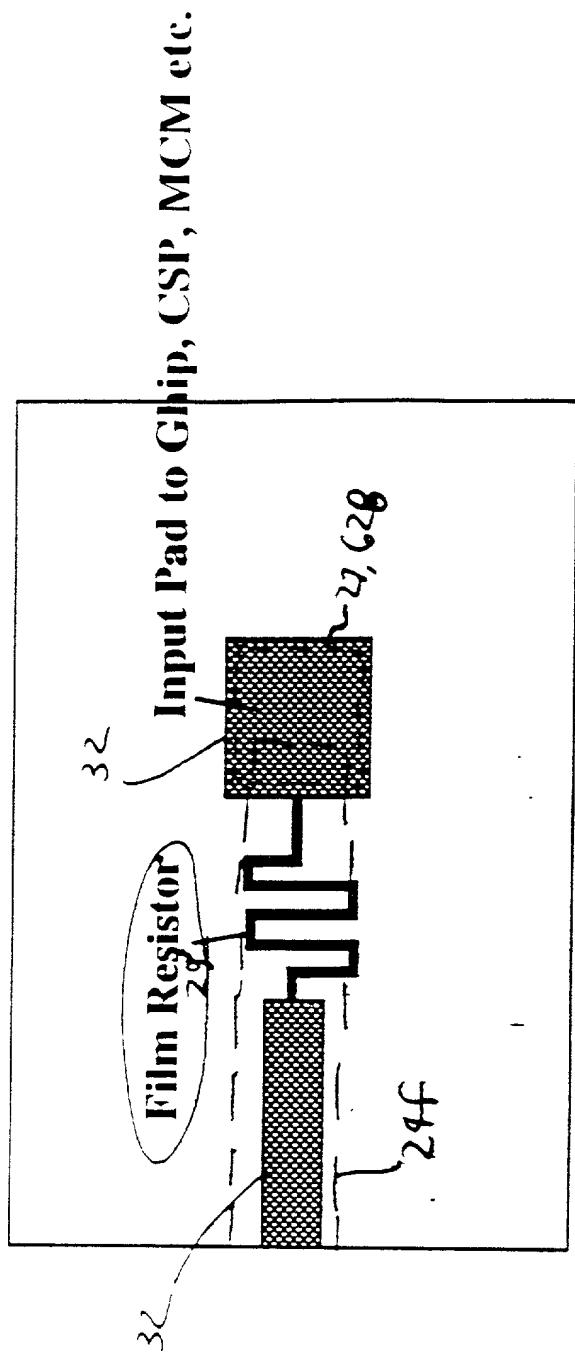
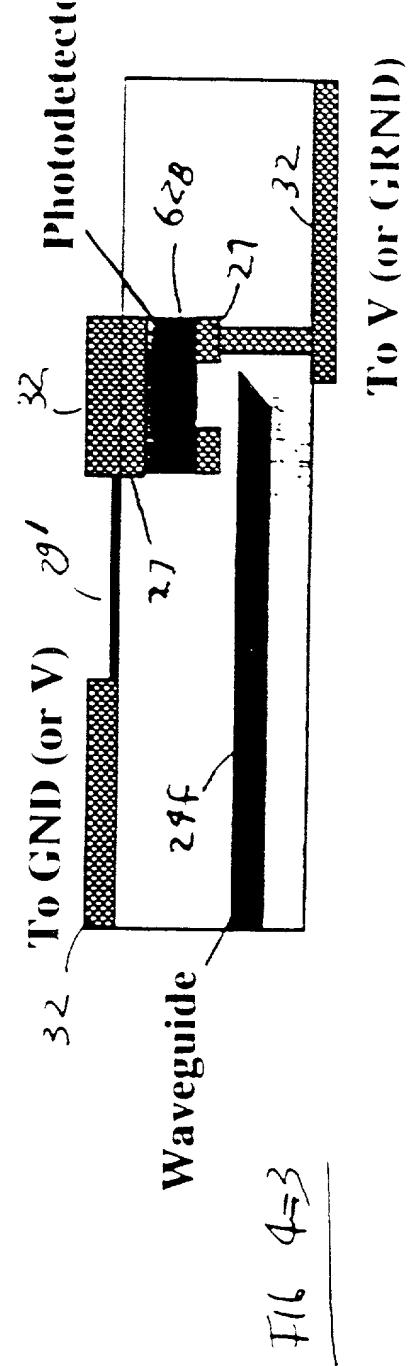


Fig. 5-3



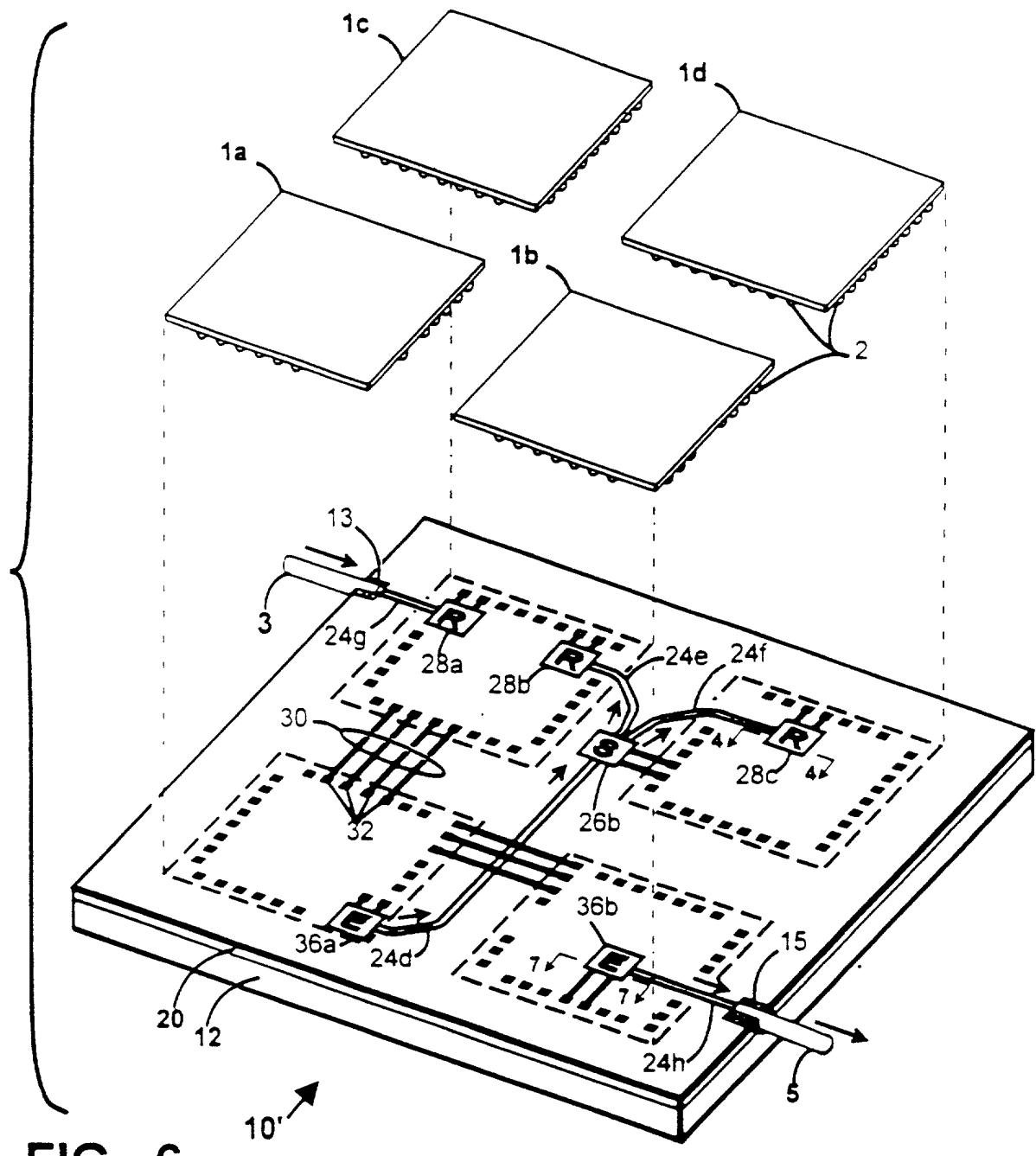


FIG. 6

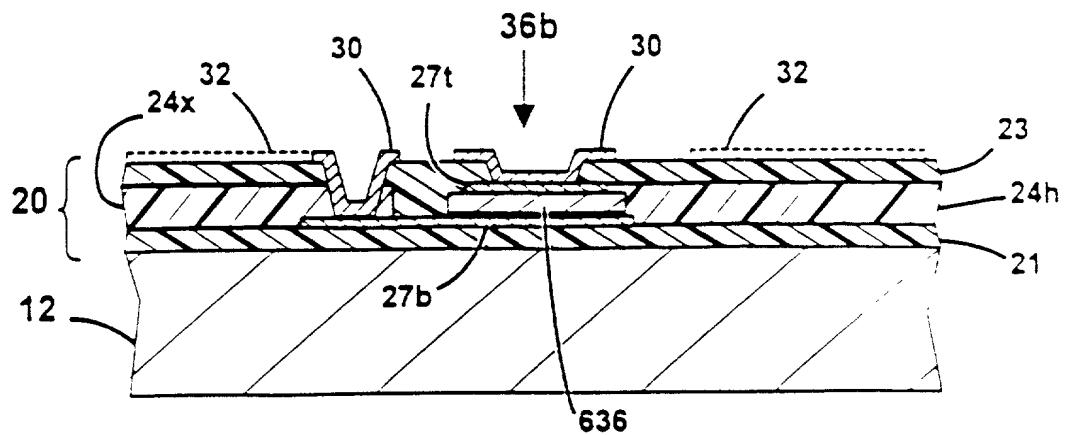


FIG._7

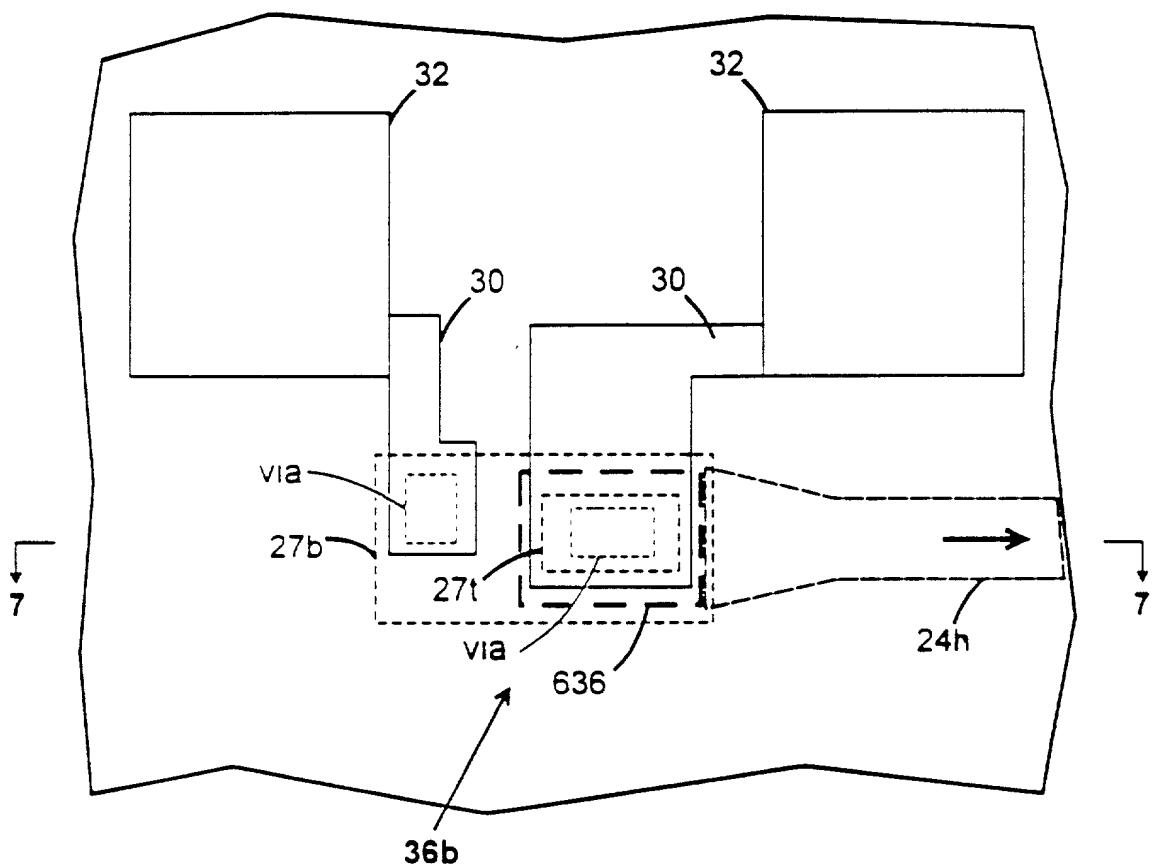


FIG._8

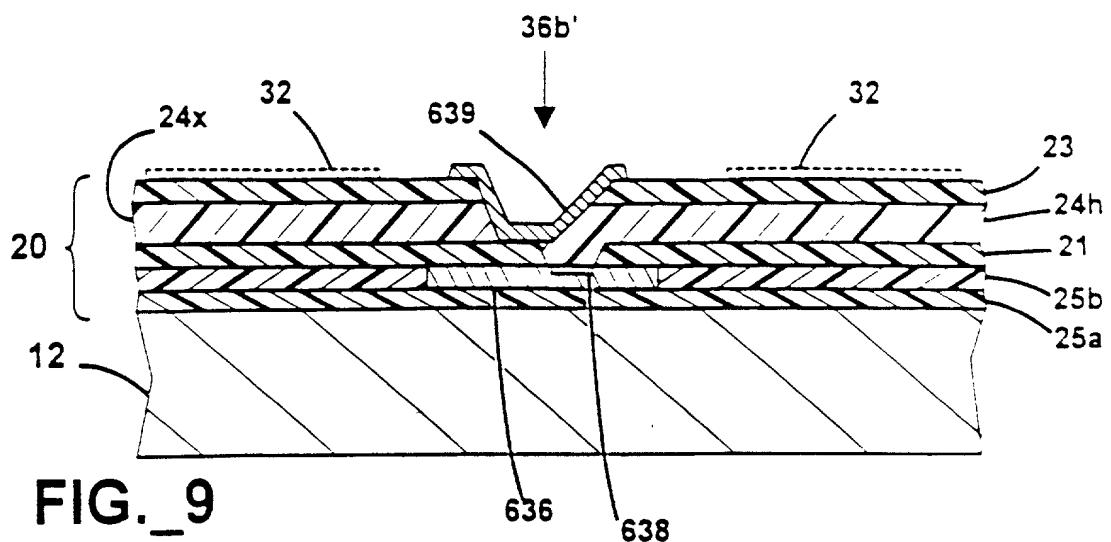


FIG._9

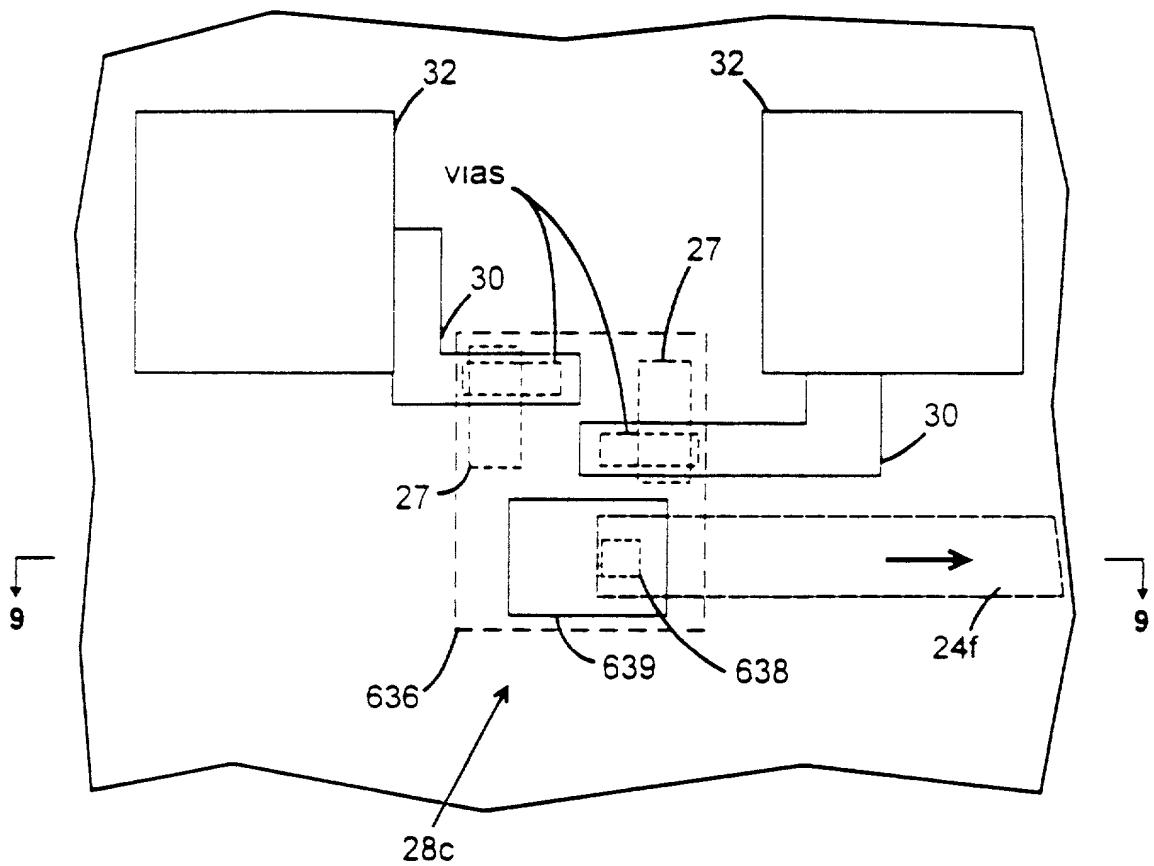
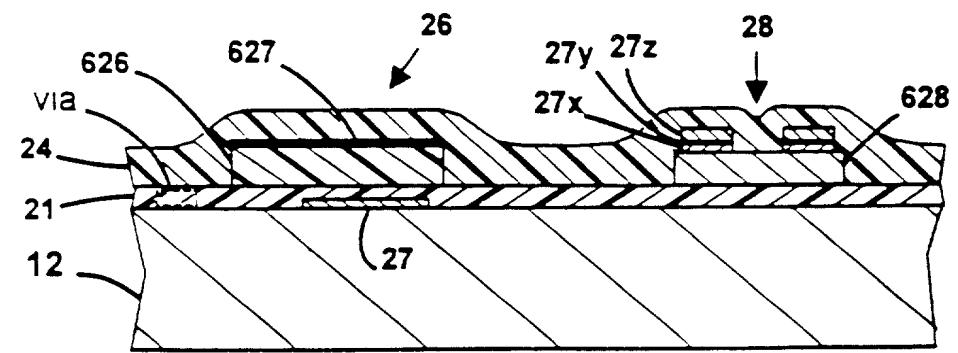
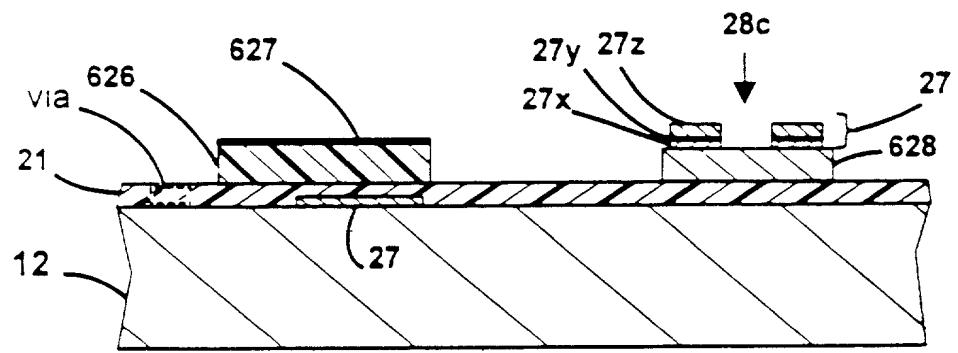
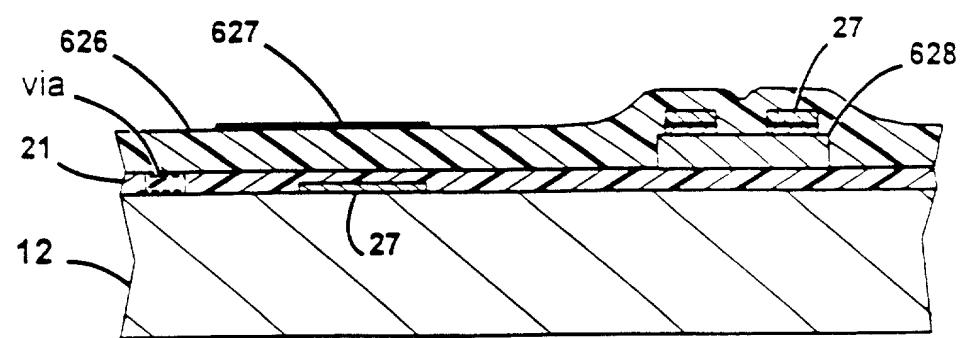
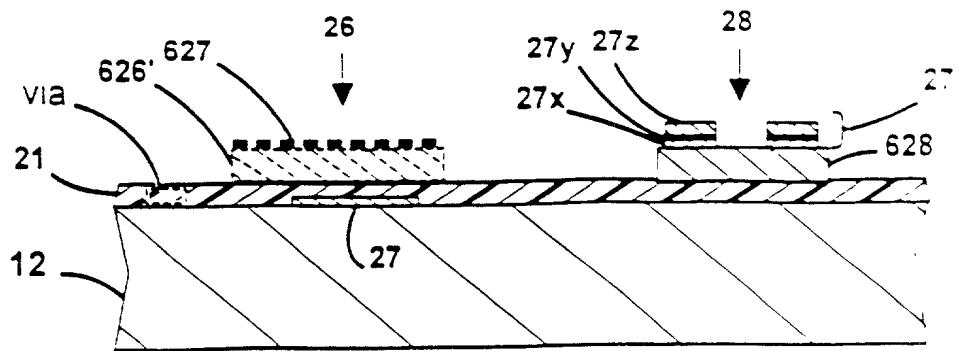


FIG._10



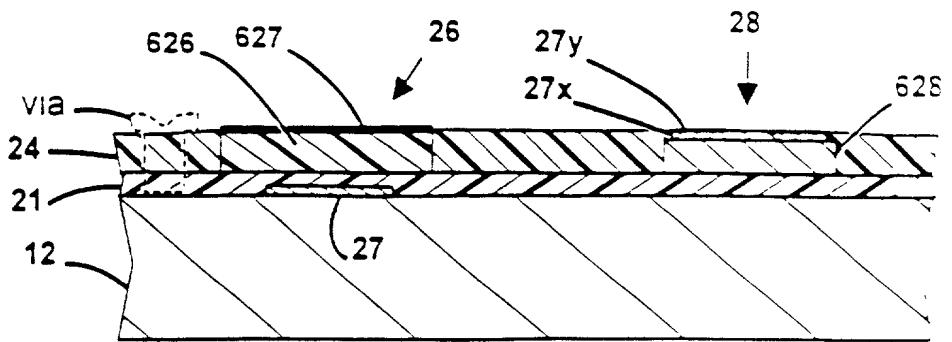


FIG._15

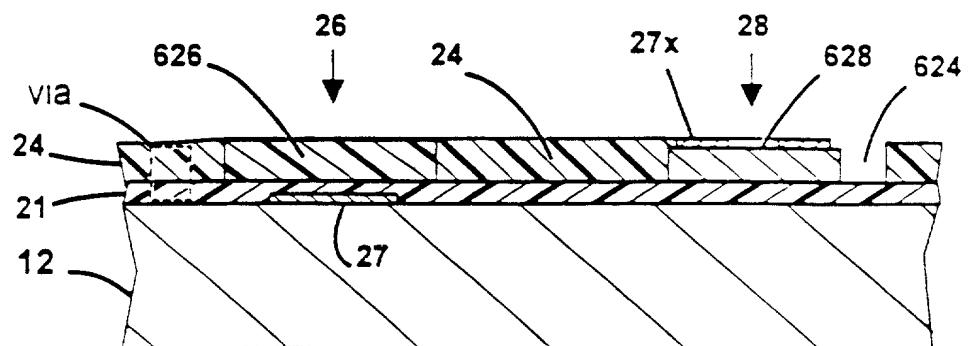


FIG._16

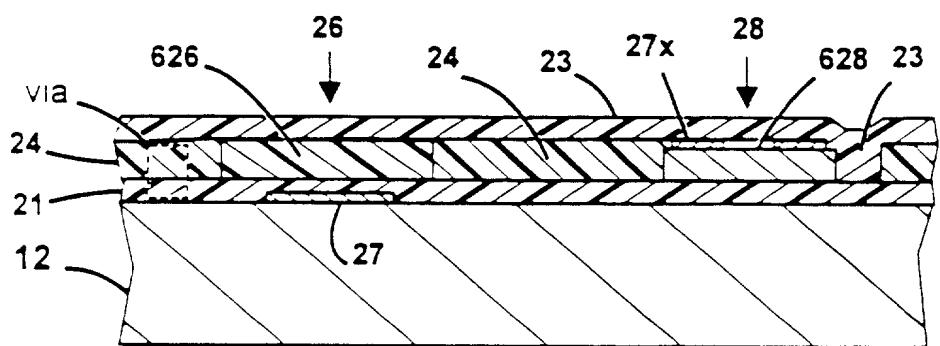


FIG._17

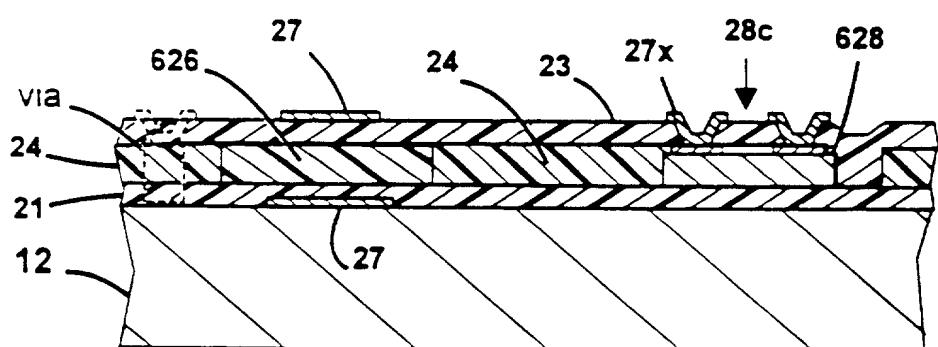


FIG._18

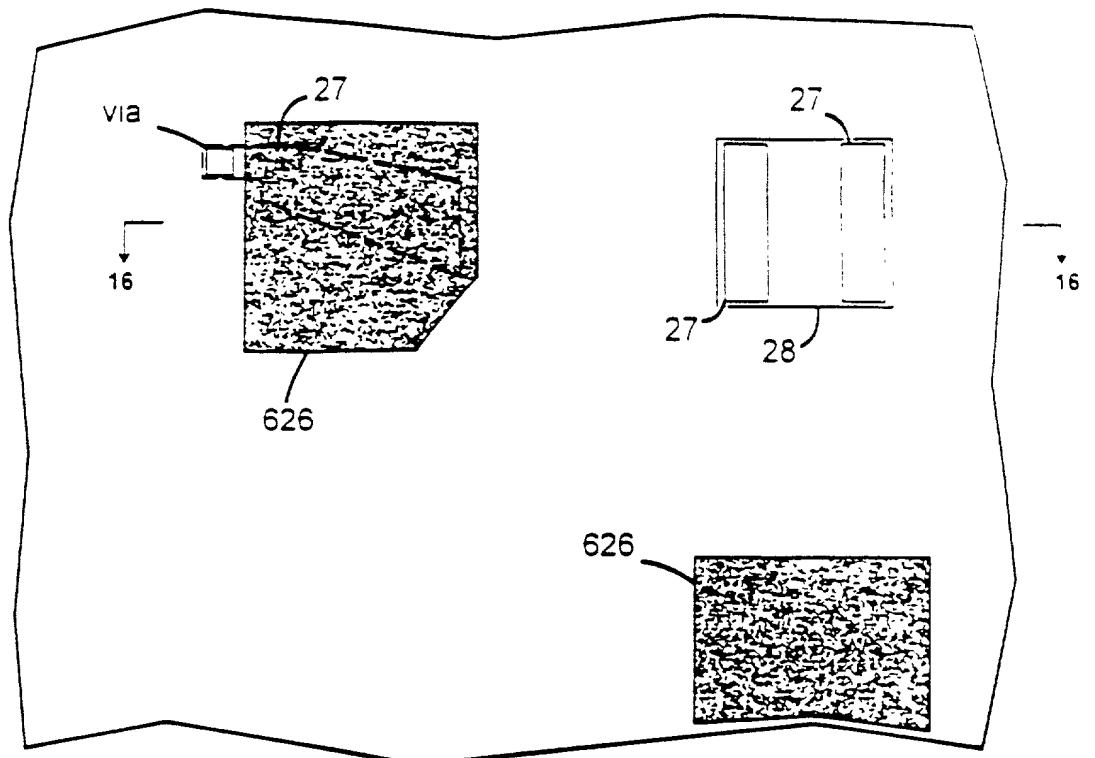


FIG._19

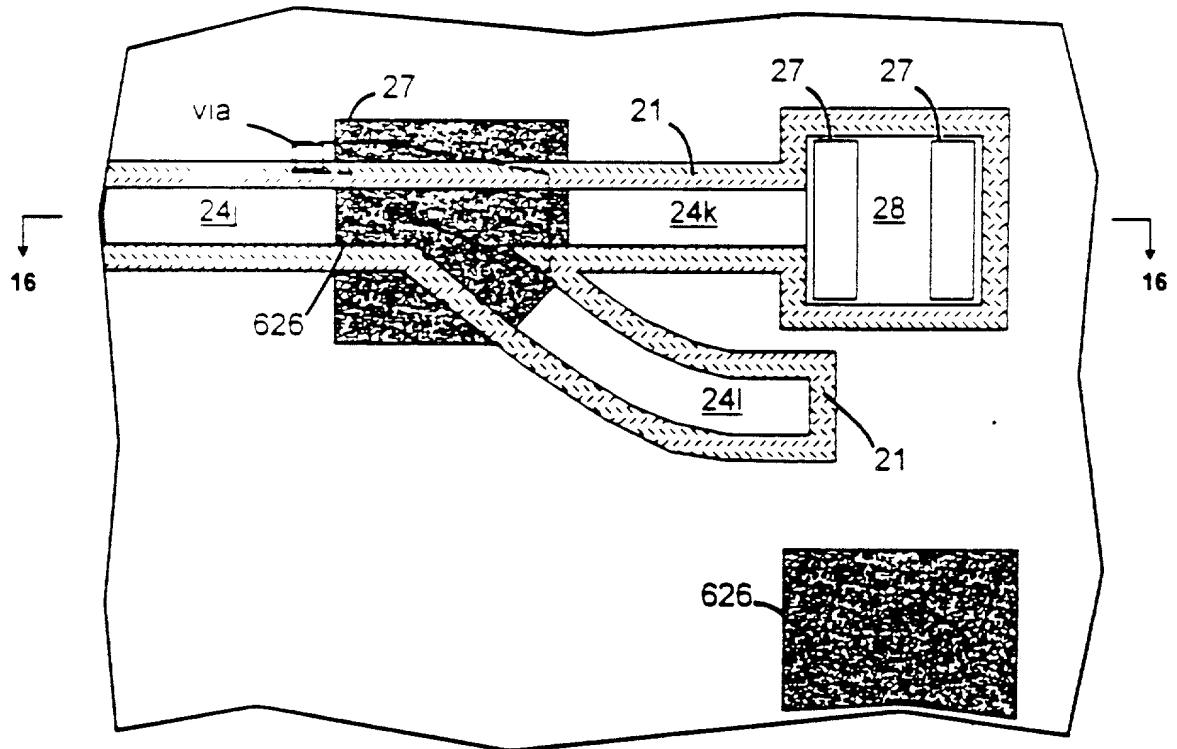


FIG._20

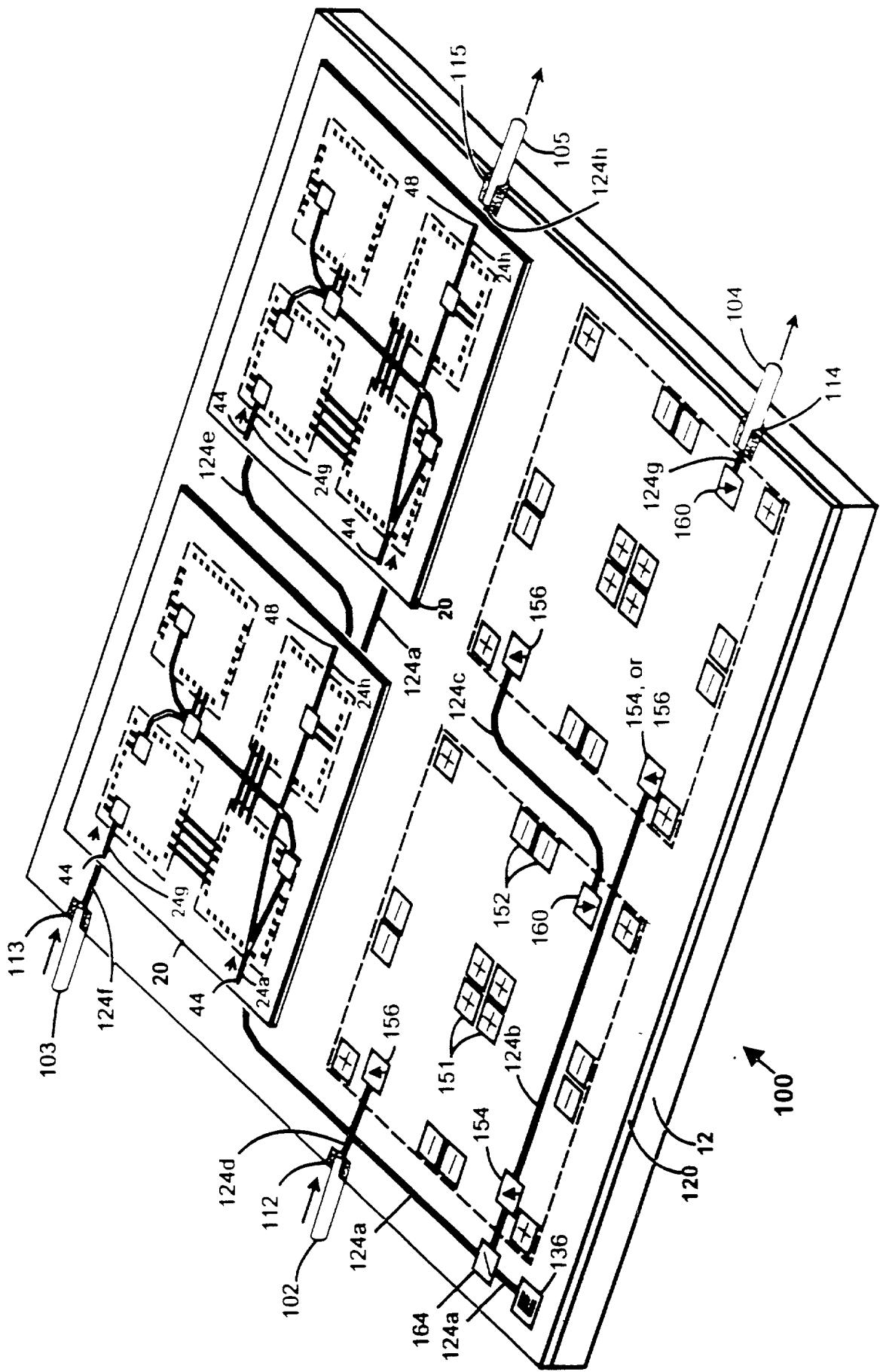
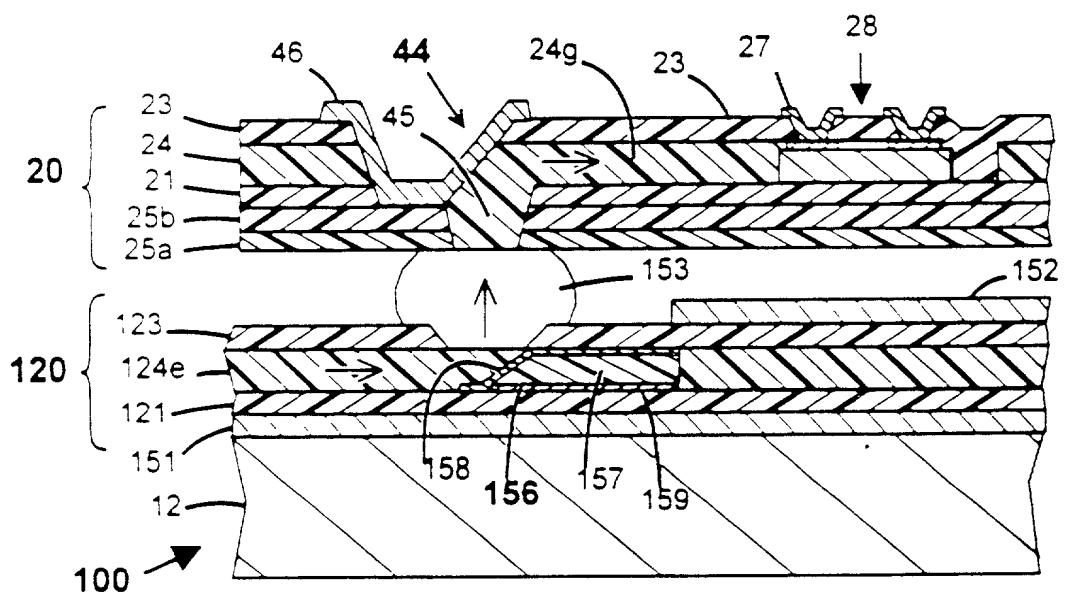
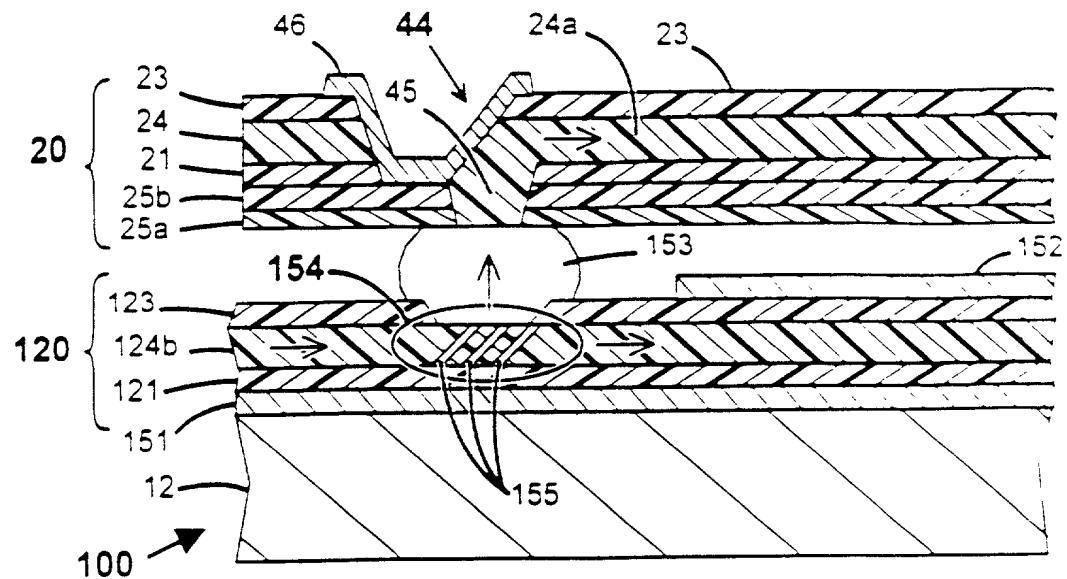


FIG. 21



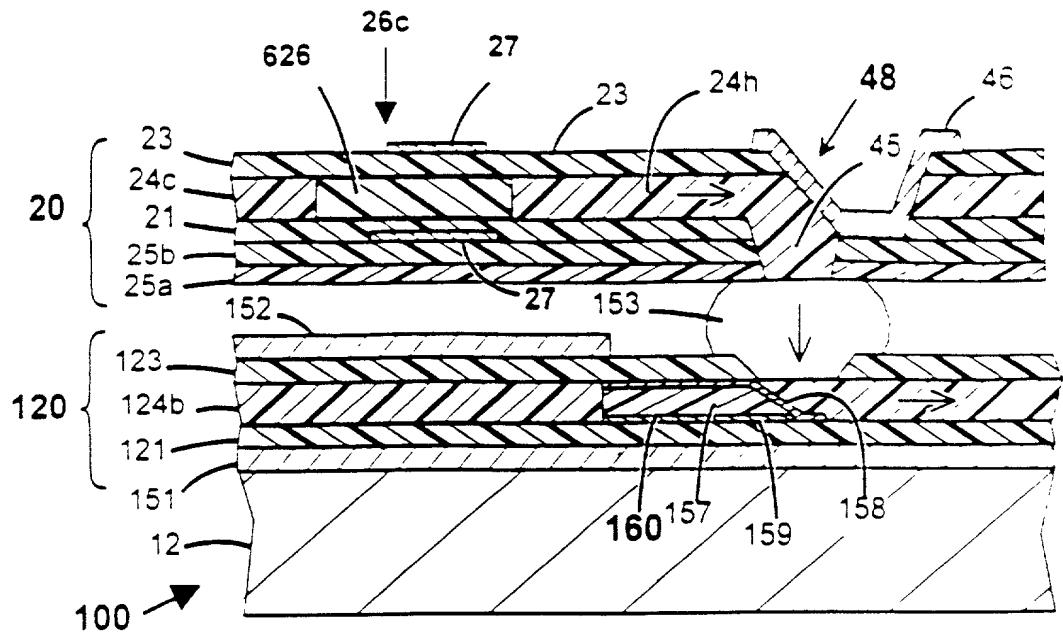


FIG. 24

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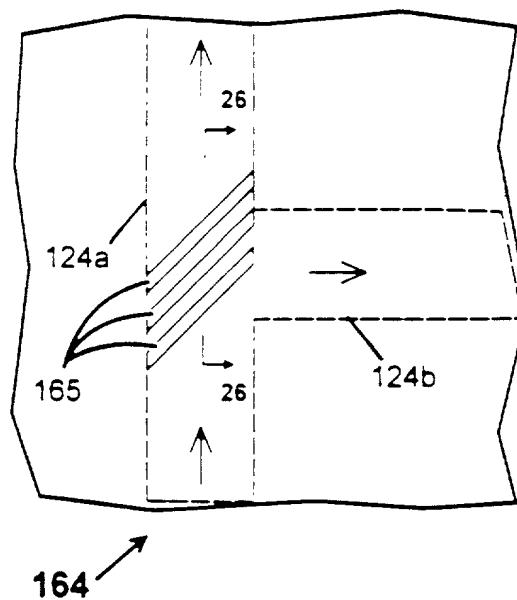


FIG. 25

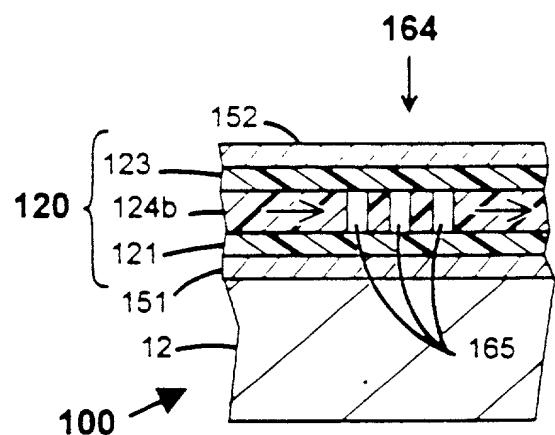


FIG. 26

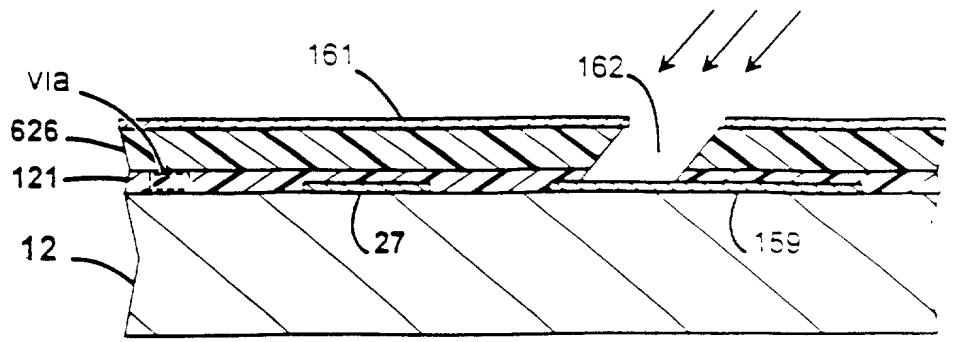


FIG. 27

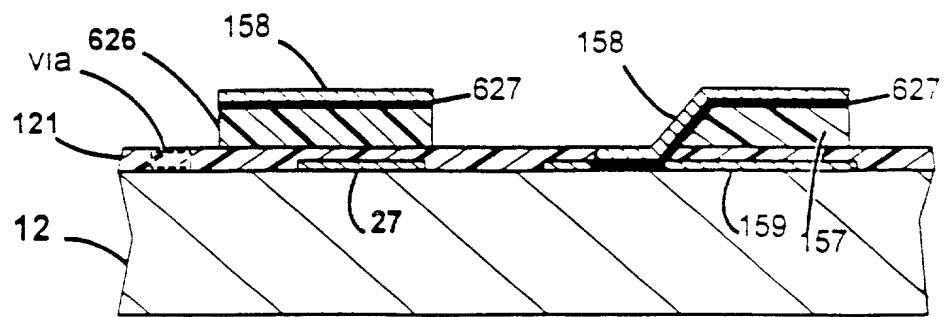


FIG. 28

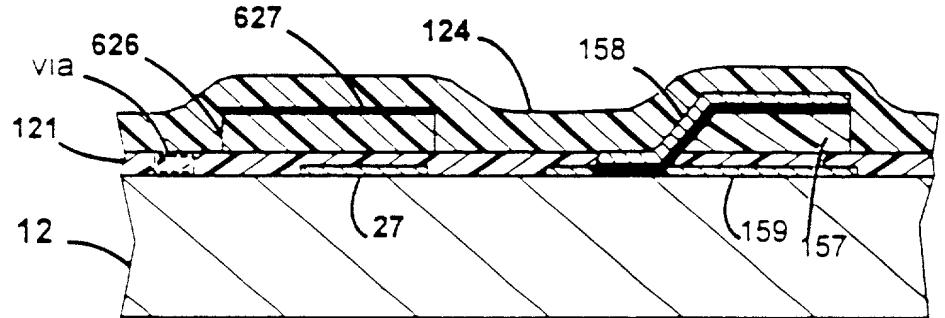


FIG. 29

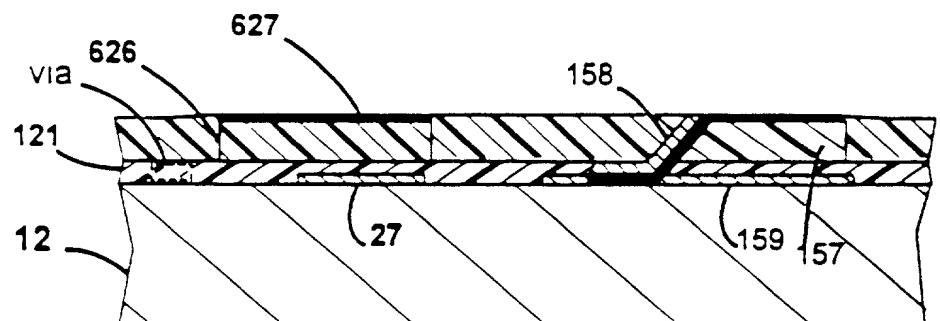


FIG. 30

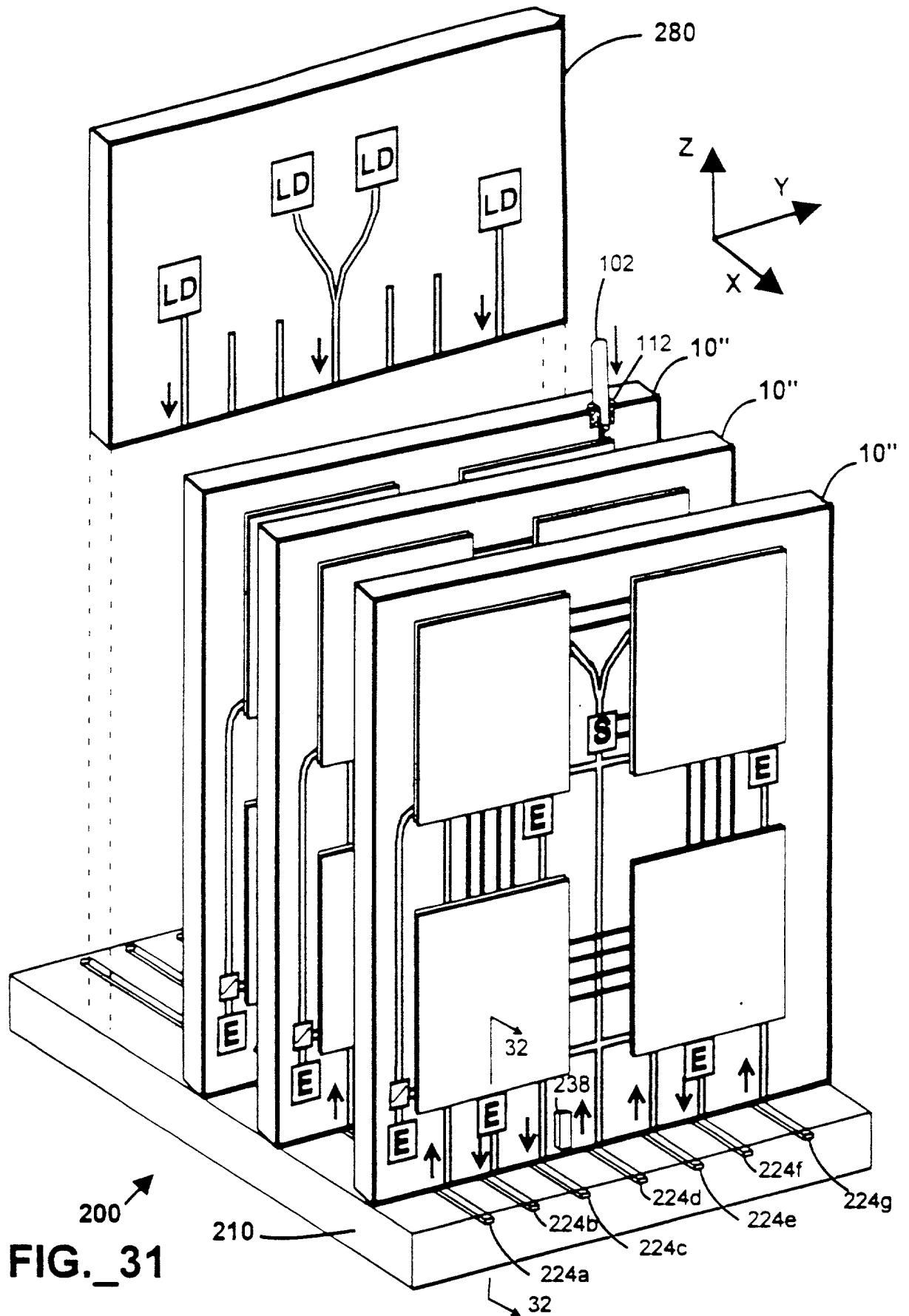


FIG. 32

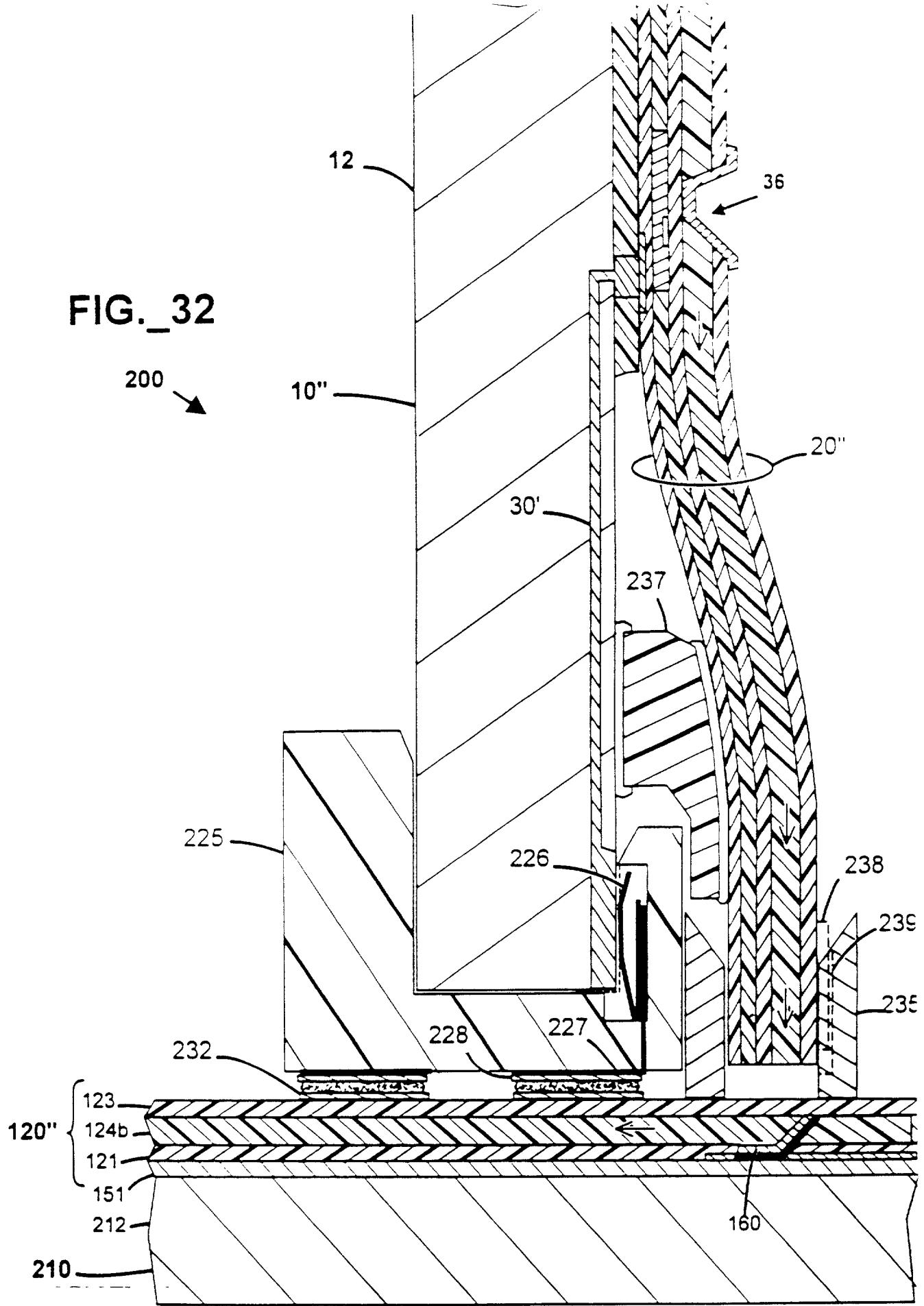
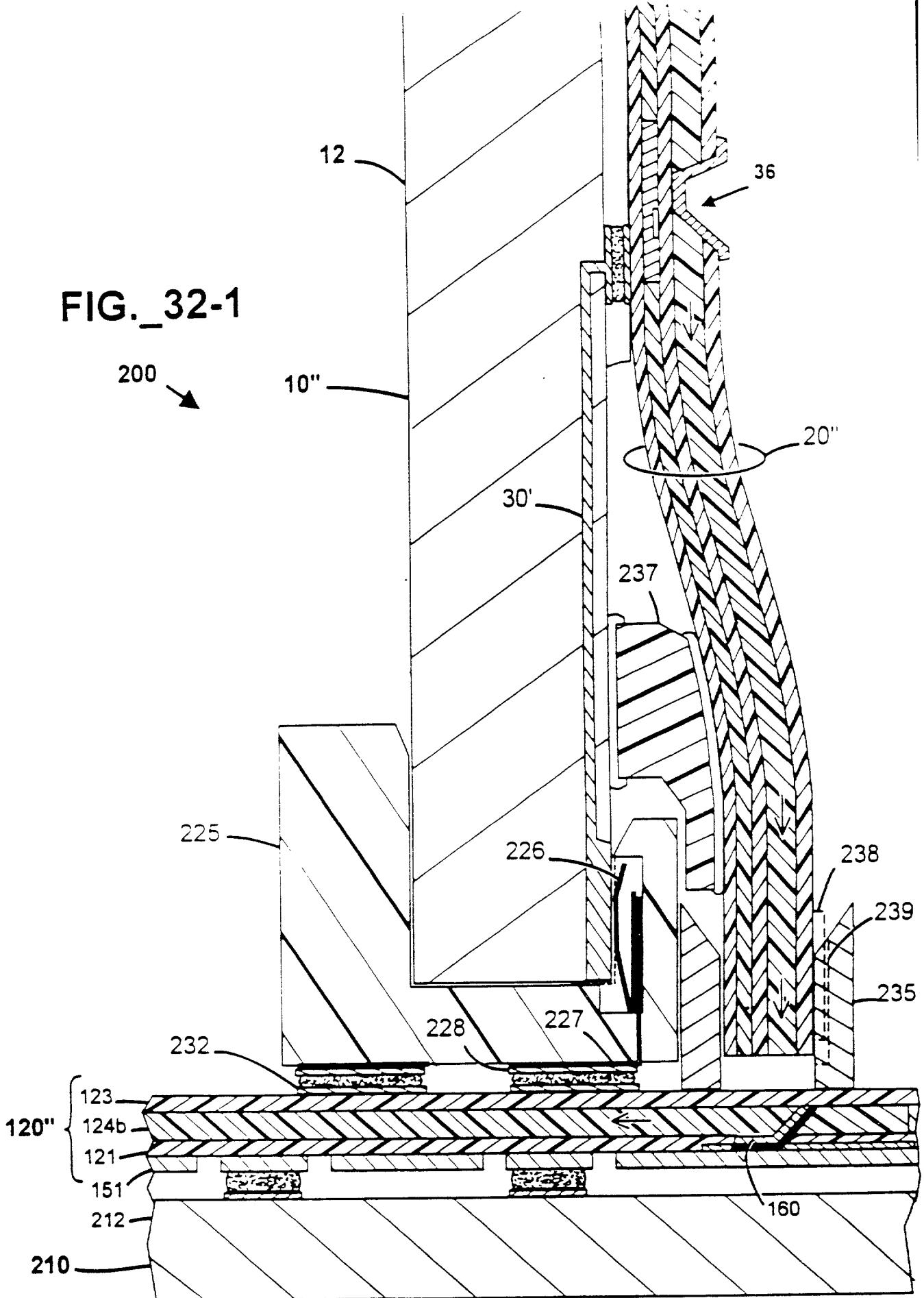


FIG._32-1



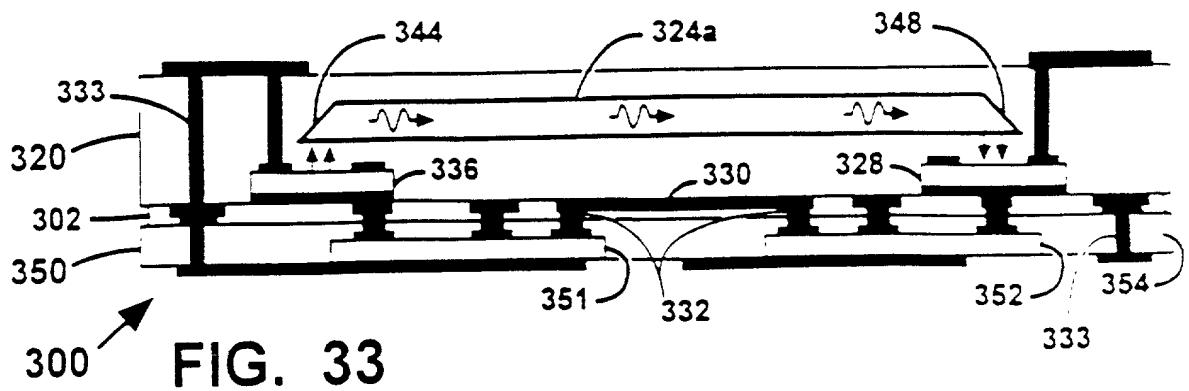


FIG. 33



FIG. 34

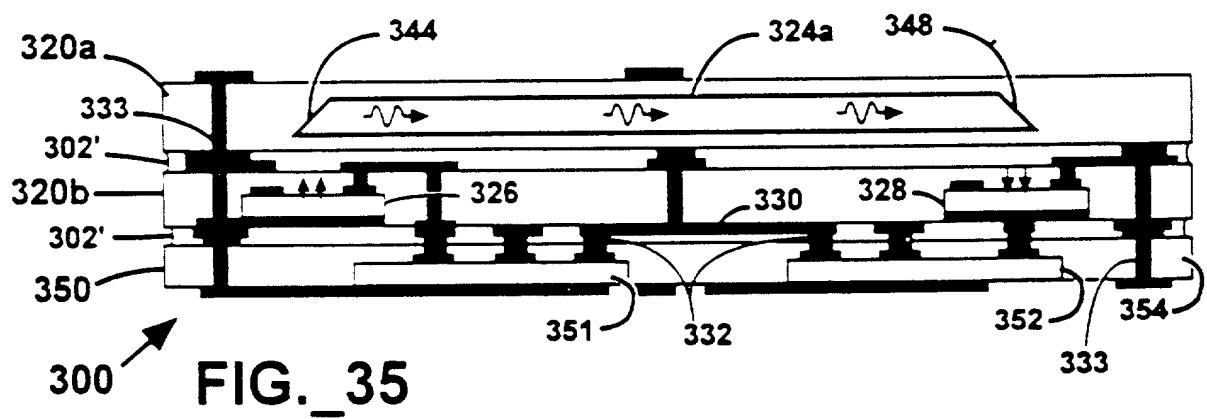


FIG. 35

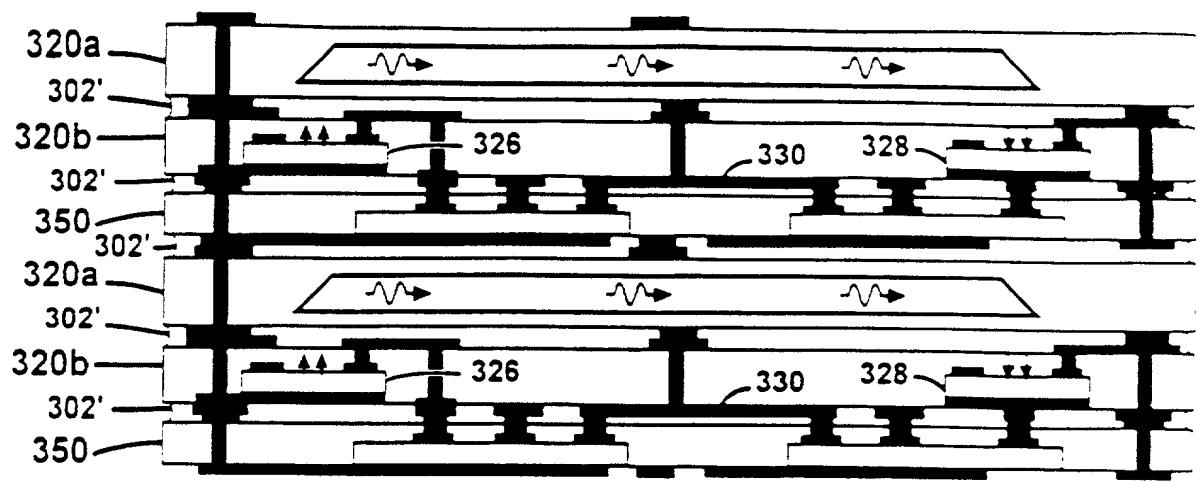


FIG. 36

007457692000

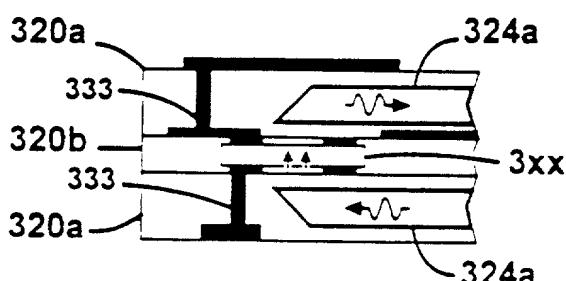


FIG. 37-1

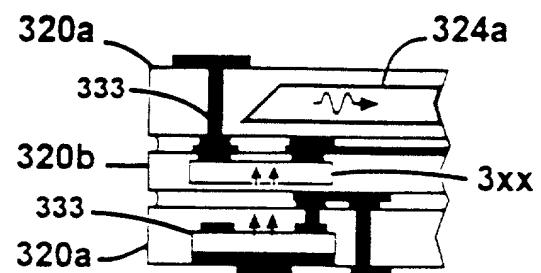


FIG. 37-2

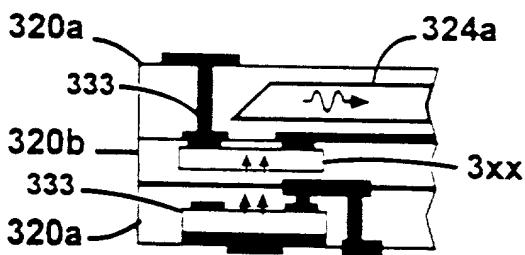


FIG. 37-3

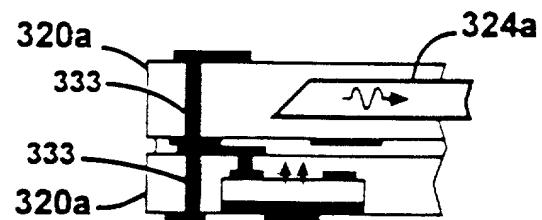


FIG. 37-4

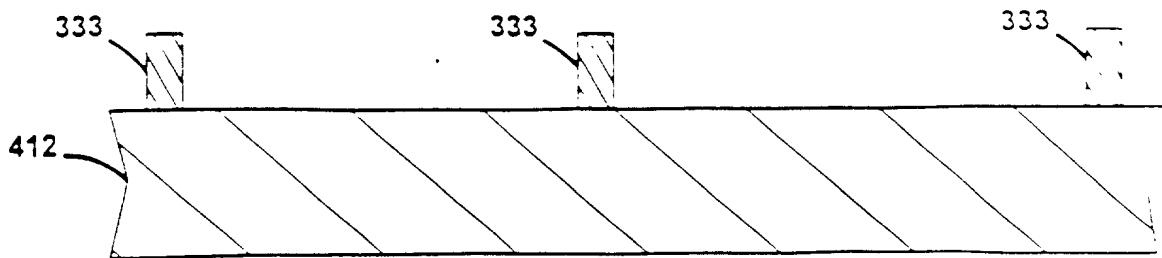


FIG._38

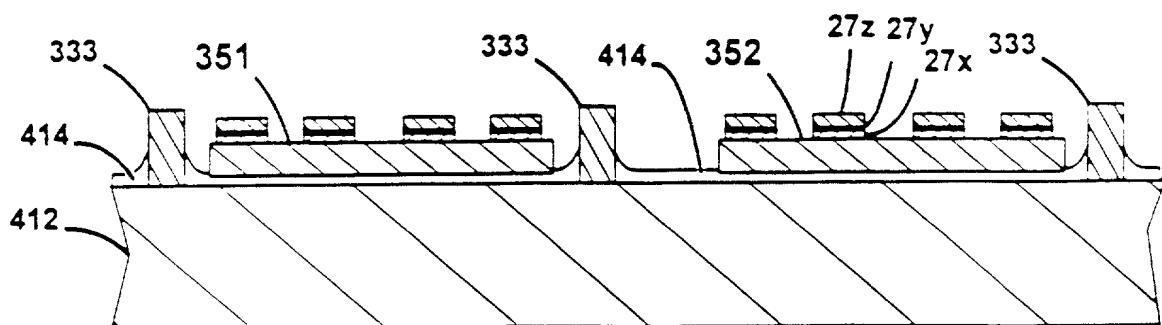


FIG._39

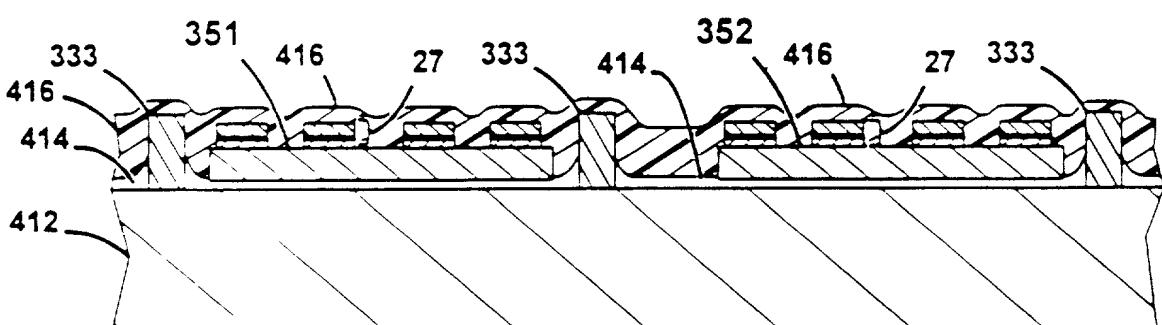


FIG._40

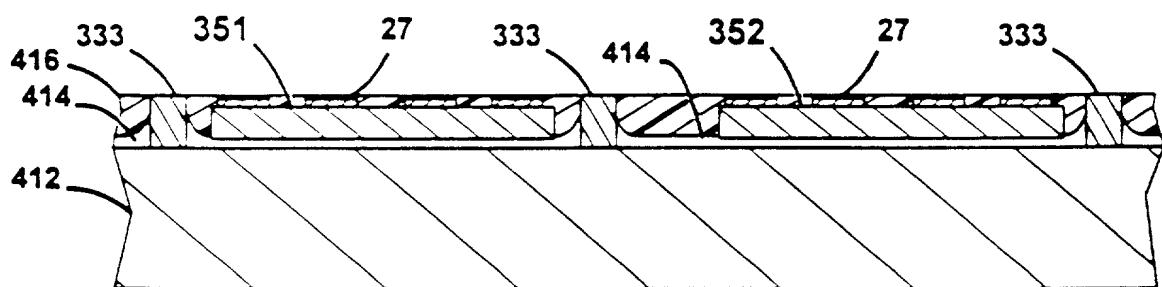


FIG._41

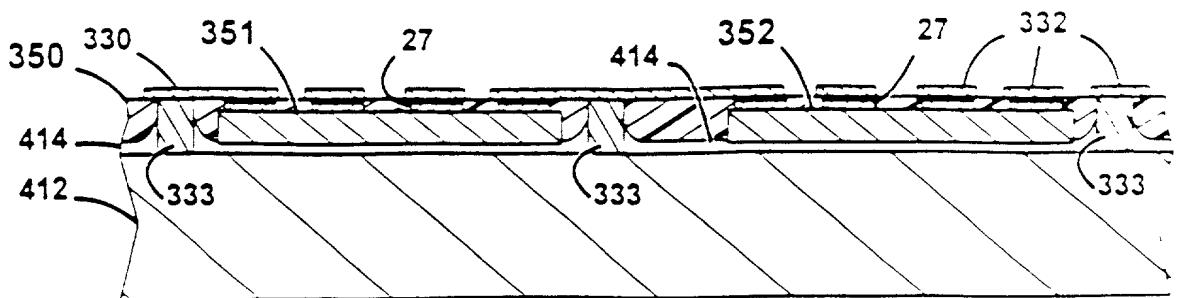


FIG._42

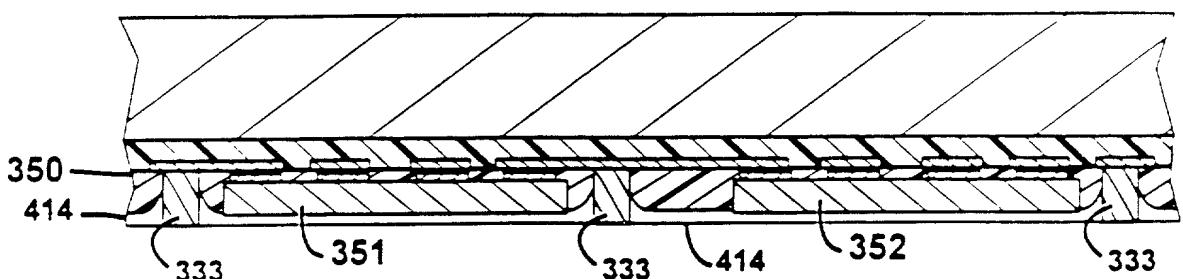


FIG._43

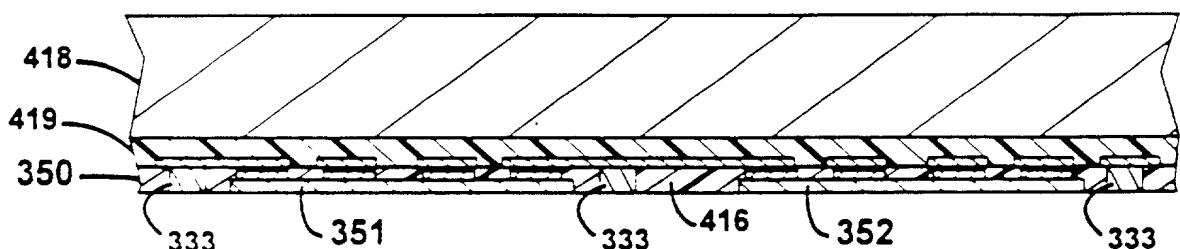


FIG._44

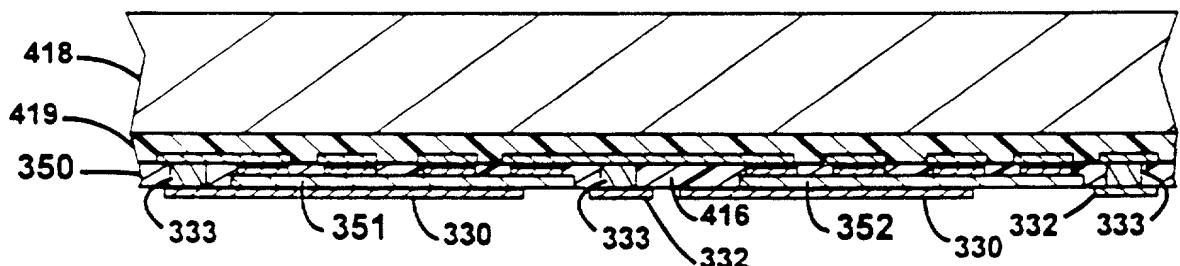
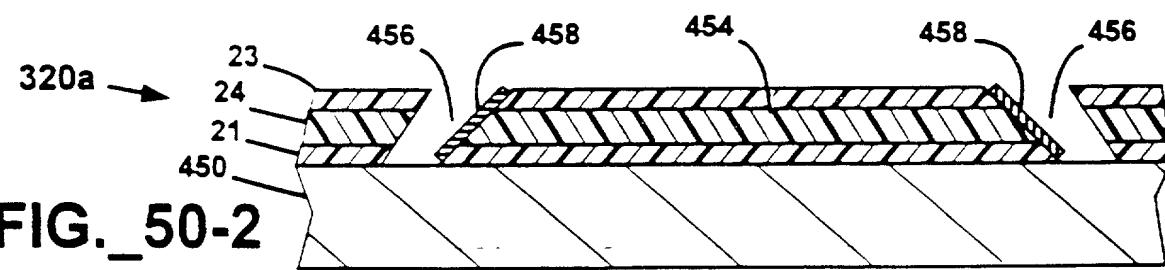
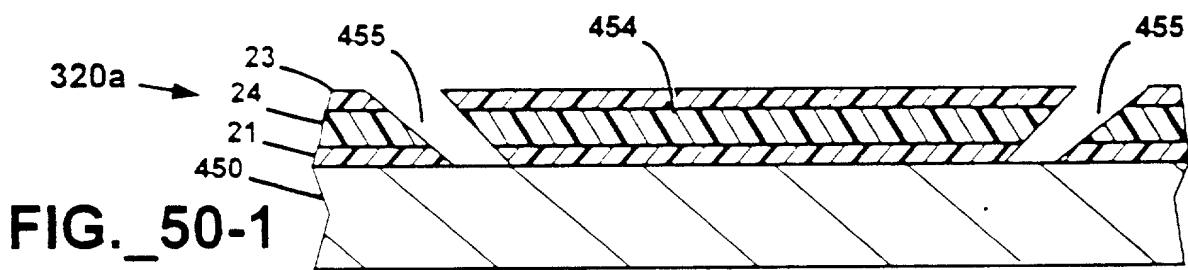
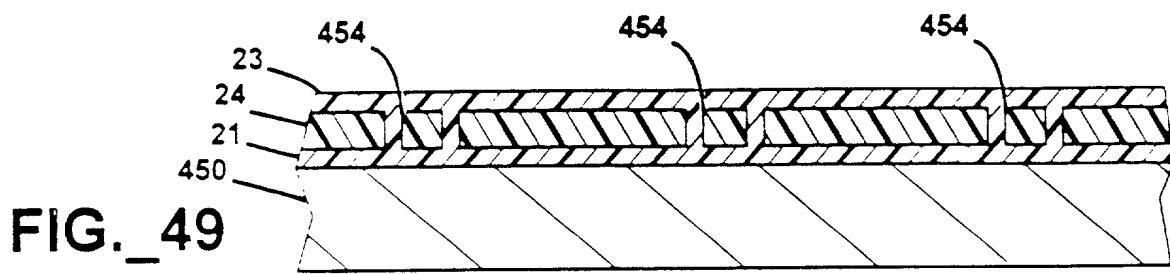
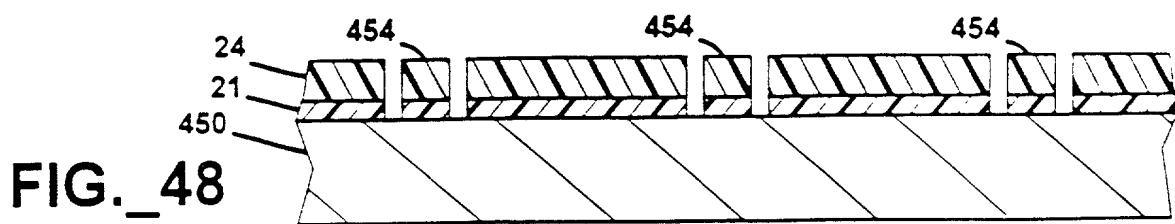
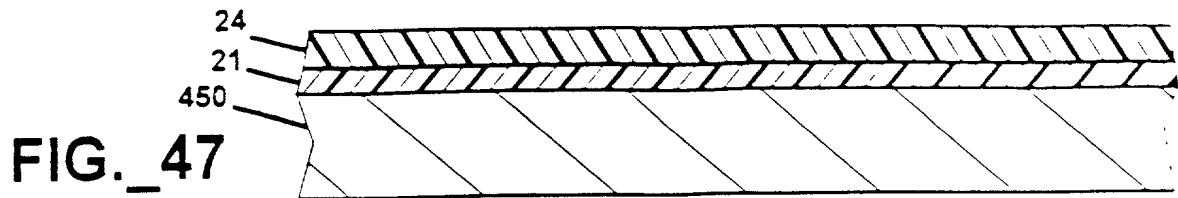
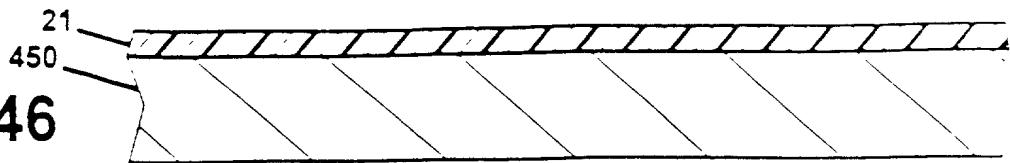


FIG._45



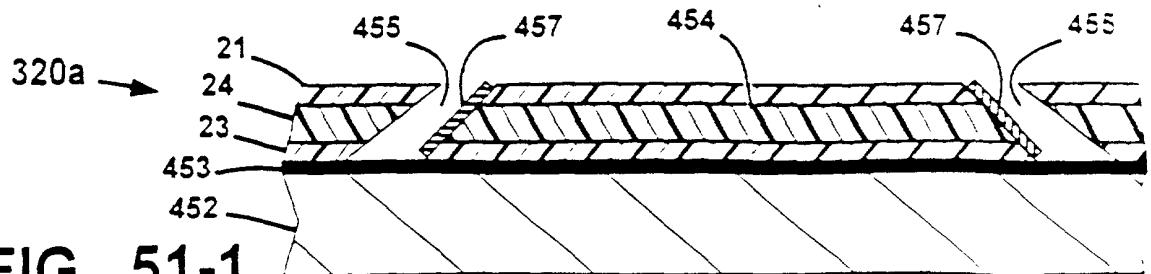


FIG._51-1

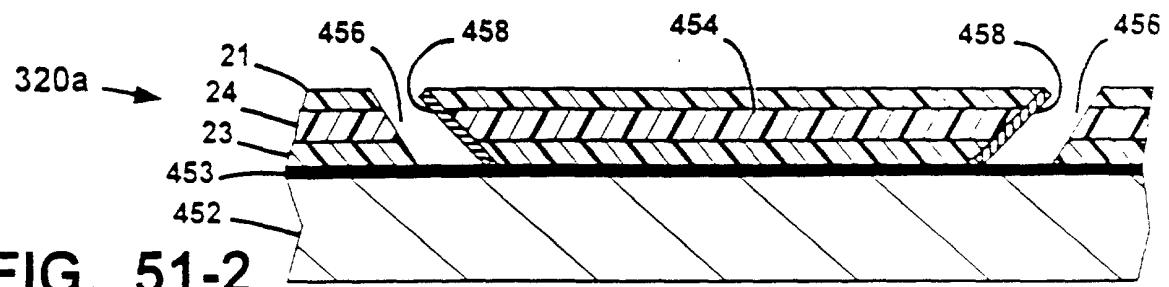


FIG._51-2

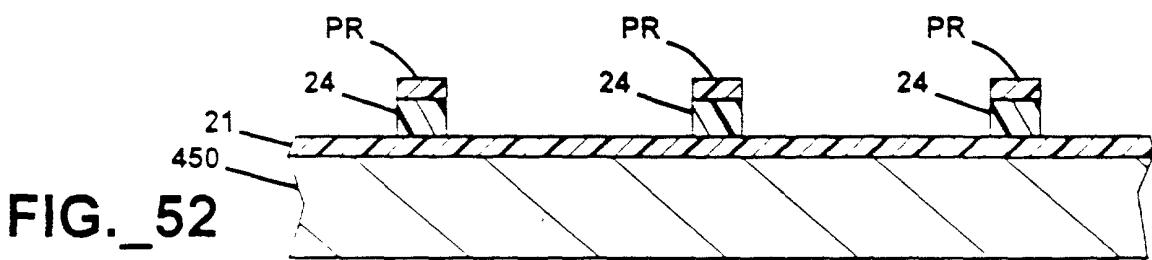


FIG._52

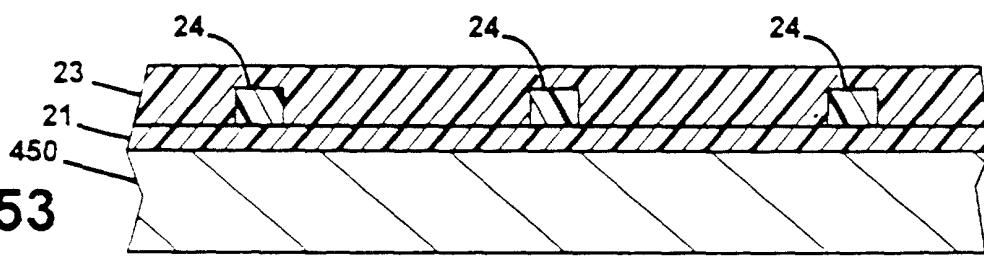


FIG._53

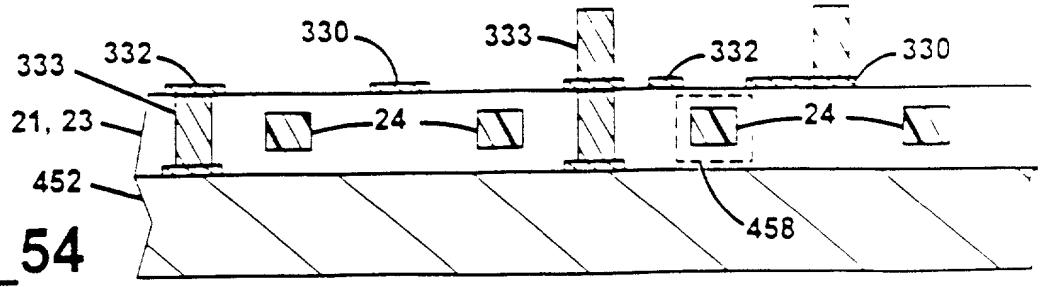


FIG. 54

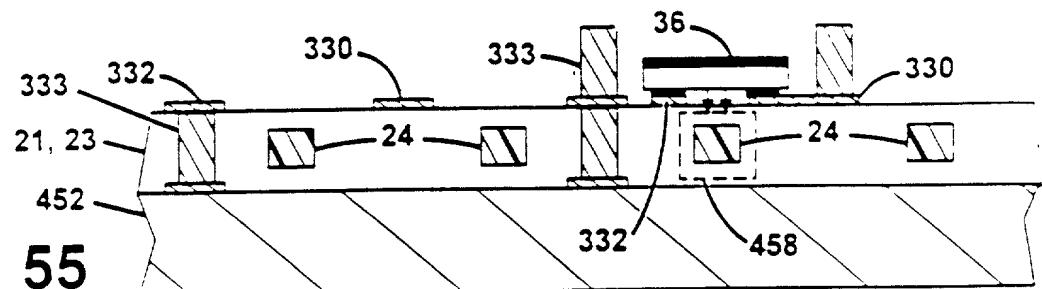


FIG. 55

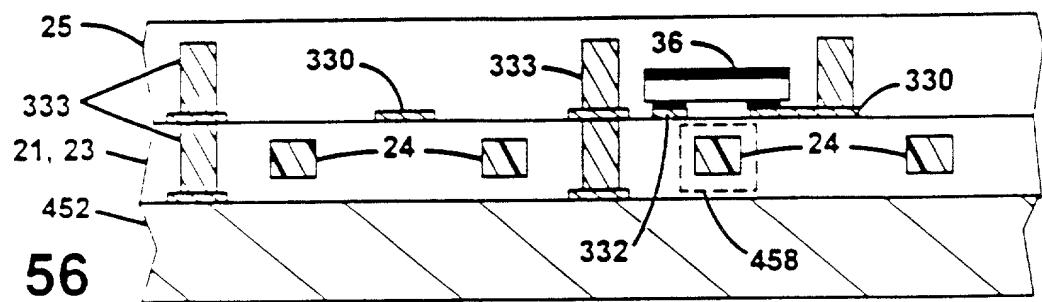


FIG. 56

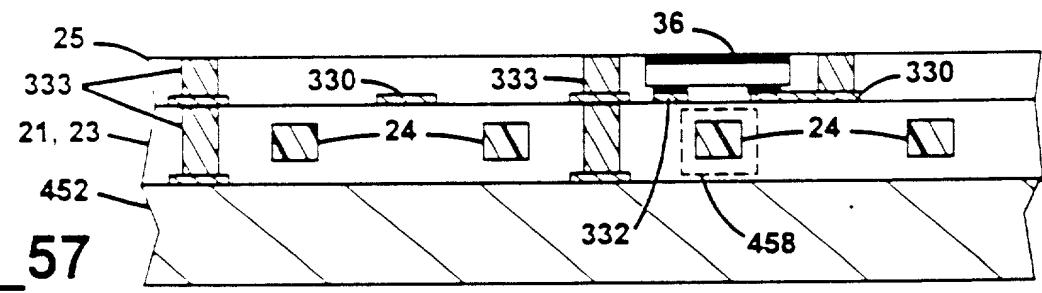


FIG. 57

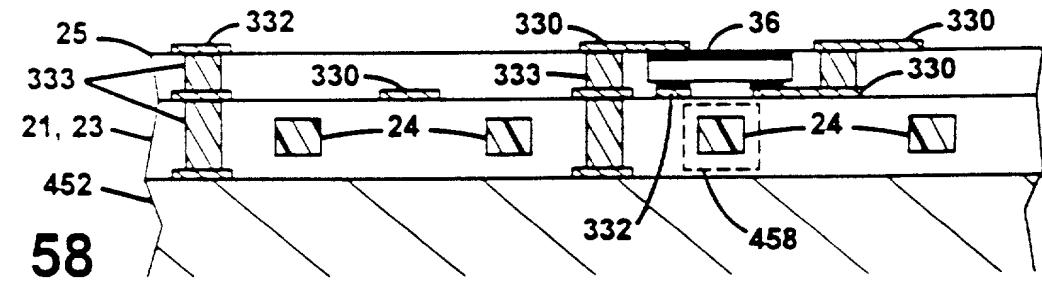


FIG. 58

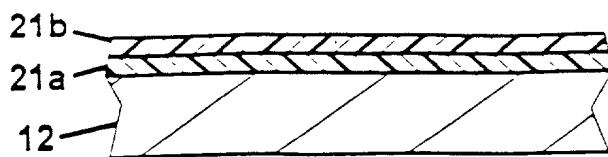


FIG. _59

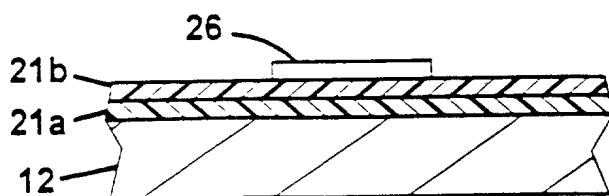


FIG. _60

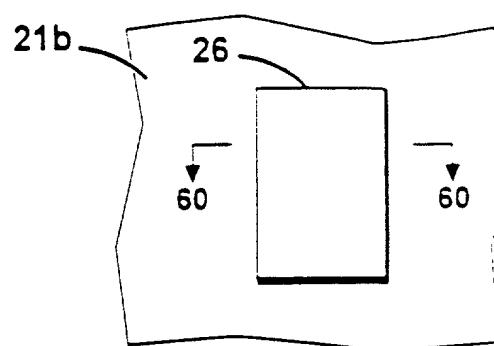


FIG. _61

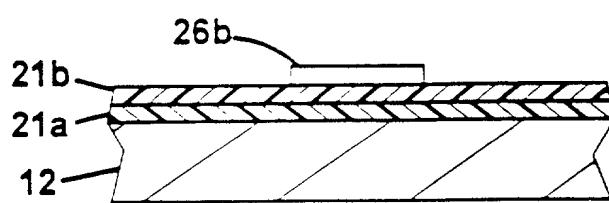


FIG. _62

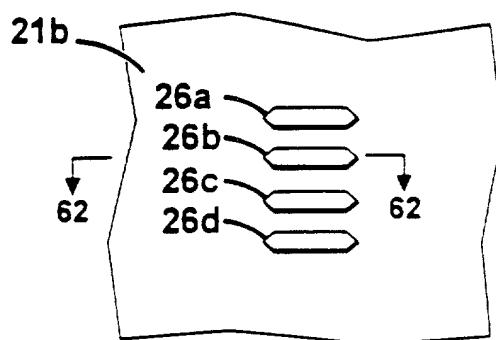


FIG. _63

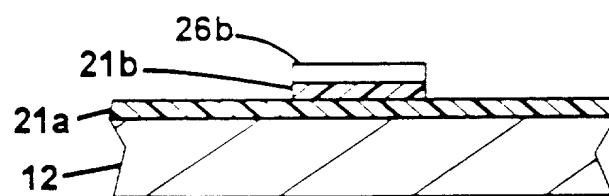


FIG. _64

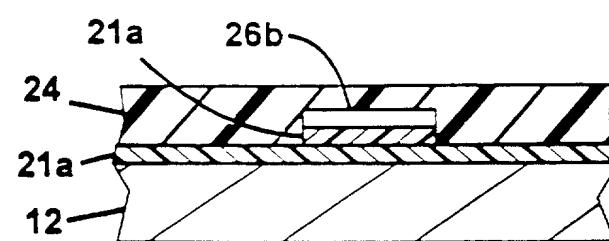


FIG. _65

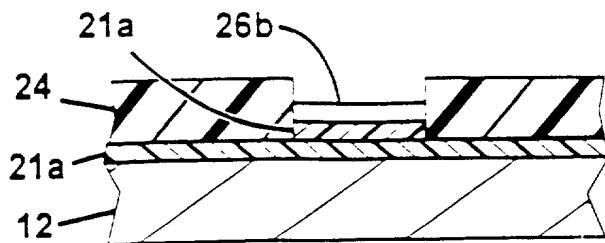


FIG. 66

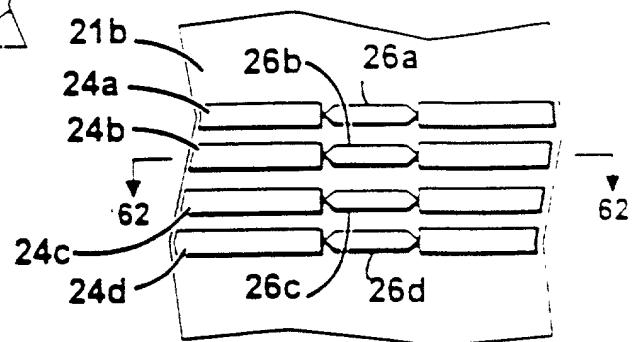


FIG. 67

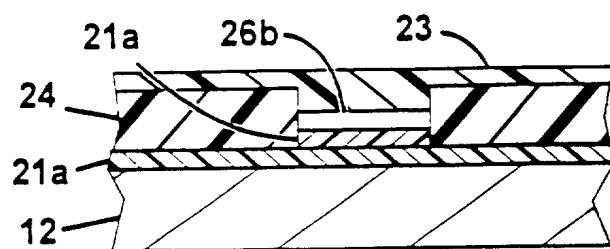


FIG. 68

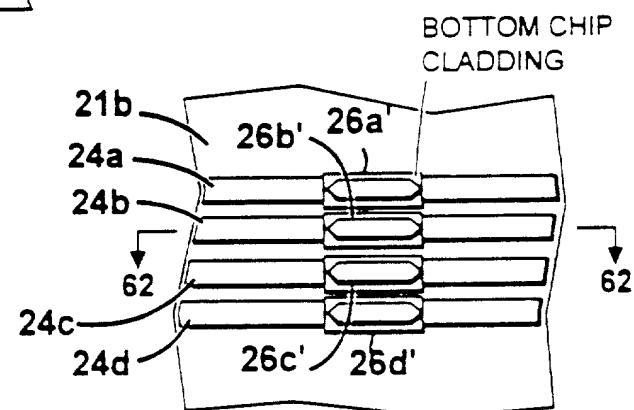


FIG. 67-2

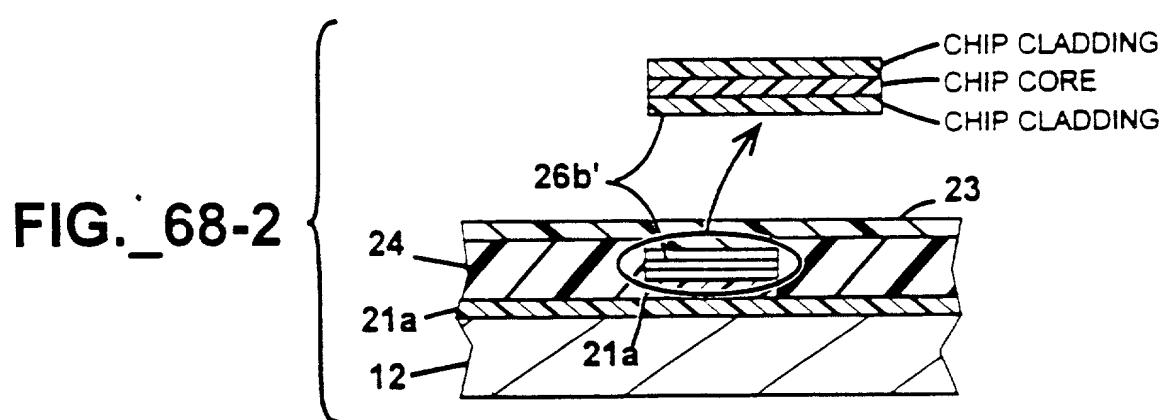


FIG. 68-2

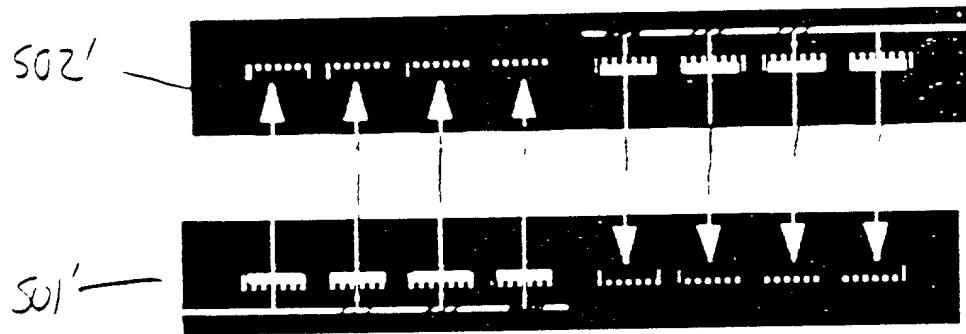
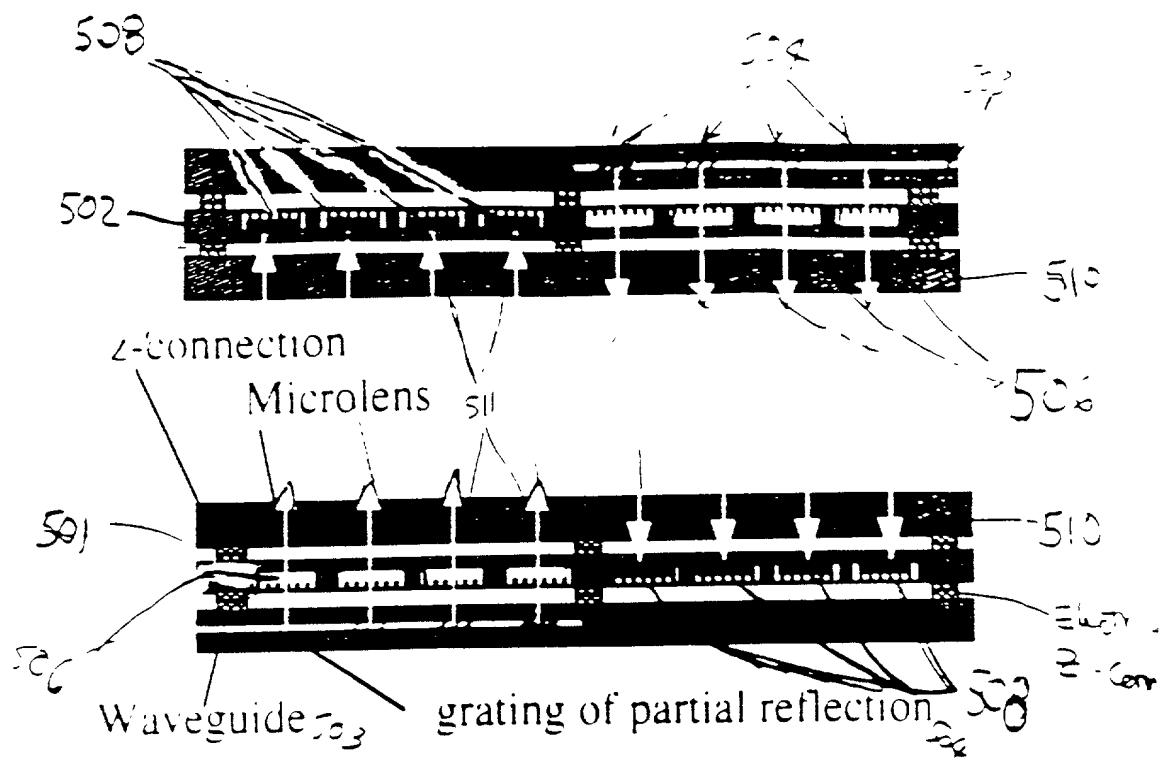
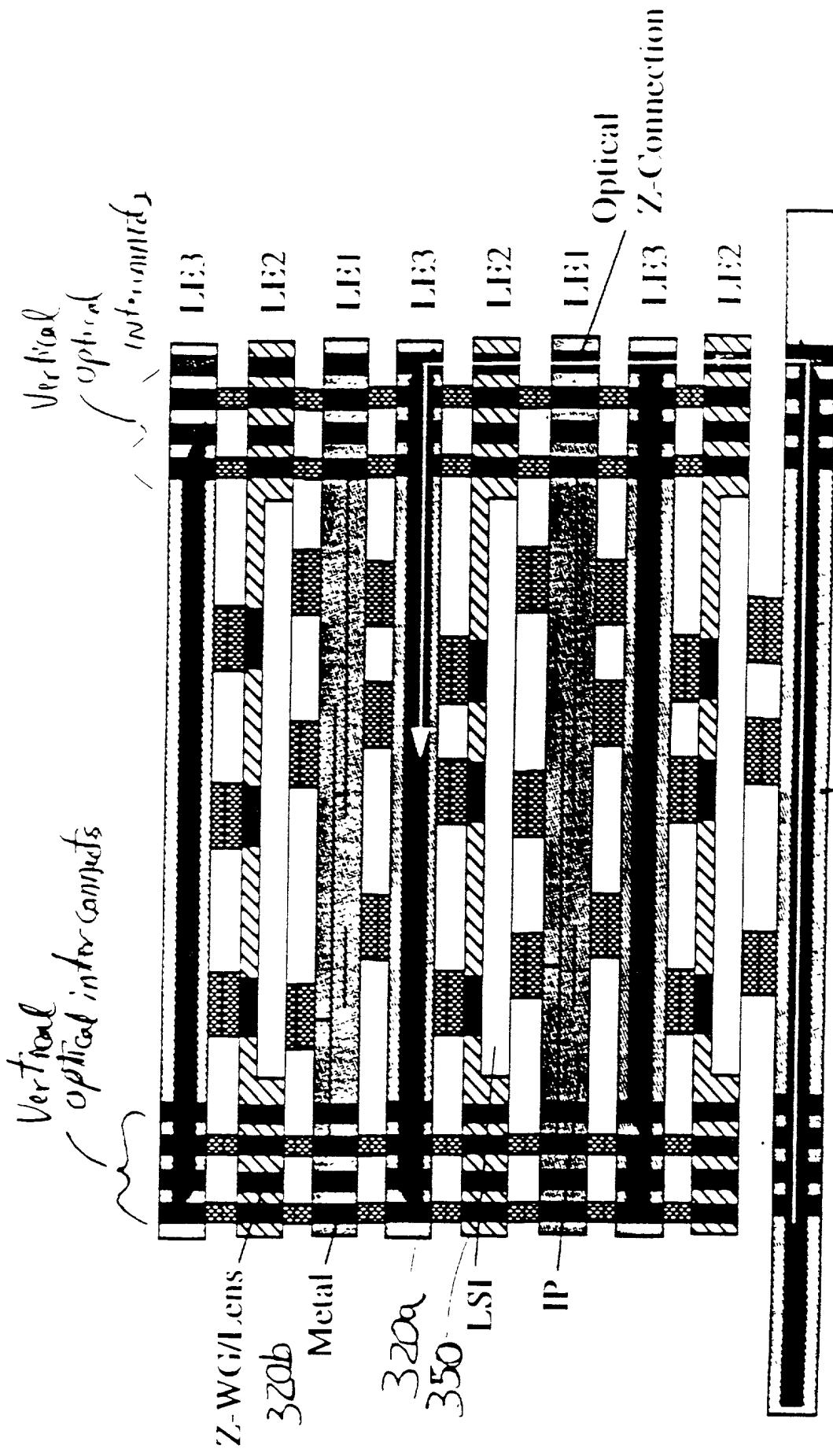


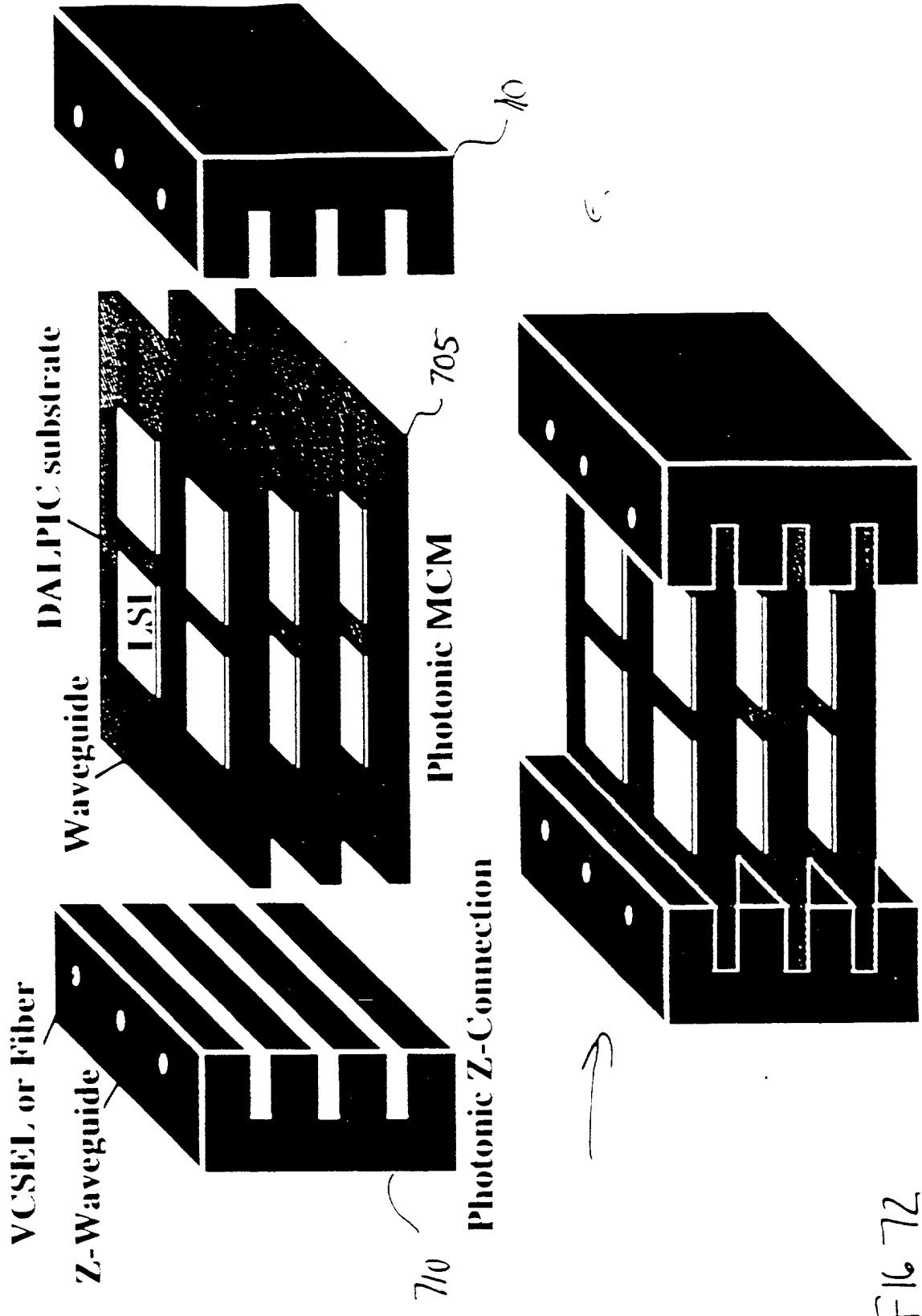
Fig. 70

F0222P0 "2B32Z3Z6D



F/6.71

Optical Backplane

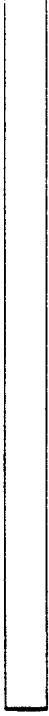


F16 72

Fig 73 -

Flexible Photo-imaginable sheet (Polyguide)

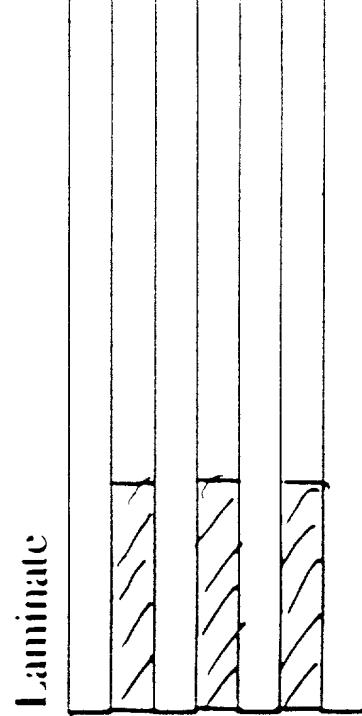
Bonding sheet attach



γ_{10} Laminate

Exposure

SOLVENT process



γ_{10} Post cure

Assemble

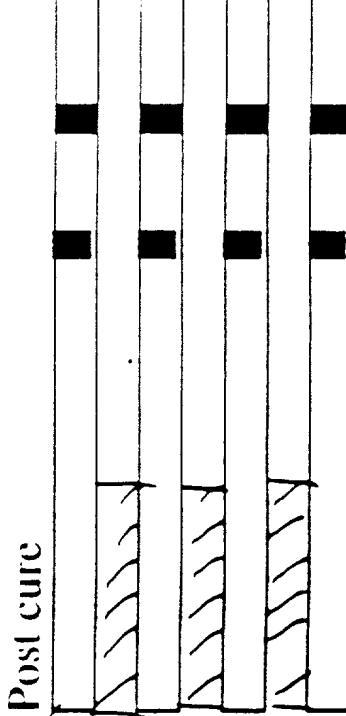


Fig 73 -

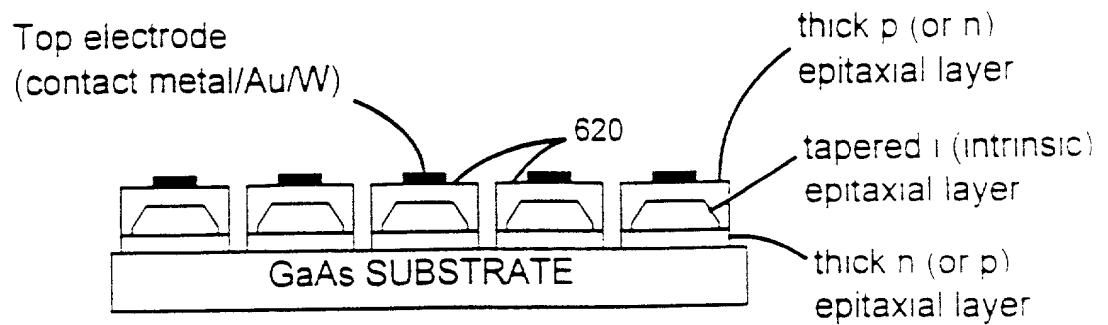


FIG._74 (Epitaxial growth and patterning)

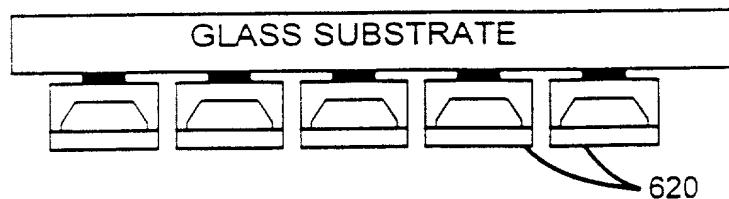


FIG._75 (Epitaxial liftoff)

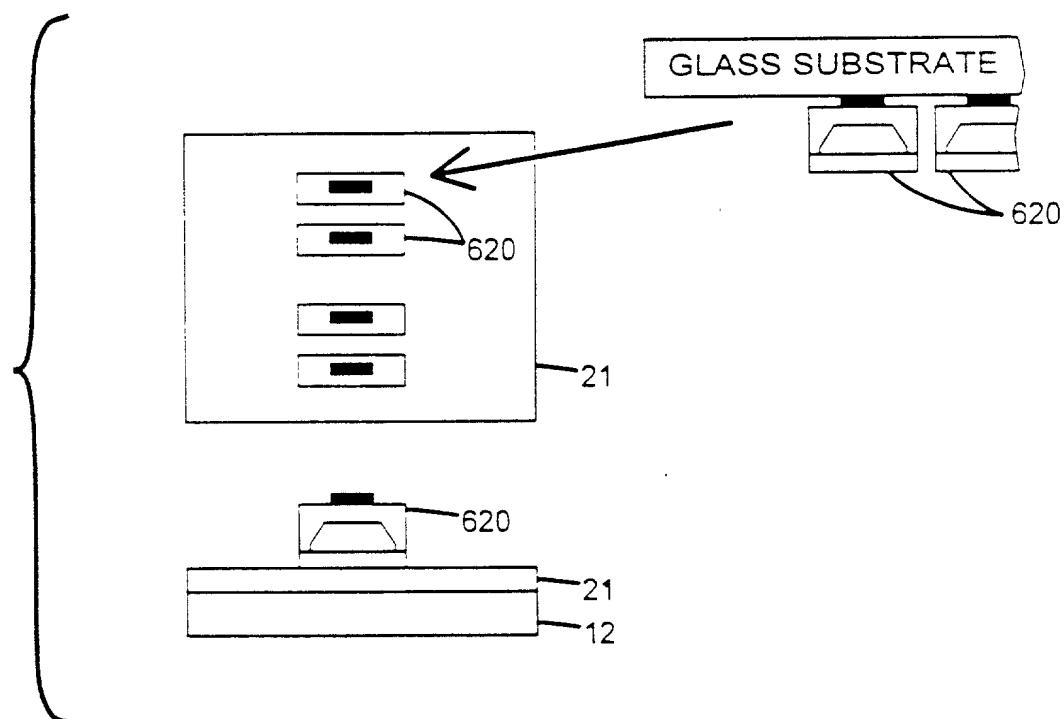
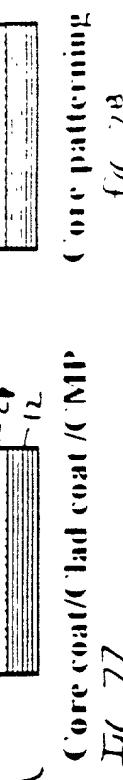


FIG._76 (Transfer)

Substrate, SiO_2 , 10nm , TiO_2 , 10nm , Al , 10nm

Via, $\text{Electrode formation}$

Ti / Al , 20nm , Clad coat



Core coat/via coat / C MP

Fig. 77



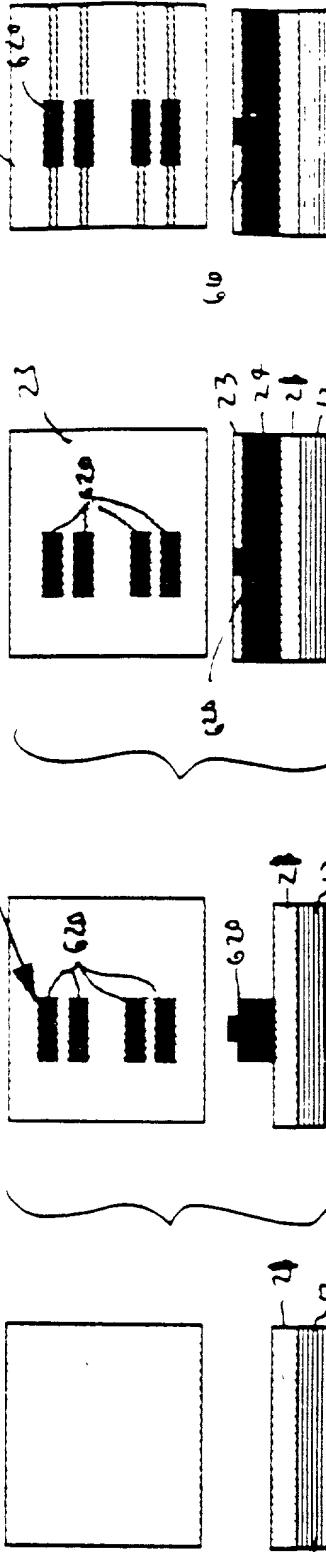
Thin-film device attach

Fig. 76



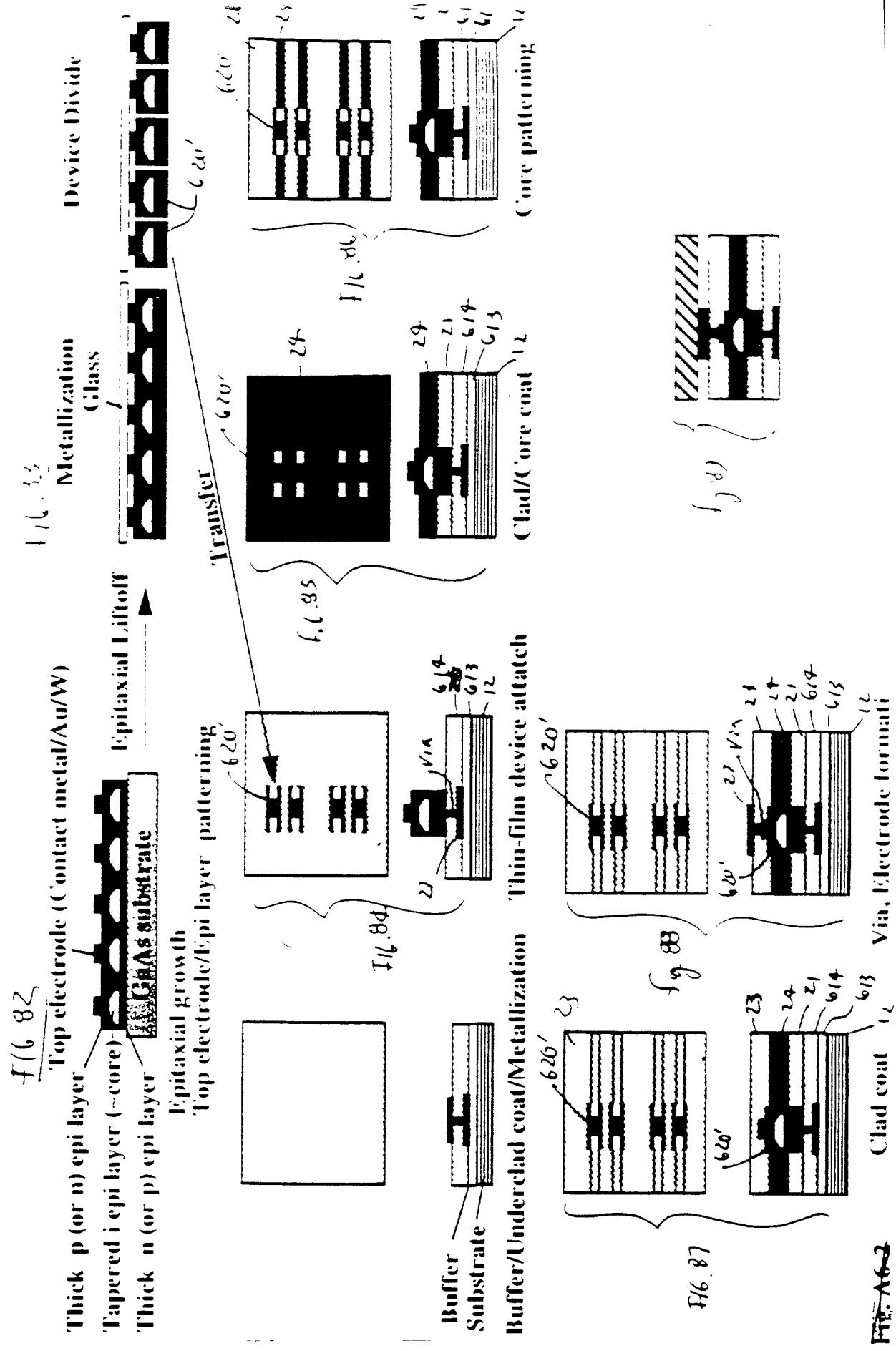
Underclad coat

Fig. 75



Clad coat

Fig. 74



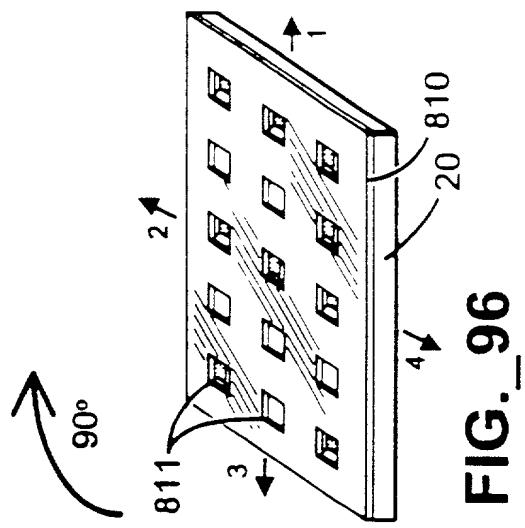


FIG. 96

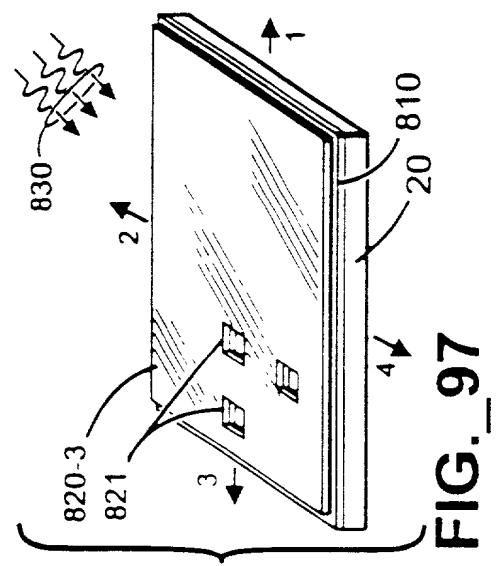


FIG. 97

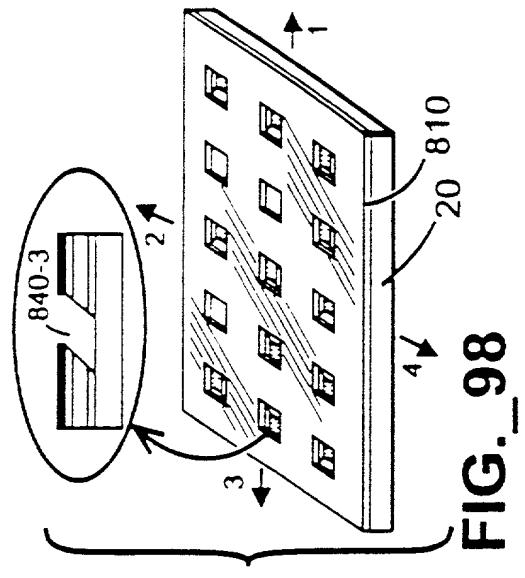


FIG. 98

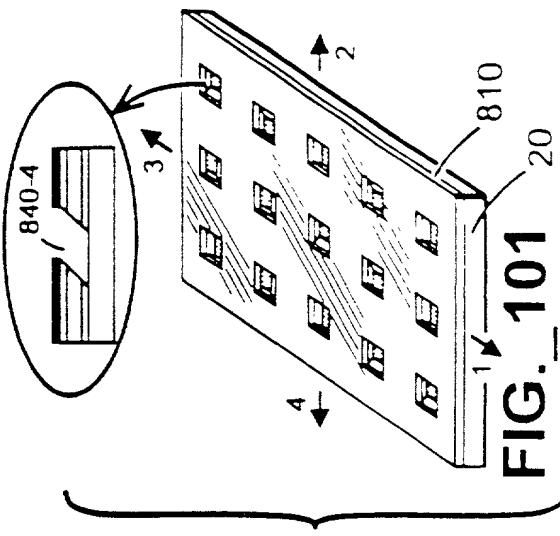


FIG. 99

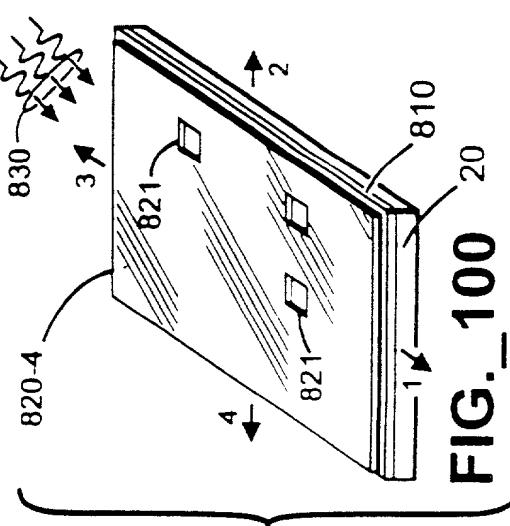


FIG. 100

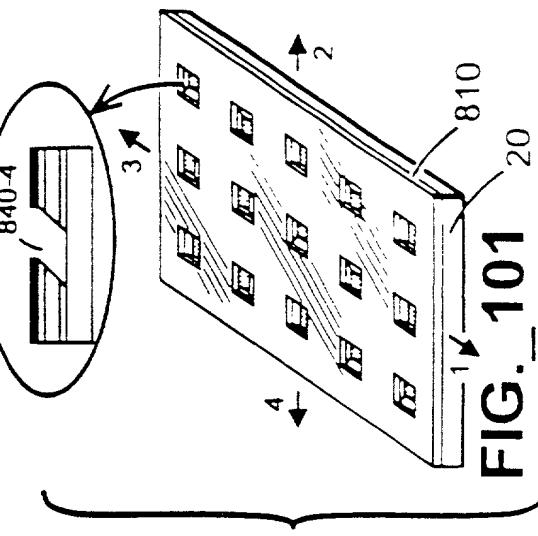
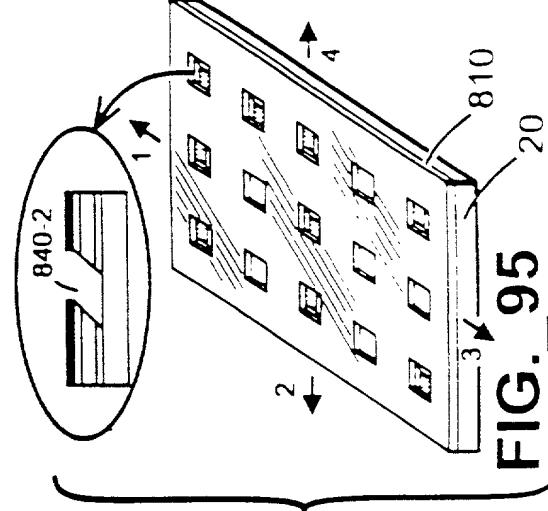
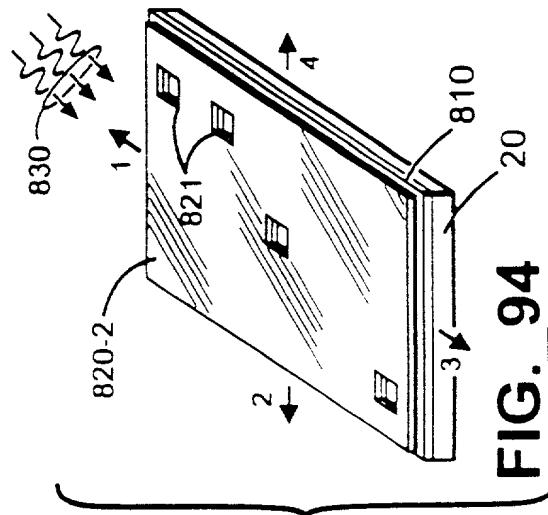
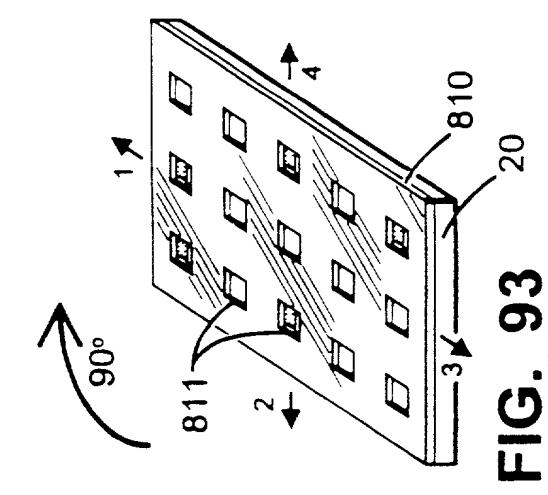
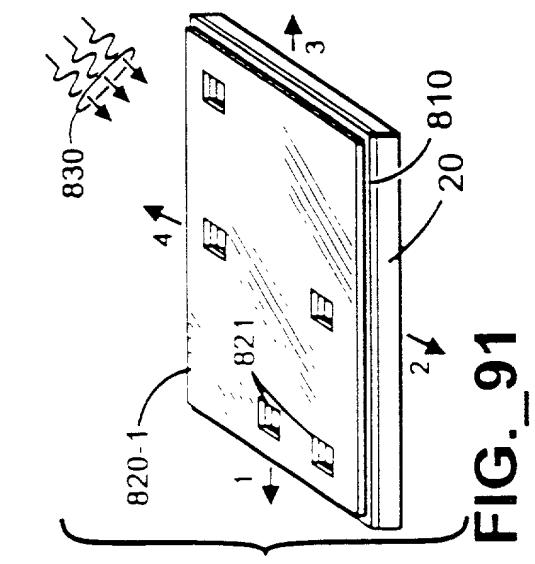
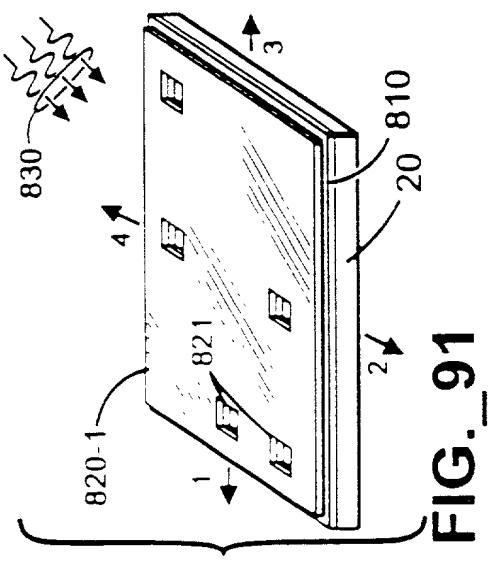
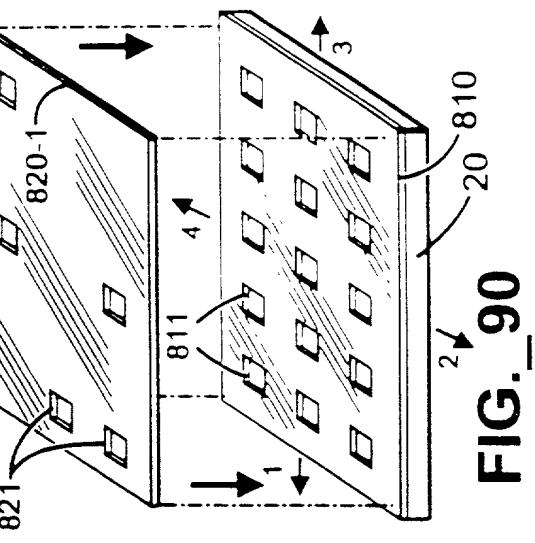


FIG. 101

102276 23573260



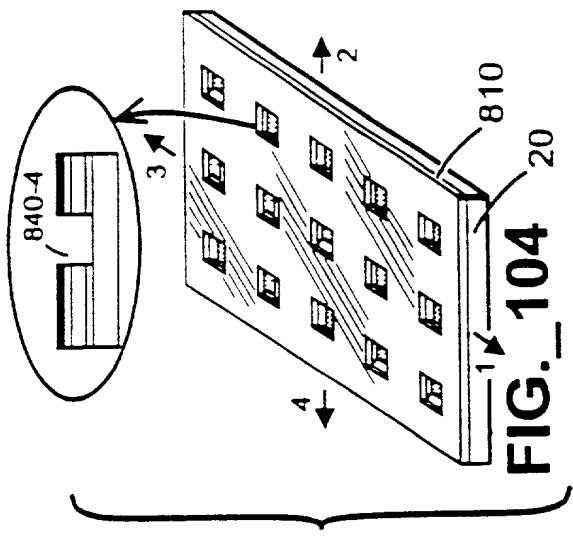


FIG. 104

20
810

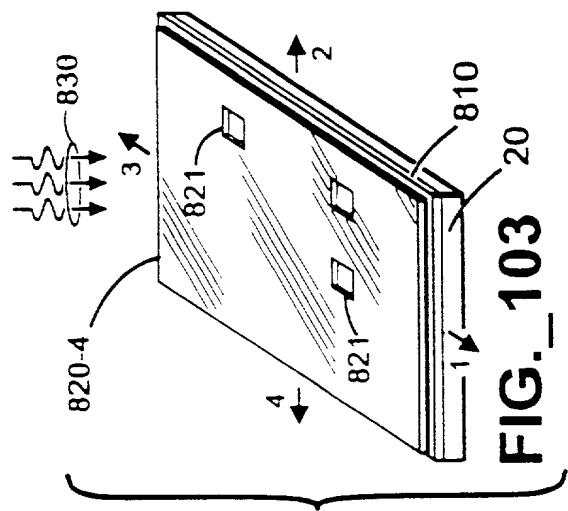


FIG. 103

20
810

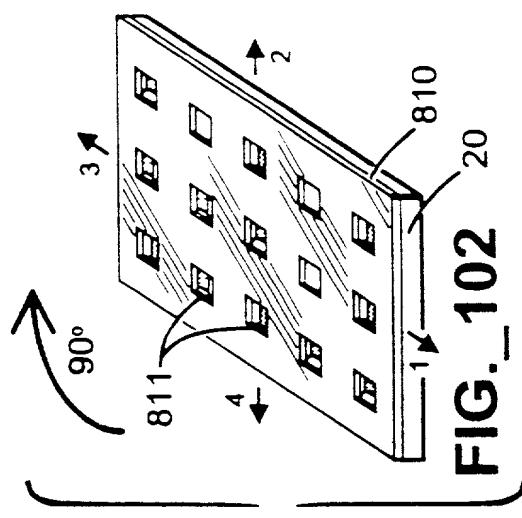


FIG. 102

20
810

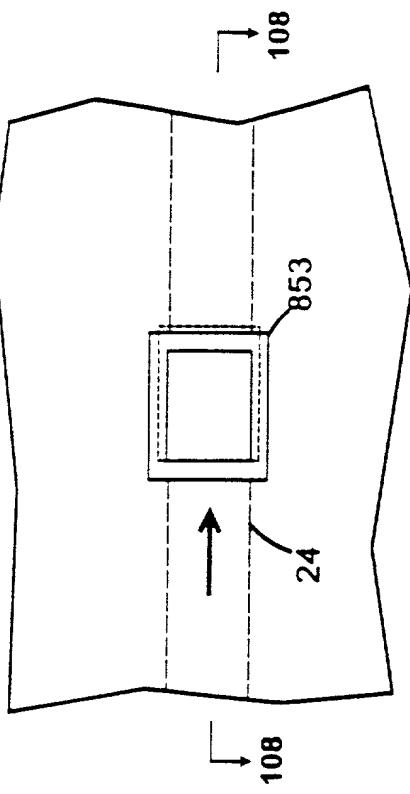


FIG. 107

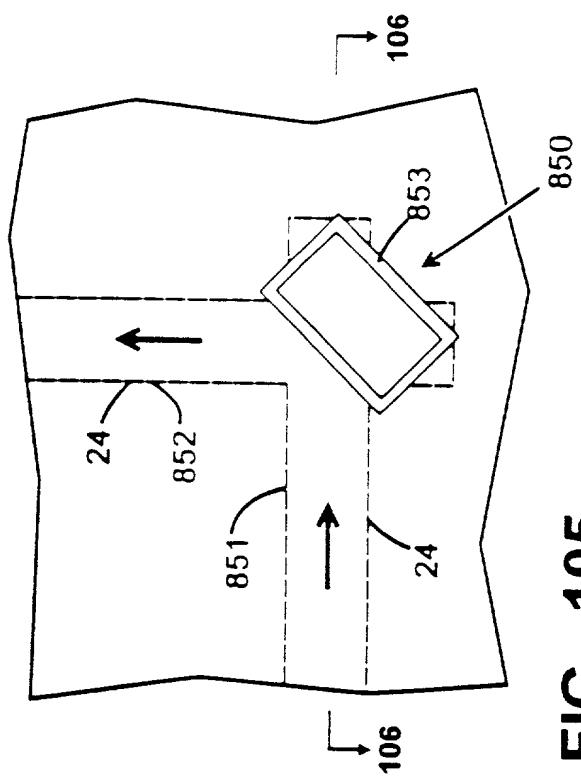


FIG. 105

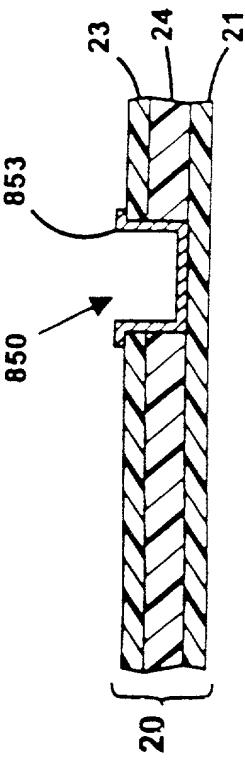


FIG. 106

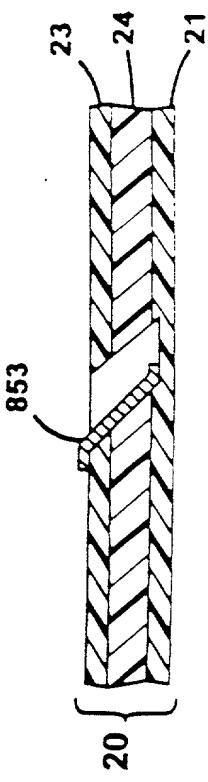


FIG. 108

GS CX/CXX OE Solution --- OE-3D-Stack

OE-film-DW (1) or (M)

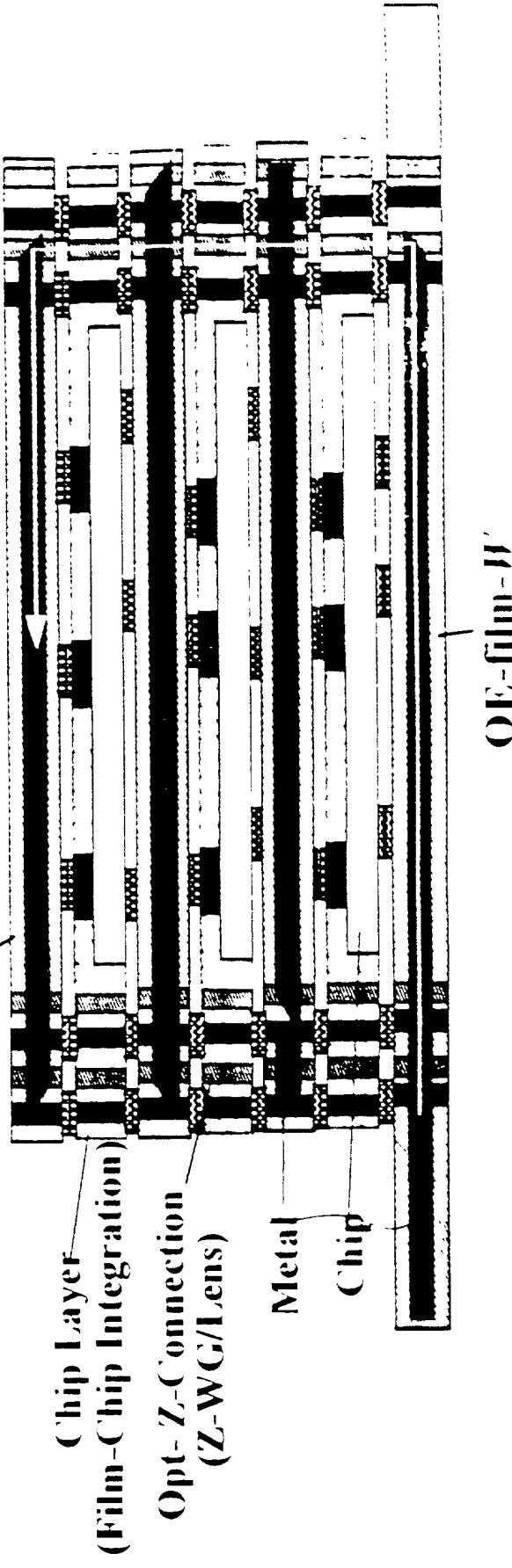
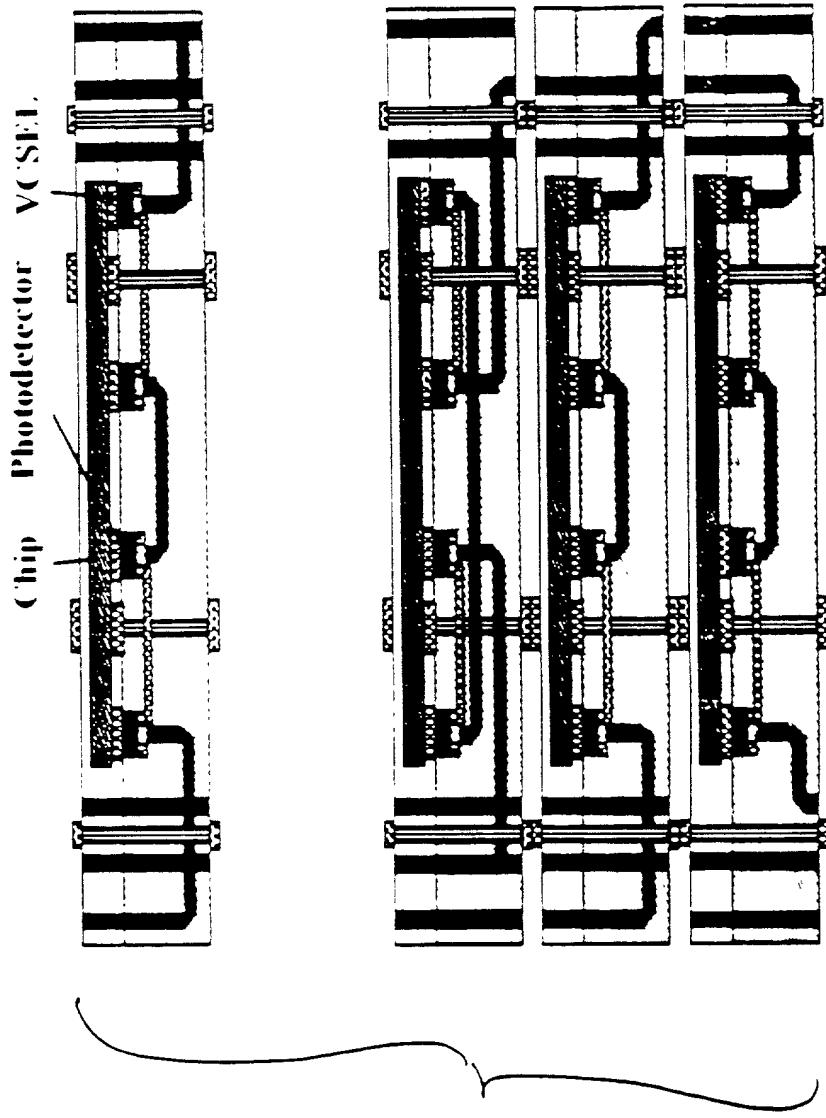


Fig. 109

2/23/99-added 7

Figure 109

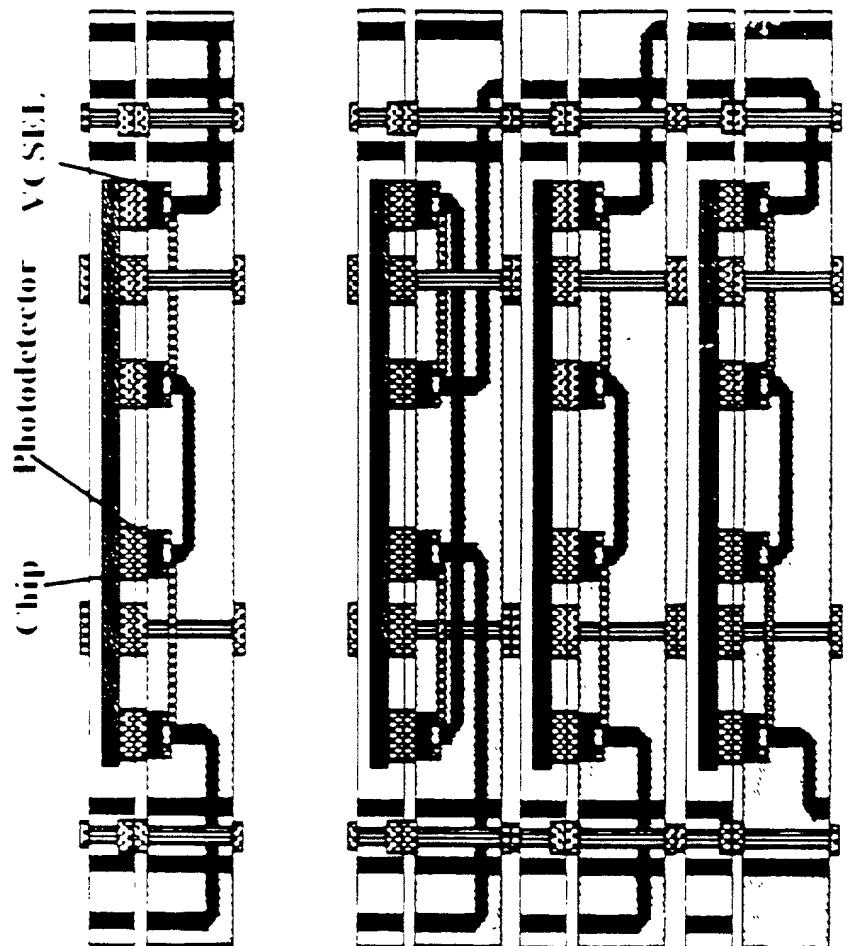


F16.110

A2

(2/23/99) AA1 Detail picture Example for 3D-stack

(New version of the AA1 of 2/5/99)



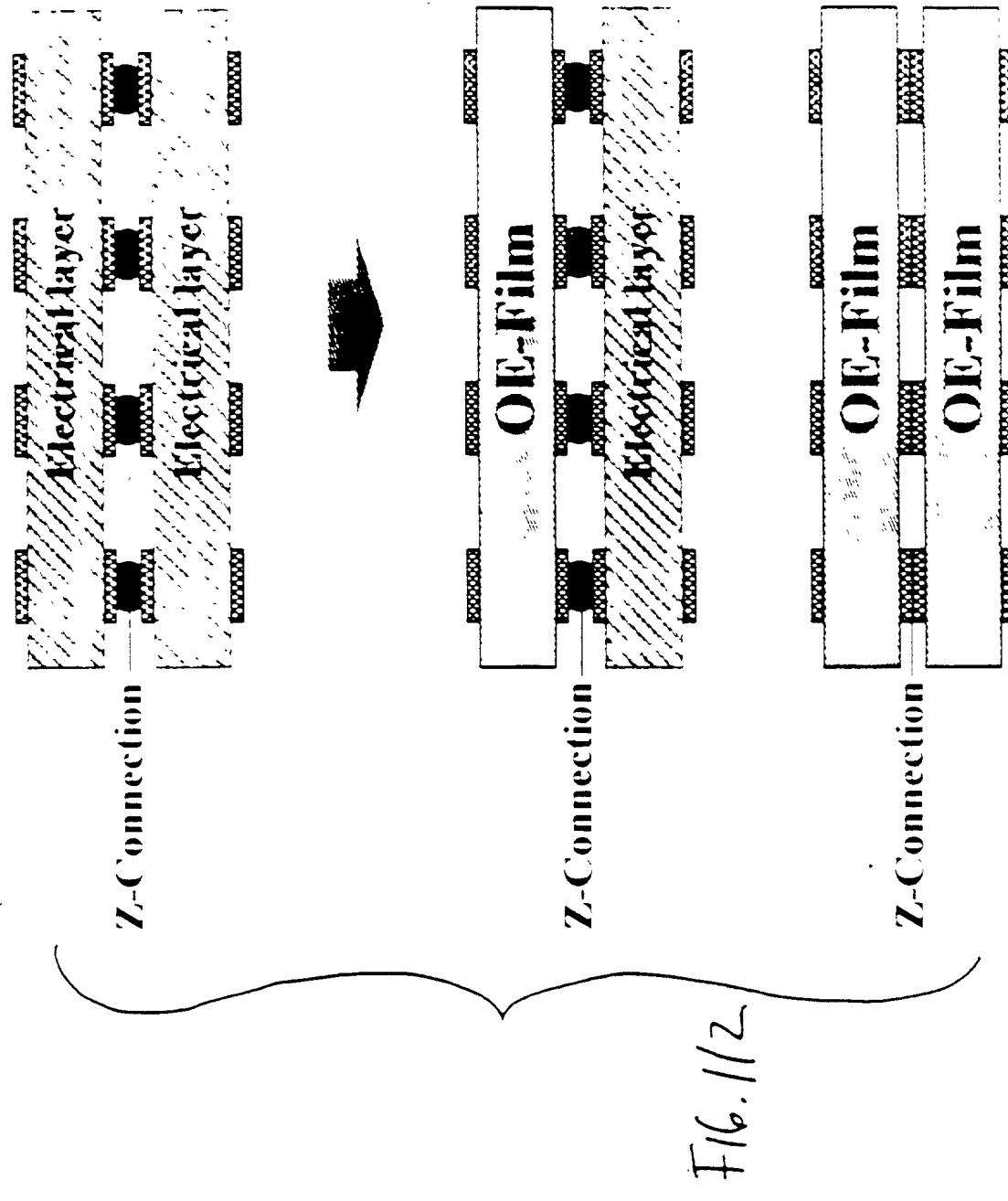
F16.11.

(2/23/99) AA2 Detail picture Example for 3D-stack'

(New version of the AA2 of 2/5/99)

A 24

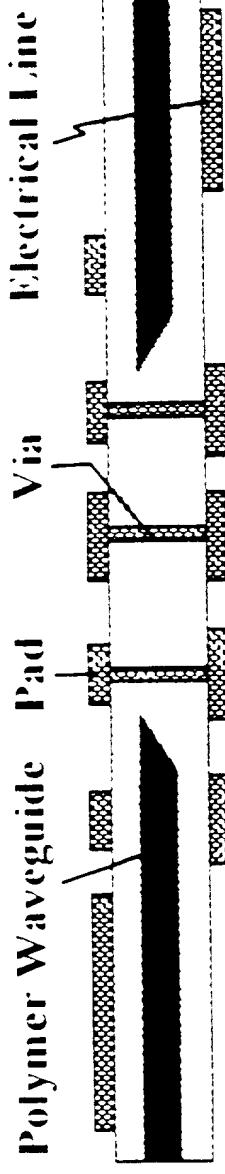
Film/Z-Connection Application to OE-Substrate



2/23/99-added 1

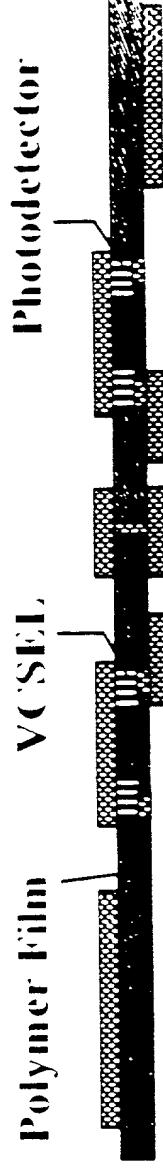
Figure 1

OE-Films



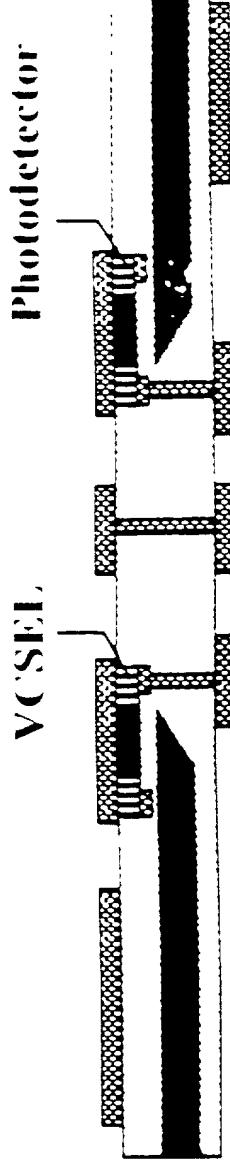
F16.113

OE-film-W



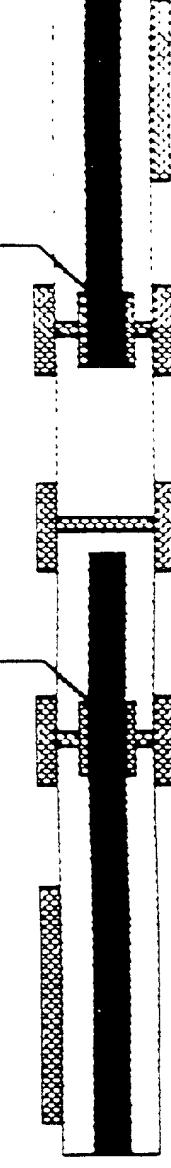
F16.114

OE-film-DW(V)



F16.115

OE-film-DW(M)
2/17/99-added 2



F16.116

2/17/99-added 2

Fiber Array OE-Film-DW (V)

Image Guide
Waveguide Array

Connector

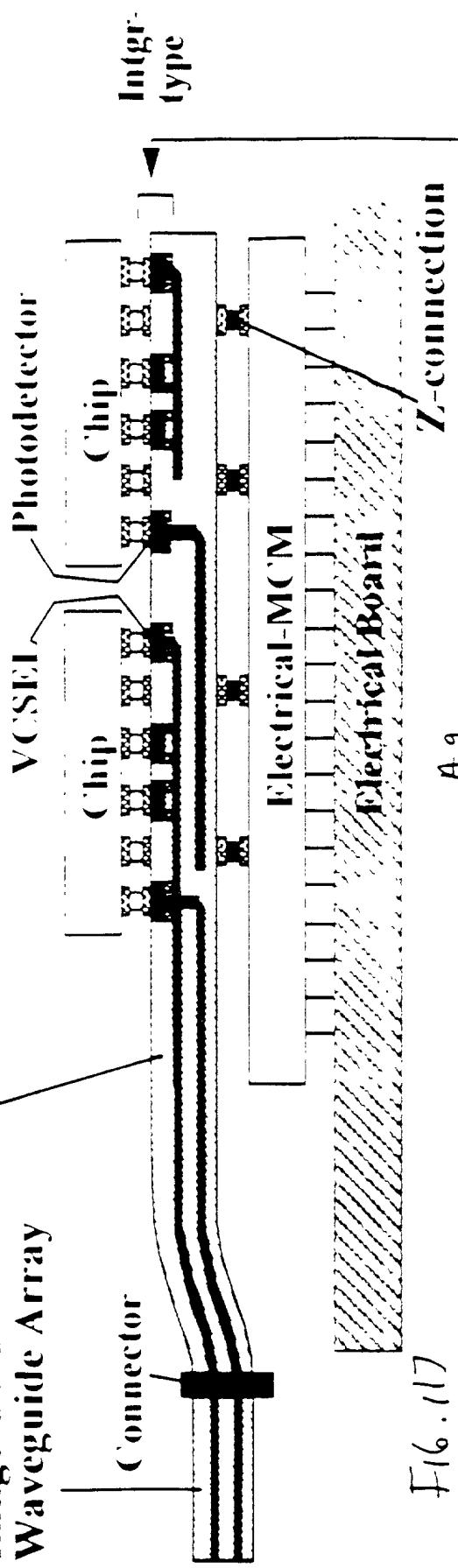
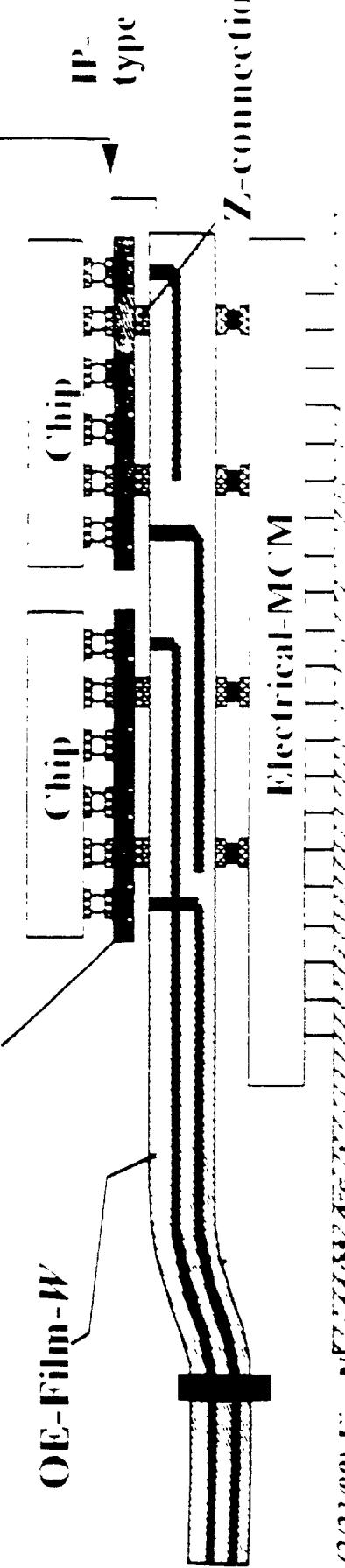


Fig. 117

A₉

OE-Film-D

OE-Film-W



*(2/23/99) Fig. No. 118 Modified
divided 1/4*

Fig. 118 A₉ = 1/3 G₉

FOLM

OE-Film-DW (1)

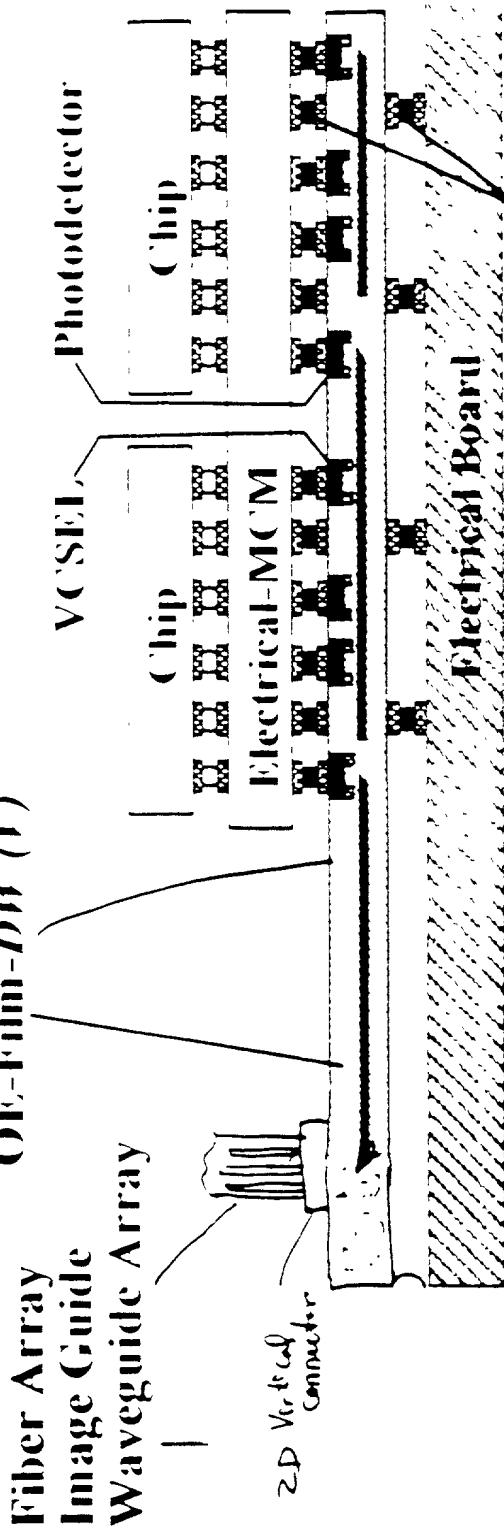


Fig. 119

OE-Film-D

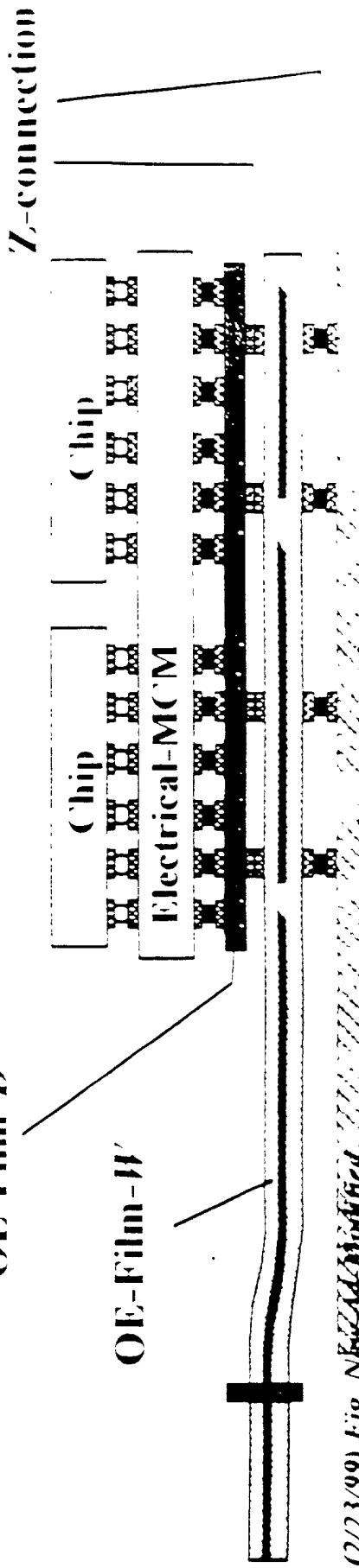
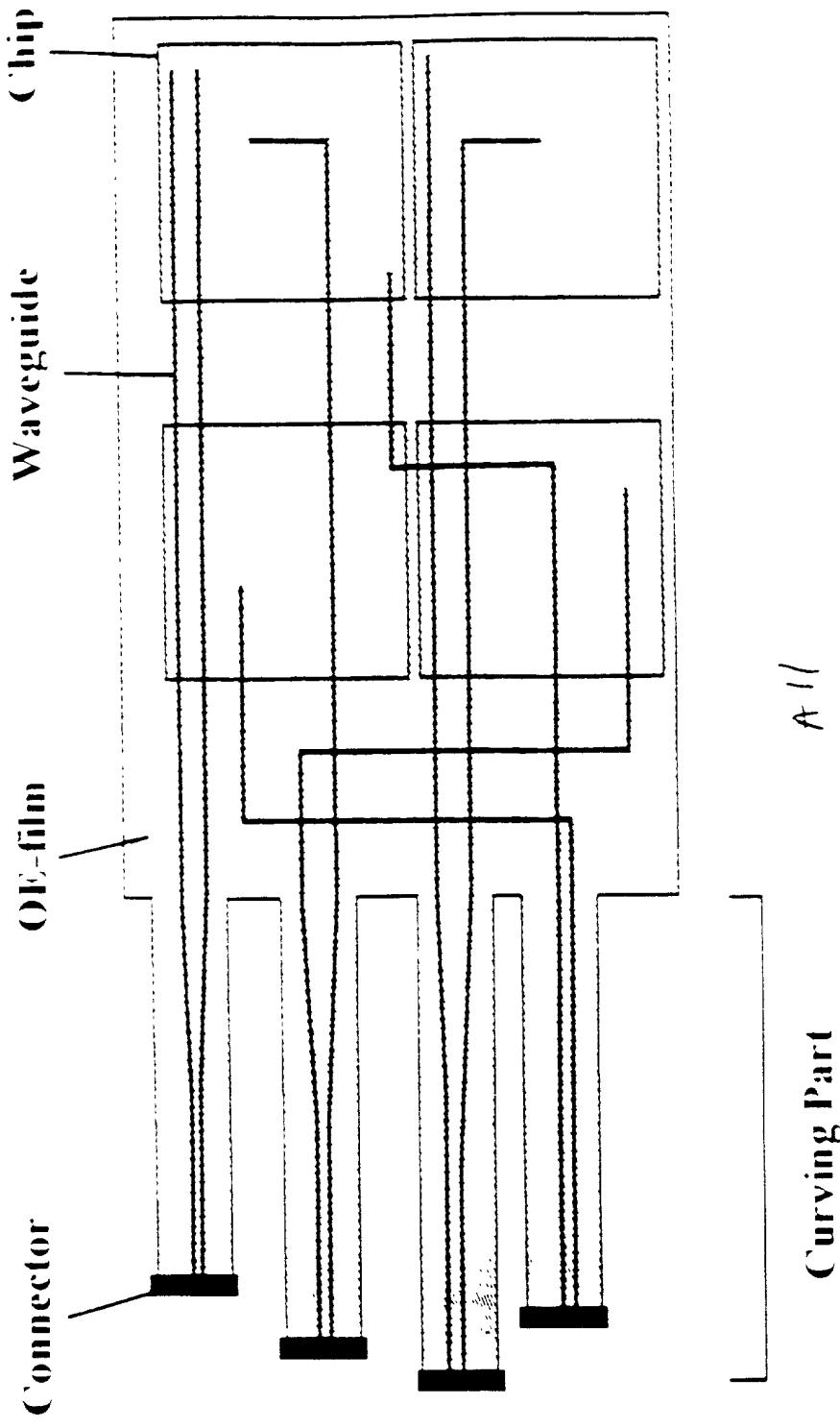
(2/23/99) Fig. No. 119
divided 1/4'

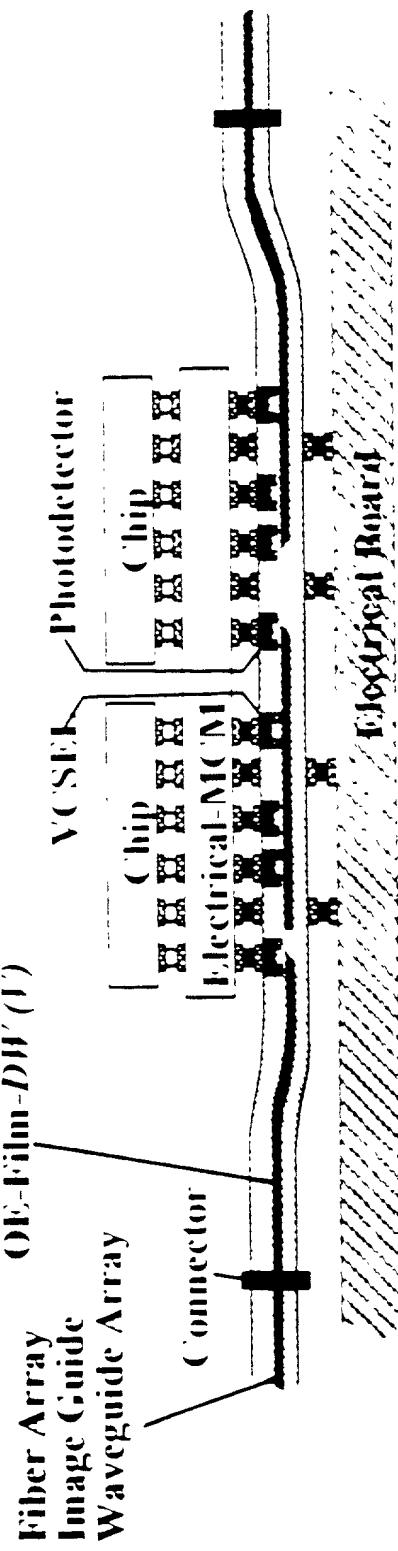
Fig. 119

FCPT FOLM with Optical Path Length Controller, Connector Buffer

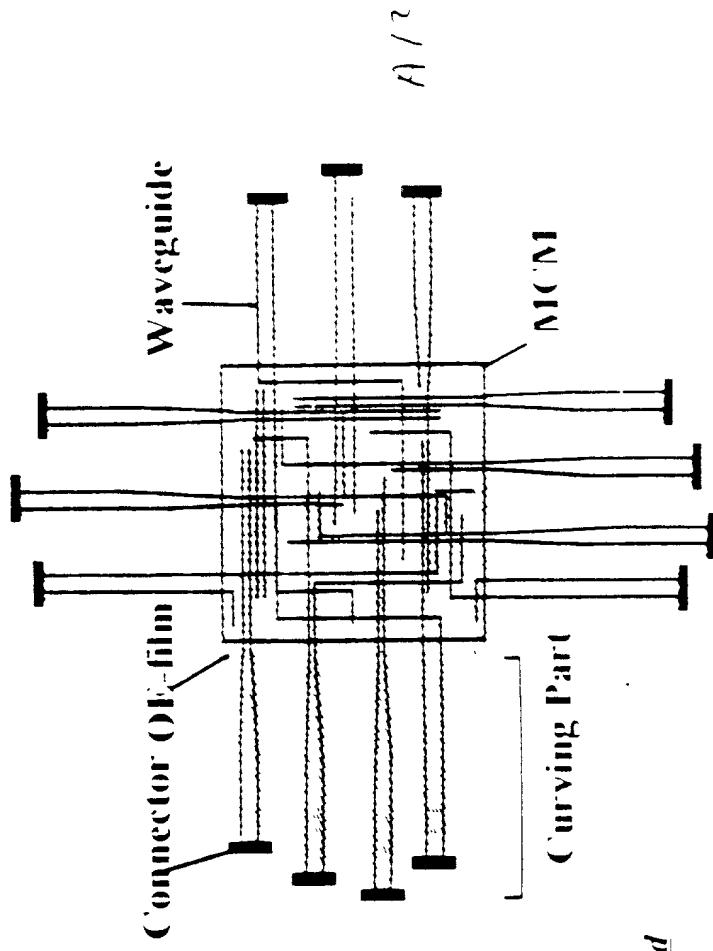


(2/17/99) Fig. New-A4 Modified
divided 2/4

FOLM with Optical Path Length Controller, Connector Buffer



F16.123

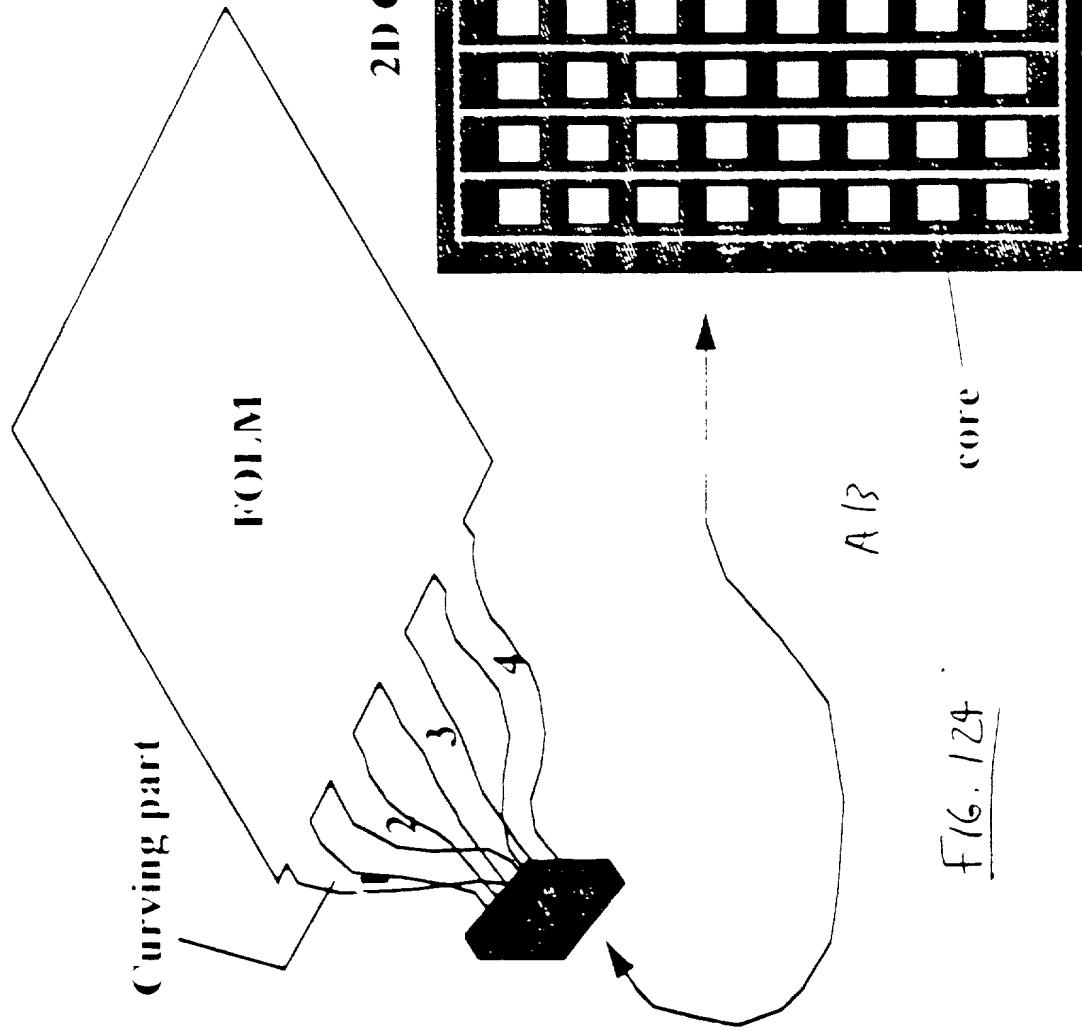


F16.122

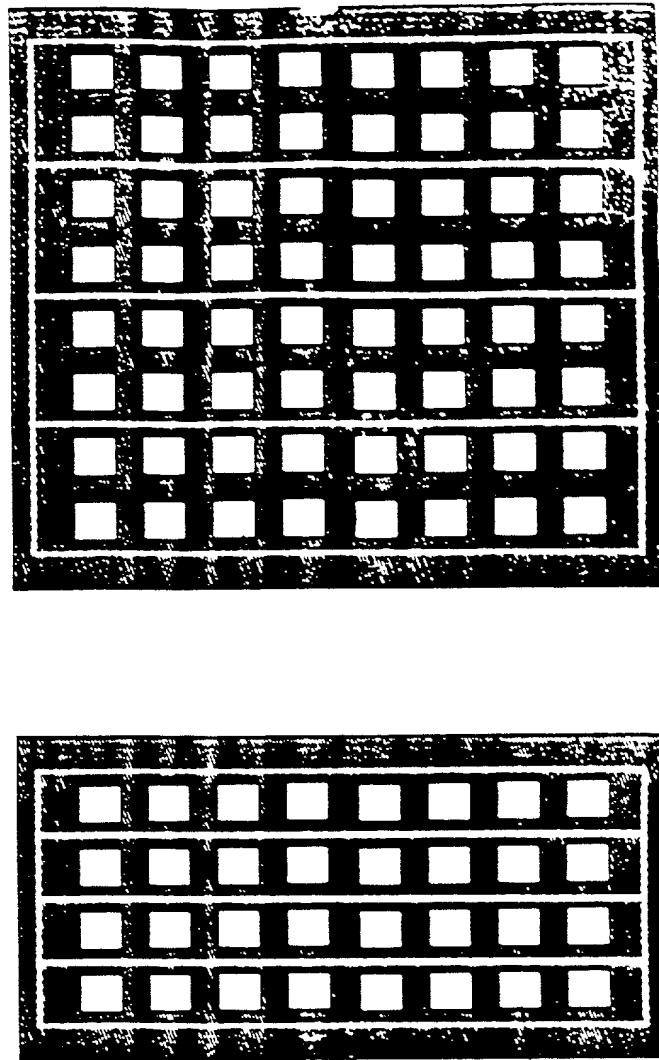
(2/23/99) Fig. New-14-Modified
divided 2/4'

Fujitsu Computer Packaging Technologies, Inc.

KOLM with 2D Waveguide Connector



2D connector cross-section



(2/23/99) Fig. New-A4-Modified
divided 3/4'

(for Single-layer waveguide) (for 2 layer waveguide) (done 1/3)

FOLM: High-Speed Option

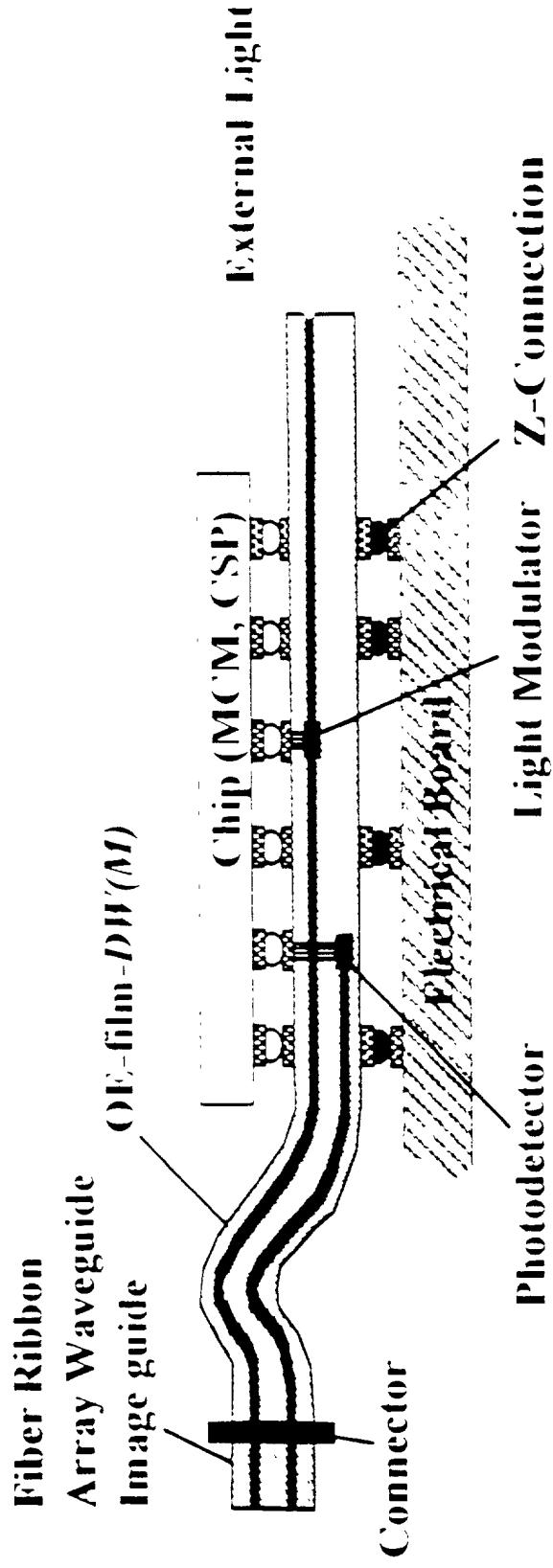
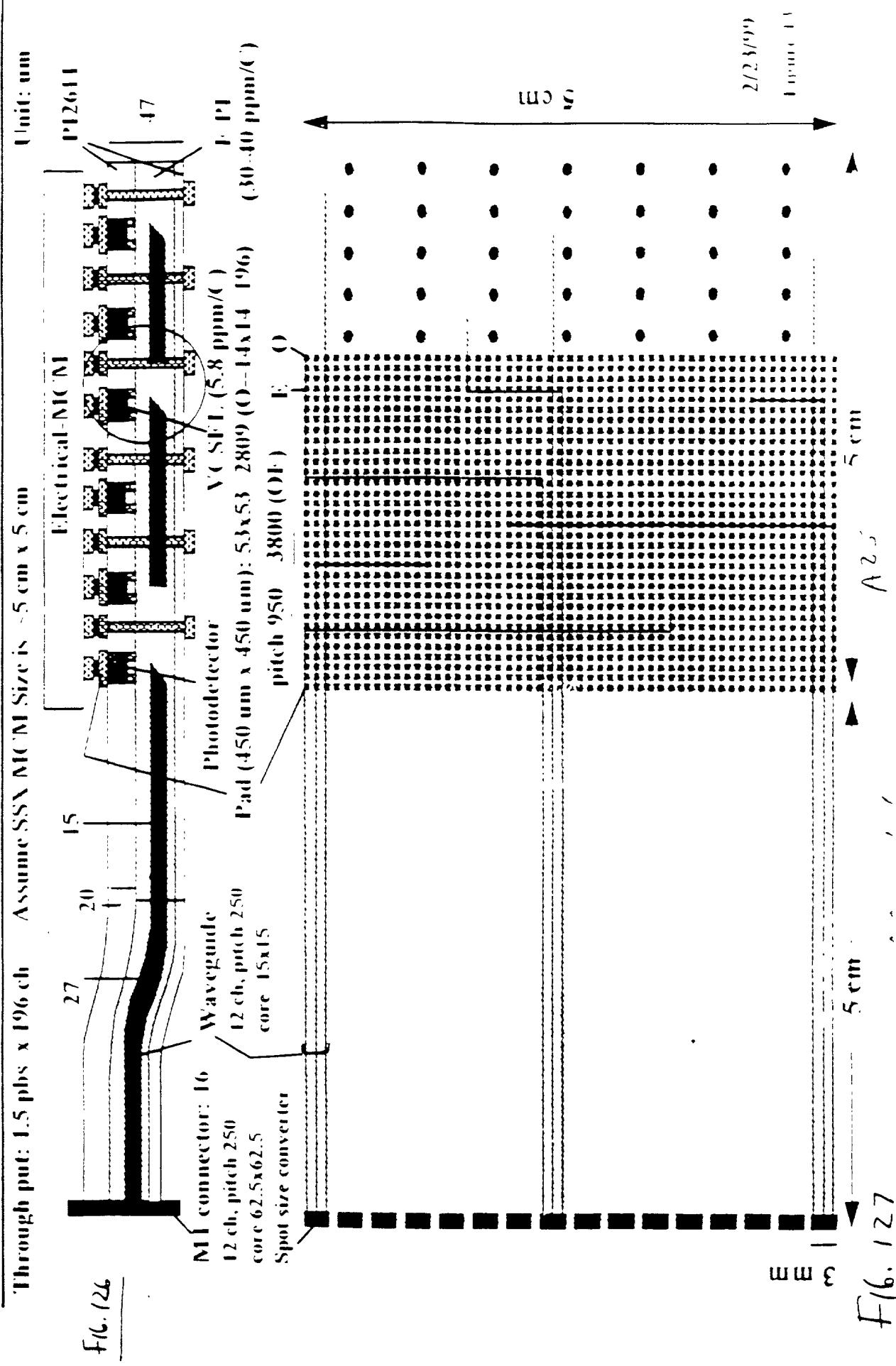


Fig. 125

A 14

FOIM Structure Example ((overall))



ROI Structure Example (VCSL part)

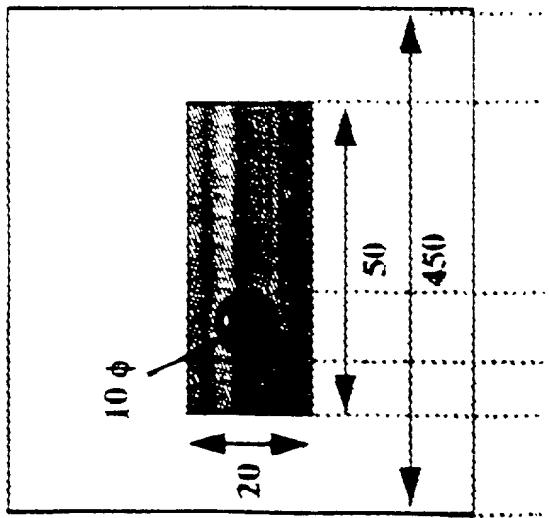
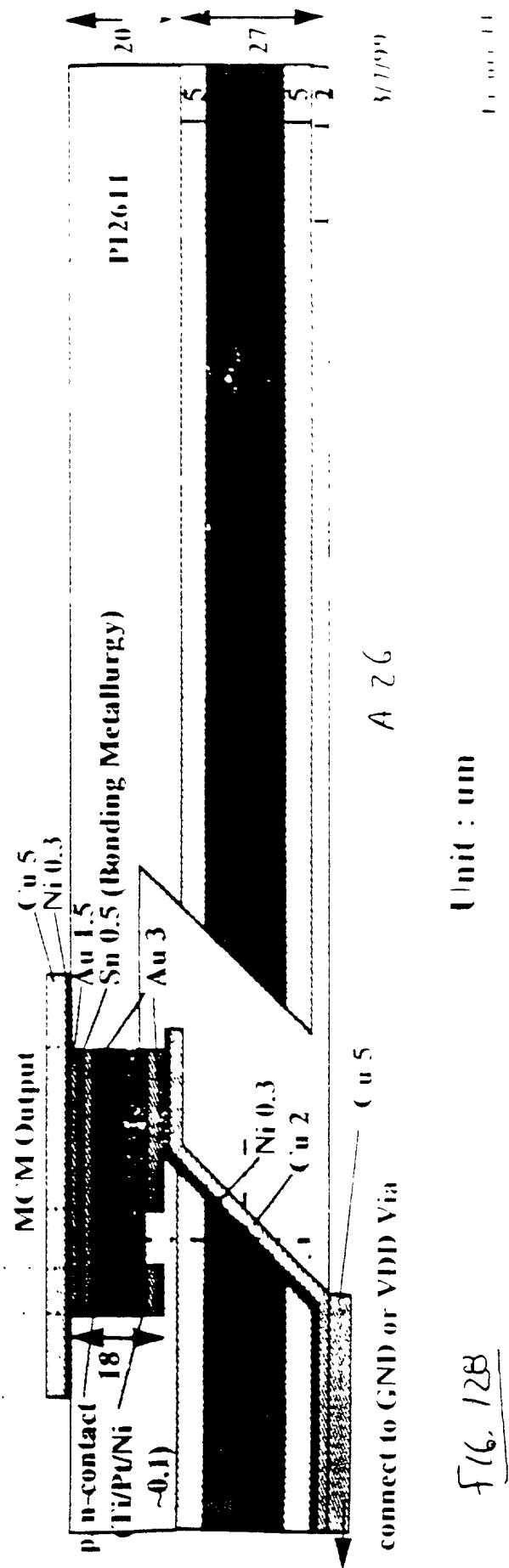
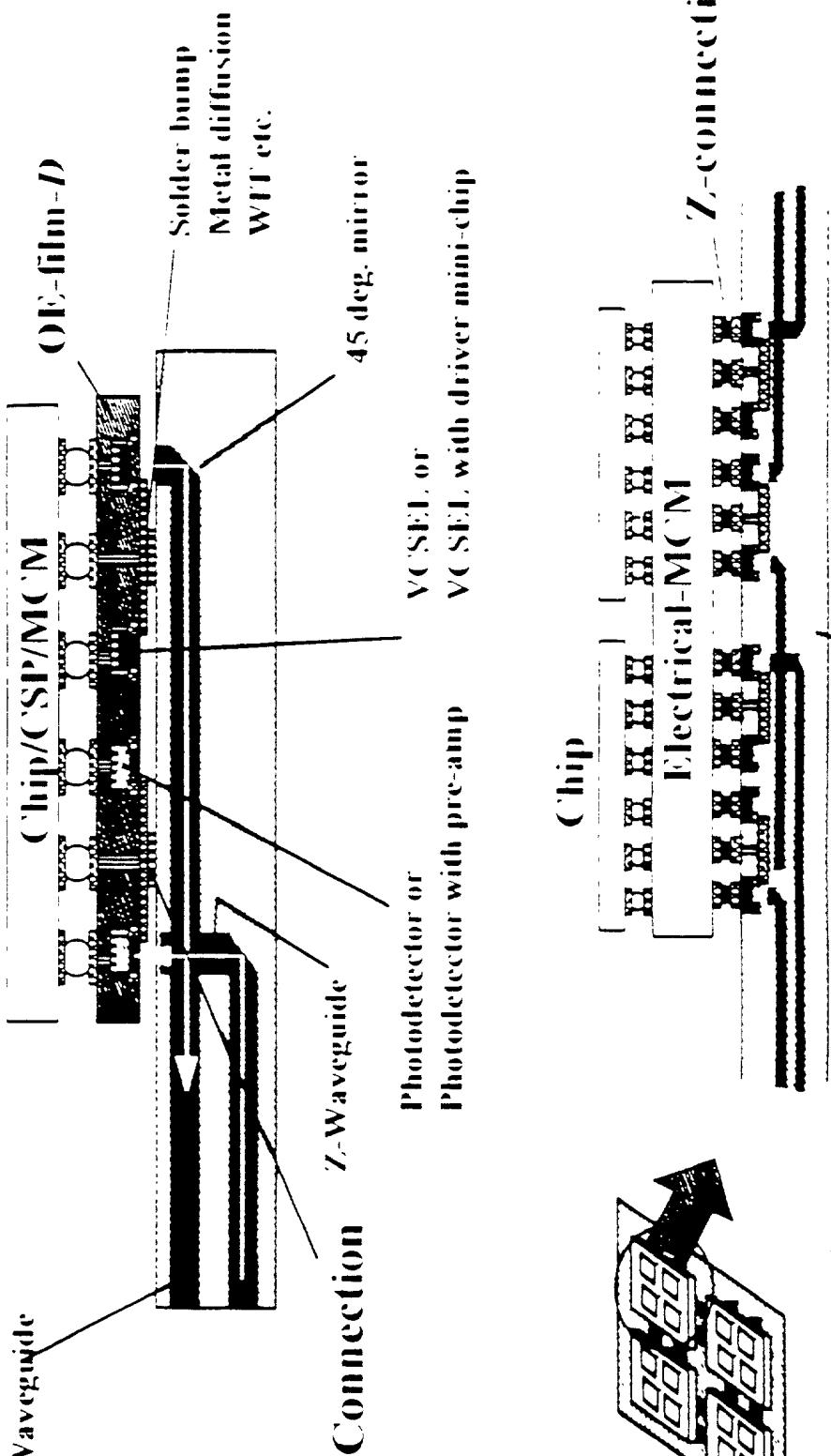


Fig. 129



OE-film: OE-IP, OE-Film-MCM



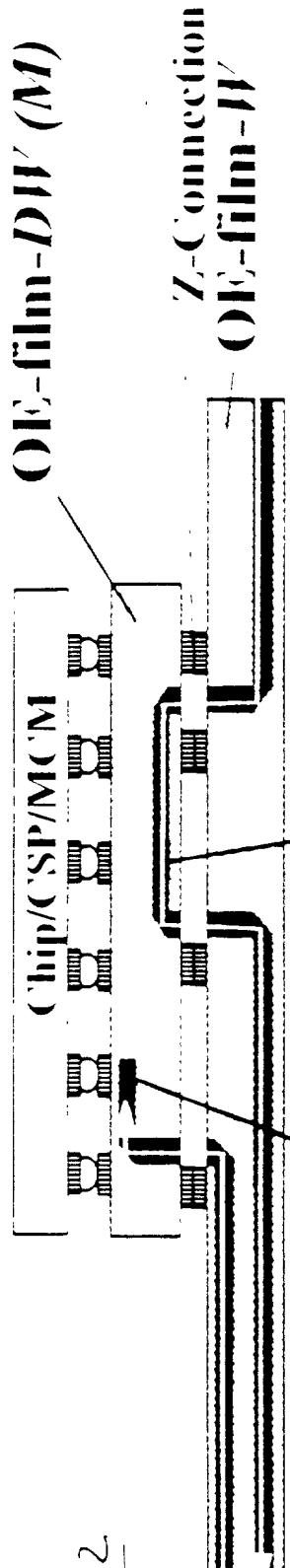
A 15 OE-film-ID (1)

Fig. 131

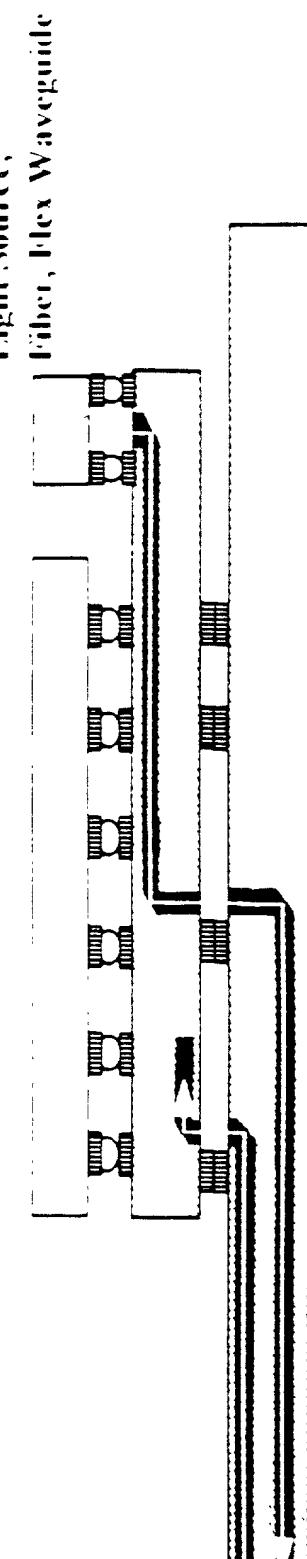
(2/23/99) Fig. New-A1-Modified

nic 2/2/99 -- 1/1/21

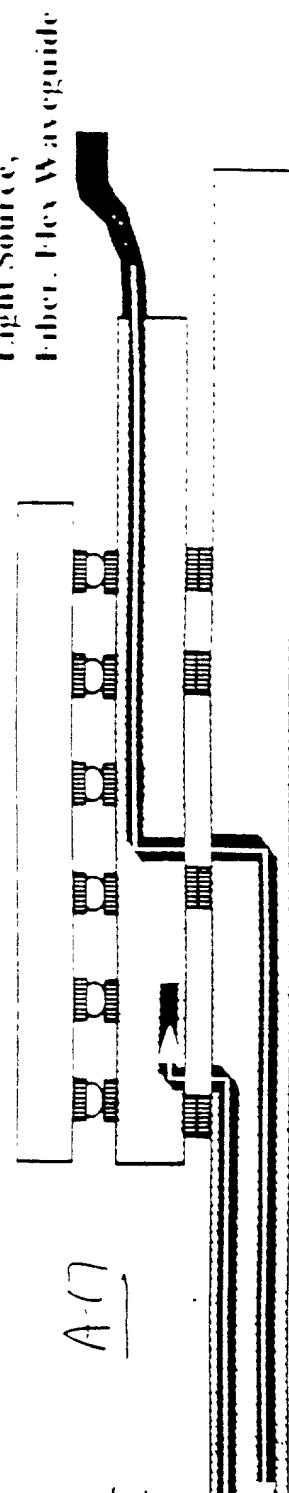
OE-film: Light Modulator Transmitters



(2/17/99) Fig. A1(b-1)



(2/17/99) Fig. A1(b-2)



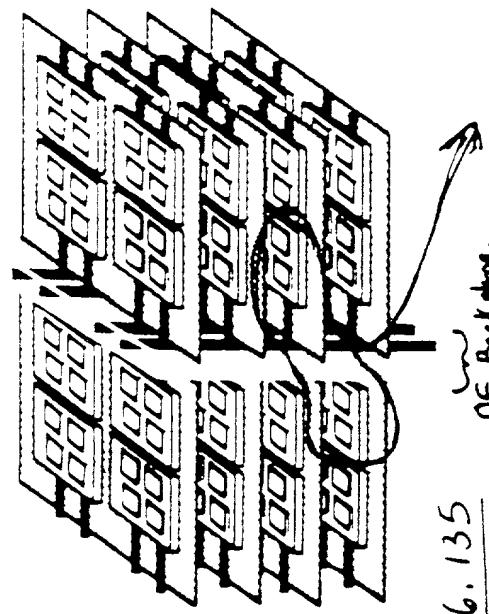
(2/23/99) Fig. A1(b-3)

Examples of Light Modulators: Electro-Optic (E-O) Modulator, Electro-Absorption (E-A) Modulator

Fig. A1(b-1)

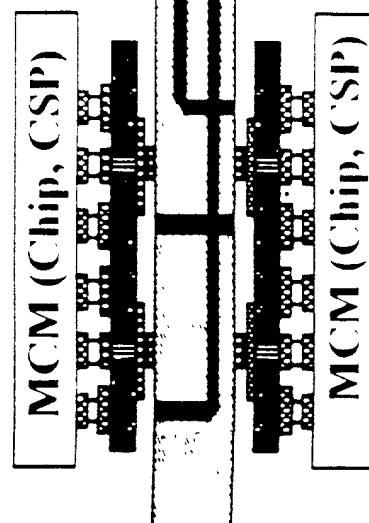
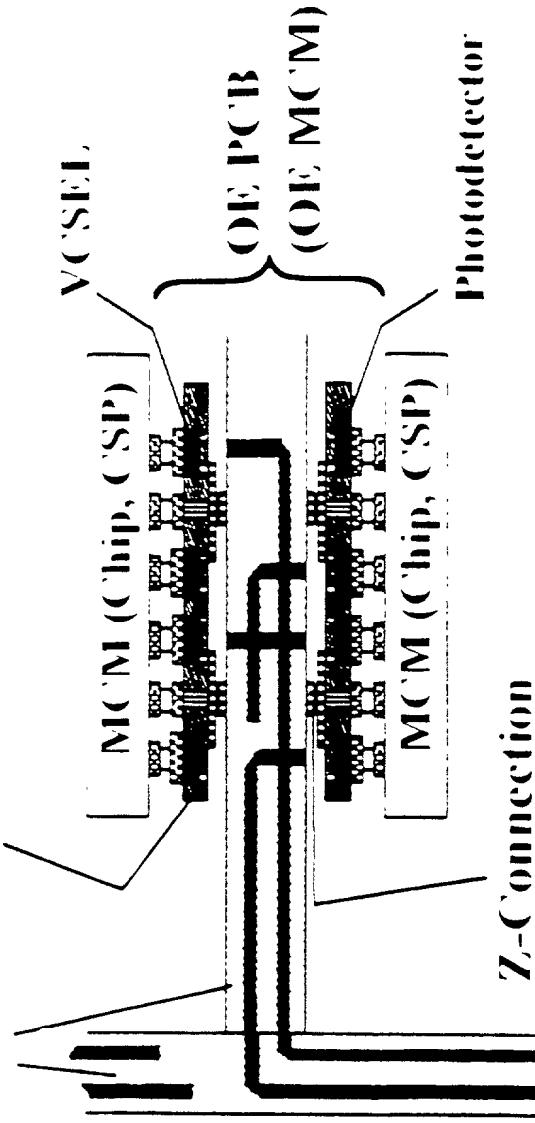
OE-film: Both-Side Packaging

(Whole structure)



F16. 135

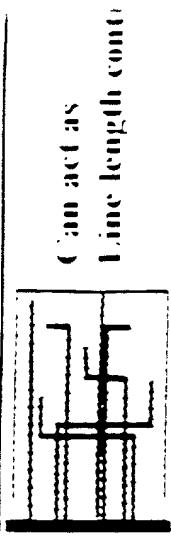
OE-film-H OE-film-D



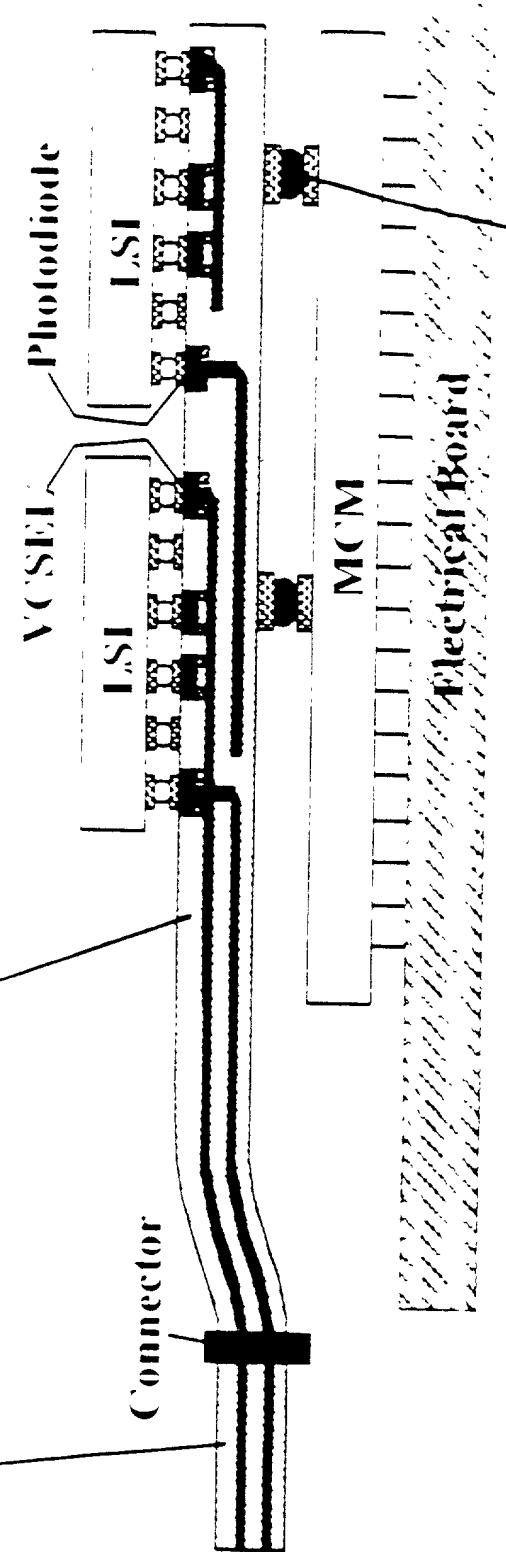
OE Backplane
(OE, PCB)

2/23/99-added 3'

Direct Jump from LSI



Fiber Ribbon Film Waveguide with Device Integration



F16.136

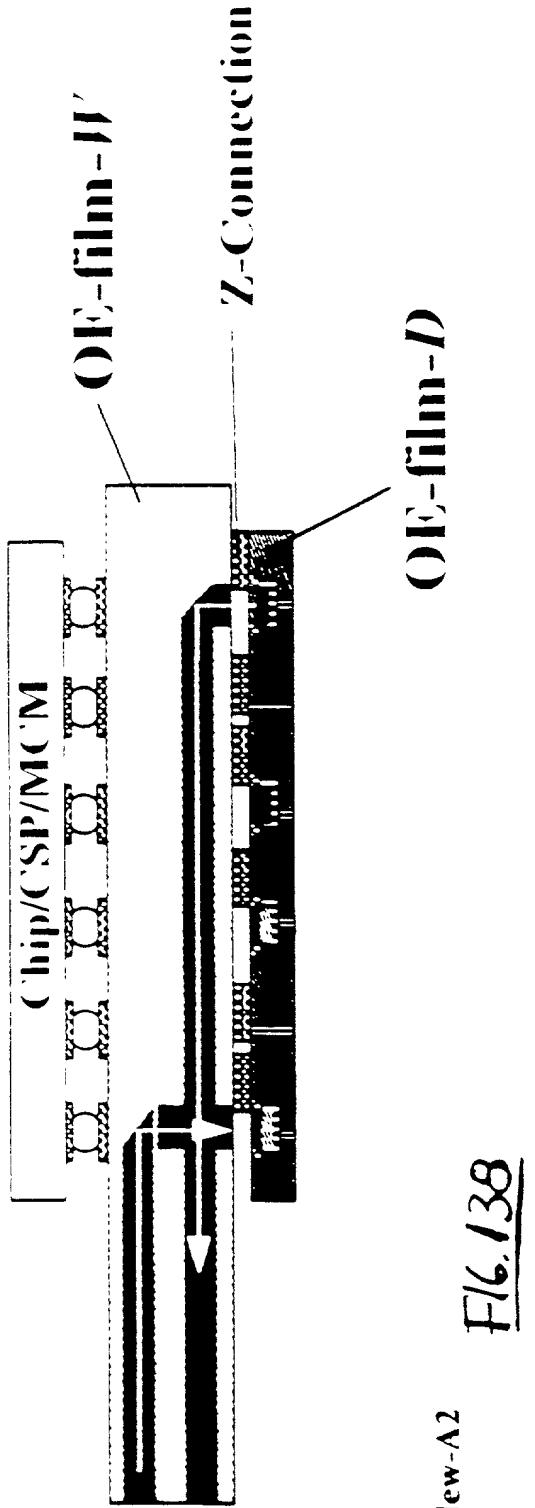


F16.137

Fig. New-A4-Modified

Z Connection
A1 Light Modulator
Photodetector

OLE IP is Placed on the Oposit Side



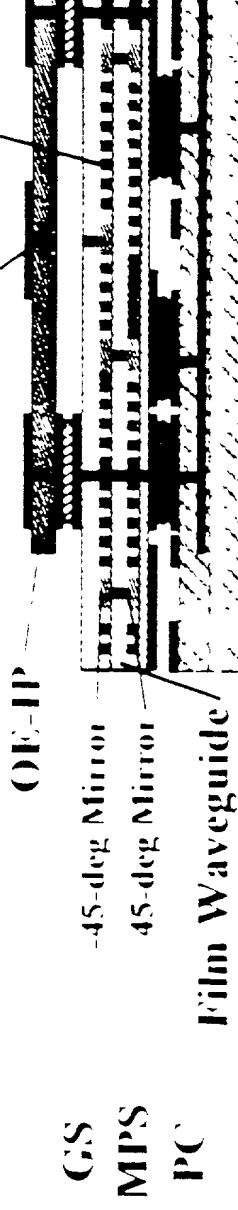
(2/23/99) Fig. New-A2

F16.138

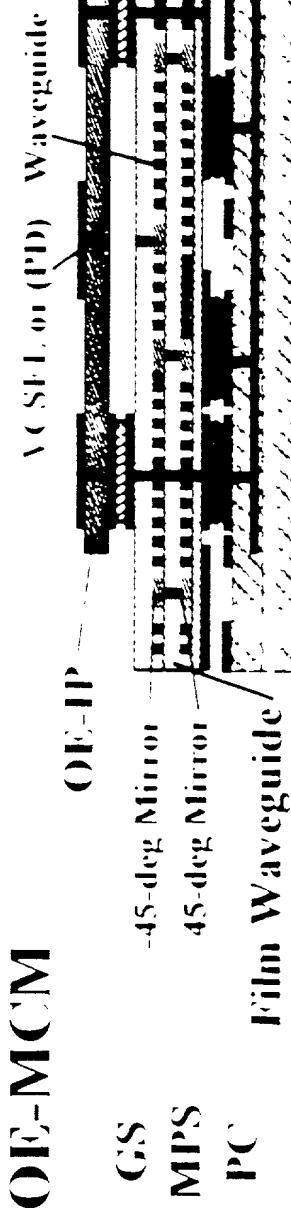
A 2°

OE-MCM

OE-MCM



F16.139



F16.140

Z-Connection

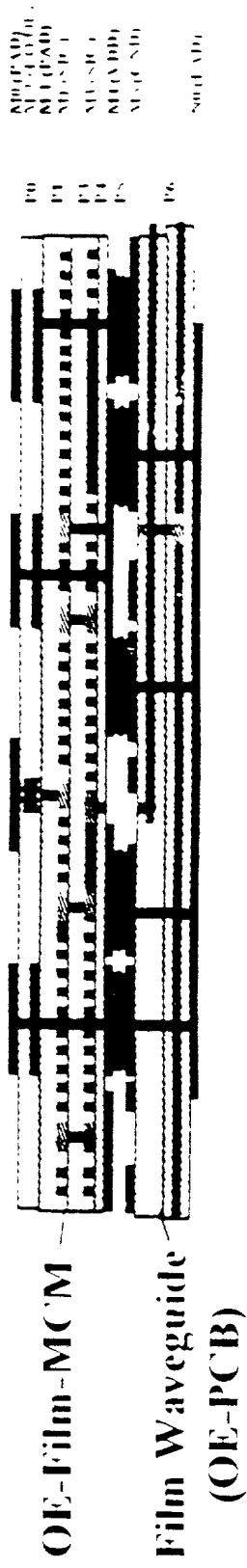
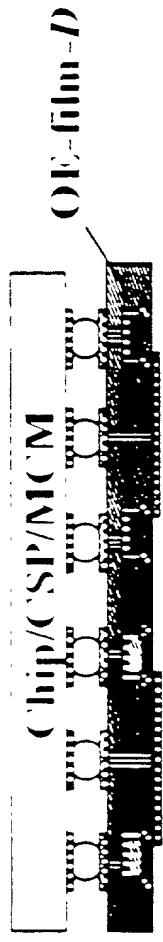


Fig. A5-Modifice

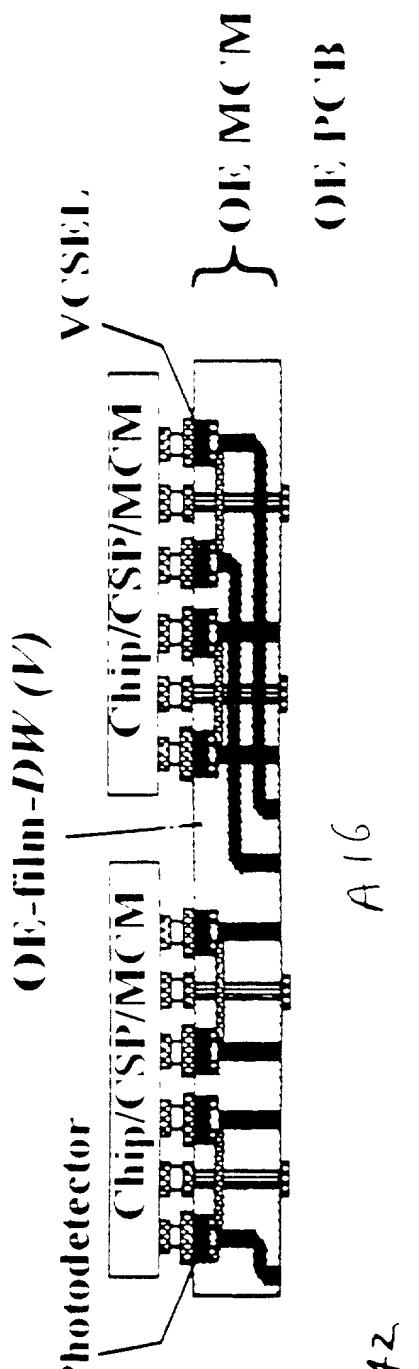
A5

AS 11/1999

OE-film: Smart Pixel



F16 / 41



F16.142

FCF OE-Film/OE-Film Stack --- Back-Side Connection

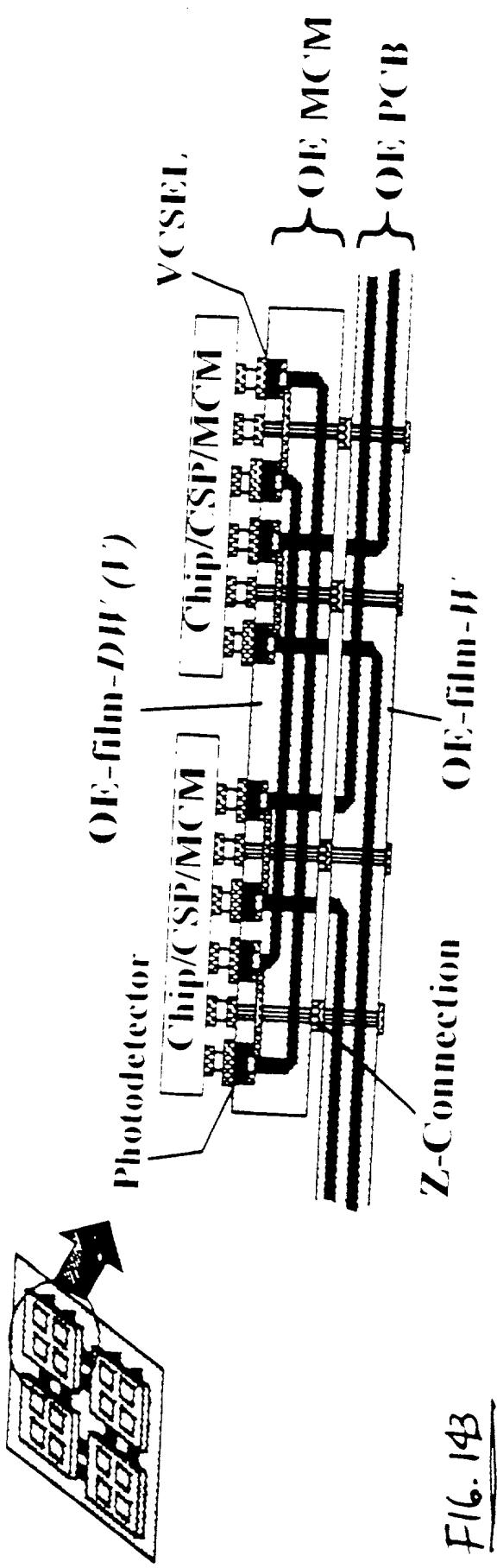
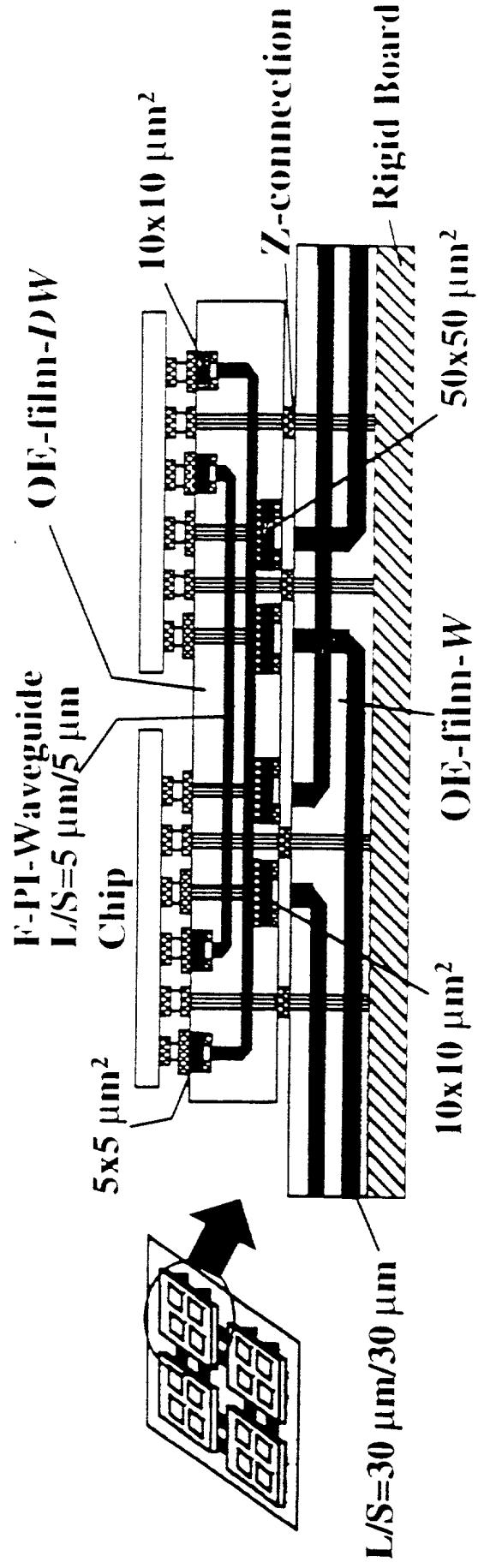


Fig. 143

2/23/99-added 4'

OE-Film/OE-Film Stack --- Back-Side Connection



F16 144

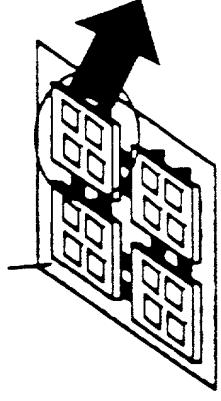
2/2

Fig. 3/18/99.1

P1 3/18/99

OE-MCM/OE-Bord Stack

Mother Board



Chip

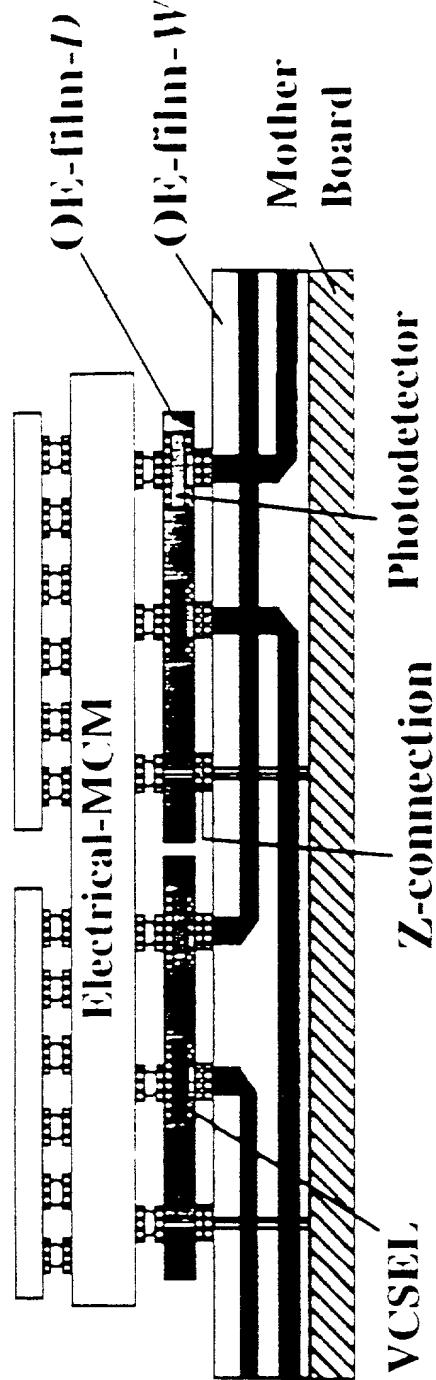


Fig. 145

Waveguide

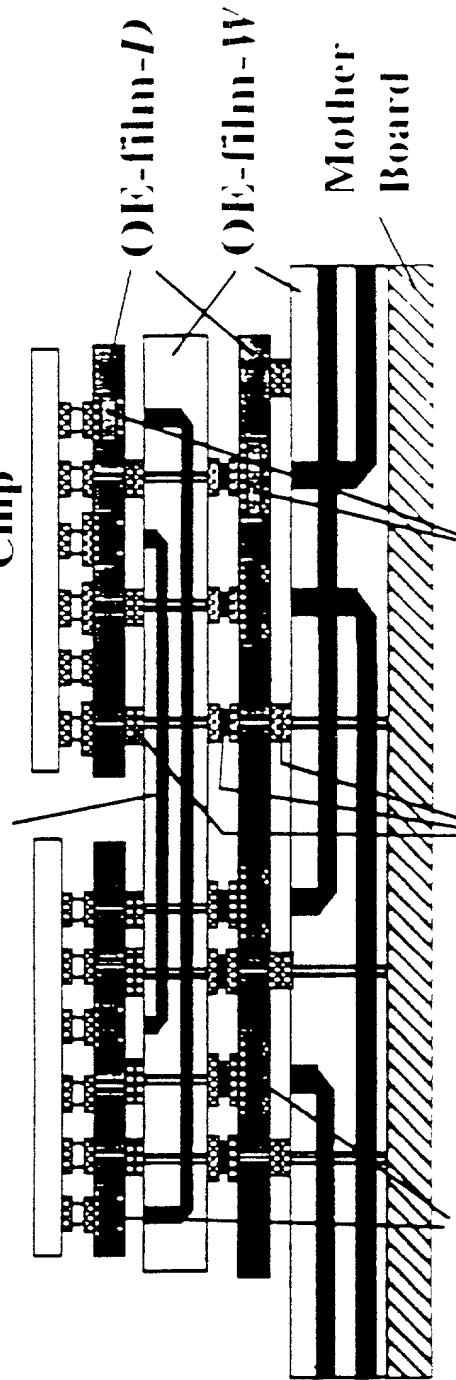


Fig. 319/99-1

VCSEL

ρ_3 Z-connection Photodetector

Fig. 146

ρ_3 3/18/99

Device Integration Process

(1) Pads/Lines formation



File 141

(2) Placement of
Thin film devices



File 148

(3) Polymer coat



File 149

(4) Planarization



File 150

(5) Vias/Pads/Lines formation



File 151

► (6) Substrate removal



File 152

OE-film-ID

A 1 /

► (6') Jump to the waveguide formation process



File 153

OE-film-IDW(1)

2/17/99-added 5

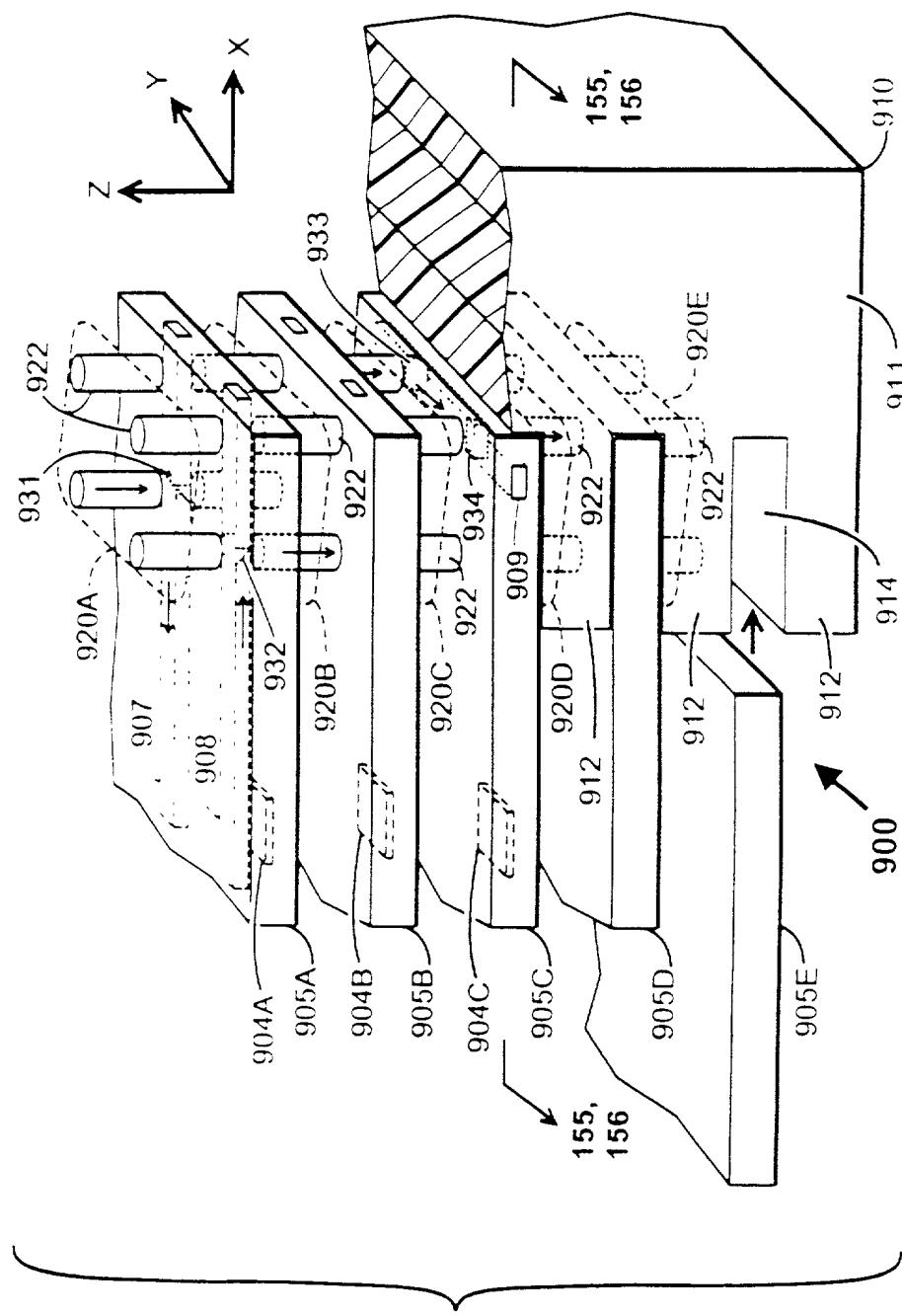
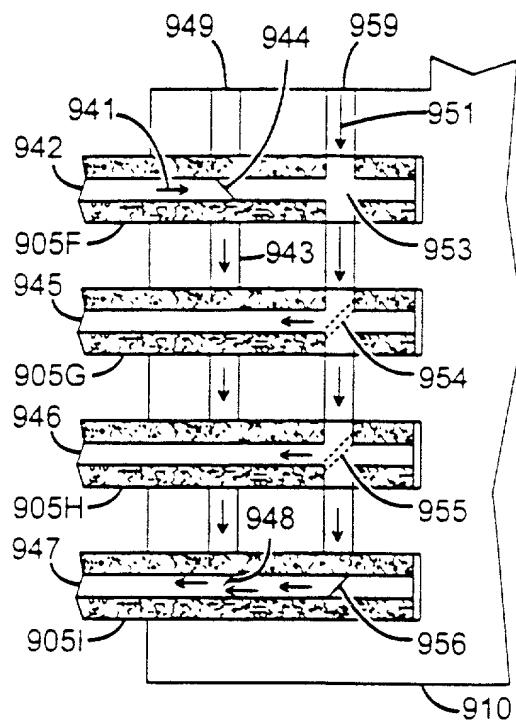
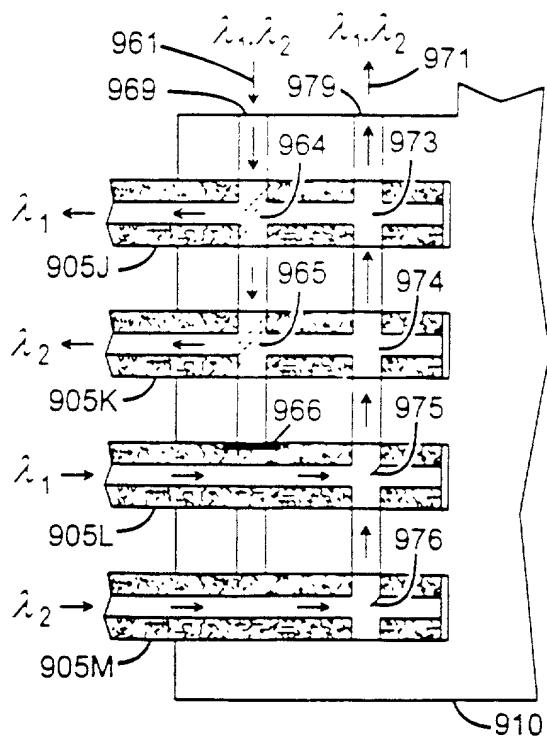
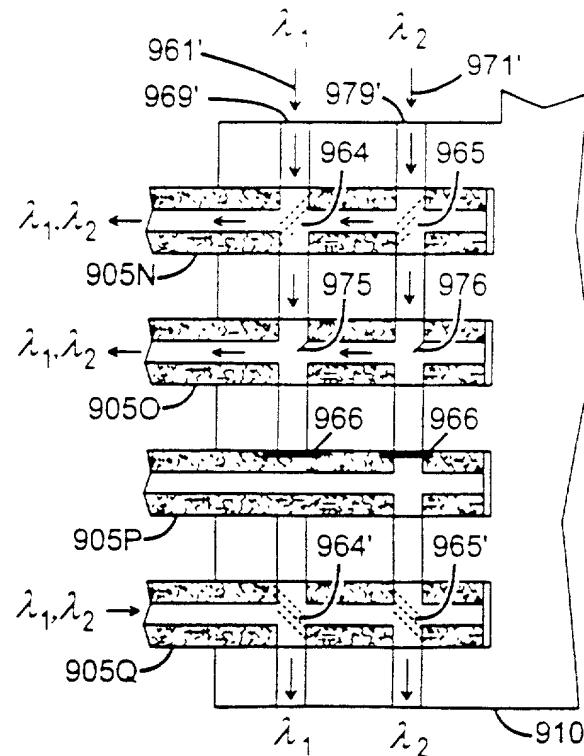


FIG. 154

1 /XX

**FIG. 155****FIG. 156-1****FIG. 156-2**

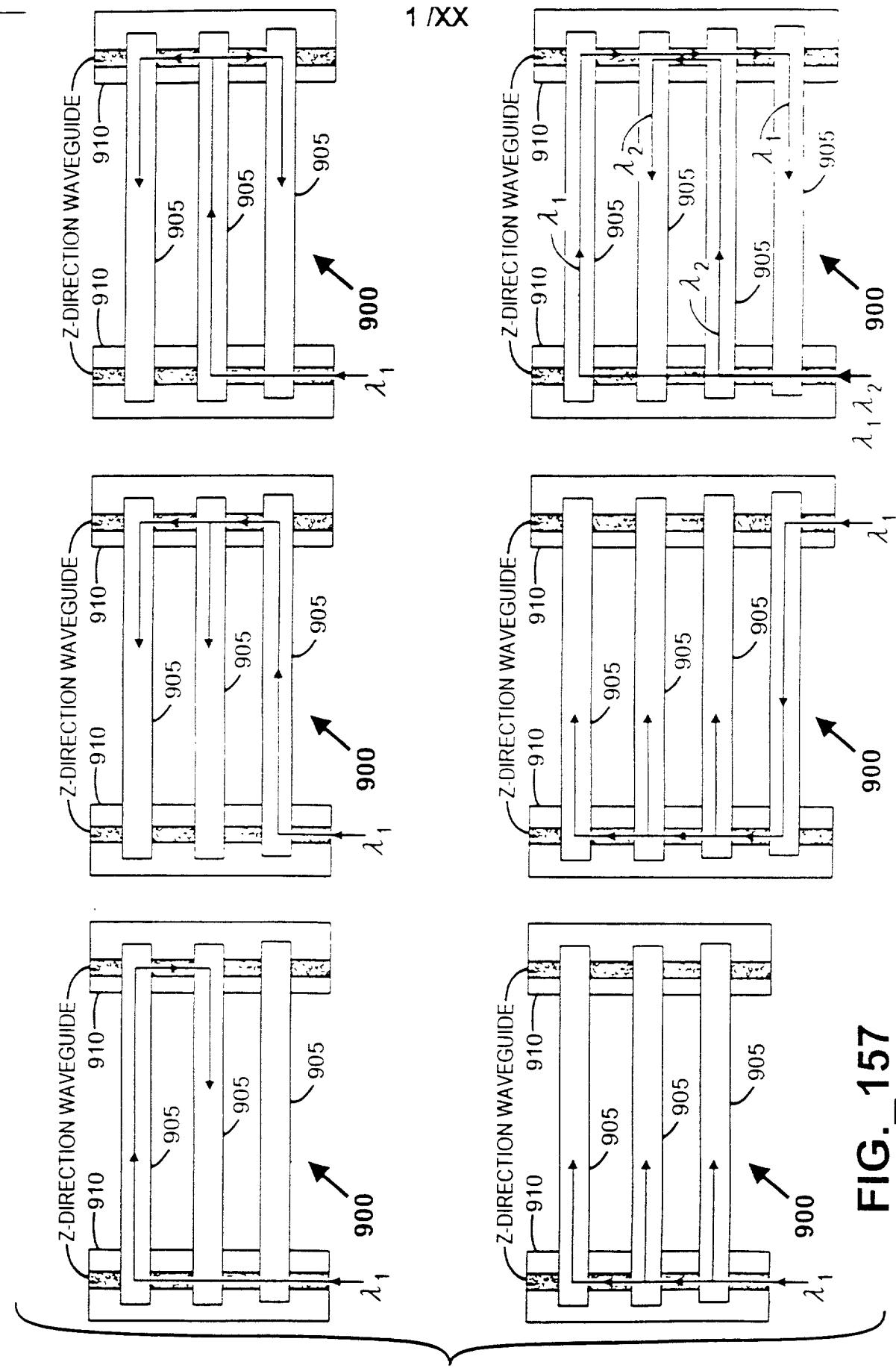
**FIG. 157**

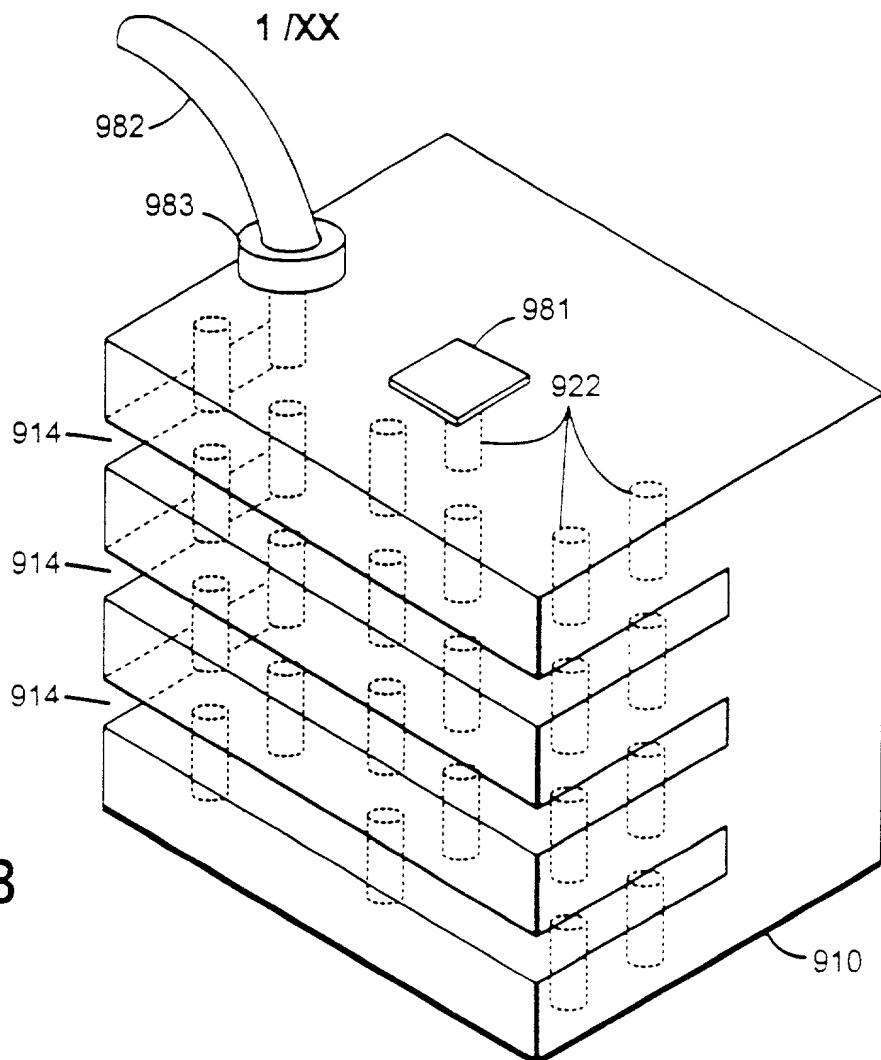
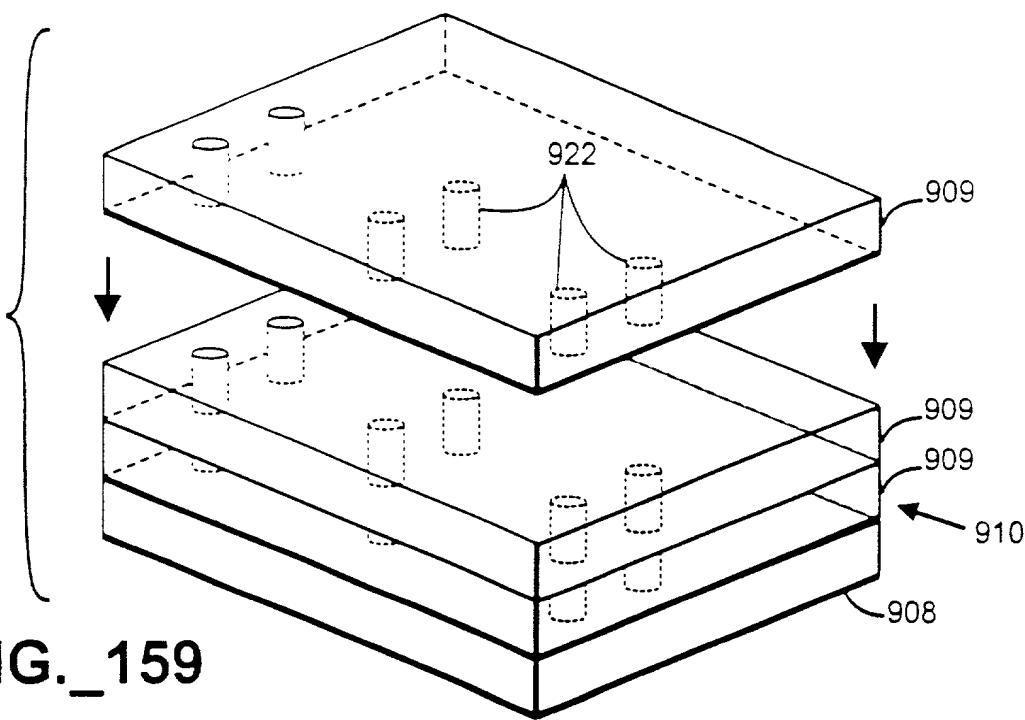
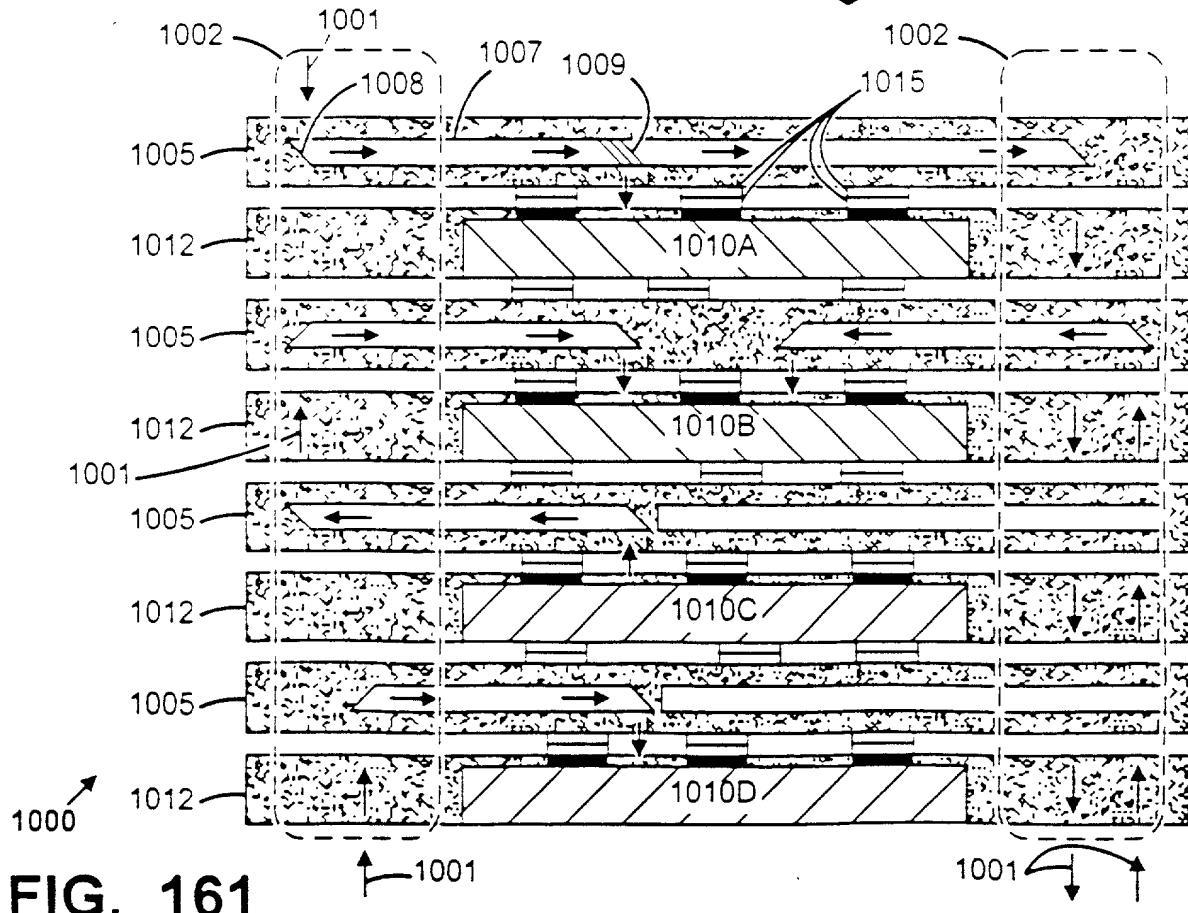
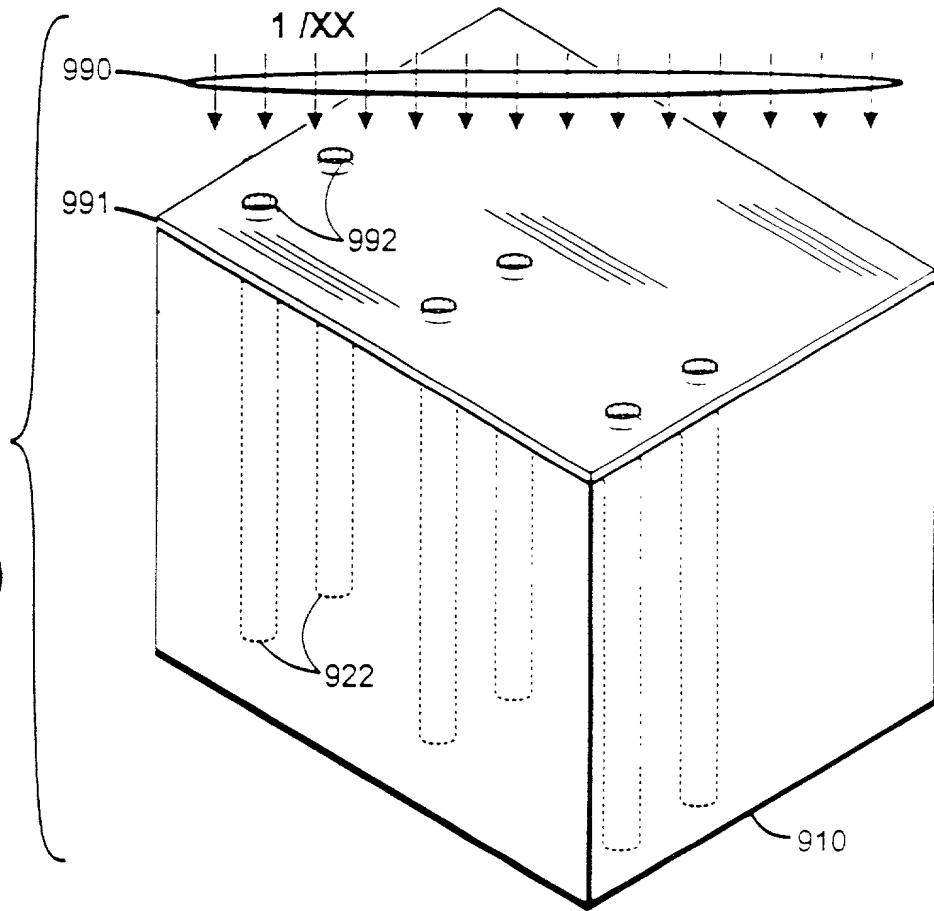
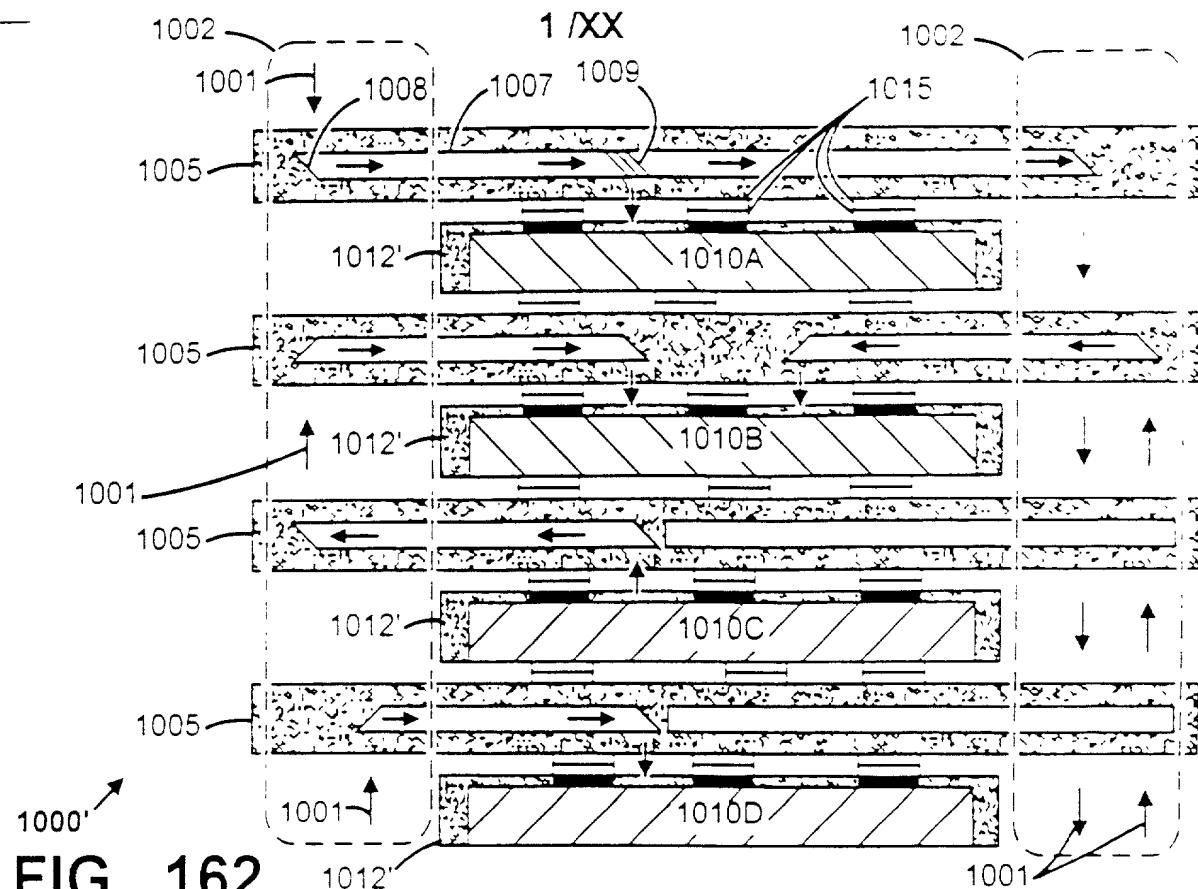
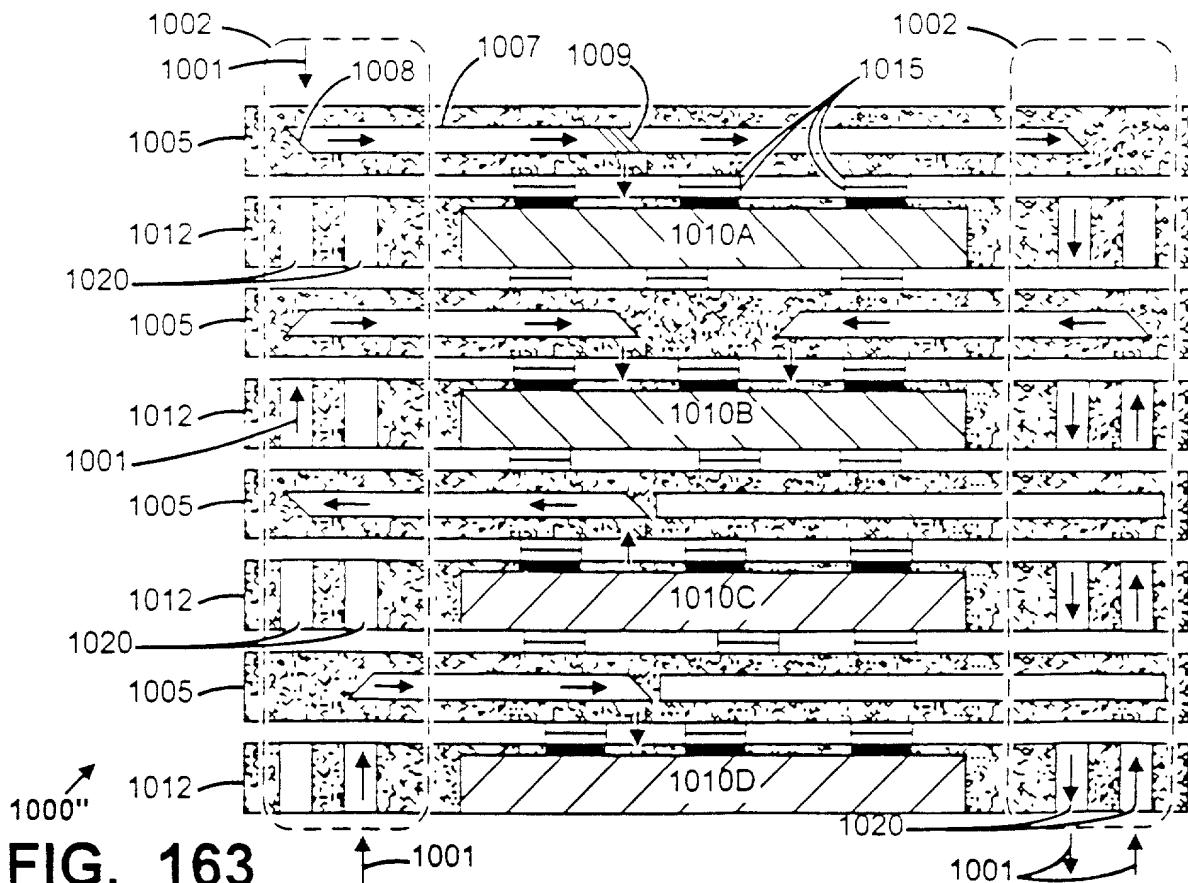
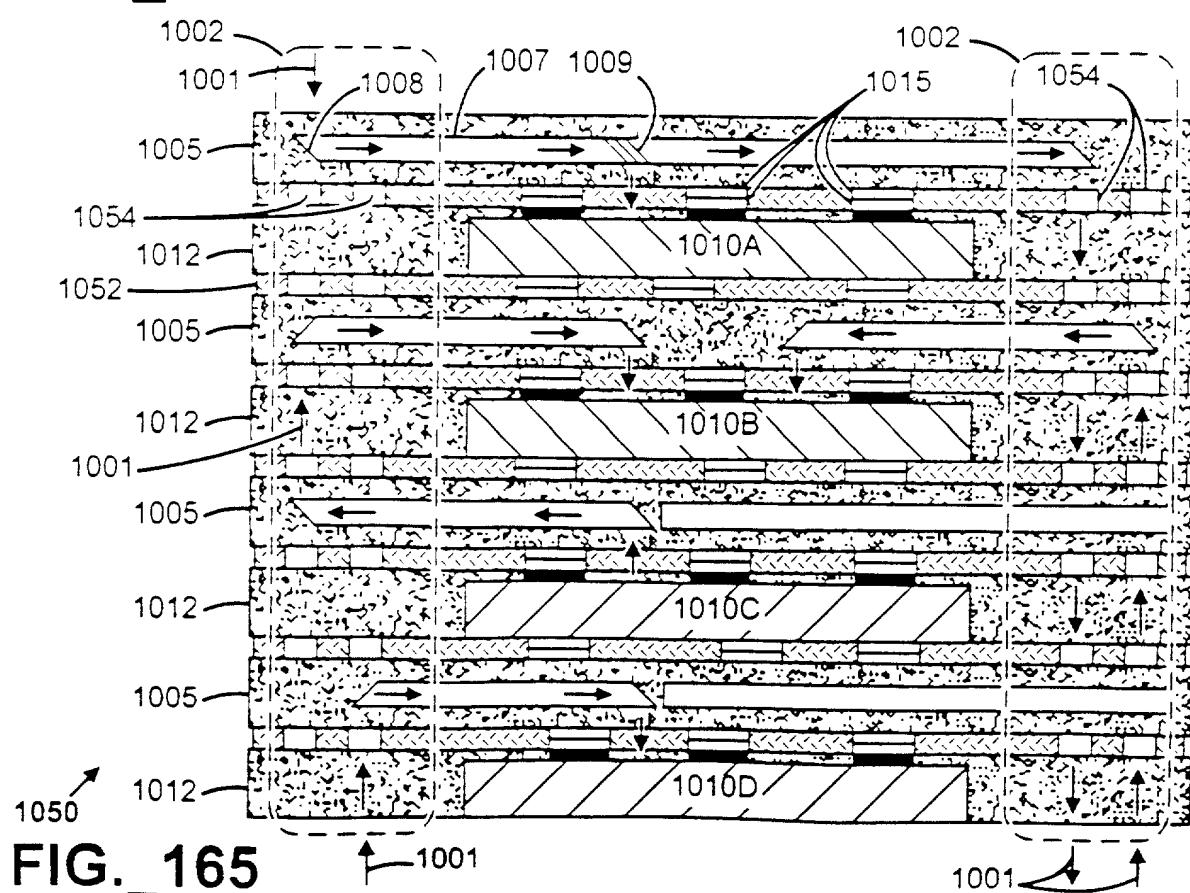
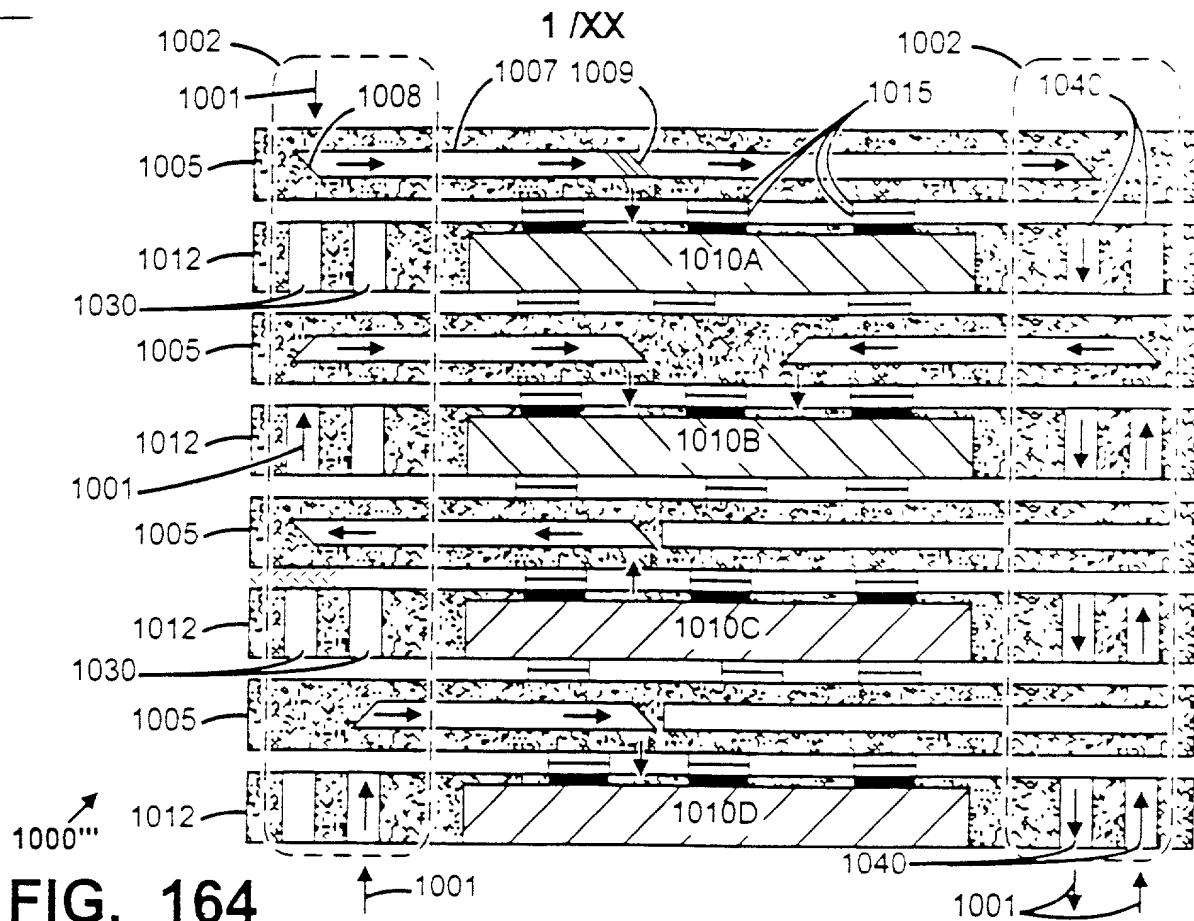
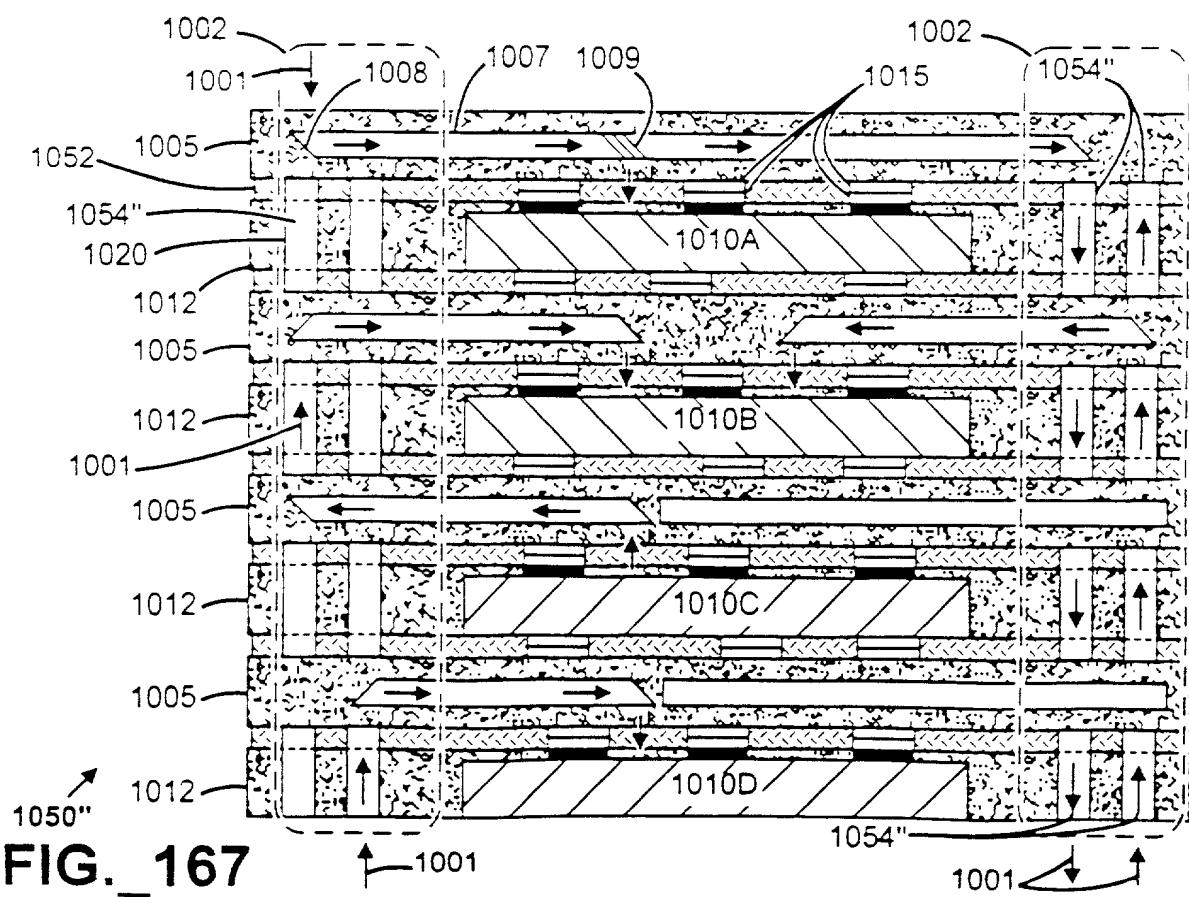
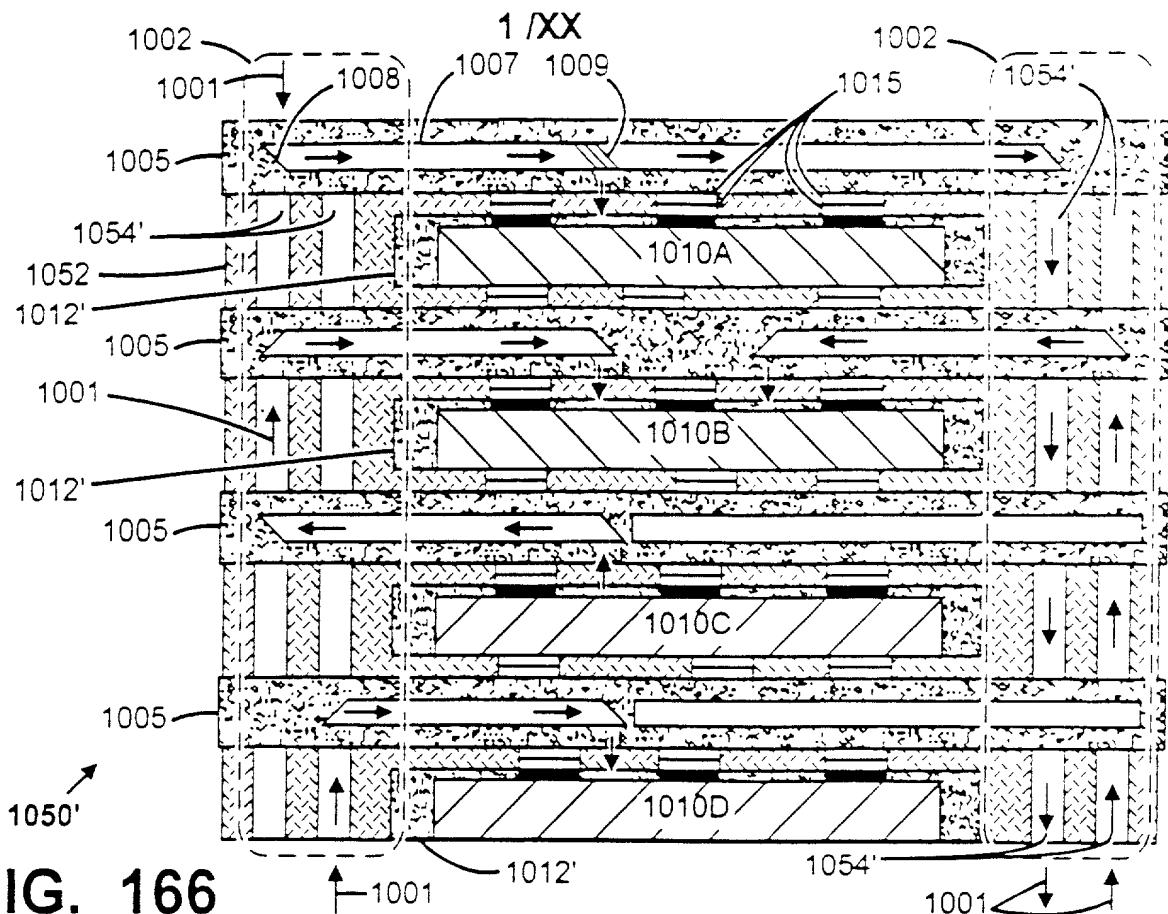
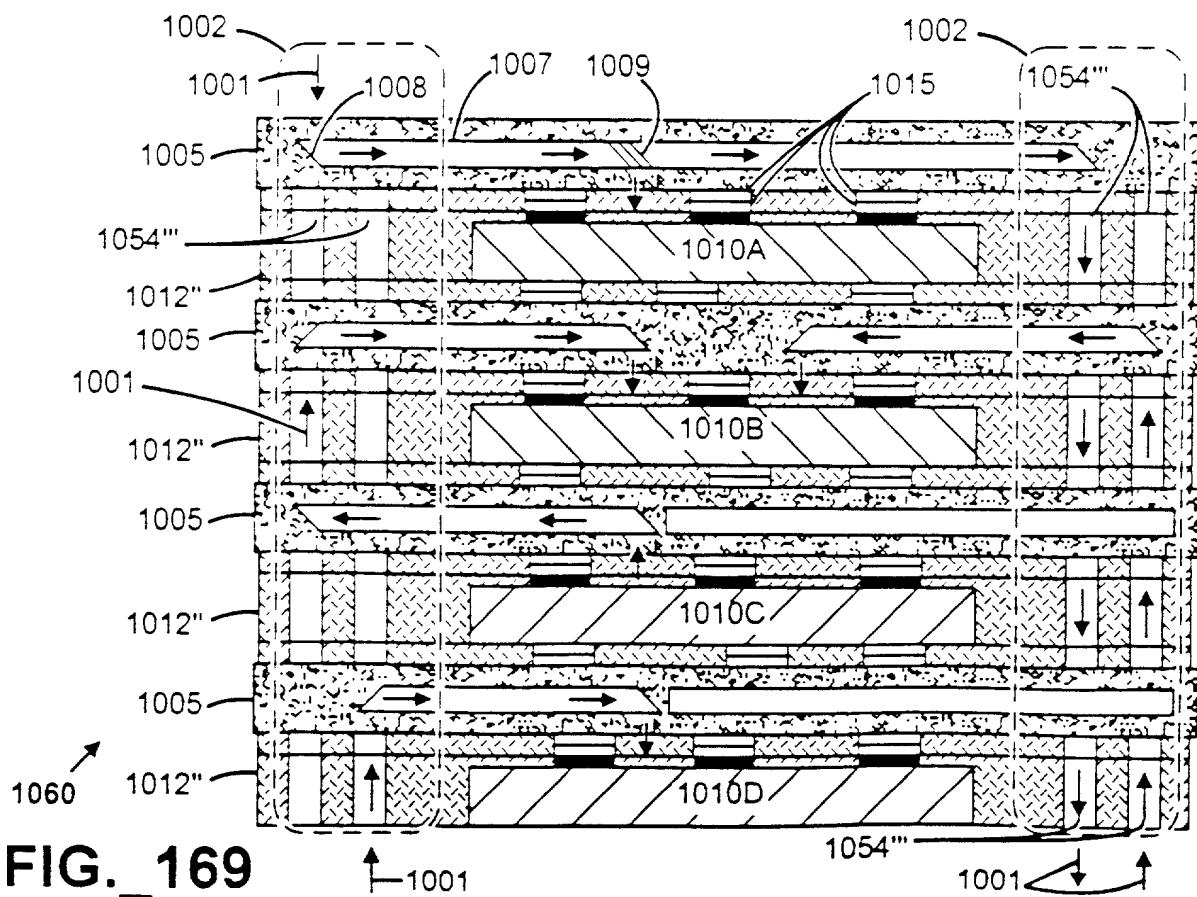
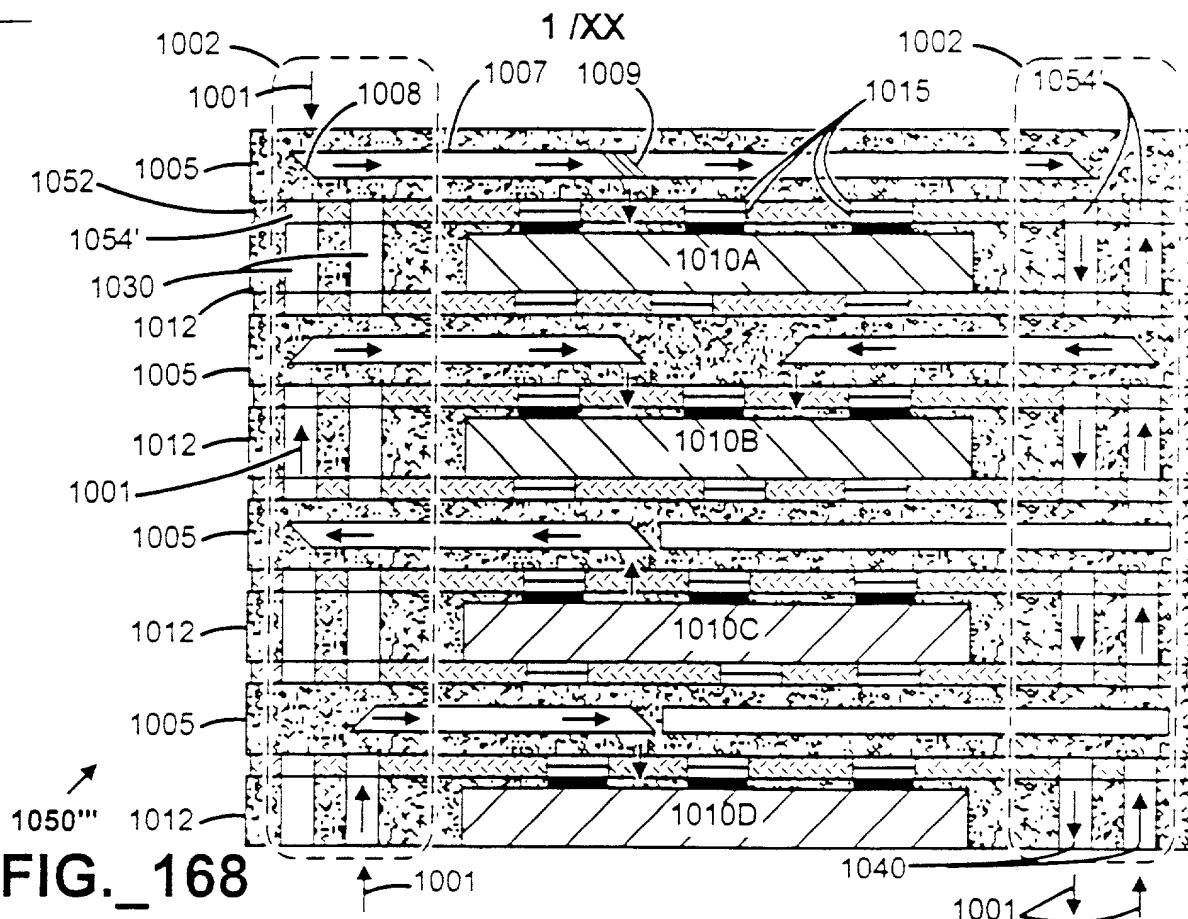
FIG._158**FIG._159**

FIG._160**FIG._161**

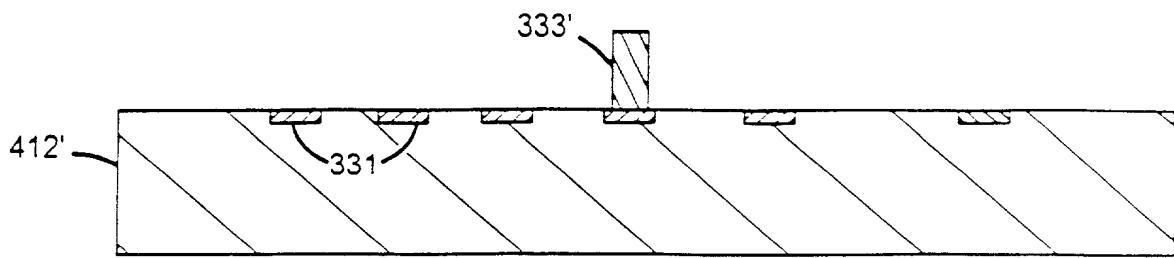
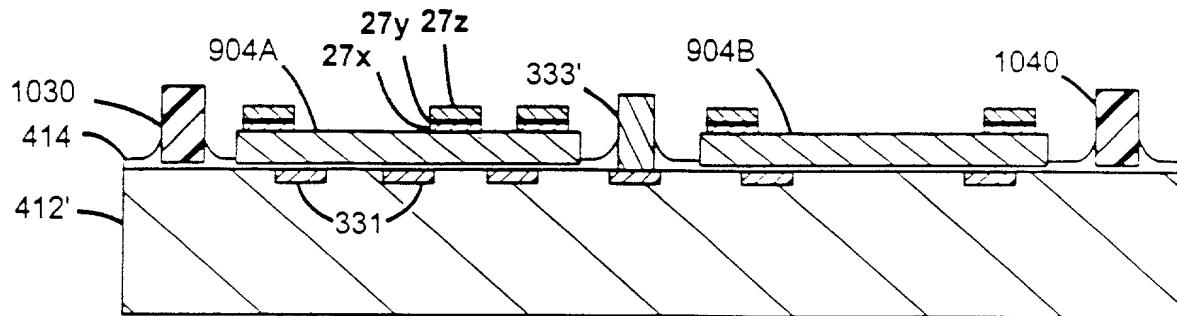
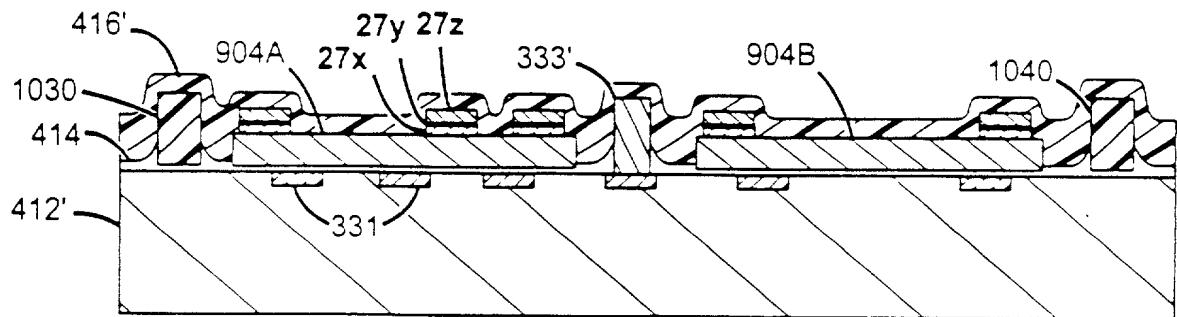
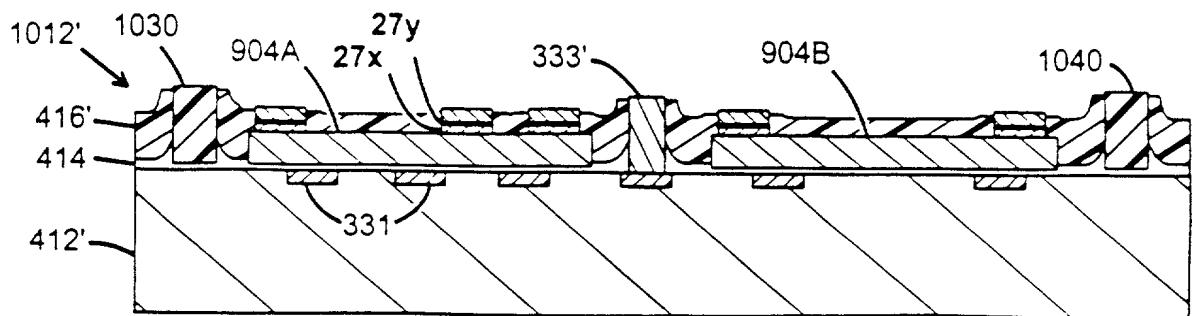
**FIG. 162****FIG. 163**

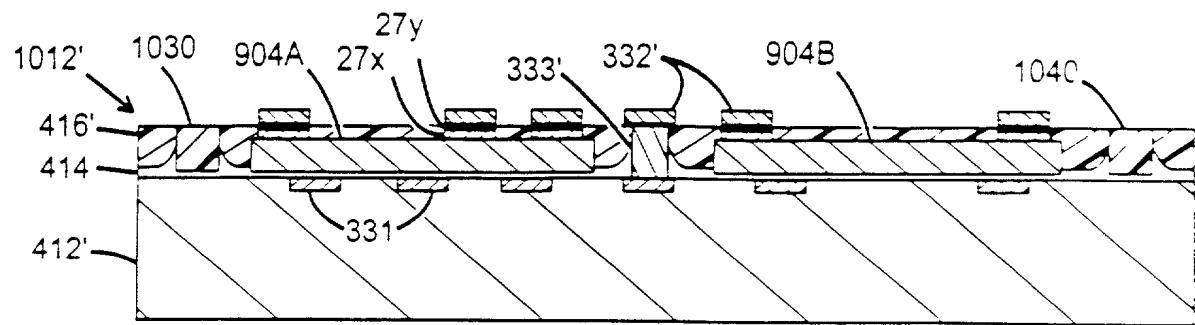
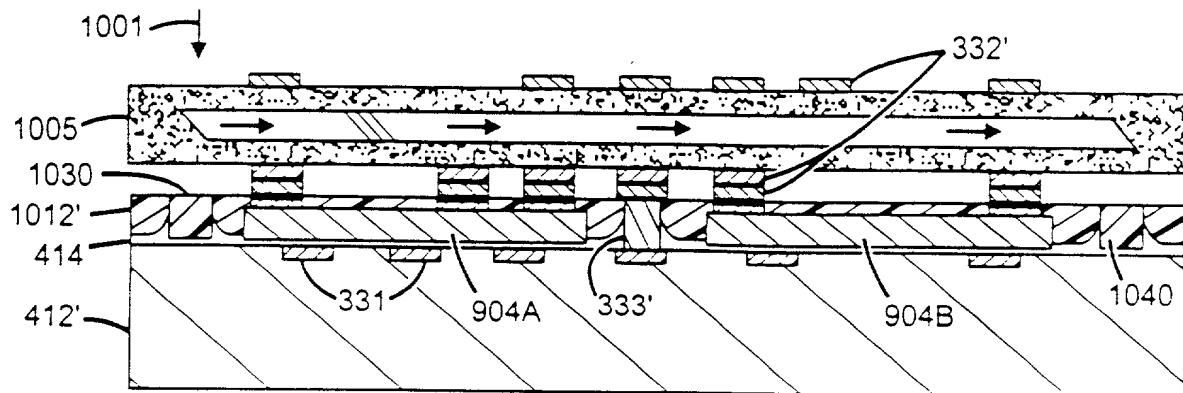
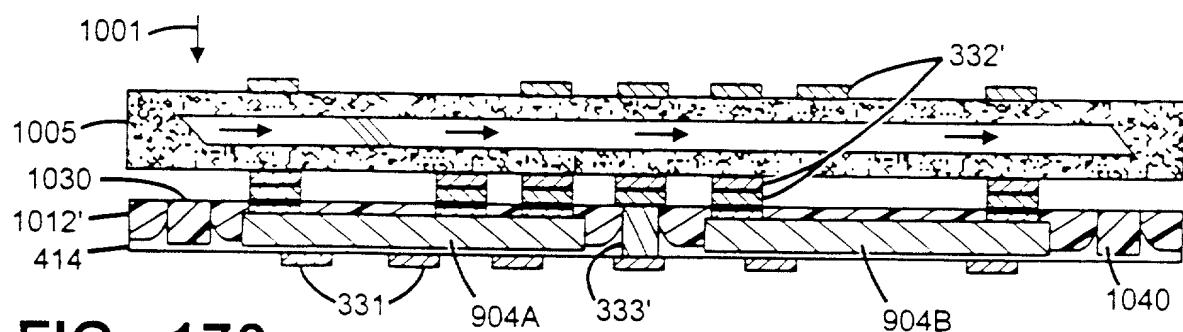




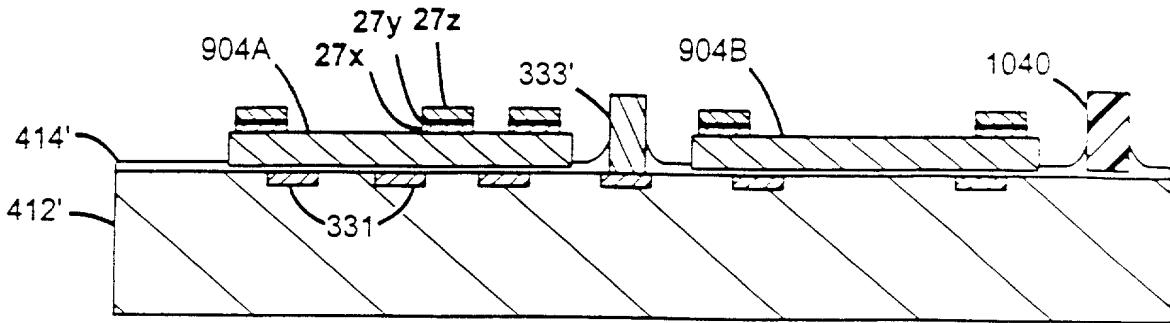
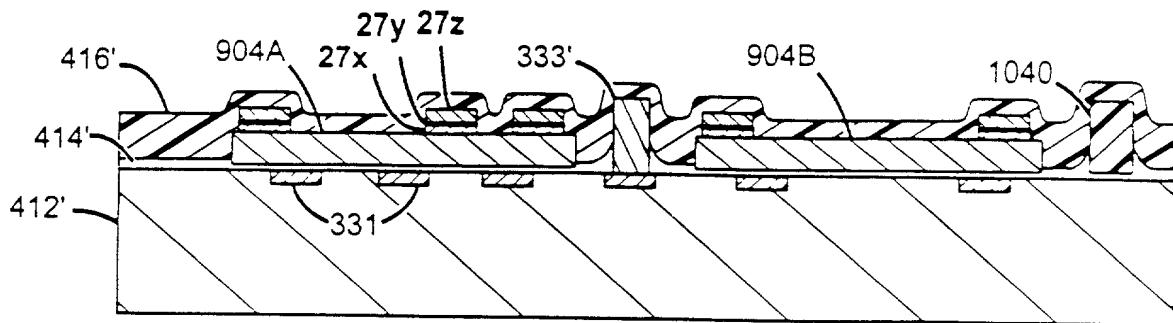
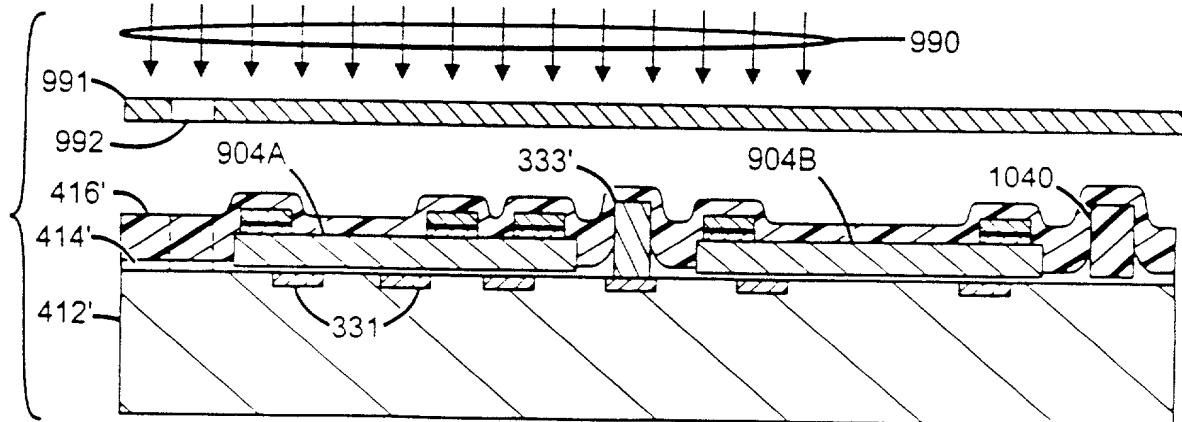
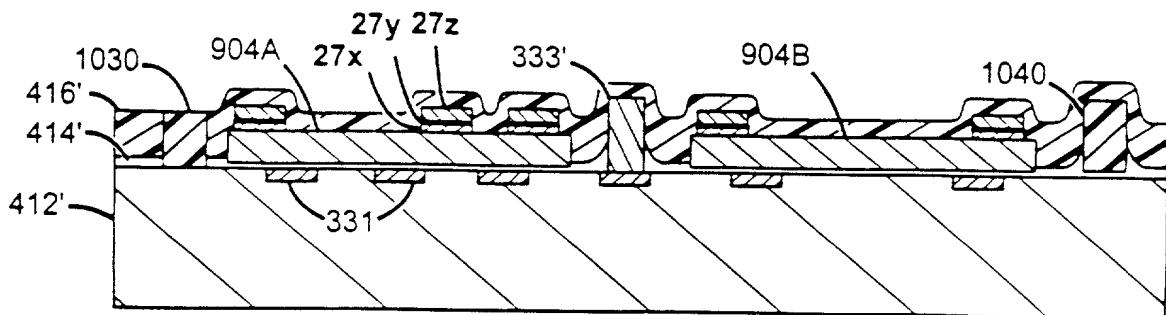


1 /XX

**FIG. 170****FIG. 171****FIG. 172****FIG. 173**

**FIG._174****FIG._175****FIG._176**

1 /XX

**FIG. 177****FIG. 178****FIG. 179****FIG. 180**

23/9/98 - 100
98-23

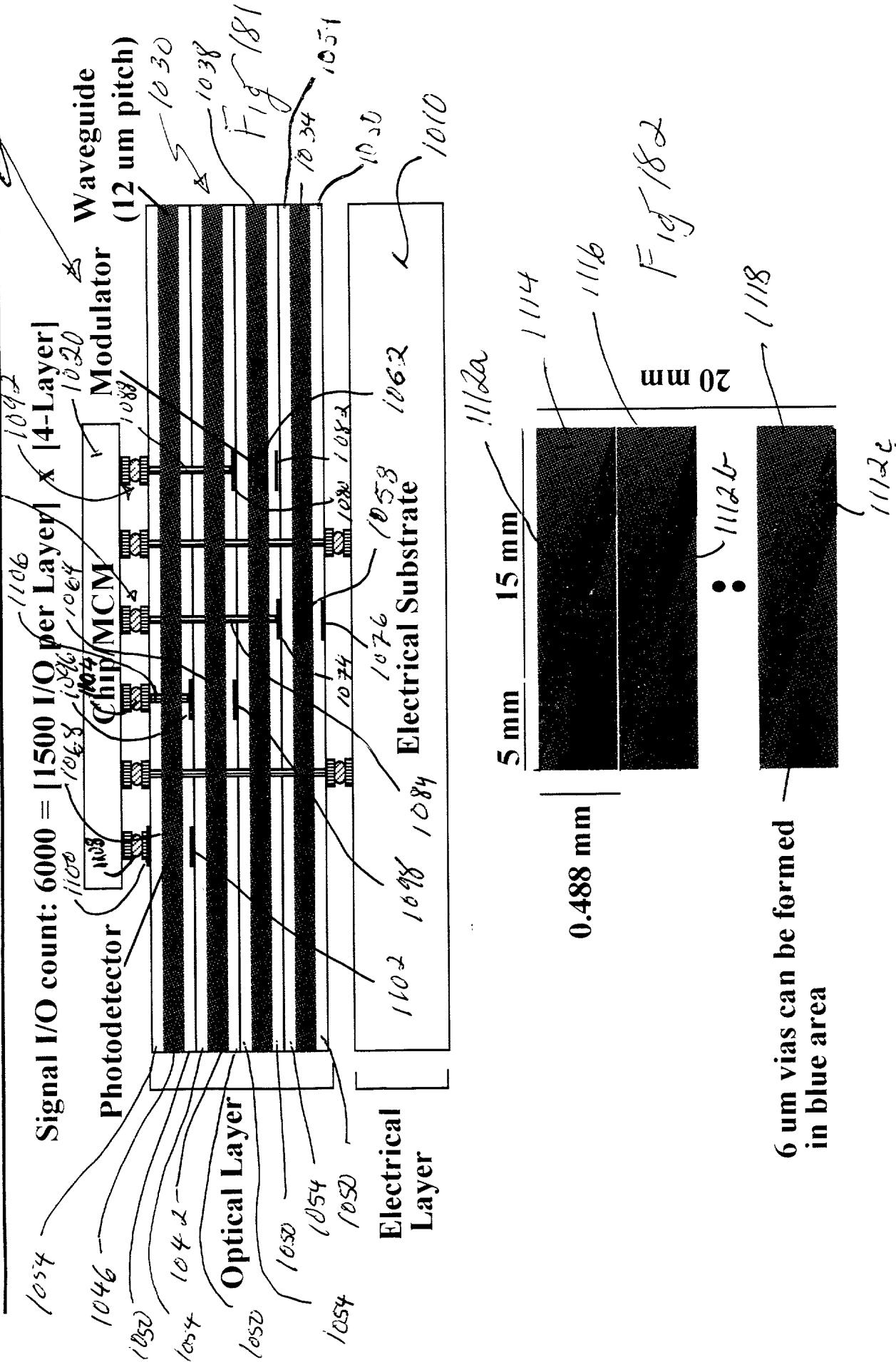
6-180
98-23

FUJITSU Computer Packaging Technologies, Inc.

I/O Connection in OE Substrate (Planar Modulator)

二

卷之三



I/O Connection in OE Substrate (OE-VLSI)

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]

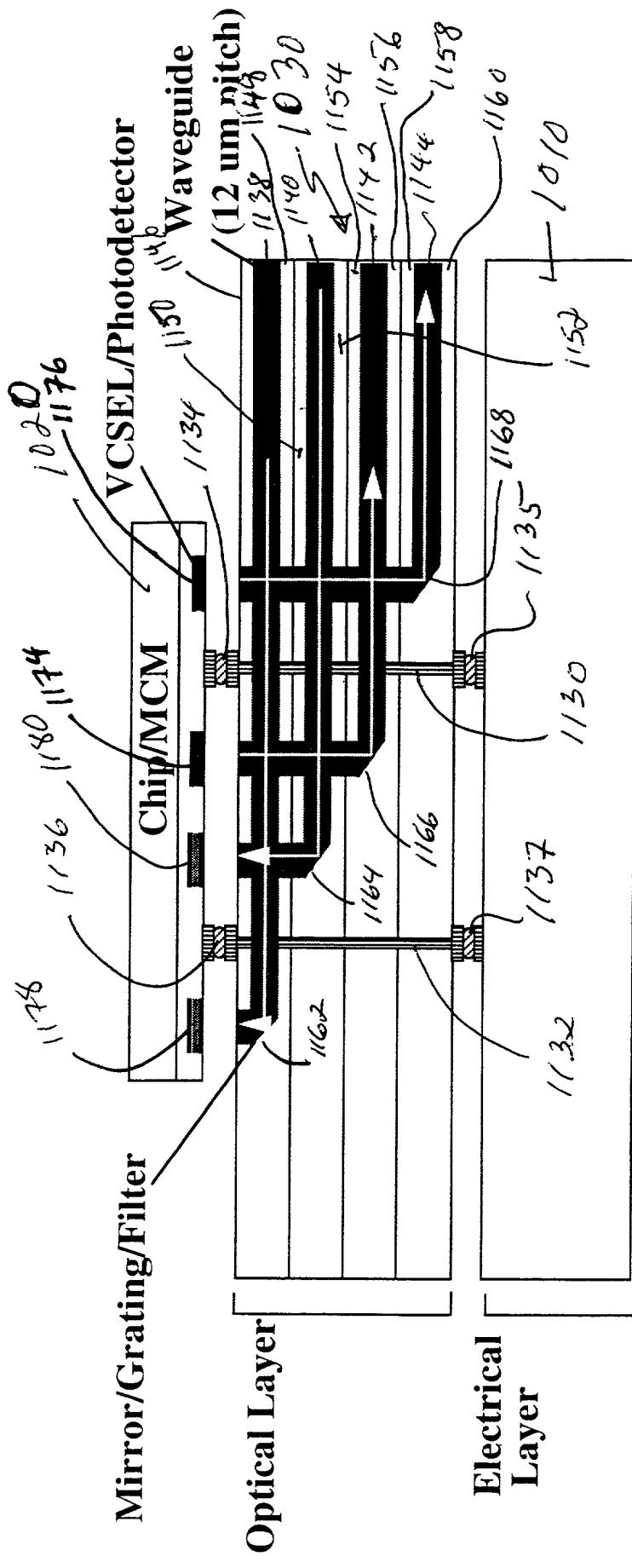


Fig 185

I/O Connection in OE Substrate (OE-VLSI)

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]

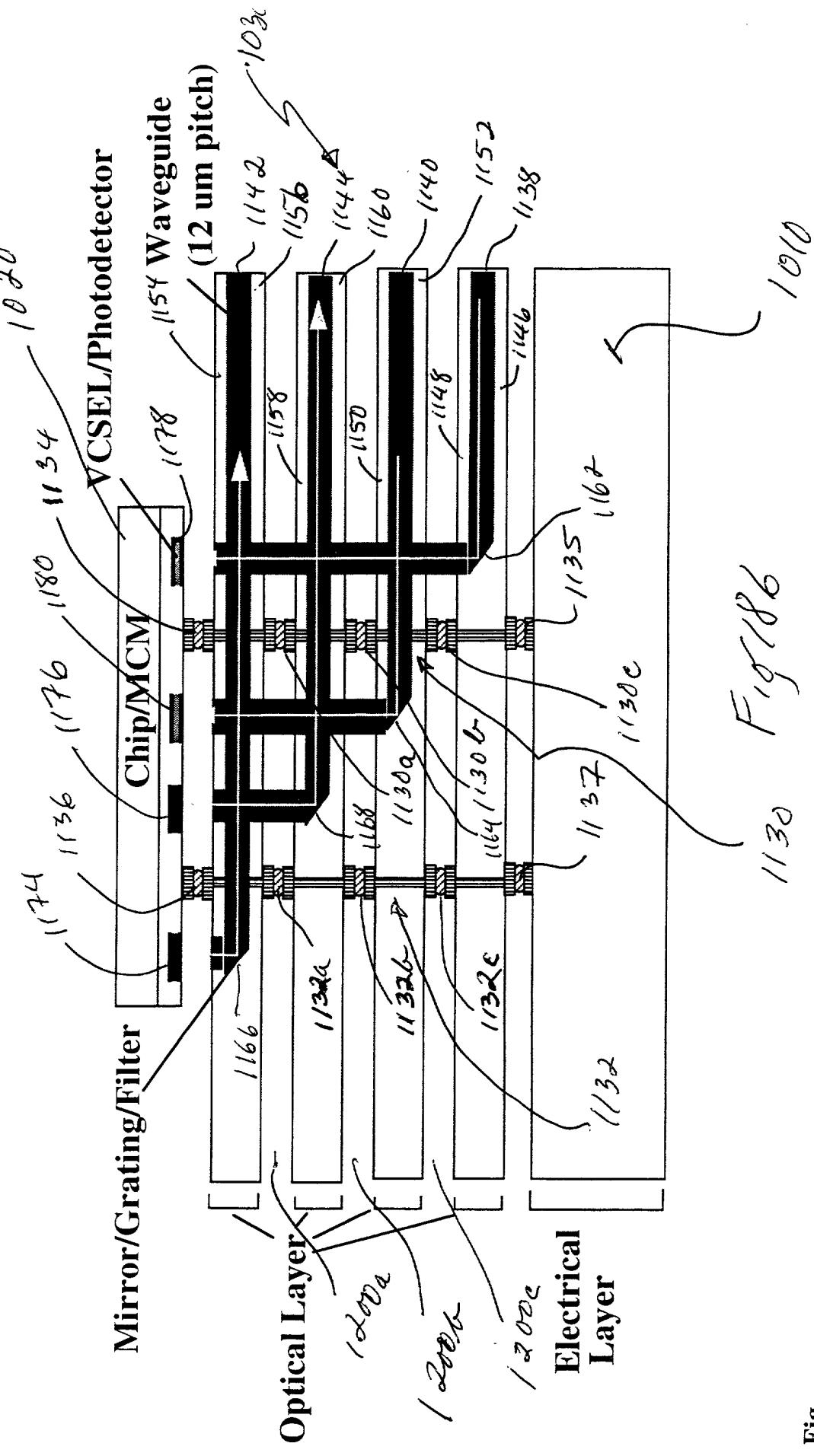
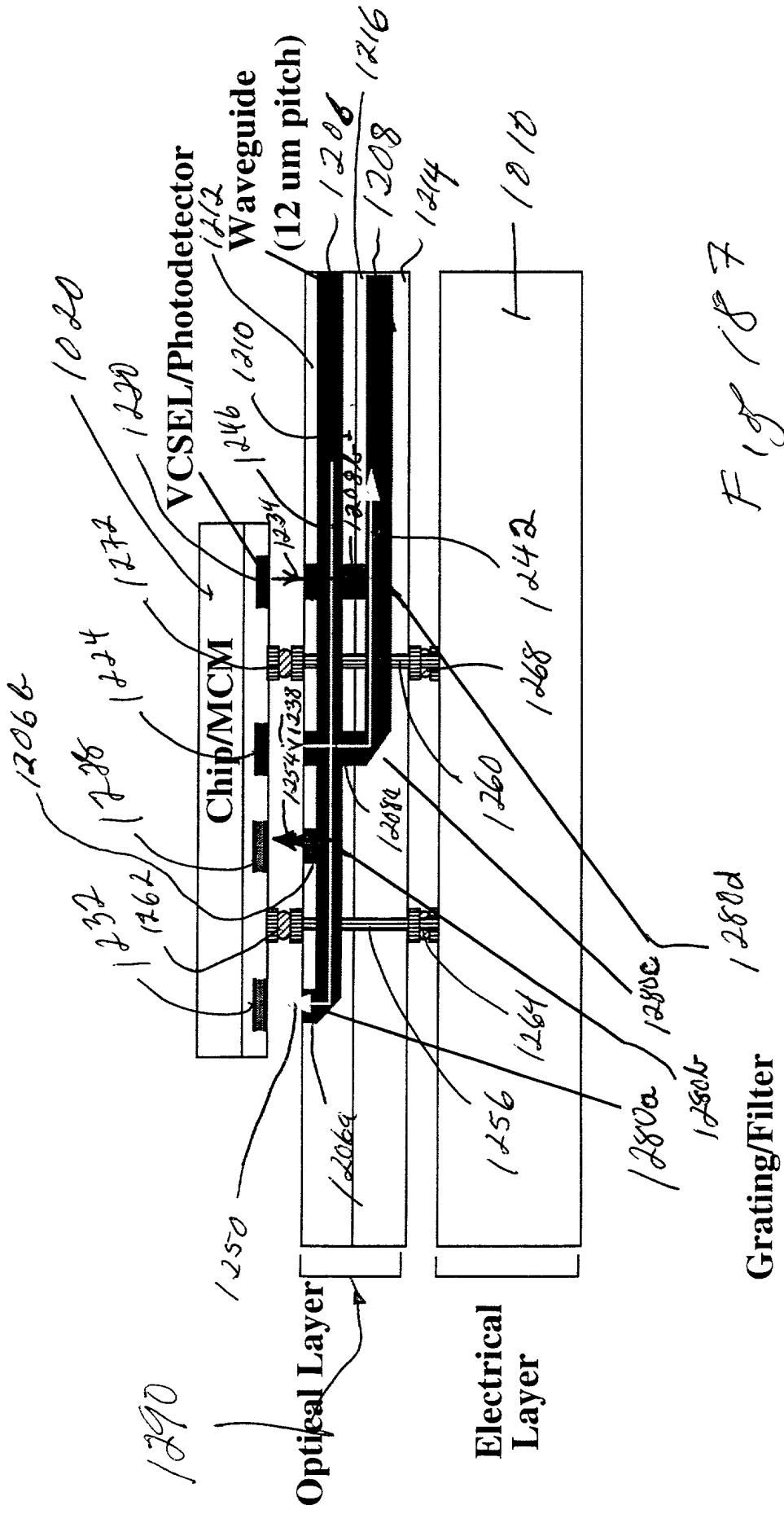


Fig.

I/O Connection in OE Substrate (OE-VLSI, WDM)

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]



I/O Connection in OE Substrate (OE-VLSI, WDM)

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]

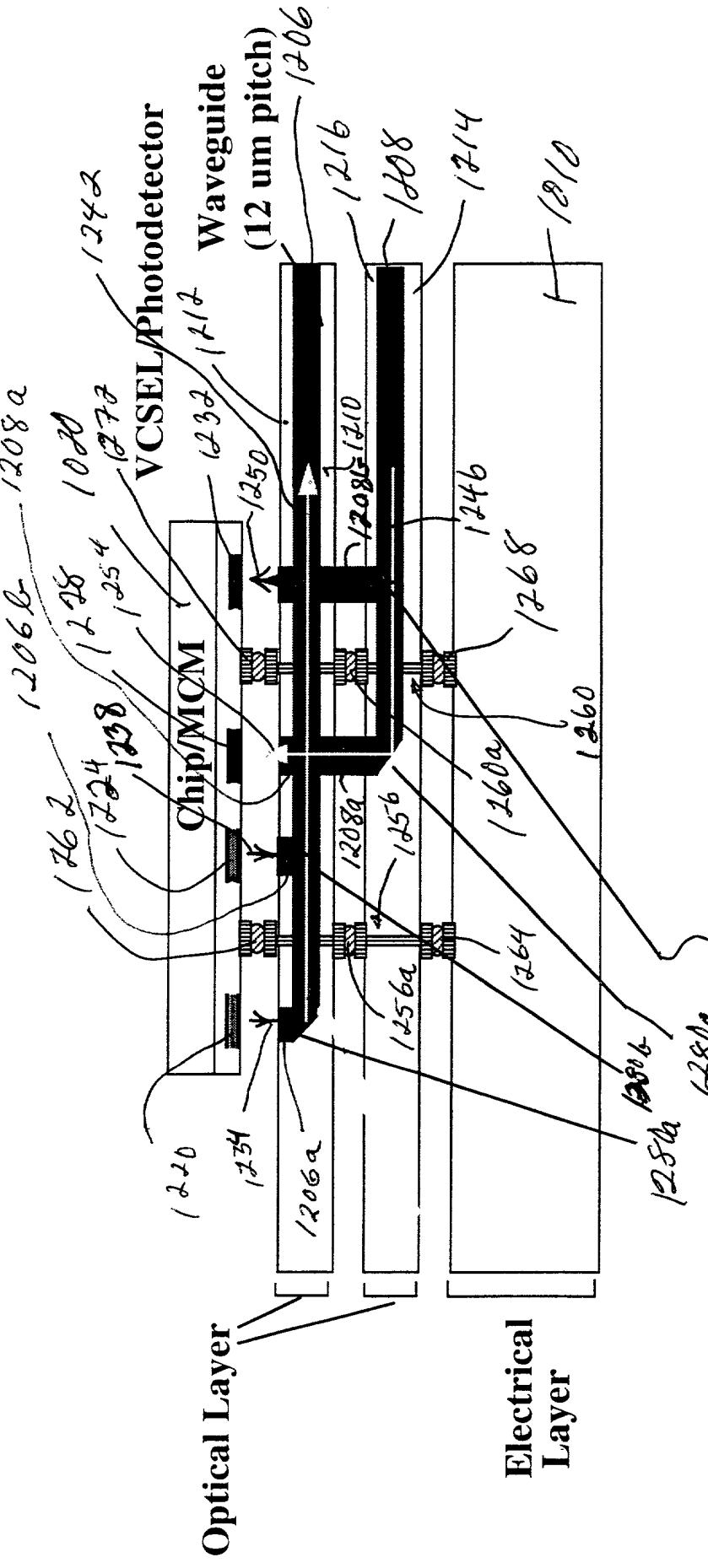
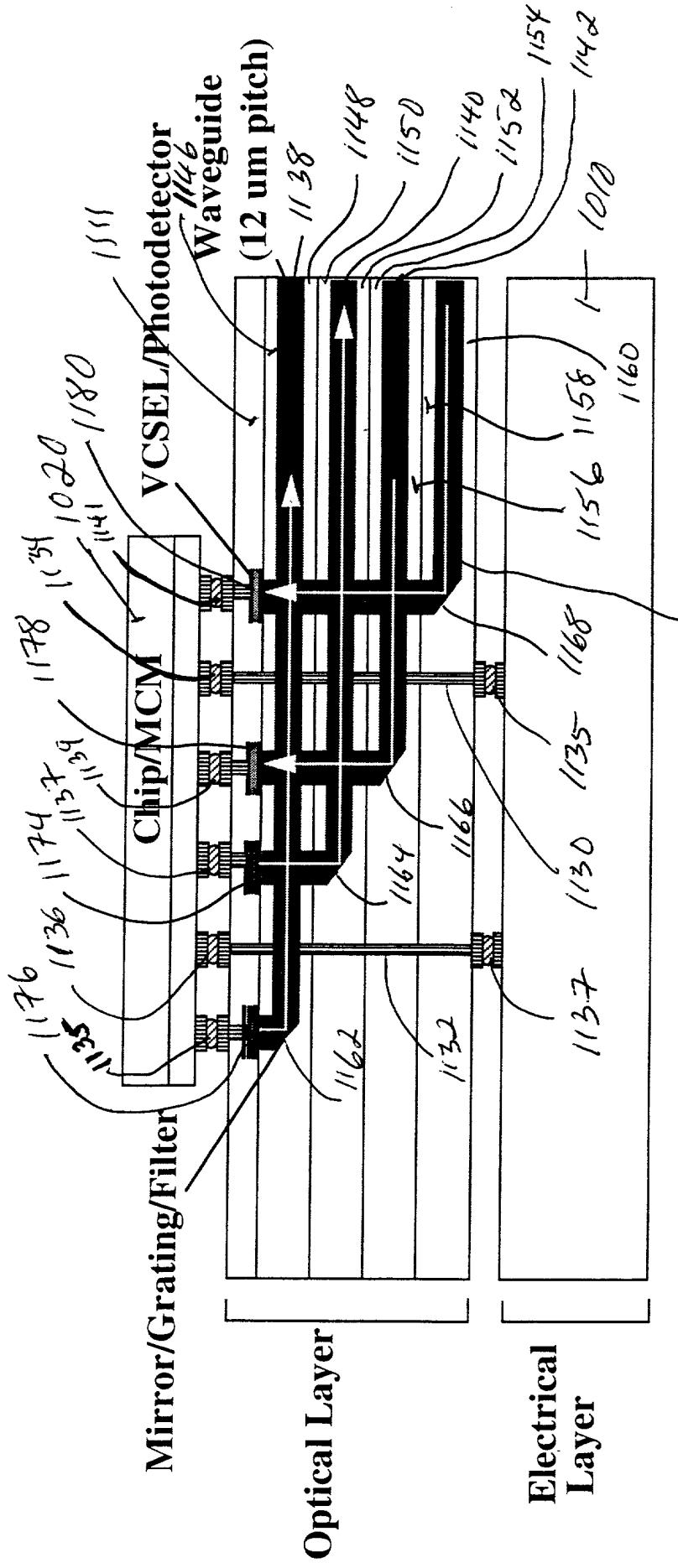


Fig 188

Grating/Filter

I/O Connection in OE Substrate (Active OE Layer)

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]

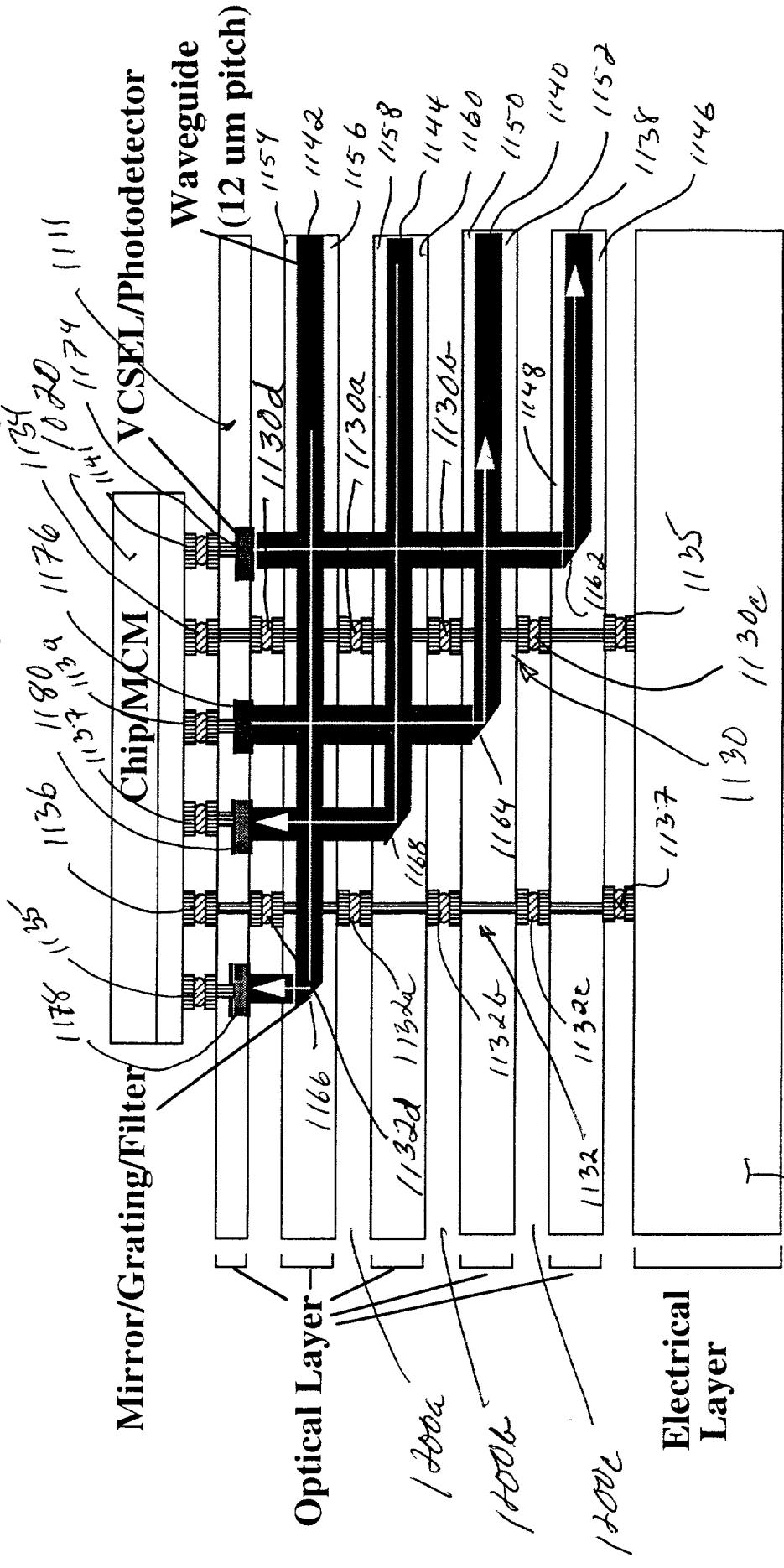


1144

Fig 189

I/O Connection in OE Substrate (Active OE Layer)

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]



6
E

Fig. 190
1010

I/O Connection in OE Substrate (Active OE Layer, WDM)

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]

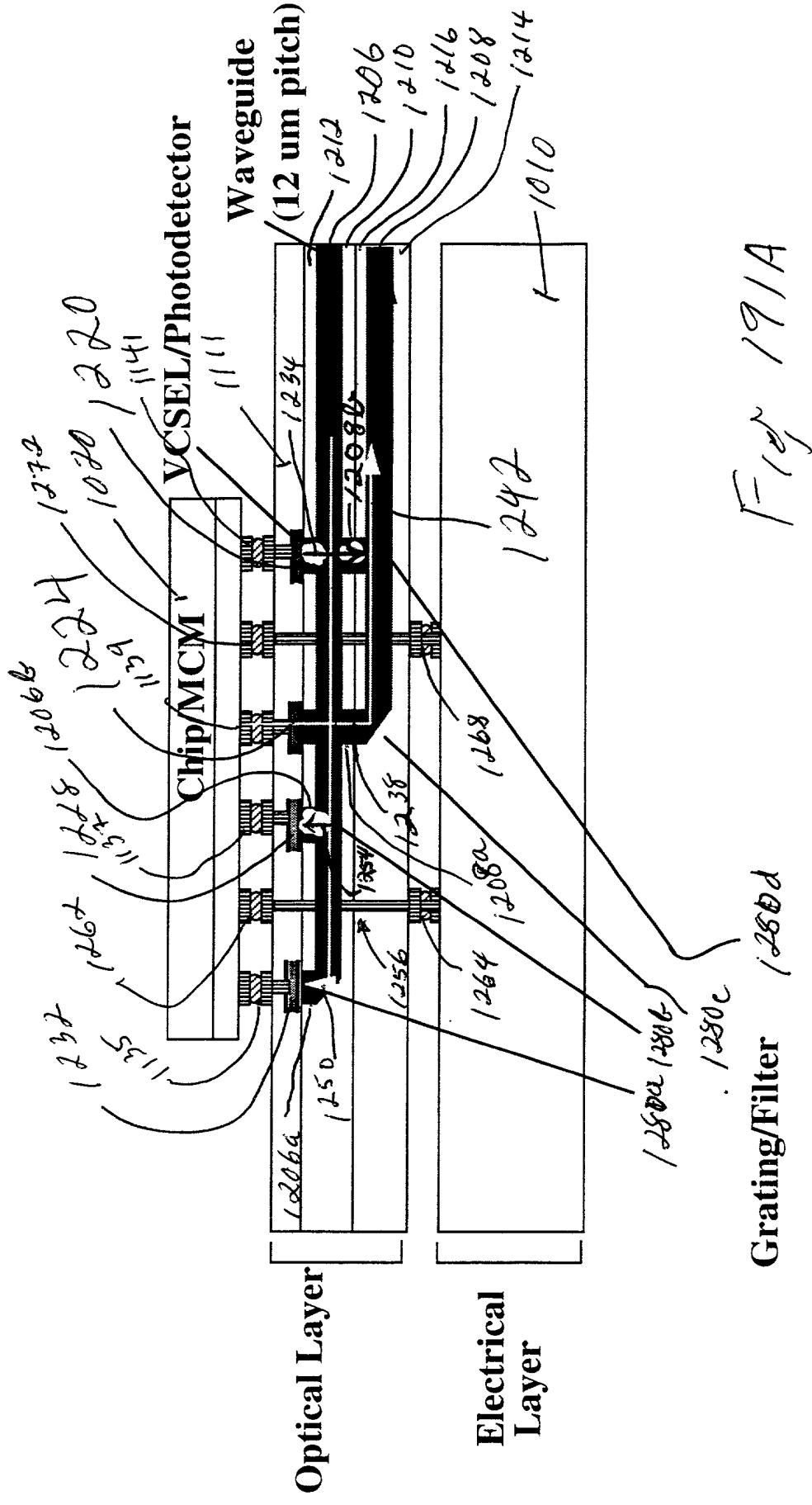


Fig. 10

I/O Connection in OE Substrate (Active OE Layer, WDM)

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]

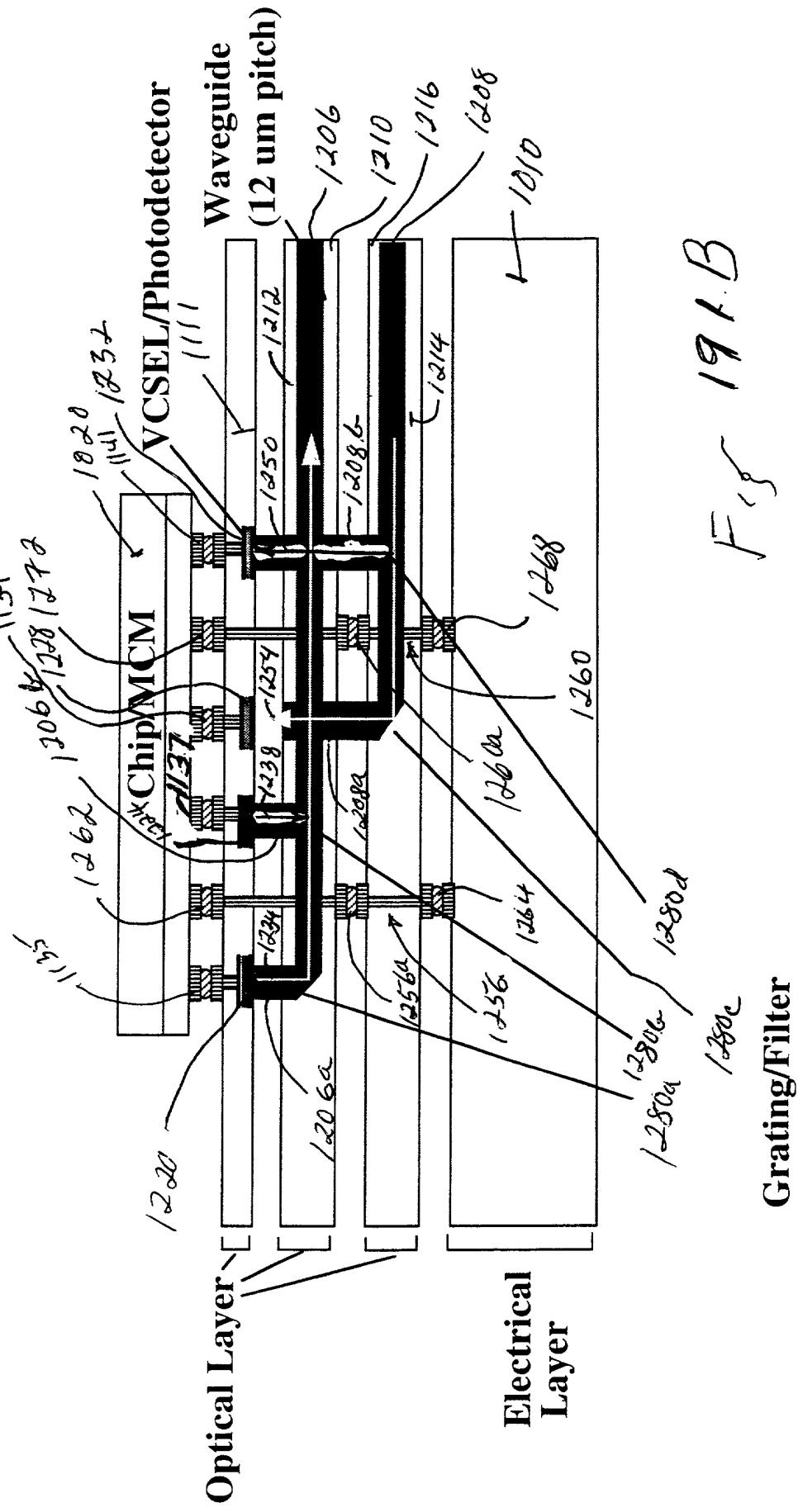


Fig. 11

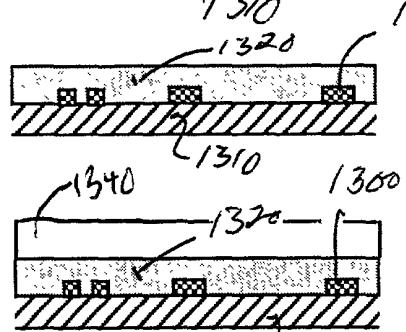
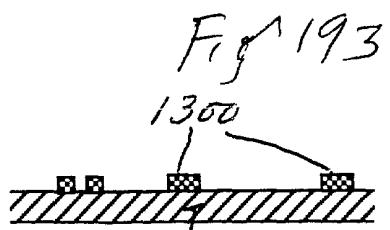
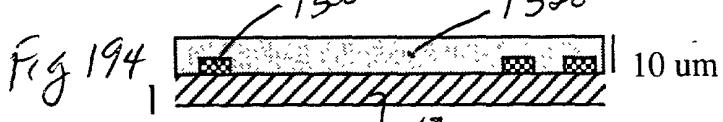
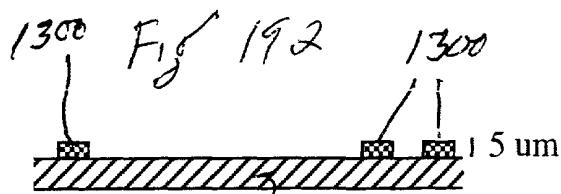
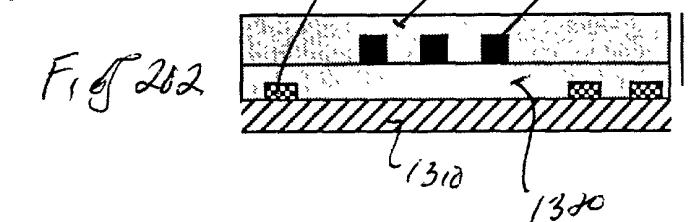
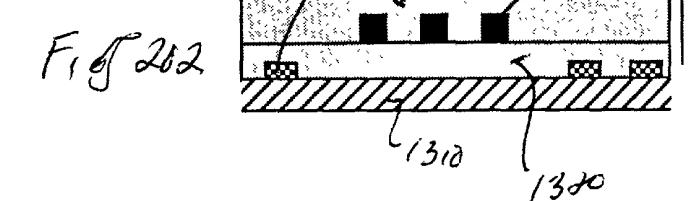
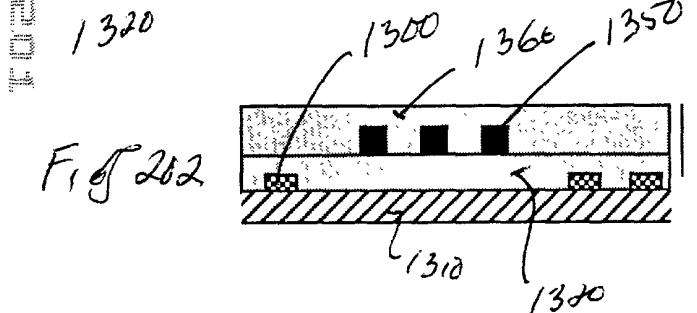
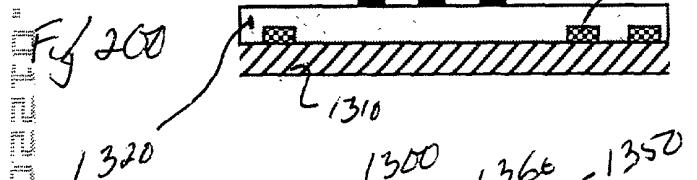
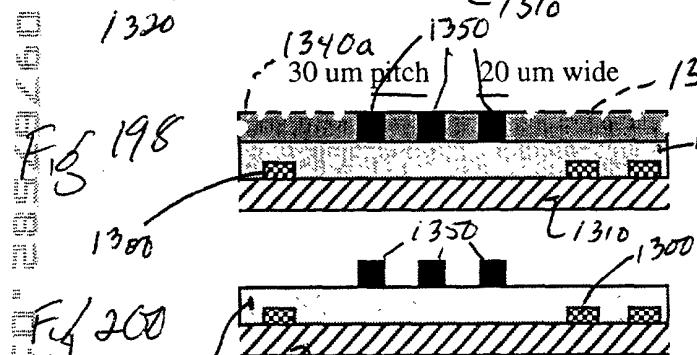
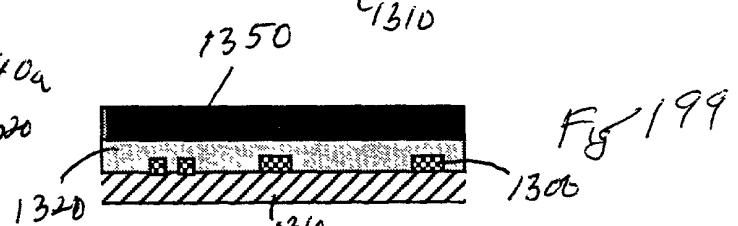
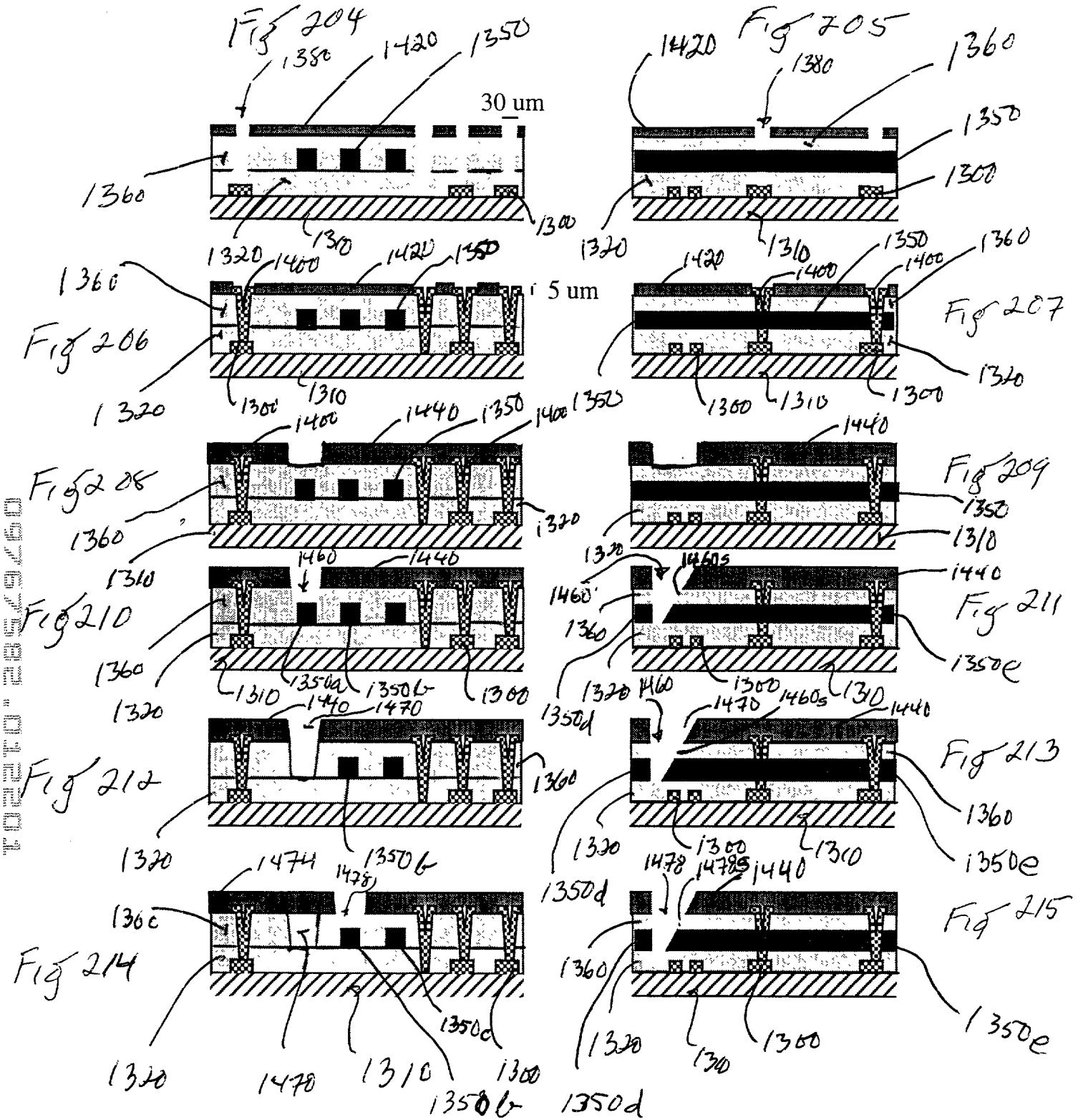
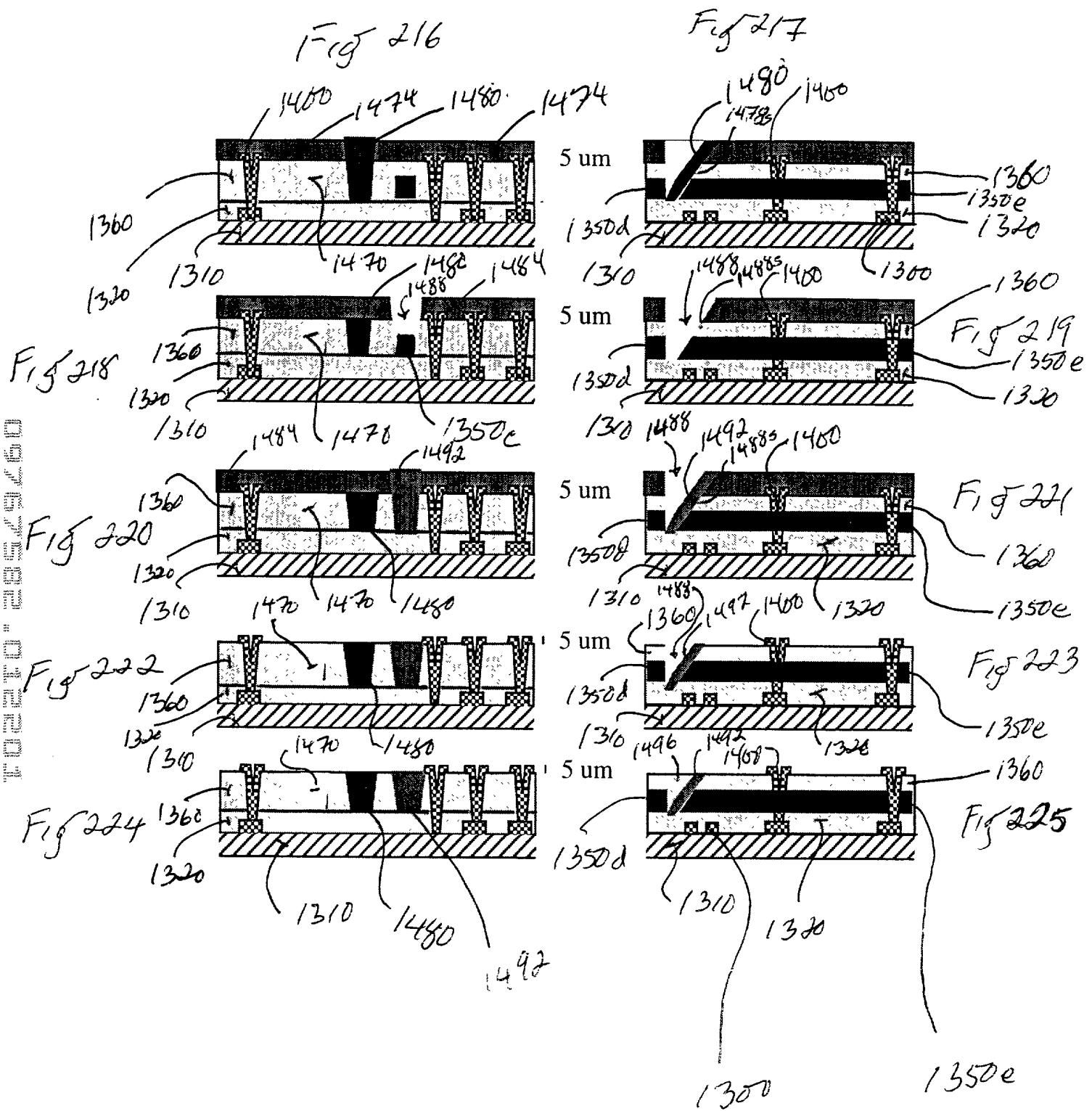


Fig 197







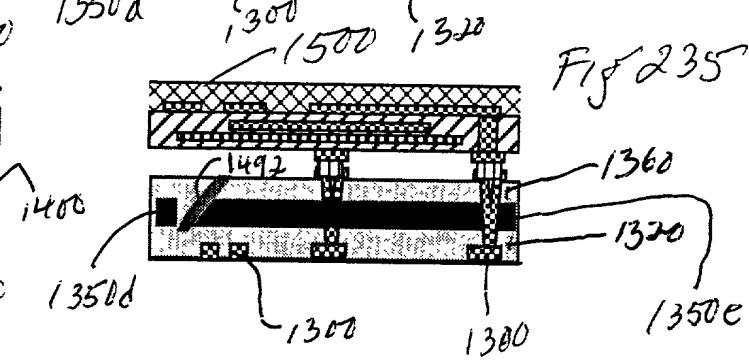
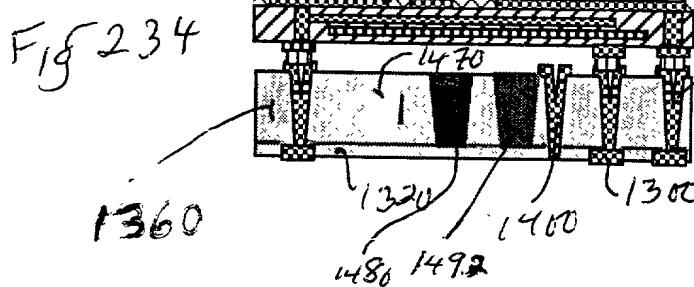
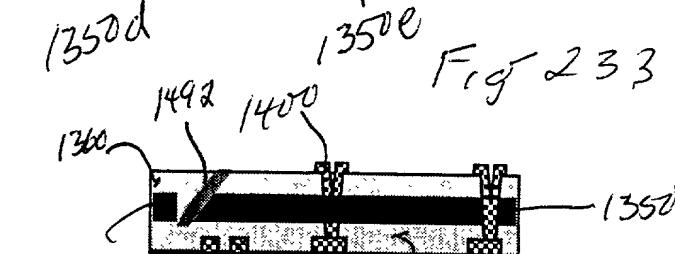
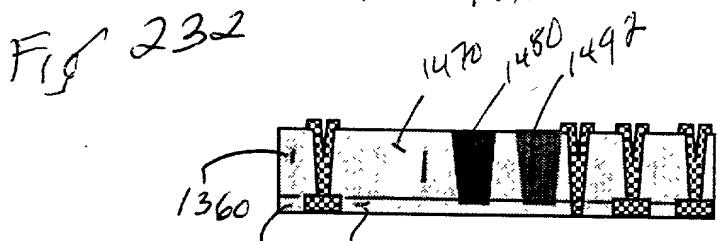
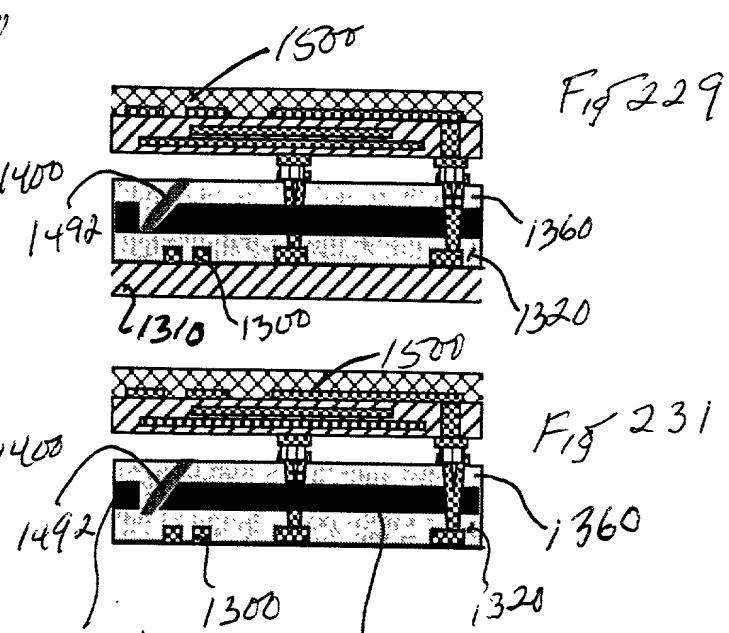
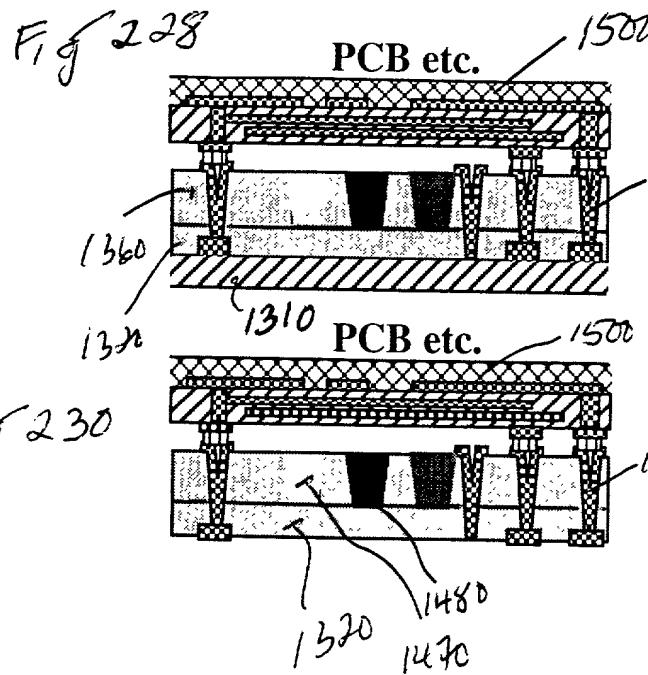
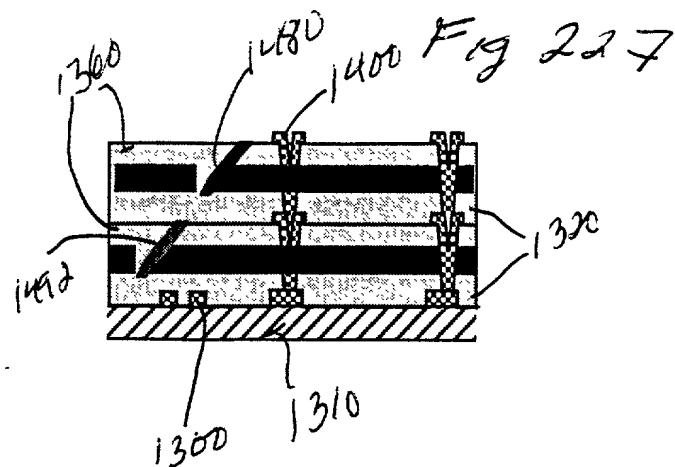
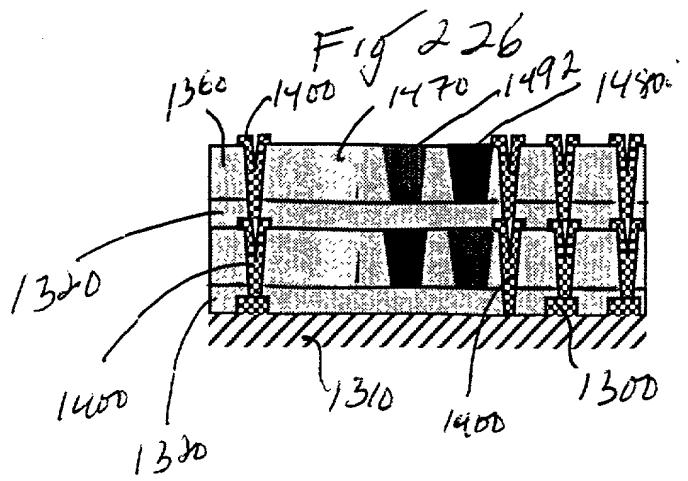


Fig 236

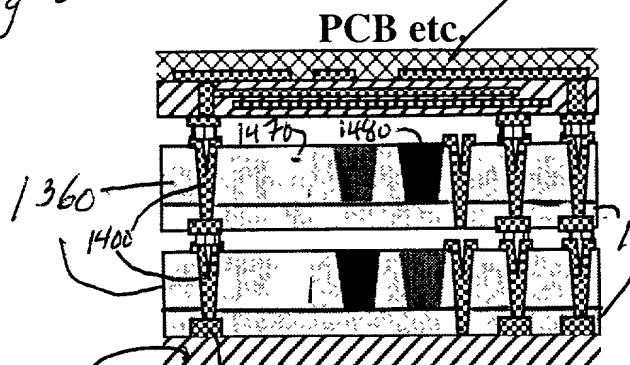


Fig 237

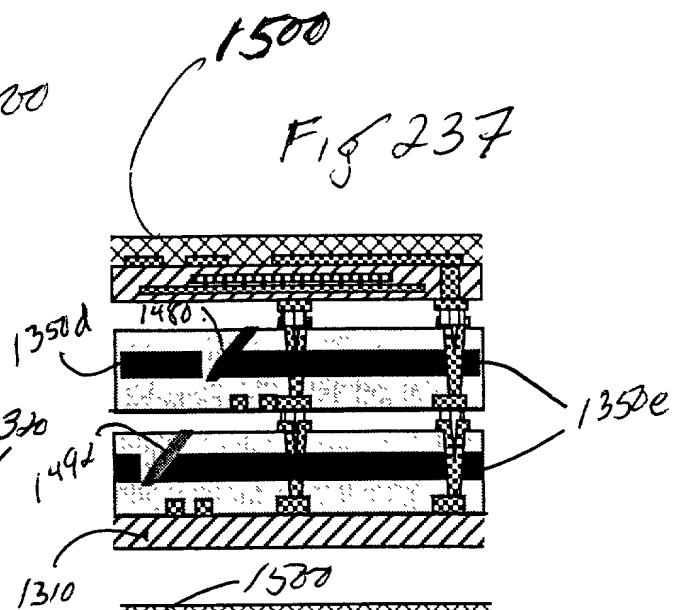


Fig 238

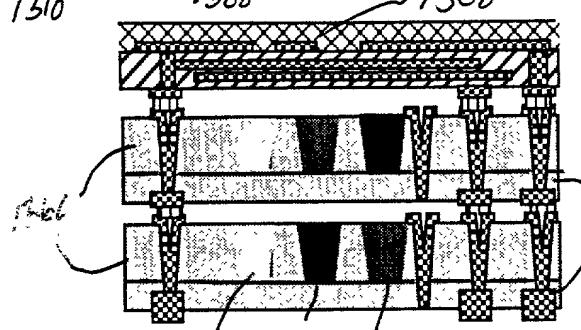


Fig 240

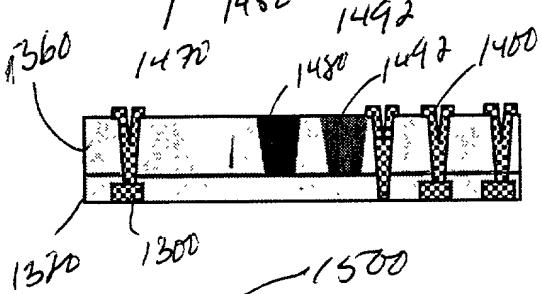


Fig 242

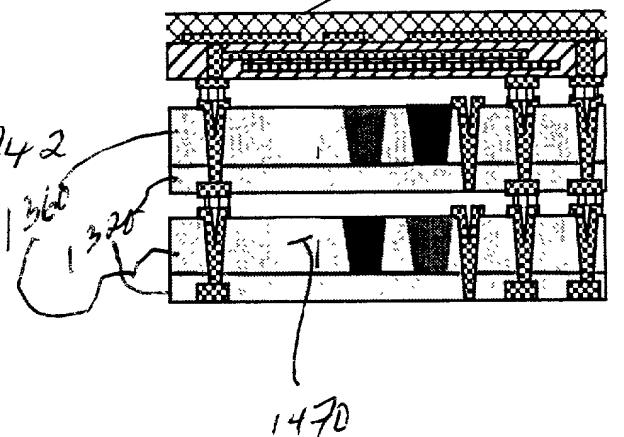


Fig 239

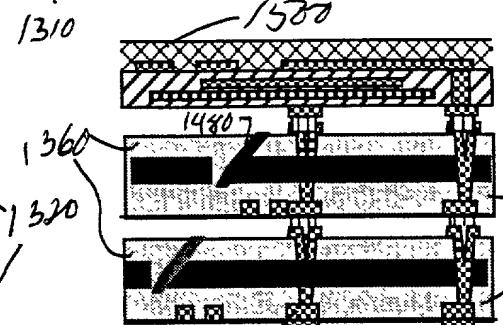


Fig 241

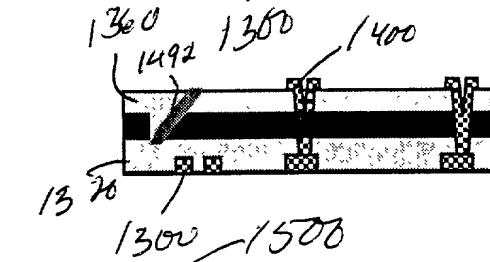


Fig 243

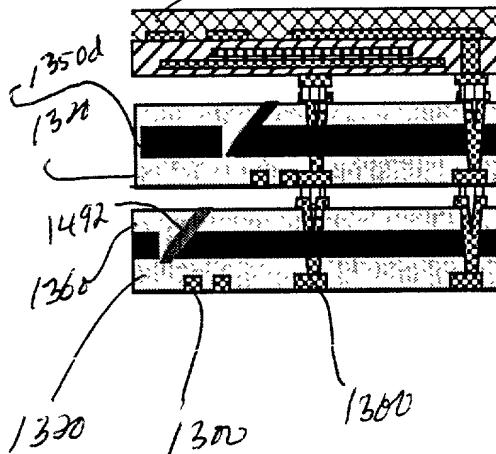


Fig 245

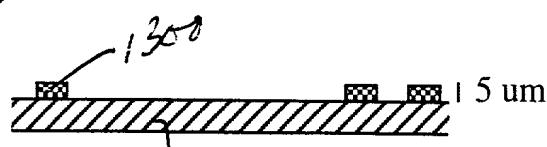


Fig 246

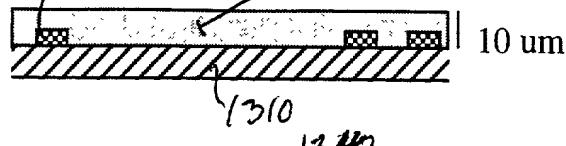


Fig 248

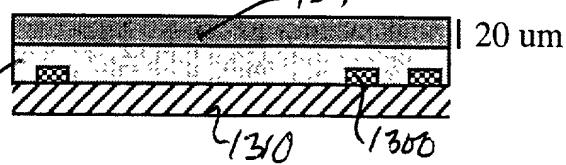


Fig 250

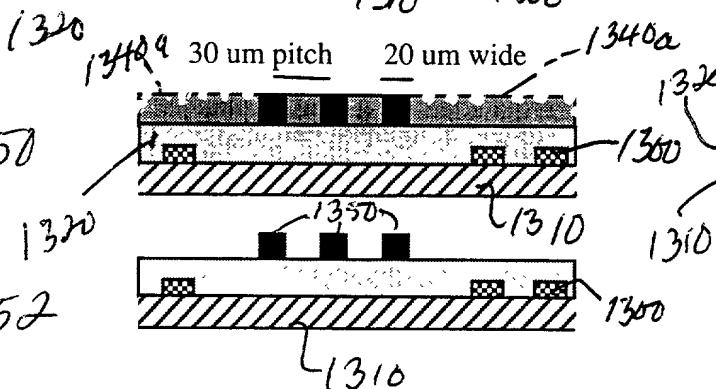
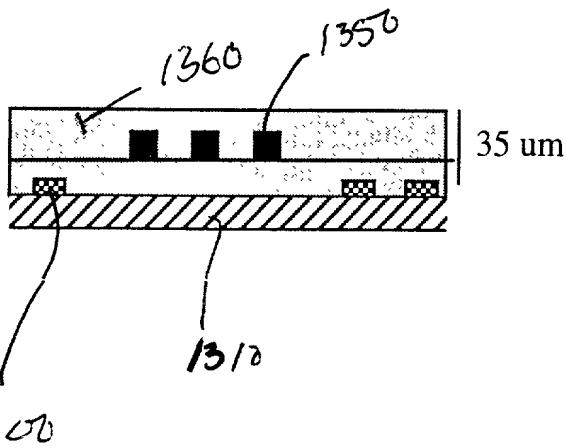
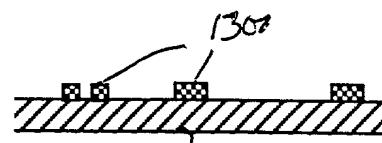


Fig 252



F18254



A hand-drawn diagram of a stepped concrete foundation. The top horizontal line is labeled '1302'. A vertical line extends downwards from the left side of this line, with an arrow pointing to a point on the next lower horizontal line, which is labeled '1310'. Another vertical line extends downwards from the right side of the '1310' line, with an arrow pointing to a point on the bottom-most horizontal line, which is labeled '1320'. The foundation itself is depicted as a series of rectangular blocks with diagonal hatching.

Fig 247

Fig 249

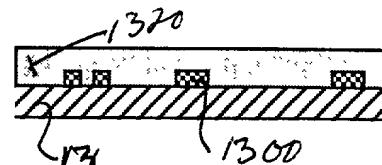
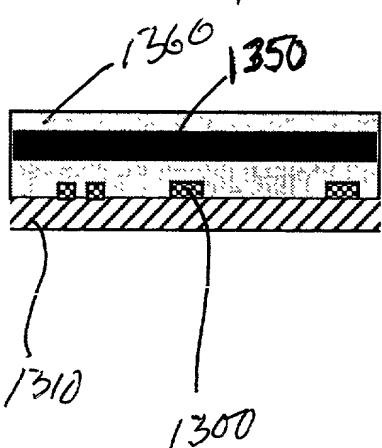
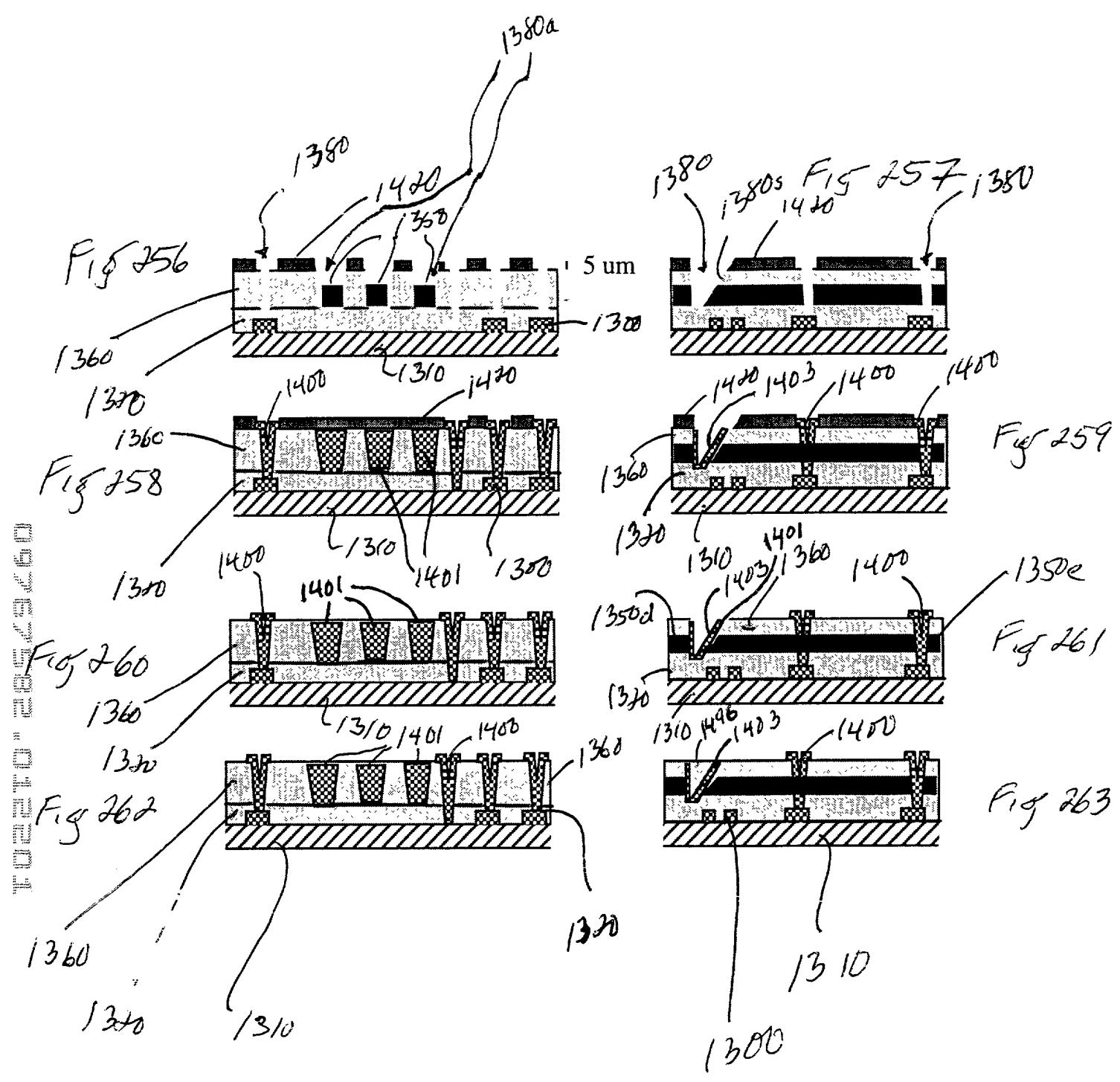
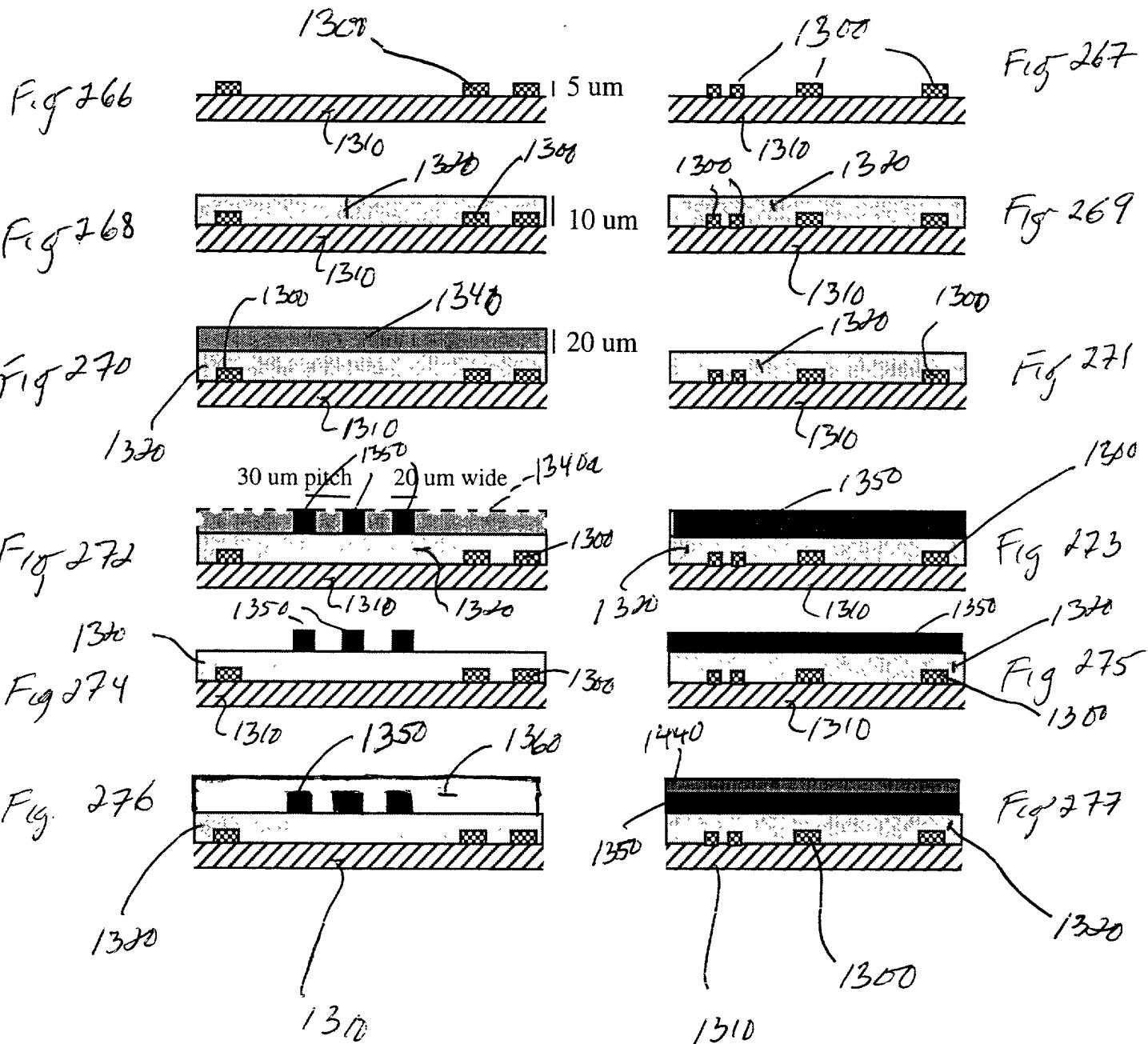
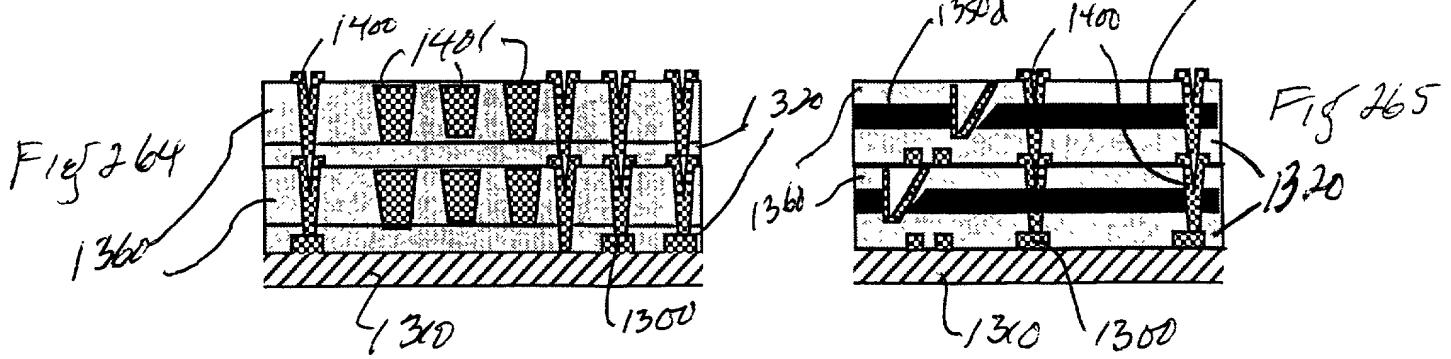


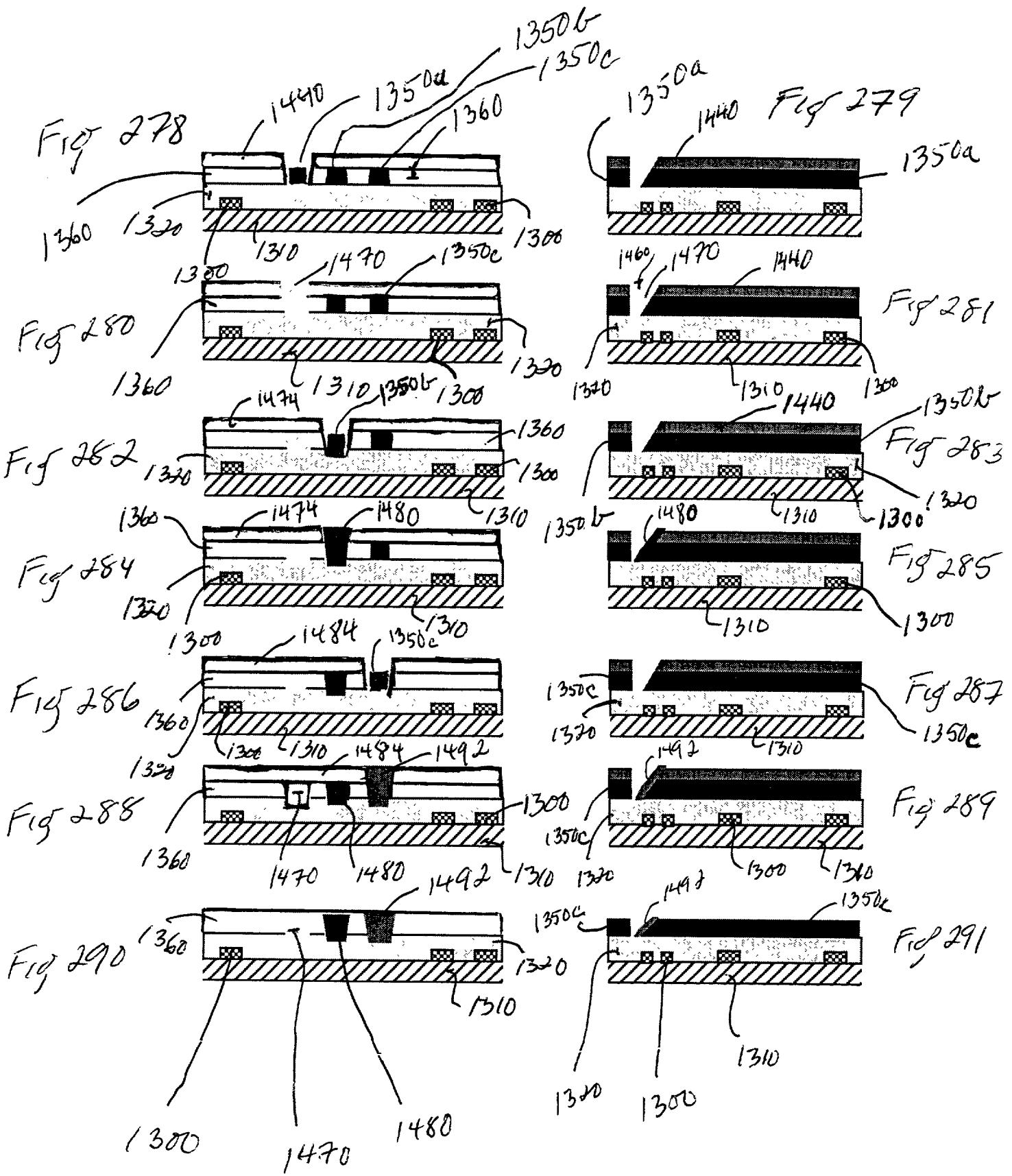
Fig 251

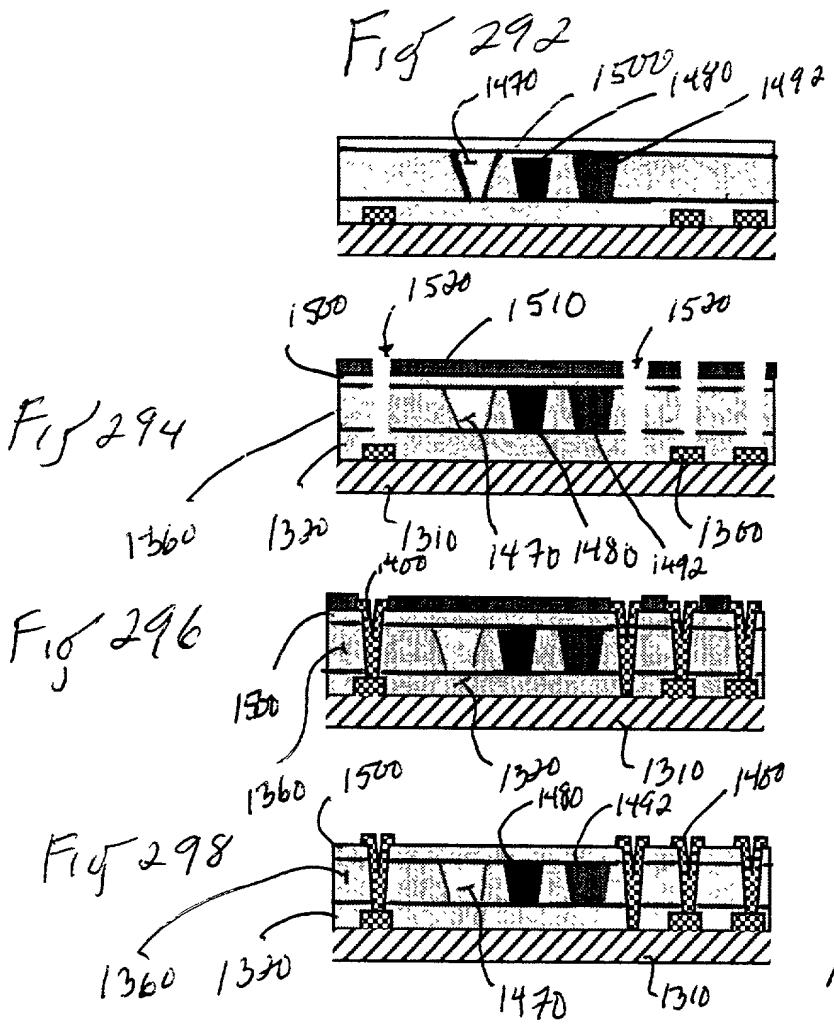
Fig 253











In the case of multi layer (a1-a16) process is repeated on the (a16).
-it is also possible to repeat (a3-a16) or (a1, a3-a16)

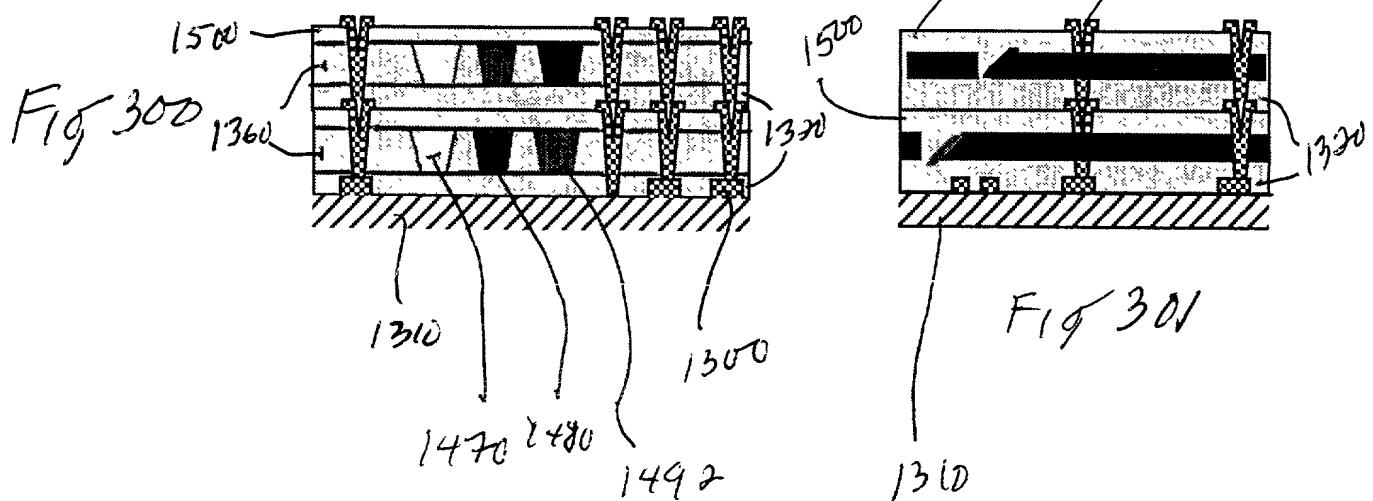


Fig 302



Fig 303

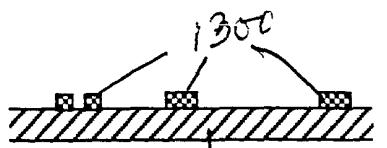


Fig 304

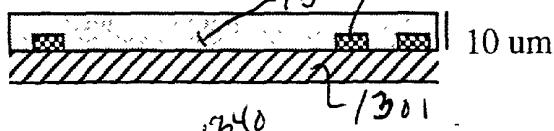


Fig
305

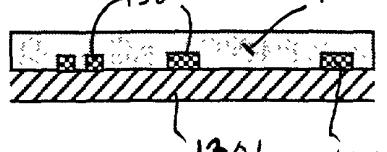


Fig 306

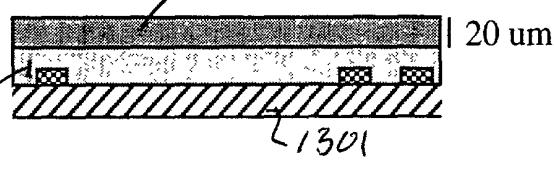


Fig 307

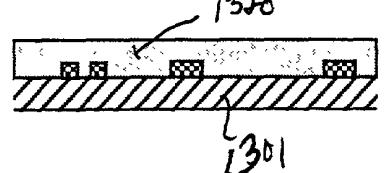


Fig 308



Fig 309

Fig 310

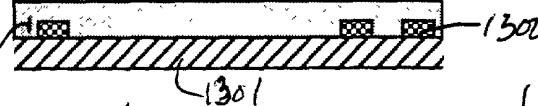


Fig
311

Fig 312

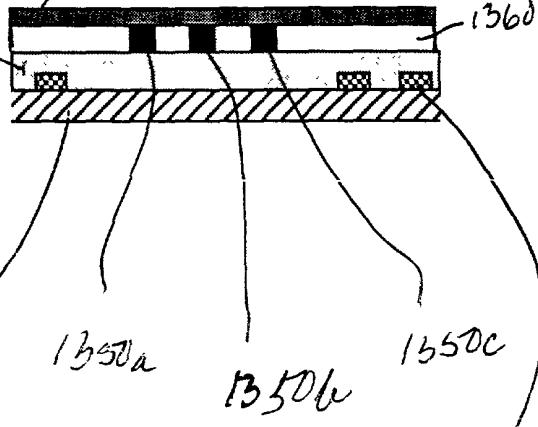
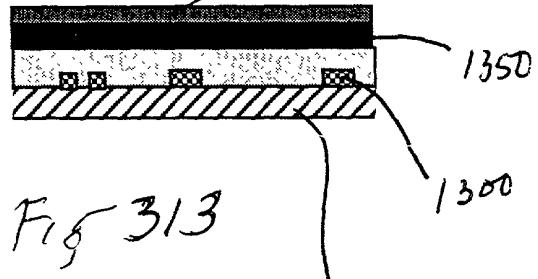


Fig 313



1301

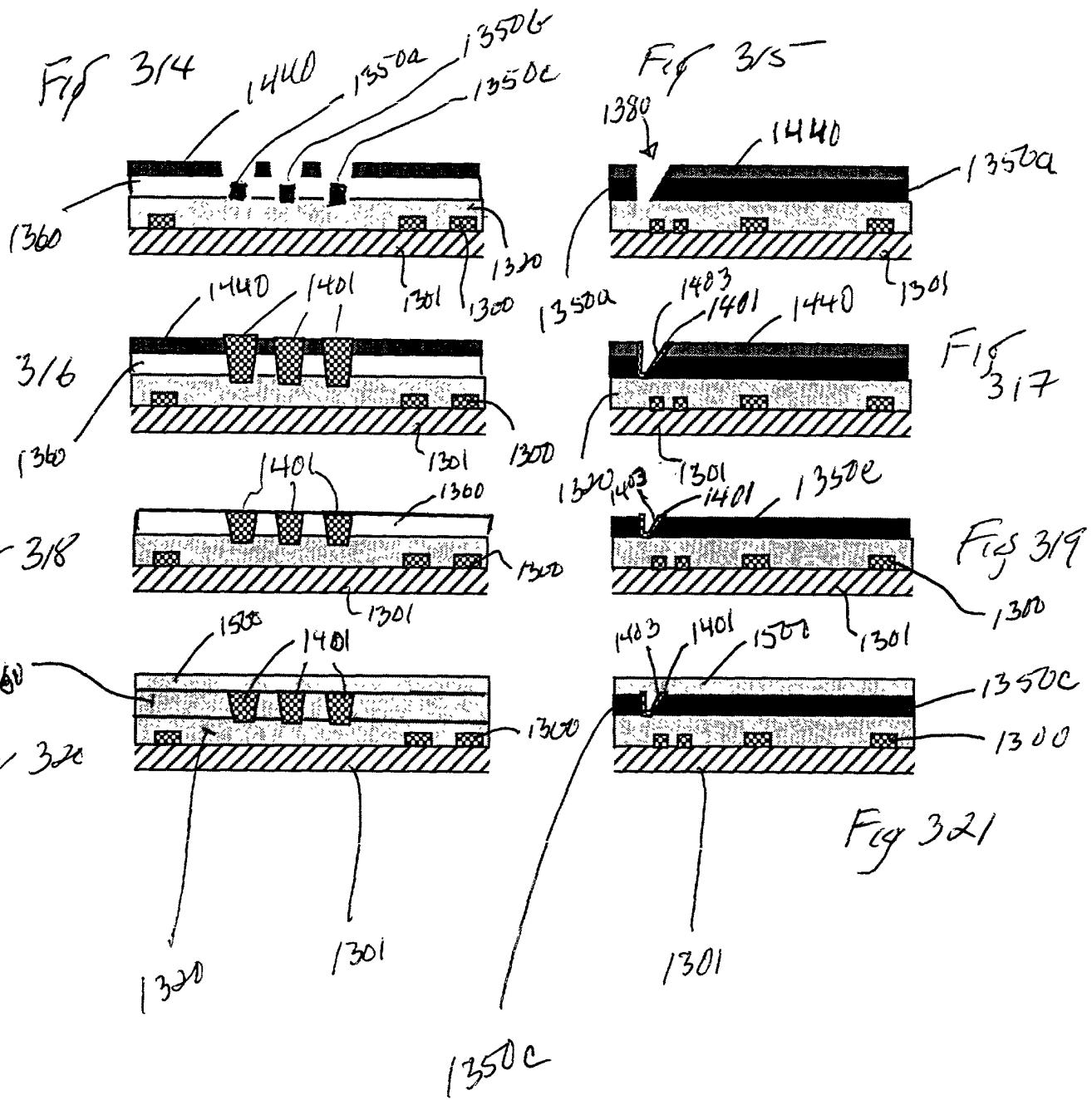
1300

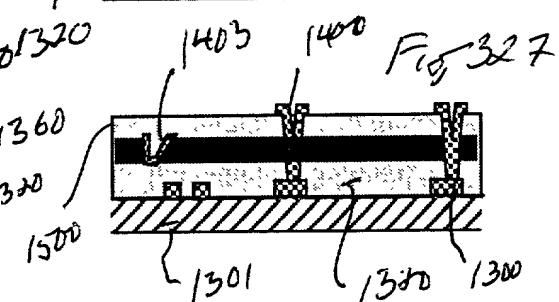
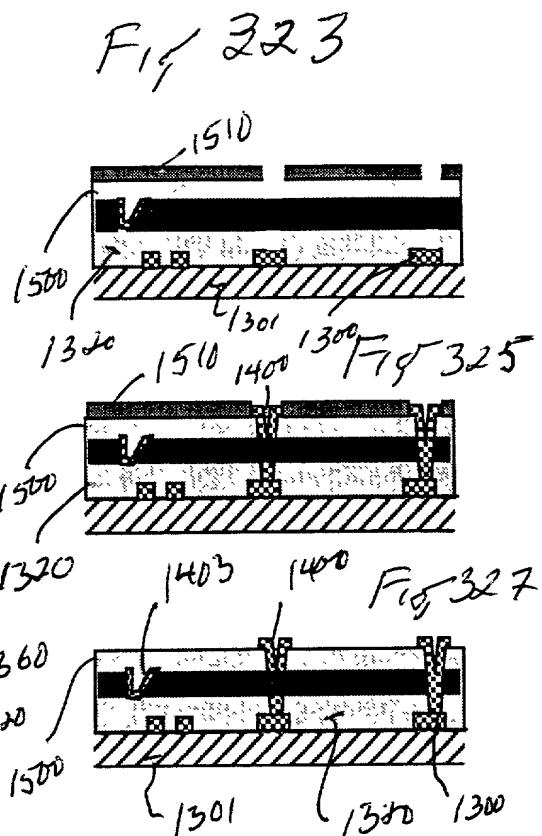
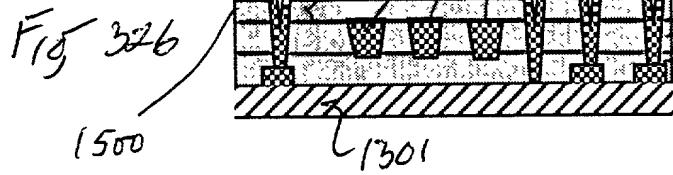
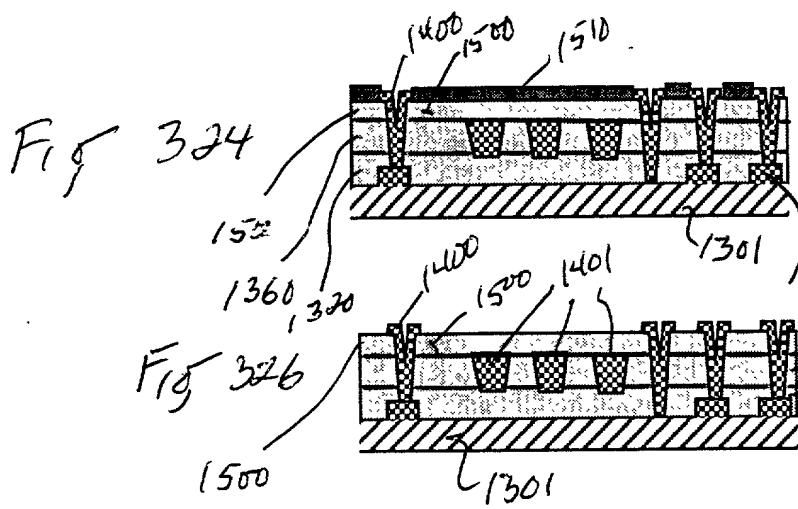
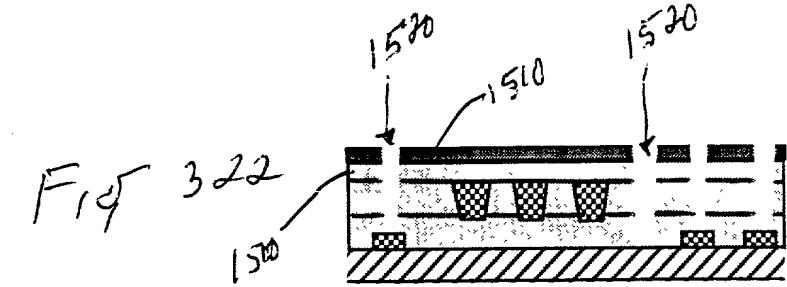
1350a

1350b

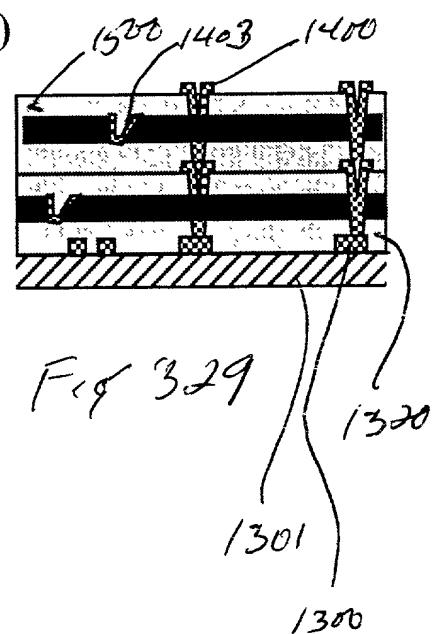
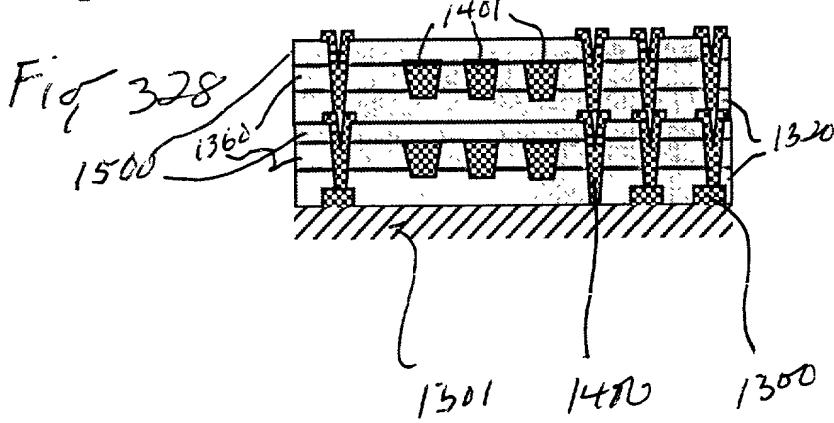
1350c

1300





In the case of multi layer (a1-a12) process is repeated on the (a12).
-it is also possible to repeat (a3-a12) or (a1, a3-a12)



Invented Corner Turning Structure (A)

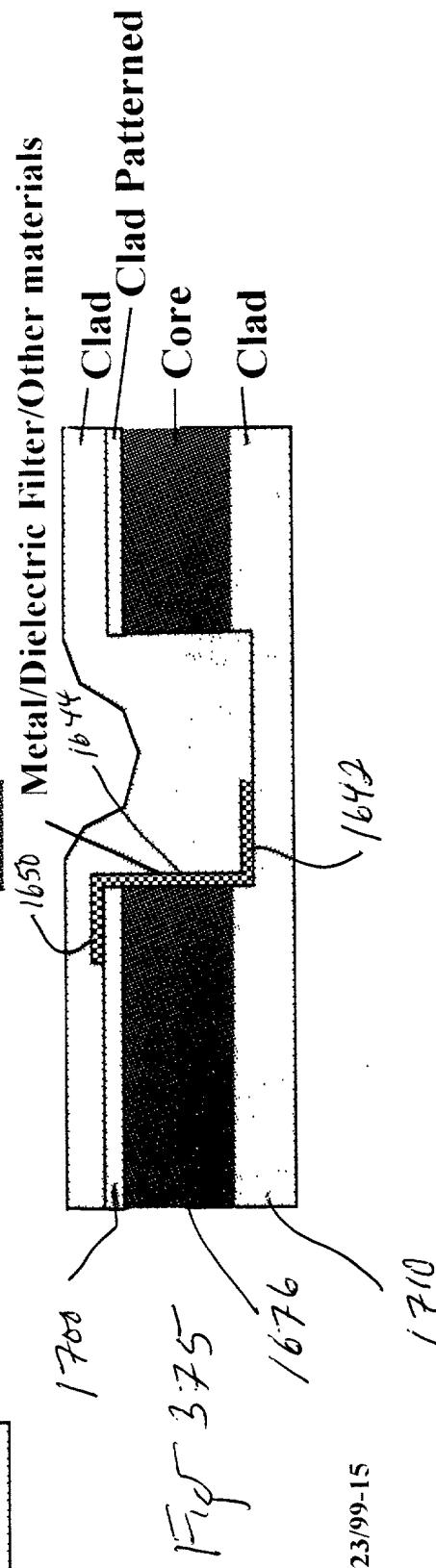
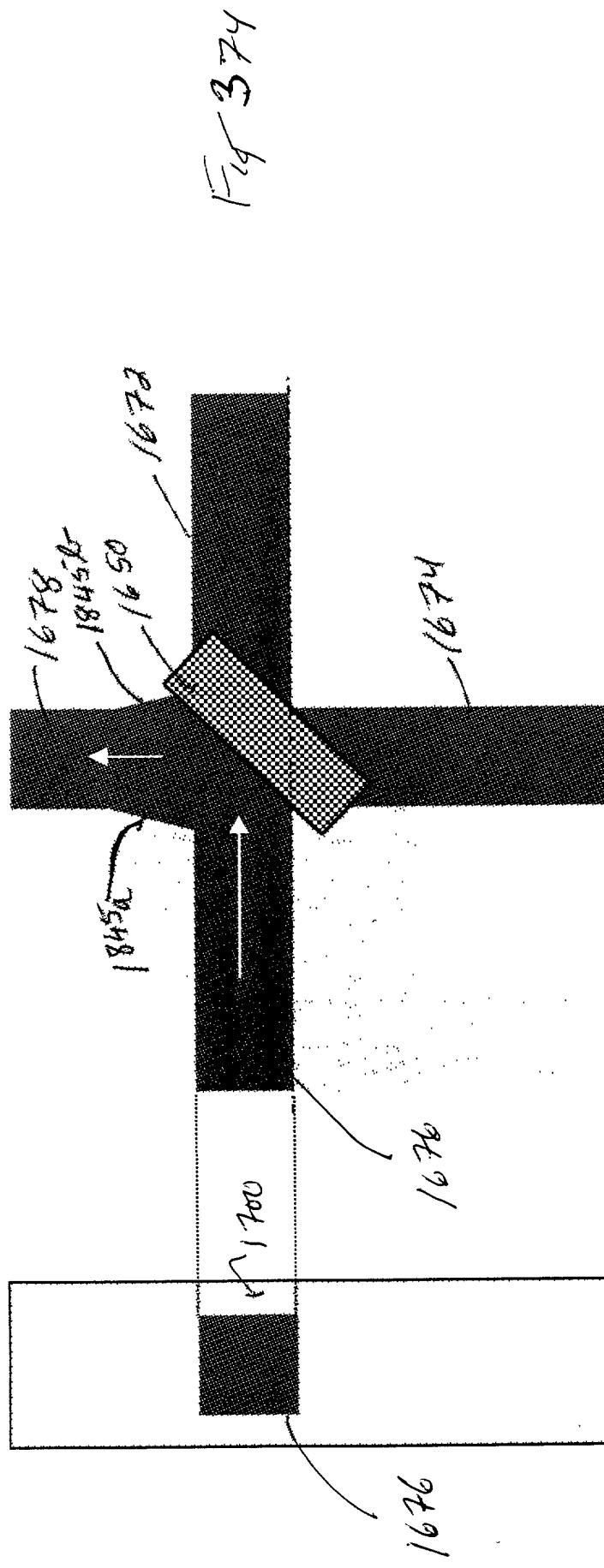


Fig. Add-9/23/99-15

i 710

1642

Fig 375

1650 Metal/Dielectric Filter/Other materials

1644

Clad

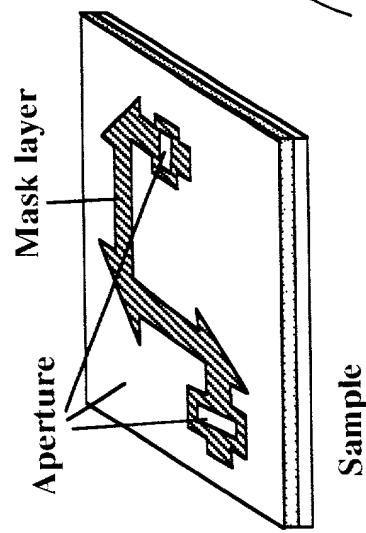
Clad Patterned

Core

Clad

MNA, MNE Example for Add2 example

Fig 372



Excimer laser (or ion beam) with vertical incident angle

Metal mask or Dielectric mirror mask

Fig 371

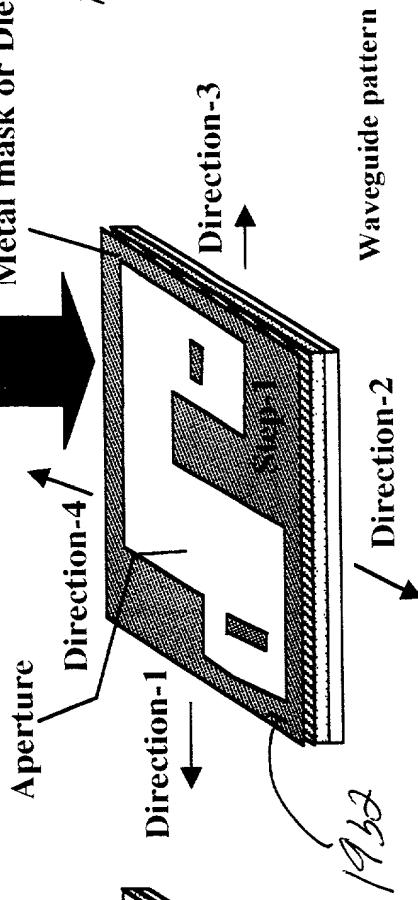


Fig 372

Excimer laser (or ion beam) with tilted incident angle

Fig 374

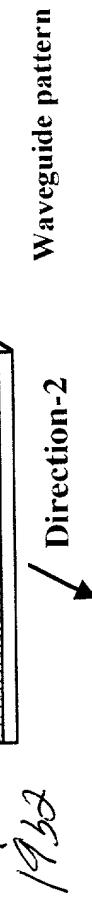
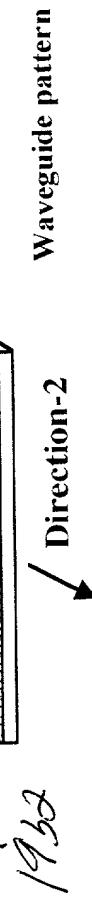
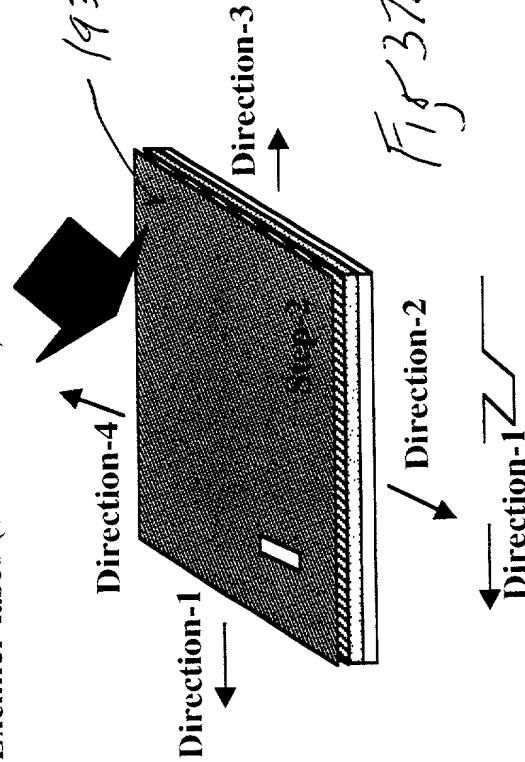


Fig 373

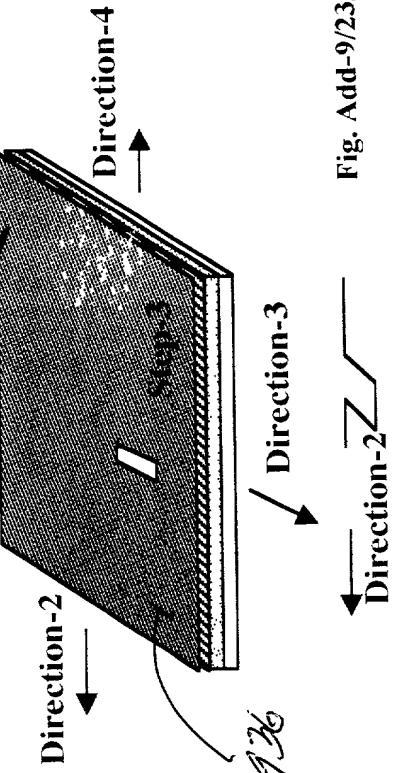


Fig 373

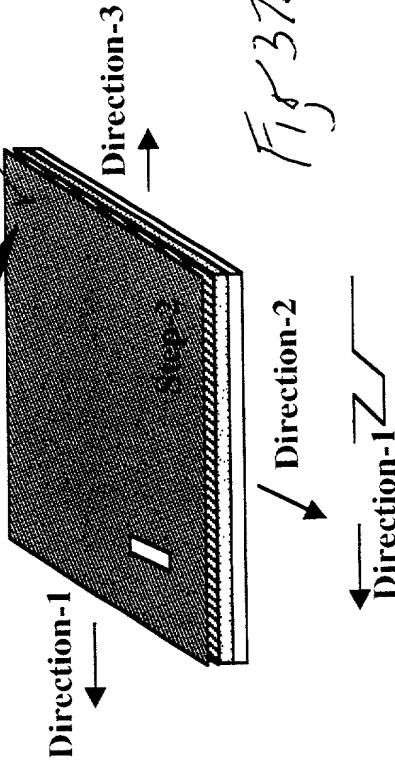


Fig. Add-9/23/99-10

Excimer Laser Ablation Example for Beveled Cut (2)

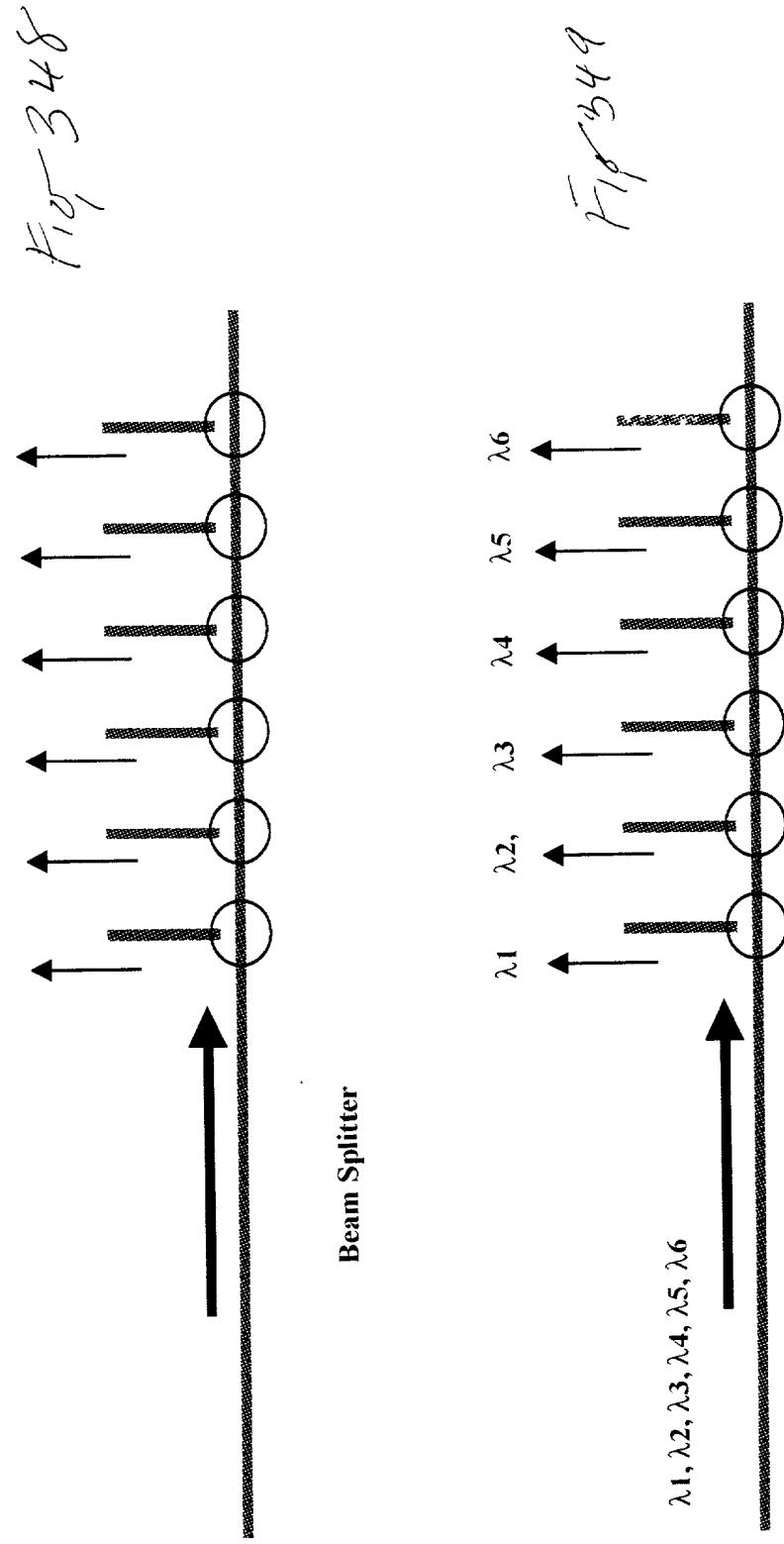
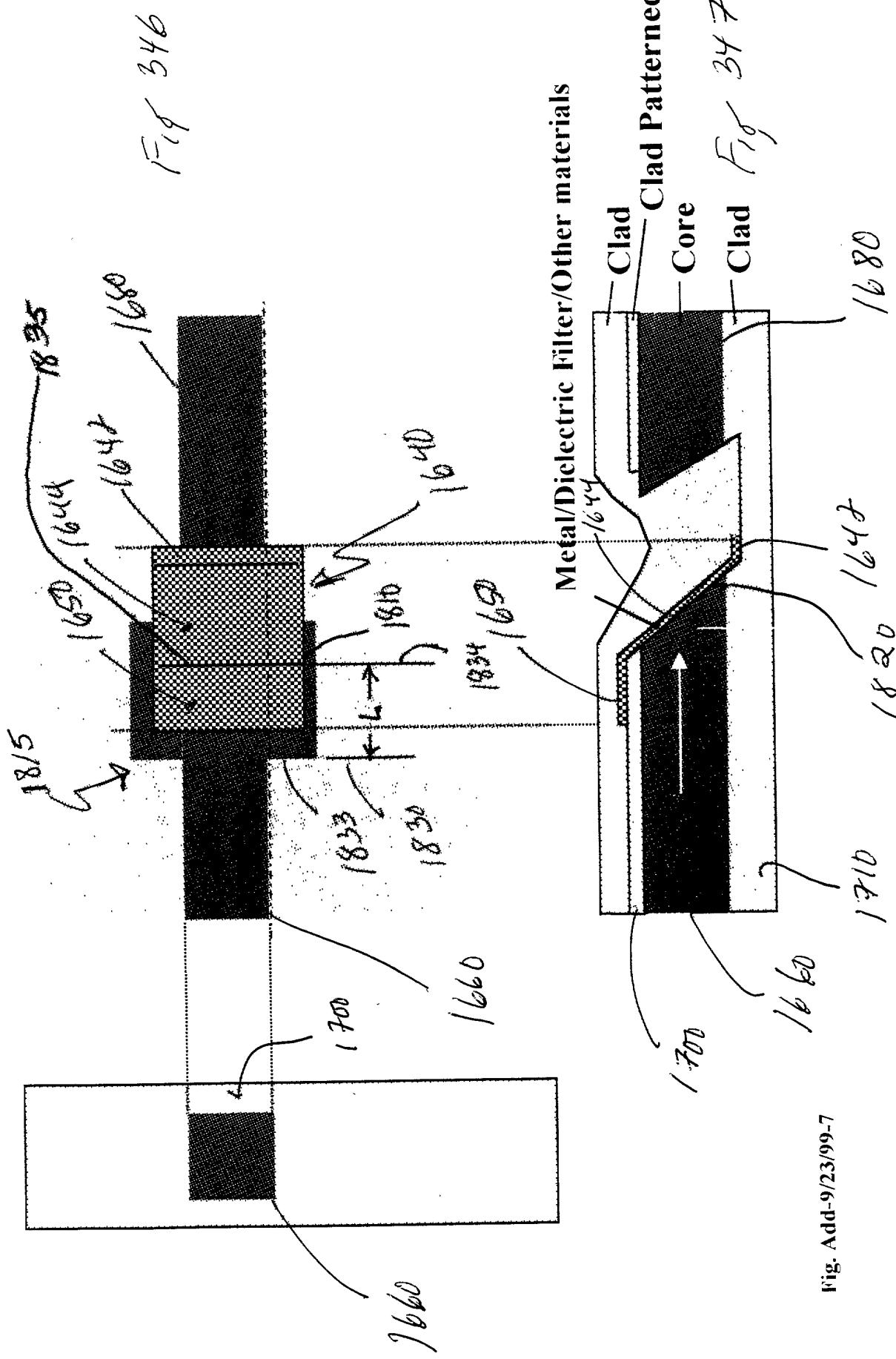
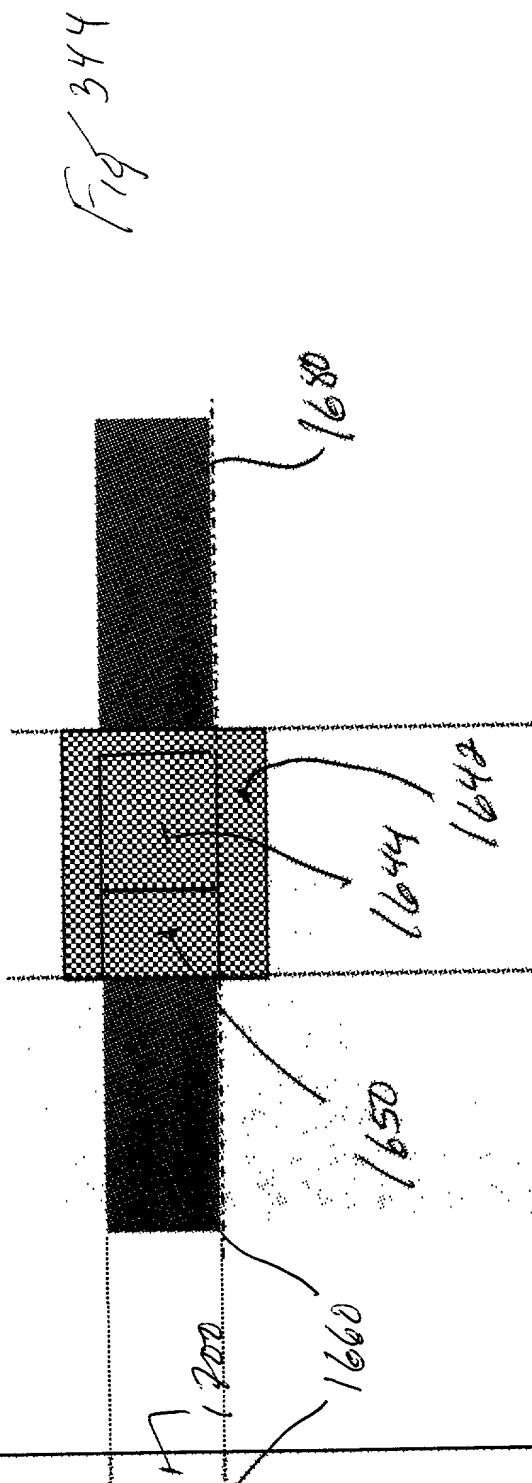
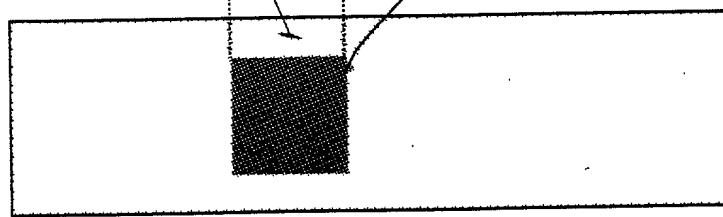


Fig. Add-9/23/99-8

Invented Coupler Structure (II)



Invented Coupler Structure (I)



1650 Metal/Dielectric Filter/Other materials

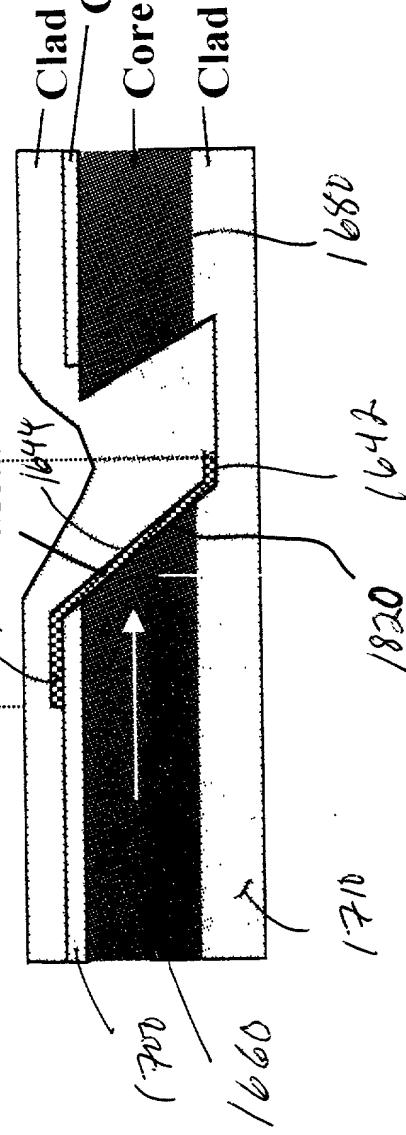


Fig. Add-9/23/99-6

Conventional Coupler Structure (I)

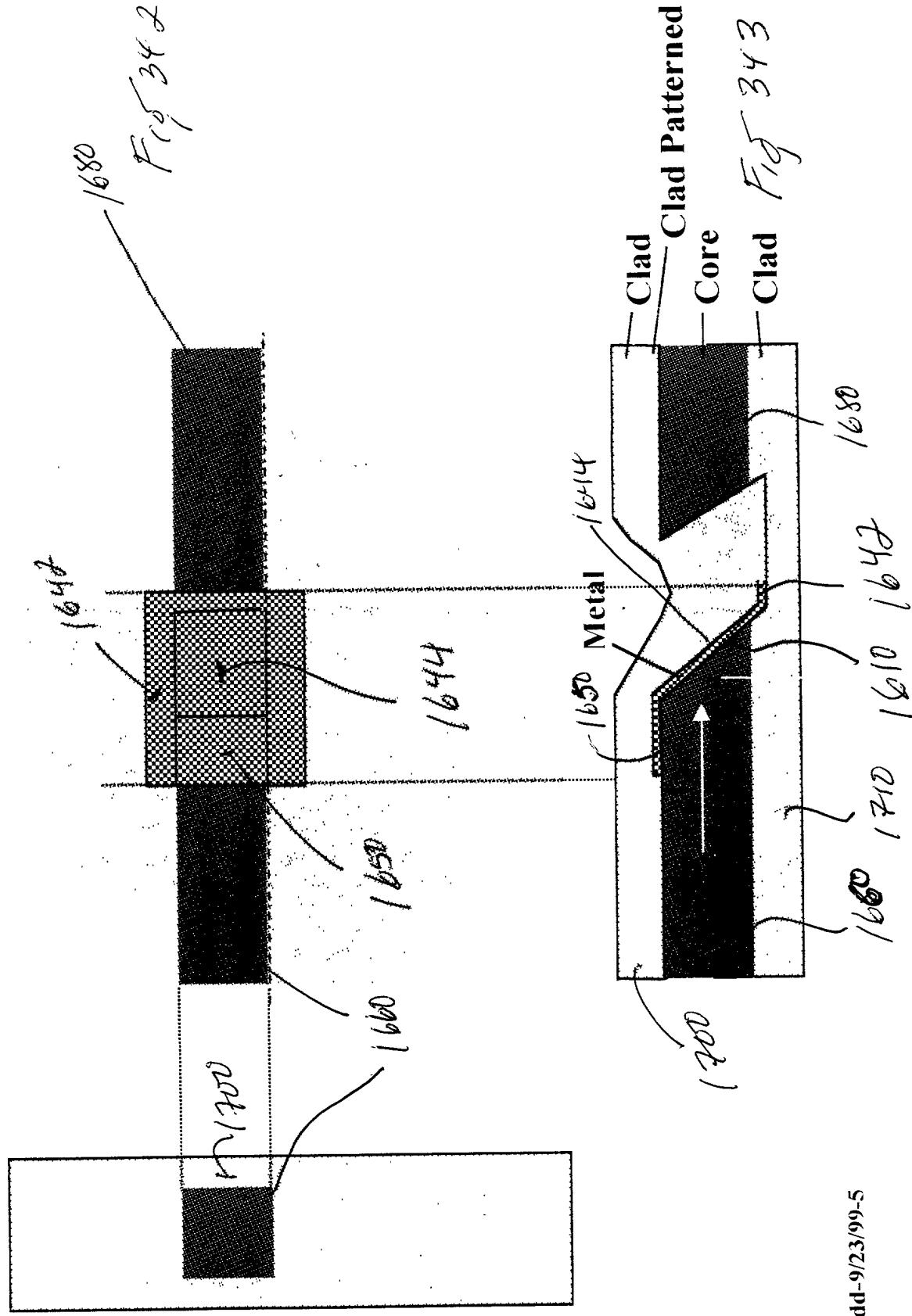


Fig. Add-9/23/99-5

Invented Corner Turning Structure (II)

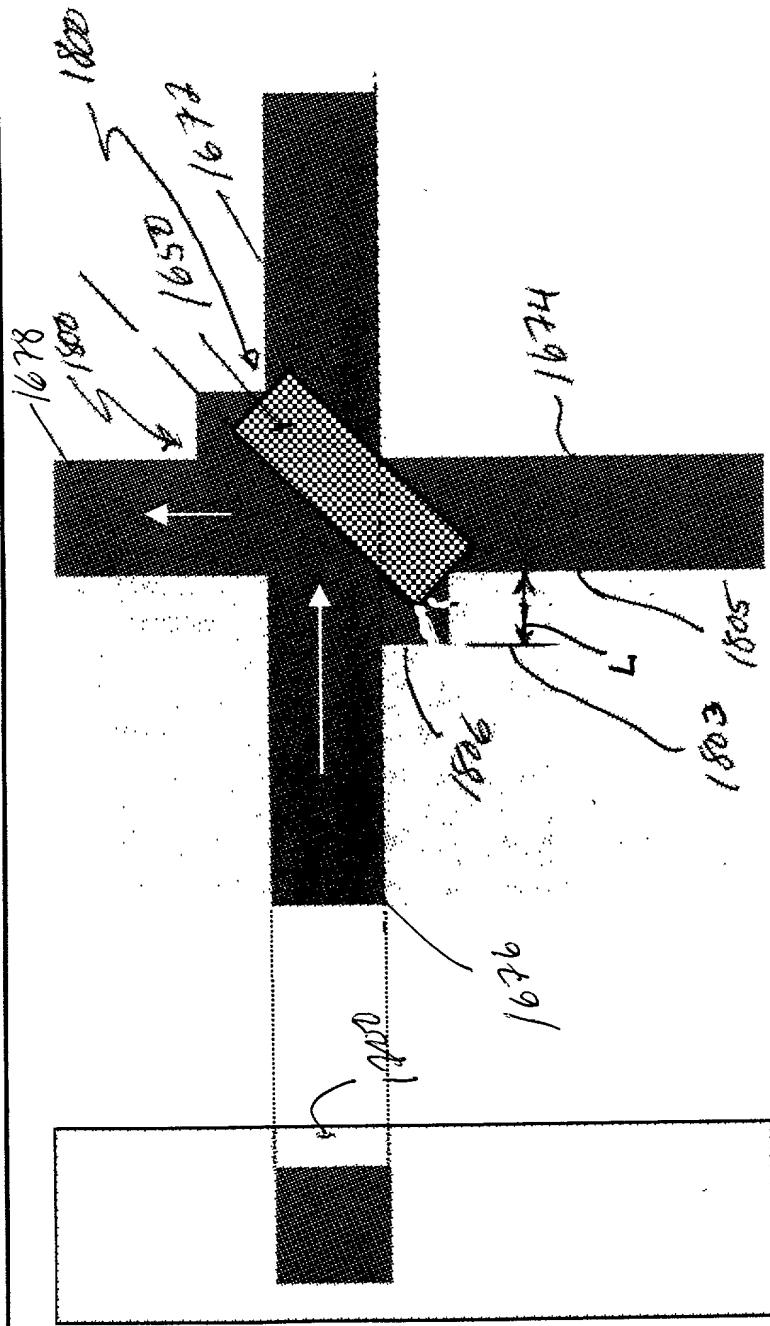


Fig. 340

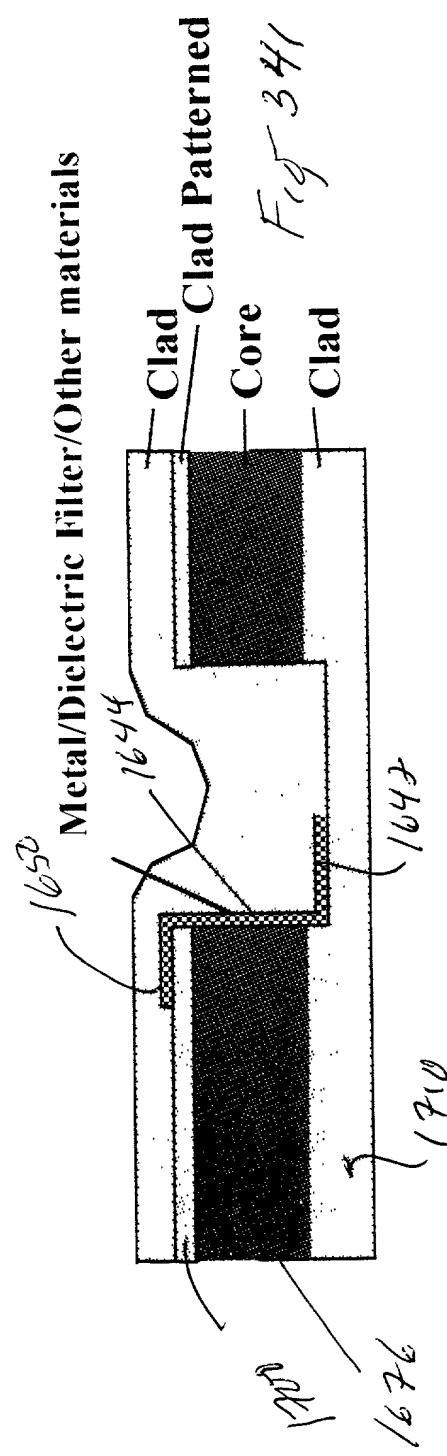


Fig. Add-9/23/99-4

Invented Corner Turning Structure (I)

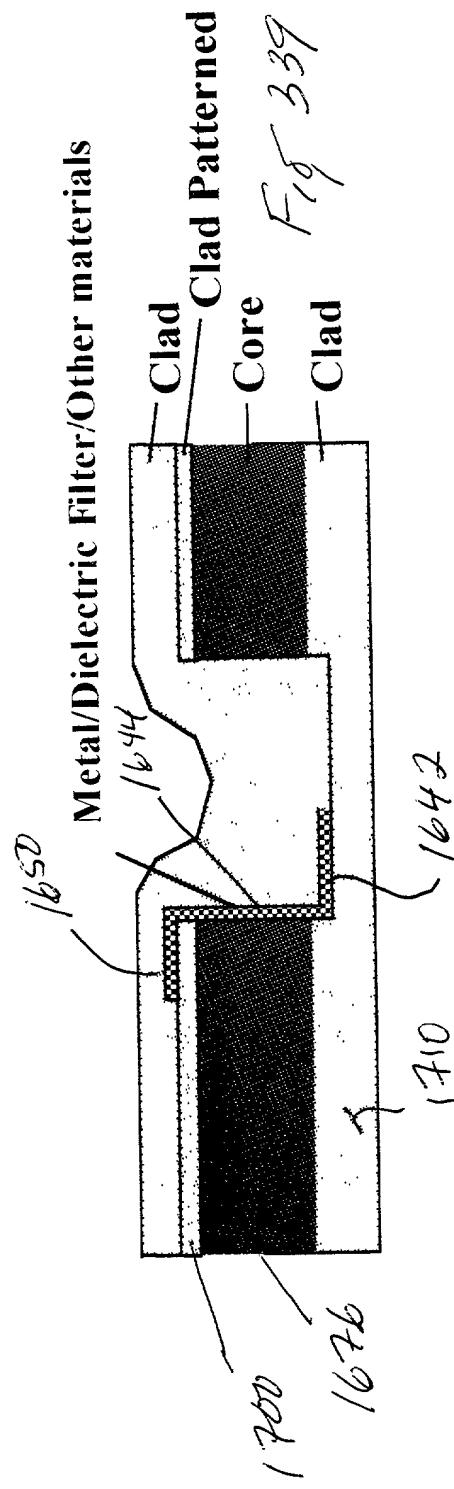
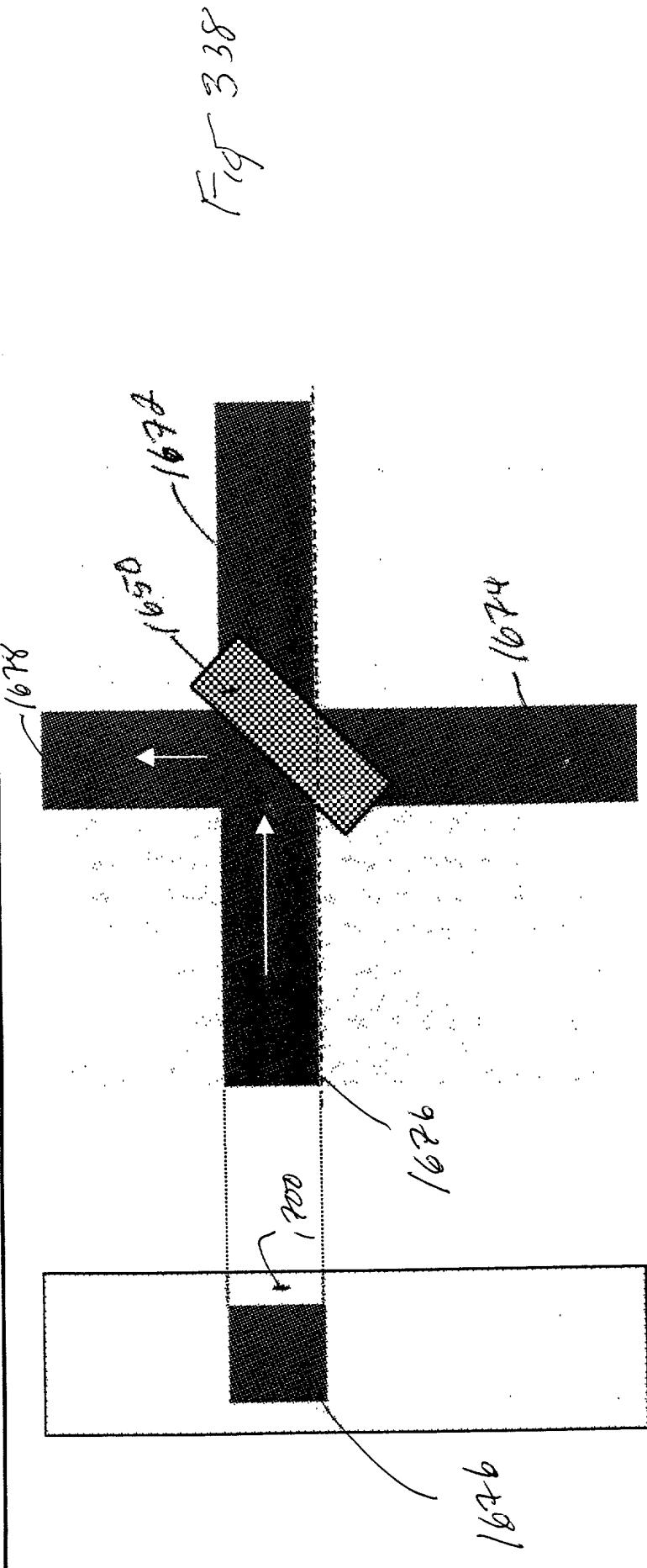


Fig. Add-9/23/99-3

1642
1710

Conventional Corner Turning Structure

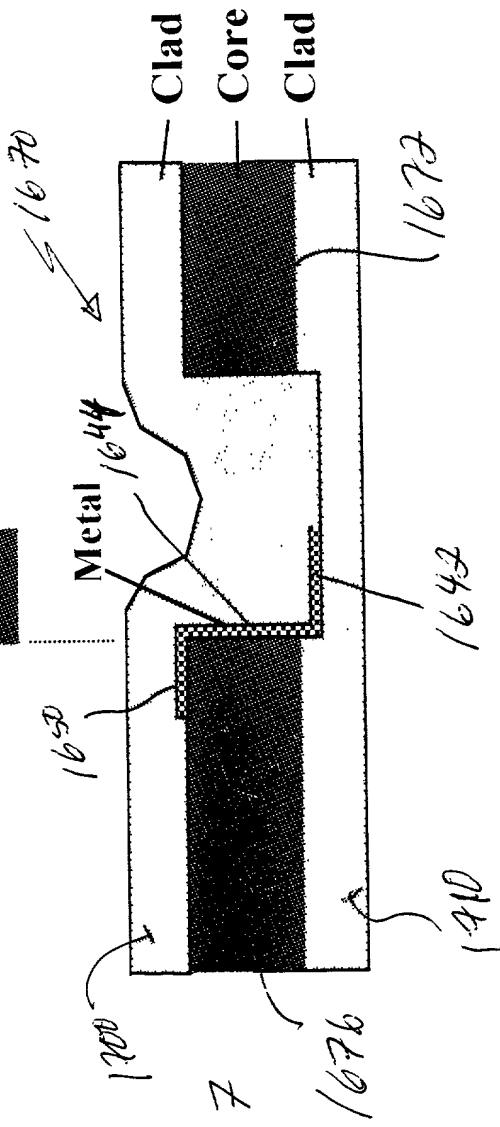
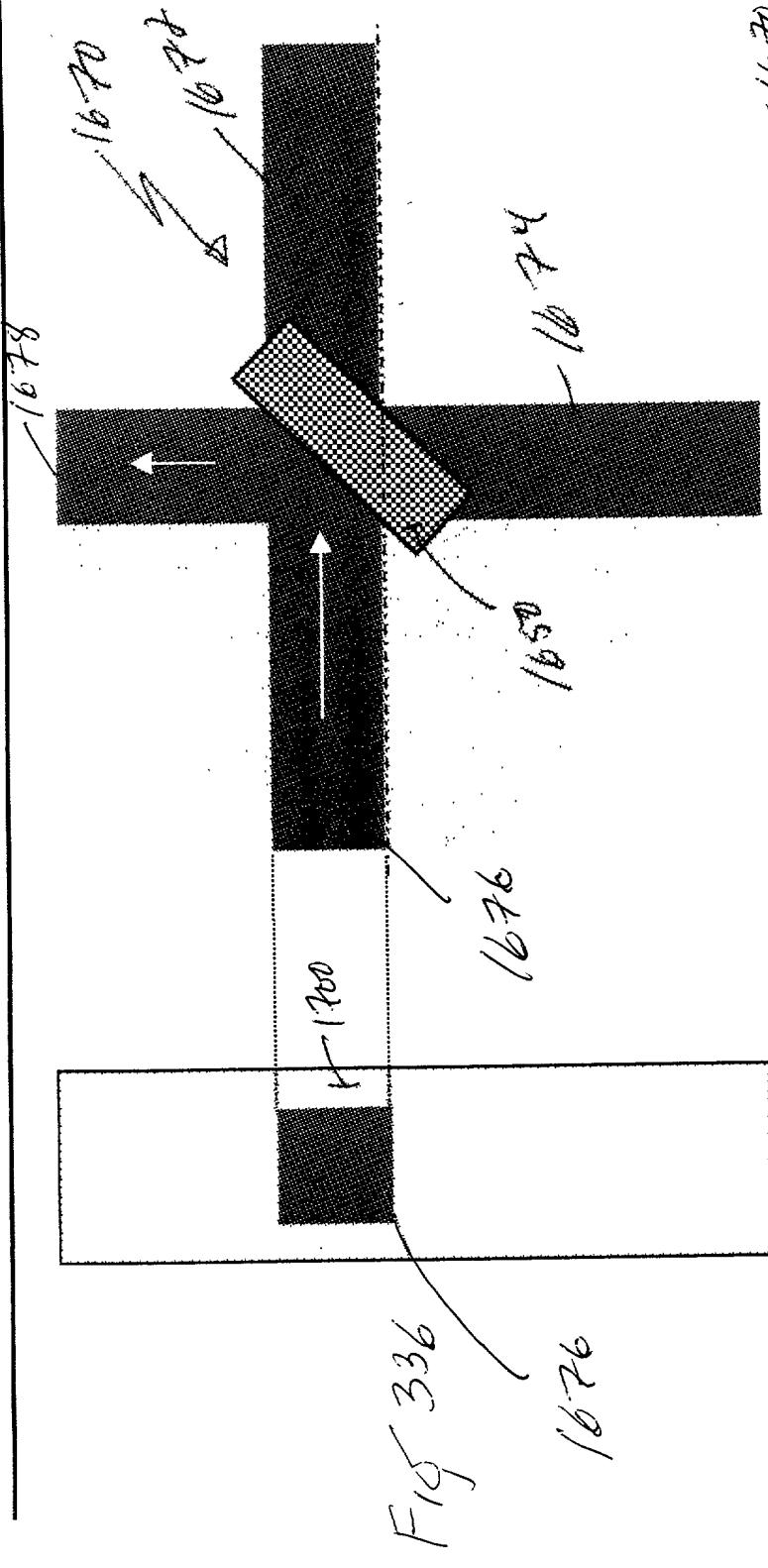
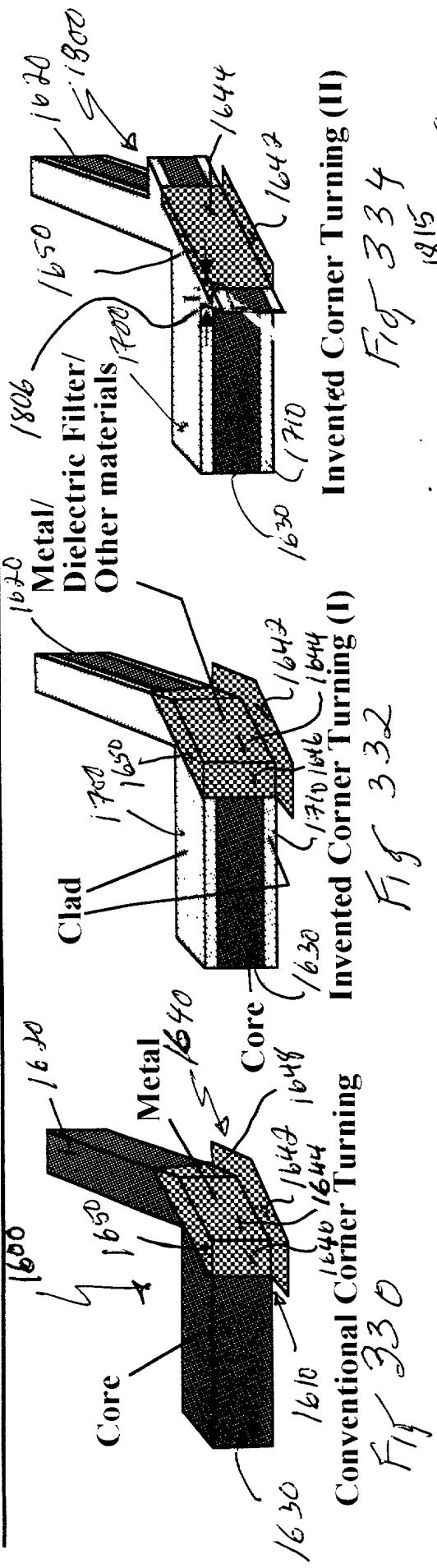


Fig. Add-9/23/99-2

Conventional and Invented Waveguide Structure Examples



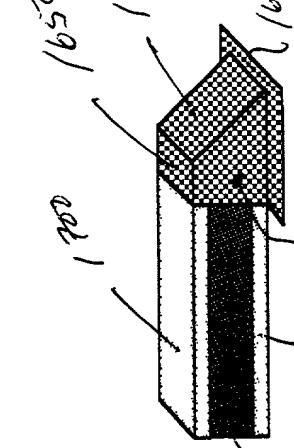
Conventional Corner Turning /*é4é /gæ:*

Fig. 330
Fig. 332



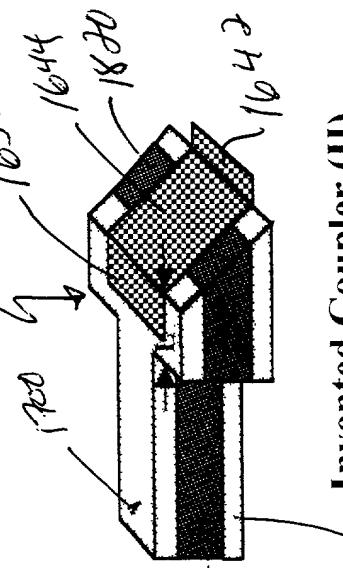
Conventional Counter

Fig 331



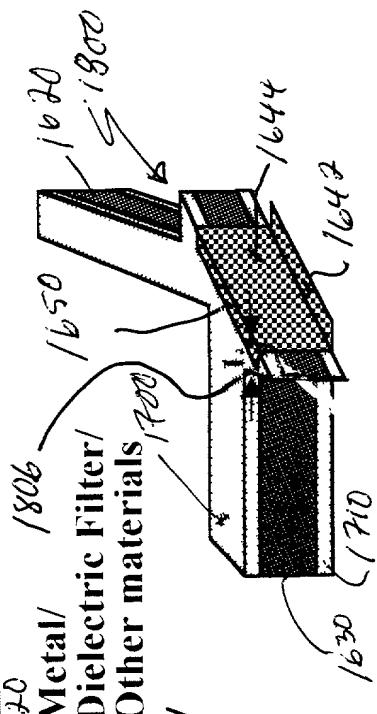
b6D Invented Coupler (I)

Fig 333



Invented Coupler (III)

Fig 335



Invented Corner Turning (I)

Invented Corner Turning (II)

Fig 332

Fig 330

Fig. 334

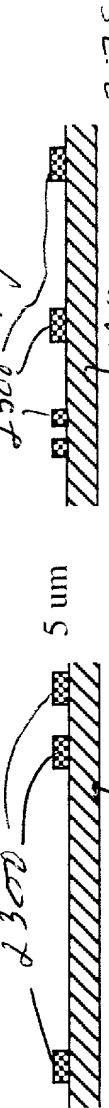
Invented Coupler (II)

Fig 335

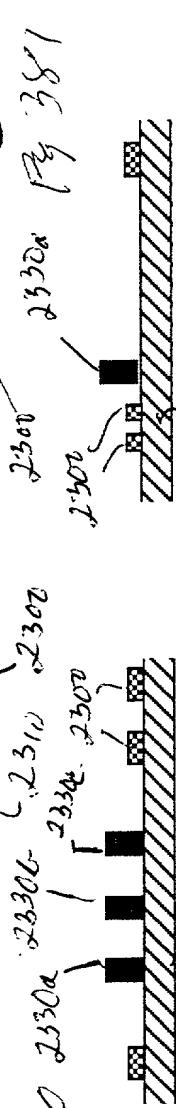
Fig. Add-9/23/99-1

Example 3: Z waveguide Fab. Process 1

(a1) Metal pattern formation F_{g} 376



(a2) Core coat⁹
[DuPont, Allie



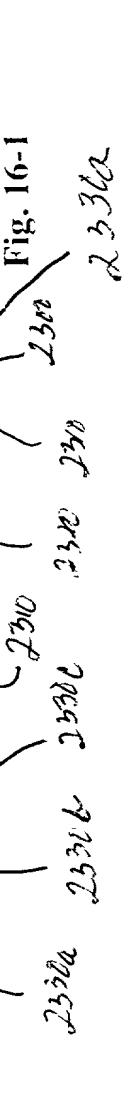
(a3) Z-WG core patterning
[UV-Exposure, mask-forma
Laser, or Dupont process]



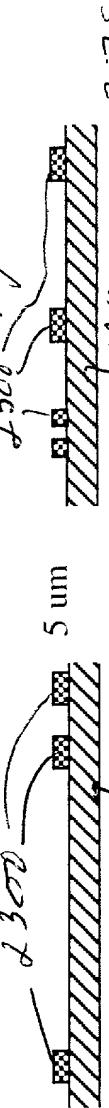
(a4) Clad coat
(for planarization viscosity adjust
if necessary CMP)



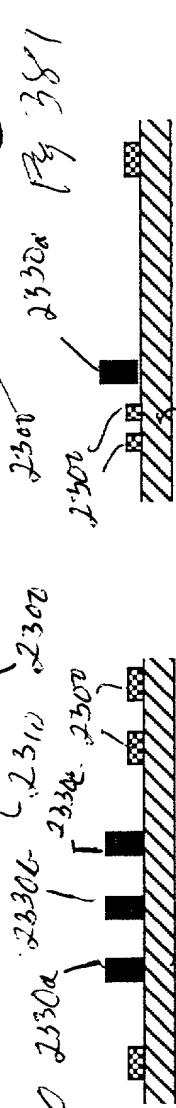
(a6) WG core patterning
[UV-Exposure, mask-formation
Laser, or Dupont process]
Development



(a1) Metal pattern formation *F_y* 376



(a2) Core coat⁹
[DuPont, AlliedSig , ORMOCERS or F-PI]
Fig 273



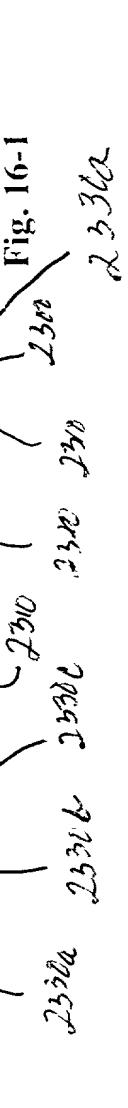
(a3) Z-WG core patterning
[UV-Exposure, mask-forming
Laser, or Dupont process]



(a4) Clad coat
(for planarization viscosity adjust
if necessary CMP)



(a6) WG core patterning
[UV-Exposure, mask-formation
Laser, or Dupont process]
Development



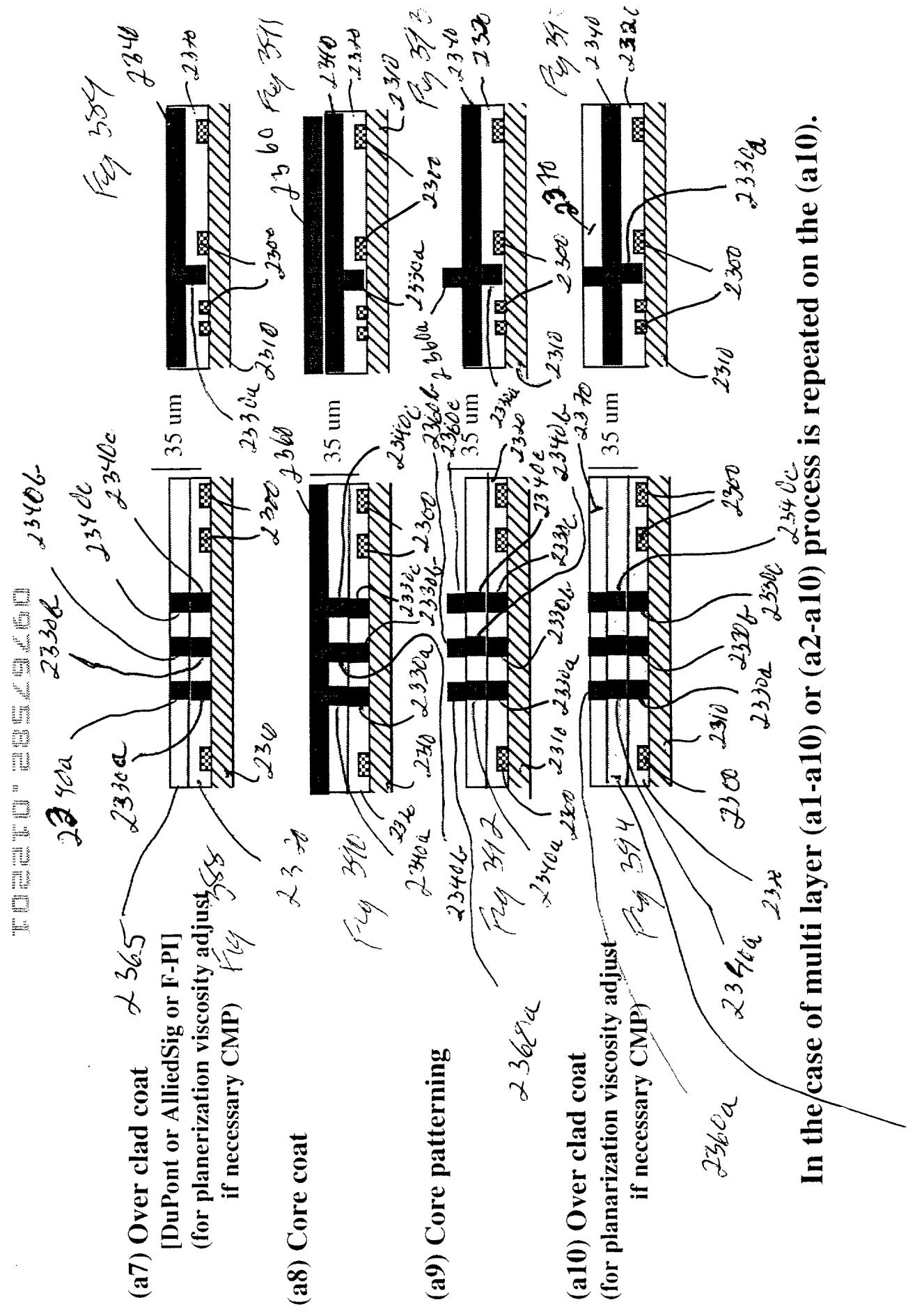


Fig. 16-2

Example 4: Z waveguide Fab. Process 2

(a1) Metal pattern formation
Fig. 39.7

(a2) Clad coat

[DuPont, AlliedSig, ORMOCTERS or F-PI]
Fig. 39.8

(a3) Clad patterning
[UV-Exposure, mask-formation+RIE,
Laser or Dupont process]
Development
(for AlliedSig, ORMOCTERS)

Fig. 40.0

(a4) Core coat
(for planarization viscosity adjust
if necessary CMP)

Fig. 40.2

(a5) WG core patterning
[UV-Exposure, mask-formation+RIE,
Laser or Dupont process]
Development
(for AlliedSig, ORMOCTERS)

Fig. 40.4

(a6) Over clad coat

[DuPont or AlliedSig or F-PI]
(for planerization viscosity adjust
if necessary CMP)

Fig. 40.6

(a7) Over clad coat
(for planerization viscosity adjust
if necessary CMP)

Fig. 40.7

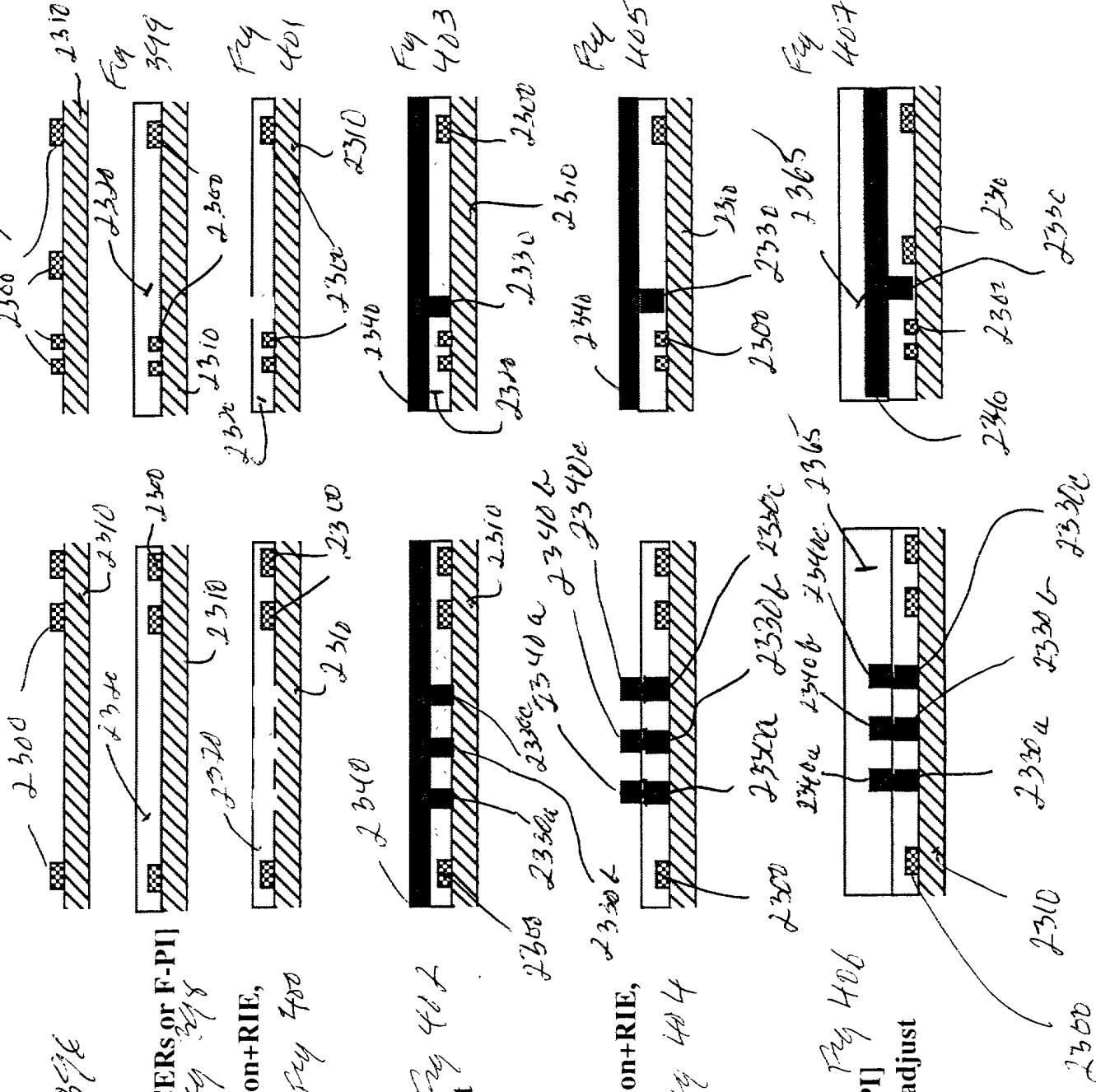
(a8) Over clad coat
(for planerization viscosity adjust
if necessary CMP)

Fig. 40.8

(a9) Over clad coat
(for planerization viscosity adjust
if necessary CMP)

Fig. 40.9

Fig. 17-1



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(a7) Clad patterning

[UV-Exposure, mask-formation+RIE,
Laser or Dupont process] *12y* 408
Development

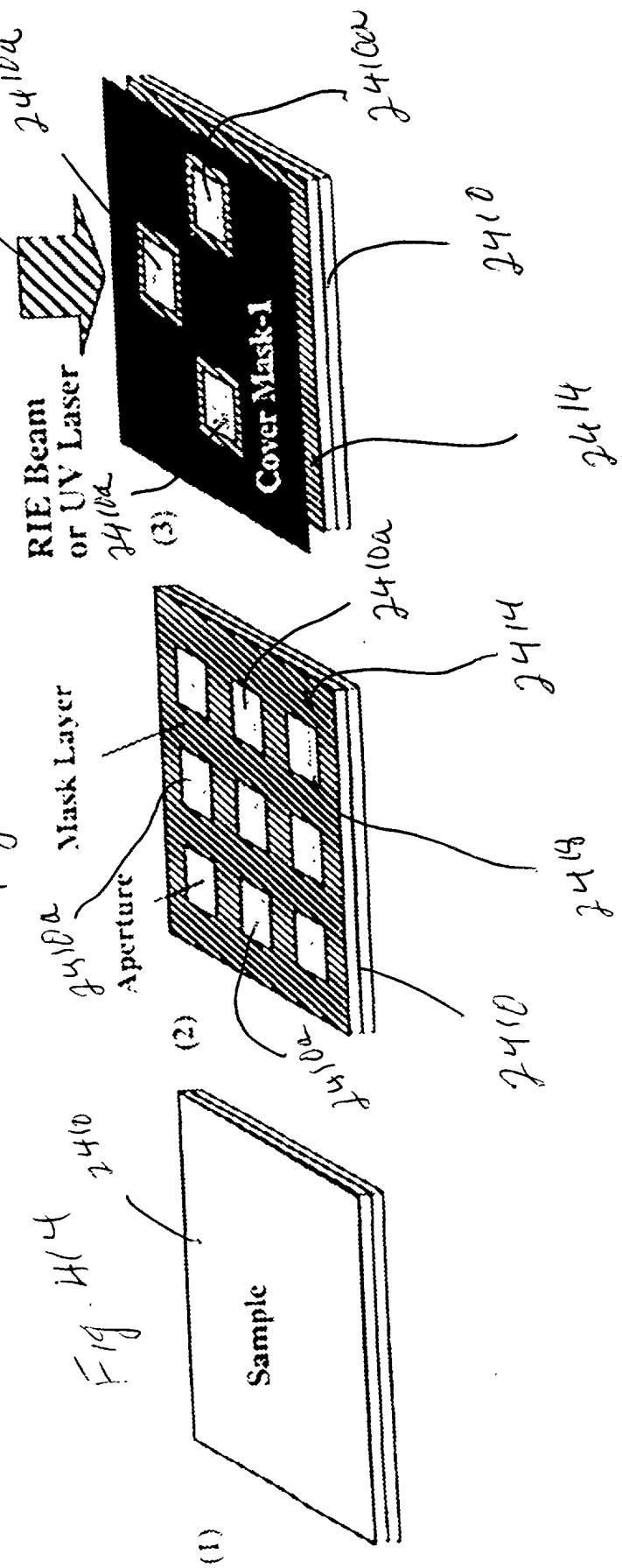
2365-2366

(for AlliedSig, ORMOCERS)

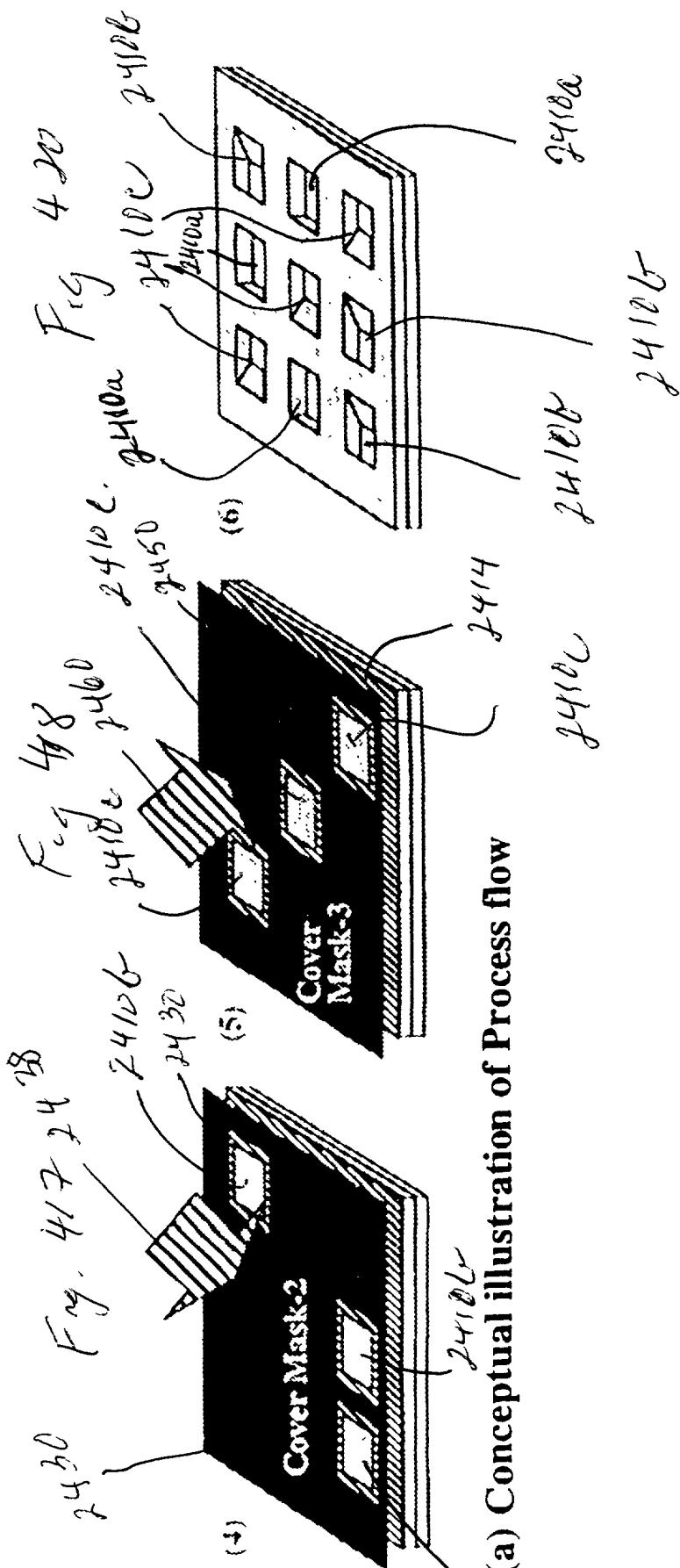
(a8) Core coat
(for planarization viscosity adjust if necessary CMP)
or

(a8) Core coat and CMP

In the case of multi layer (a1, a5-a8) or (a5-a8) process is repeated on the (a8).



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(a) Conceptual illustration of Process flow

(b) Trench wall formation of three different angles

